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JOURNAL OF CRYSTAL GROWTH

Author index to volumes 111–120

Abell, J.S., see Gencer 112 (1991) 337
Abernathy, C.R., S.J. Pearton, D.A. Bohling and G.T. Muhr, The roles of aluminum and hydrogen in impurity contamination of AlGaAs grown by MOMBE 111 (1991) 574
Abernathy, C.R., S.J. Pearton, F. Ren and J. Song, Sn doping of GaAs and AlGaAs by MOMBE using tetraethyltin 113 (1991) 412
Abernathy, C.R. and D.A. Bohling, Low temperature growth of AlGaAs by MOMBE (CBE) using trimethylamine alane 120 (1992) 195
Abernathy, C.R., F. Ren, S.J. Pearton, T.R. Fullowan, R.K. Montgomery, P.W. Wisk, J.R. Lothian, P.R. Smith and R.N. Nottenburg, Growth of GaAs/AlGaAs HBTs by MOMBE (CBE) 120 (1992) 234
Abramof, E., see Kudlek 117 (1992) 290
Abstreiter, G., see Eberl 111 (1991) 882
Adachi, S., see Takeyama 117 (1992) 1081
Adair, J.H., see Rossetti, Jr. 116 (1992) 251
Adams, S.J.A., see Simpson 117 (1992) 134
Adams, S.J.A., see Wallace 117 (1992) 320
Aers, G.C., see Wasilewski 111 (1991) 70
Agostinelli, E., see Leccabue 112 (1991) 644
Aguekian, V.F., see Takeyama 117 (1992) 1081
Agulló-Rueda, F., see Hong 111 (1991) 1016
Aibara, S. and Y. Morita, Crystal growth of hen egg-white lysozyme using a crystallization vessel produced for spacelab experiment 116 (1992) 289
Airaksinen, V.M., see Ravila 114 (1991) 569
Akasaki, I., see Yanagase 115 (1991) 304
Akasaki, I., see Kuwano 115 (1991) 381
Akasaki, I., see Hiramatsu 115 (1991) 628
Akasaki, I., see Takeuchi 115 (1991) 634
Akasaki, I., see Koide 115 (1991) 639
Akasaki, I., see Murakami 115 (1991) 648
Aketagawa, K., T. Tatsumi and J. Sakai, Limitations of selective epitaxial growth conditions in gas-source MBE using Si_2H_6 111 (1991) 860
Aketagawa, K., see Tatsumi 120 (1992) 275
Akimoto, K., T. Miyajima, H. Okuyama and Y. Mori, Oxide interfacial layer in Au ohmic contacts to p-type ZnSe 115 (1991) 683
Akimoto, K., see Okuyama 117 (1992) 139
Akimoto, K., H. Okuyama, M. Ikeda and Y. Mori, Oxygen doping in CdTe, CdS and ZnS 117 (1992) 420
Akimoto, K., see Miyajima 117 (1992) 694
Akimoto, K., see Nakano 117 (1992) 797
Akinaga, M. and H. Fukuda, Thin film growth of Bi(Pb)–Sr–Ca–Cu–O on piezoelectric $PbTiO_3$ films 115 (1991) 765
Akita, K., see Hiratani 111 (1991) 570
Akiyama, H., see Tokizaki 117 (1992) 603
Al Allak, H.M., see Simmons 117 (1992) 959
Alcobé, X., see Ferrater 113 (1991) 181
Alexander, J.I.D., S. Amiroudine, J. Ouazzani and F. Rosenberger, Analysis of the low gravity tolerance of Bridgman–Stockbarger crystal growth. II. Transient and periodic accelerations 113 (1991) 21
Alexander, J.I.D., see Nadarajah 118 (1992) 49
Alexander, K., see Brown 118 (1992) 464
Alexandre, F., see Benchimol 120 (1992) 189
Alexiev, D., Extraction of metallic impurity from gallium 116 (1992) 240
Allard, L.F., see Bamberger 112 (1991) 47
Allen, J.W, see Zheng 117 (1992) 358
Allenson, M.B., see Lane 120 (1992) 245
Allerman, A.A., P.A. Barnes and S.D. Walck, Uniform radial flow epitaxy for thin layer heterostructures 112 (1991) 583
Allovon, M., M. Quillec, M. Blez and C. Kazmierski, MBE growth of graded index AlGaInAs MQW lasers on InP 111 (1991) 484
Alnajjar, A.A., see Loginov 117 (1992) 259
Alnajjar, A.A., C.C.R. Watson, A.W. Brinkman and K. Durose, Post-growth doping of bulk CdTe crystals with phosphorus 117 (1992) 385
Alonso, R.G., see Samarth 111 (1991) 816
Amano, H., see Kuwano 115 (1991) 381
Amano, H., see Hiramatsu 115 (1991) 628
Amano, H., see Takeuchi 115 (1991) 634
Amano, H., see Koide 115 (1991) 639
Amano, H., see Murukami 115 (1991) 648
Ambrosius, H.P.M.M., see Frijlink 115 (1991) 203
Amin, S.J., see Skevington 120 (1992) 135
Amin, S.J., see Skevington 120 (1992) 328
Amiroudine, S., see Alexander 113 (1991) 21

An, C.Y., see Regel 119 (1992) 94
Ananth, R. and W.N. Gill, Criteria for making uniform films by chemical vapor deposition 118 (1992) 60
Anastassakis, E., Elastic distortions of strained layers grown epitaxially in arbitrary directions 114 (1991) 647
Anayama, C., T. Tanahashi and K. Nakajima, Selective embedded growth of GaAs by MOVPE 115 (1991) 65
Anayama, C., see Domen 115 (1991) 529
Ando, H., see Sandhu 111 (1991) 559
Ando, H., N. Okamoto, A. Sandhu and T. Fujii, Gas-source MBE growth of n-type InP using TEI, PH_3, and Si_2H_6 115 (1991) 464
Ando, H., T. Fujii, A. Sandhu, T. Takahashi, H. Ishikawa, N. Okamoto and N. Yokoyama, Growth of carbon-doped base GaAs/AlGaAs HBT by gas-source MBE using TEG, TEA, TMG, AsH_3, and Si_2H_6 120 (1992) 228
Ando, H., see Sandhu 120 (1992) 296
Ando, K., see Ohki 117 (1992) 102
Ando, K., J. Palmer, A. Ohki, S. Tohno and S. Zembutsu, Interface defect characteristics of Zn(SSe)–ZnSe and ZnSe–(ZnCd)S hetero-epitaxial systems 117 (1992) 560
Ando, M. and Y.A. Ono, Temperature effects in the emission characteristics of CaS : Eu thin-film electroluminescent devices 117 (1992) 969
Ando, S., S.S. Chang and T. Fukui, Selective epitaxy of GaAs/AlGaAs on (111)B substrates by MOCVD and applications to nanometer structures 115 (1991) 69
Ando, S., T. Okada, S. Endo, T. Irie, T. Miya and H. Nakanishi, Edge emission enhancement in CdS by laminated $CdInGaS_4$ 117 (1992) 362
Andonov, P., see Chibani 113 (1991) 681
André, R., see Cibert 117 (1992) 424
Andrew, N.L., see Woodbridge 111 (1991) 339
Andrews, J.B., A.L. Schmale and A.C. Sandlin, The influence of gravity level during directional solidification of immiscible alloys 119 (1992) 152
Andrieu, S. and F. Arnaud d'Avitaya, Ga adsorption on Si ⟨111⟩ analysed by RHEED and in situ ellipsometry 112 (1991) 146
Anno, H., T. Koyanagi and K. Matsubara, Epitaxial growth of zincblende MnTe films as a new magneto-optical material 117 (1992) 816
Antar, B.N., Convective instabilities in the melt for solidifying mercury cadmium telluride 113 (1991) 92
Antolini, A., see Genova 120 (1992) 333
Aoyama, S., see Okuyama 114 (1991) 107
Appenzeller, J., see Hardtdegen 116 (1992) 521
Arai, H., see Nakahara 117 (1992) 830
Arbet-Engels, V., see Kallel 111 (1991) 897
Archer, N.A., H.D. Palfrey and A.F.W. Willoughby, The influence of dislocations on mercury self-diffusion in epitaxial and bulk grown $Cd_xHg_{1-x}Te$ 117 (1992) 177
Ariel, Y., see Schieber 115 (1991) 31
Arima, Y. and T. Irisawa, Influence of surface diffusion on the structure of growing crystal surface 115 (1991) 428
Arivuoli, D., see Ganesha 119 (1992) 303
Armitage, D.N., H.M. Yates, J.O. Williams, D.J. Cole-Hamilton and I.P. Patterson, ZnS grown by metalorganic chemical vapour deposition (MOCVD) on GaAs-(100) using t-butyl mercaptan and dimethylzinc 117 (1992) 1082
Armour, E.A., see Sun 113 (1991) 103
Armstrong, J.V., T. Farrell, T.B. Joyce, P. Kightley, T.J. Bullough and P.J. Goodhew, Monitoring real-time CBE growth of GaAs and AlGaAs using dynamic optical reflectivity 120 (1992) 84
Armstrong, J.V., see Farrell 120 (1992) 395
Armstrong, S., see Joyce 115 (1991) 338
Armstrong, S.R., R.D. Hoare, M.E. Pemble, I.M. Povey, A. Stafford and A.G. Taylor, Optical second harmonic generation studies of the nature of the GaAs(100) surface in air 120 (1992) 94
Arnaud d'Avitaya, F., see Andrieu 112 (1991) 146
Arnold, W.A., W.R. Wilcox, F. Carlson, A. Chait and L.L. Regel, Transport modes during crystal growth in a centrifuge 119 (1992) 24
Arrott, A., see Strong 119 (1992) 200
Arterton, B., see Viney 117 (1992) 806
Arterton, B., J.W. Brightwell, S. Mason, B. Ray and I.V.F. Viney, Impact of phase concentrations on structure and electroluminescence of ZnS : Cu 117 (1992) 1008
Arthur, J.R., see Yoo 111 (1991) 1095
As, D.J., see Hingerl 117 (1992) 341
Asahi, H., see Hasegawa 111 (1991) 371
Asahi, H., see Takeyasu 111 (1991) 502
Asahi, H., see Kaneko 111 (1991) 638
Asahi, H., see Okuno 115 (1991) 236
Asahi, H., see Kaneko 120 (1992) 39
Asahi, H., T. Kaneko, Y. Okuno, Y. Itani, K. Asami and S. Gonda, MOMBE growth characteristics of antimonide compounds 120 (1992) 252
Asahi, T., see Murakami 115 (1991) 648
Asaka, N., see Isoda 115 (1991) 388
Asami, K., see Takeyasu 111 (1991) 502
Asami, K., see Okuno 115 (1991) 236
Asami, K., see Asahi 120 (1992) 252
Asano, J., see Minemura 114 (1991) 307

Asano, M., see Harada 116 (1992) 243
Aseev, A.L., A.V. Latyshev and A.B. Krasilnikov, Direct observation of monoatomic step behaviour in MBE on Si by reflection electron microscopy 115 (1991) 393
Aseev, A.L., see Krasilnikov 116 (1992) 178
Ashenford, D.E., P. Devine, J.H.C. Hogg, B. Lunn, C.G. Scott and M. Verma, Variations in the structural and electrical properties as a function of depth in CdTe layers grown on InSb substrates 117 (1992) 233
Ashenford, D.E., see Jackson 117 (1992) 867
Ashida, M., see Ueda 112 (1991) 507
Ashida, M., see Ueda 113 (1991) 69
Aslam, N., E.D. Jones, T.C.Q. Noakes, J.B. Mullin and A.F.W. Willoughby, The diffusion of zinc in cadmium telluride 117 (1992) 249
Asom, M.T., G. Livescu, M. Geva, V. Swaminathan, L.C. Luther, R.E. Leibenguth, V.D. Mattera, E.F. Schubert, J.M. Kuo and R. Kopf, Comparison of delta doped GaAs grown by MBE and GSMBE using different arsenic species 111 (1991) 246
Asom, M.T., V. Swaminathan, G. Livescu, M. Geva, L.C. Luther, R.E. Leibenguth, V.D. Mattera and T. Hayes, Hydrogen passivation of delta doped GaAs 111 (1991) 260
Asom, M.T., J. Mosovsky, R.E. Leibenguth, J.L. Zilko and G. Cadet, Transient arsine generation during opening of solid source MBE chambers 112 (1991) 597
Asonen, H., see Tappura 112 (1991) 27
Asonen, H., see Tappura 120 (1992) 145
Asonen, H., see Zhang 120 (1992) 172
Aspnes, D.E., R. Bhat, C. Caneau, E. Colas, L.T. Florez, S. Gregory, J.P. Harbison, I. Kamiya, V.G. Keramidas, M.A. Koza, M.A.A. Pudensi, W.E. Quinn, S.A. Schwarz, M.C. Tamargo and H. Tanaka, Optically monitoring and controlling epitaxial growth 120 (1992) 71
Assenov, R. and E.K. Polychroniadis, On the comparative characterization of single crystalline PbTe(I) grown by vertical Bridgman and travelling heater methods 112 (1991) 227
Astles, M.A., see Berlouis 117 (1992) 918
Astles, M.G., N. Shaw, G. Blackmore and R.S. Hall, Improved control of composition and electrical properties of liquid phase epitaxial (CdHg)Te layers 117 (1992) 213
Atasoy, O.A., see Yilmaz 118 (1992) 377
Atherton, L.J., see De Yoreo 113 (1991) 691
Atwater, H.A., see Tsai 111 (1991) 931
Aubin, M., see Gagnon 114 (1991) 186
Augustus, P.D., see Kightley 112 (1991) 359
Aulombard, R.L., see Pagés 117 (1992) 569
Austin, R.F., see Doran 117 (1992) 465
Austin R.F., see Feldman 118 (1992) 295
Awschalom, D.D., see Hong 111 (1991) 1016
Ayers, J.E., S.K. Ghandhi and L.J. Schowalter, Crystallographic tilting of heteroepitaxial layers 113 (1991) 430
Azoulay, M., S. Rotter, G. Gafni and M. Roth, The crystalline quality distribution in CdZnTe single crystal correlated to the interface shape during growth 116 (1992) 515
Azoulay, M., S. Rotter, G. Gafni, R. Tenne and M. Roth, Zinc segregation in CdZnTe grown under Cd/Zn partial pressure control 117 (1992) 276
Azuma, M., see Nakayama 115 (1991) 831
Azzam, W.J., see Bahl 111 (1991) 479

Baar, D.J., see Hayashi 115 (1991) 782
Babijchuk, I.P., E.F. Dolzhenkova, M.B. Kosmyna and V.V. Nekrasov, Growth of HTSC Bi-containing single crystals by the spontaneous crystallization method 116 (1992) 529
Bachem, K.H., see Köhler 111 (1991) 295
Bachmann, K.J., see Xing 113 (1991) 113
Bacsa, W., see Von Känel 111 (1991) 889
Badia, F., see Ferrater 113 (1991) 181
Baeta Moreira, M.V., M.A. Py and E. Tuncel, A correlation between surface morphology and RHEED intensity variation for growth of GaAs by molecular beam epitaxy 112 (1991) 14
Bagai, R.K., M. Srivastava, K. Sharma and W.N. Borle, In-situ delineation of defects in ISOVPE-grown $Hg_{1-x}Cd_xTe$ layers 112 (1991) 402
Bagot, D., S. Rolland, R. Granger and R. Triboulet, Linear thermal expansion coefficient in $Hg_{1-x}Cd_xTe$ and $Hg_{1-x}Zn_xTe$ 117 (1992) 189
Bahl, S.R., W.J. Azzam and J.A. del Alamo, Orientation dependence of mismatched $In_xAl_{1-x}As/In_{0.53}Ga_{0.47}As$ HFETs 111 (1991) 479
Baldereschi, A., see Von Känel 111 (1991) 889
Baldwin, K.W., see Pfeiffer 111 (1991) 333
Balk, P., see Kayser 112 (1991) 111
Ball, G., see Lane 120 (1992) 245
Ballingall, J., see Hersee 120 (1992) 218
Ballingall, J.M., see Ho 111 (1991) 233
Ballman, A.A., see Cheng 112 (1991) 309
Ballutaud, D., see Marbeuf 117 (1992) 197
Baltramiejūnas, S. Pakalnis and G. Tamulaitis, Transient effects in photoexcited CdS microcrystals 117 (1992) 622
Balyakina, I.V., see Kulakov 113 (1991) 653
Balzuweit, K., see Vogels 116 (1992) 397
Bamberger, C.E., L.F. Allard, D.W. Coffey and M.R. Bennett, Whiskers of TiN by topochemical reaction 112 (1991) 47
Ban, V.S., see Jones 120 (1992) 150

Banan, M., R.T. Gray and W.R. Wilcox, An experimental approach to determine the heat transfer coefficient in directional solidification furnaces 113 (1991) 557
Banan, M., see Caram 114 (1991) 249
Bandeira, I.N., see Regel 119 (1992) 94
Bando, Y., see Terashima 115 (1991) 745
Banyai, L., see Uhrig 117 (1992) 598
Baranyuk, V.Ye., see Kosyachenko 117 (1992) 583
Barber, P.G., J.T. Petty and R.L. Stevens, Crystal growth precursors of $YBa_2Cu_3O_{7-x}$ predicted from crystal habits by use of moments of momentum 112 (1991) 613
Bárczy, P., J. Sólyom and L.L. Regel, Solidification of Al–Al_3Ni(Cu) eutectics at high gravity 119 (1992) 160
Barilo, S.N., A.P. Ges, S.A. Guretskii, D.I. Zhigunov, A.V. Zubets, A.A. Ignatenko, A.N. Igumentsev, I.D. Lomako, A.M. Luginets, V.N. Yakimovich, L.A. Kurochkin, L.V. Markova and O.I. Krot, Growth of bulk single crystals of $YBa_2Cu_3O_{7-\delta}$ from a new type of crucible 119 (1992) 403
Barlow, R.D., see Powell 111 (1991) 907
Barnes, P.A., see Allerman 112 (1991) 583
Barrau, J., see Starck 120 (1992) 180
Barski, A., see Garcia 111 (1991) 578
Barthe, F., see Moisson 111 (1991) 141
Barthou, C., see Zeinert 117 (1992) 1016
Bartoli, F.J., see Youngdale 111 (1991) 693
Basaran, E., see Powell 111 (1991) 907
Basavalingu, B. and J.A.K. Tareen, Hydrothermal phase relations in V_2O_5–H_2O system 113 (1991) 659
Basmaji, P., see Notari 116 (1992) 518
Bassani, F., K. Saminadayar, S. Tatarenko, K. Kheng, R.T. Cox, N. Magnea and C. Grattepain, Indium doping of CdTe layers and CdTe/$Cd_{1-x}Zn_xTe$ microstructures 117 (1992) 391
Batur, C., R.B. Sharpless, W.M.B. Duval, B.N. Rosenthal and N.B. Singh, Identification and control of a multizone crystal growth furnace 119 (1992) 371
Baturin, N.A., see Vorobiov 119 (1992) 111
Bauer, G., see Springholz 113 (1991) 593
Bauer, G., see Enichlmair 117 (1992) 844
Bauer, S., A. Rosenauer, J. Skorsetz, W. Kuhn, H.P. Wagner, J. Zweck and W. Gebhardt, Investigation of strained ZnTe epilayers by high resolution electron microscopy 117 (1992) 297
Baughman, R.J., Quartz crystal growth 112 (1991) 753
Baur, B., see Heinecke 111 (1991) 599
Baur, B., see Heinecke 120 (1992) 140
Baur, B., see Beer 120 (1992) 312
Baur, B., see Heinecke 120 (1992) 376
Bauser, E., see Hansson 114 (1991) 573
Bauser, E., see Chen 118 (1992) 452
Baxter, C.S., W.M. Stobbs and J.H. Wilkie, The morphology of ordered structures in III–V alloys: inferences from a TEM study 112 (1991) 373
Beaglehole, D., Surface melting of small particles, and the effects of surface impurities 112 (1991) 663
Beall, R.B., see Harris 111 (1991) 239
Beam III, E.A., T.S. Henderson, A.C. Seabaugh and J.Y. Yang, The use of tertiarybutylphosphine and tertiarybutylarsine for the metalorganic molecular beam epitaxy of the $In_{0.53}Ga_{0.47}As$/InP and $In_{0.48}Ga_{0.52}P$/GaAs materials systems 116 (1992) 436
Bechhoefer, J., see Géminard 114 (1991) 640
Bechtold, J., see Tao 114 (1991) 279
Beck, W.A., see Svensson 111 (1991) 450
Becker, E.E., see Chand 111 (1991) 20
Beer, K., B. Baur, H. Heinecke and R. Treichler, Improvements in silicon doping of InP and GaInAs in metalorganic molecular beam epitaxy 120 (1992) 312
Bell, W., A.E.D. McQueen, J.C. Walton, D.F. Foster, D.J. Cole-Hamilton and J.E. Hails, Decomposition and reactivity of tellurium alkyls in the liquid and gas phases; dihex-5-enyltellurium and dipent-4-enyltellurium as mechanistic probes 117 (1992) 58
Benalloul, P., see Zeinert 117 (1992) 1016
Ben-Amar, G., see Horowitz 119 (1992) 391
Benchimol, J.L., X.Q. Zhang, Y. Gao, G. Le Roux, H. Thibierge and F. Alexandre, Chemical beam epitaxy of AlGaAs and AlInAs using trimethylamine alane precursor 120 (1992) 189
Benhlal, J.T., R. Granger, D. Lemoine, R. Triboulet and Y. Marqueton, Irreversible optical response in $Cd_{1-x}Zn_xTe$ mixed crystals 117 (1992) 281
Benisty, H., see Böckenhoff 114 (1991) 619
Bennema, P., see Boek 114 (1991) 389
Bennema, P., see Vogels 116 (1992) 397
Bennett, M.R., see Bamberger 112 (1991) 47
Benoit, J., see Zeinert 117 (1992) 1016
Bensaoula, A., see Hansen 116 (1992) 271
Bensaoula, A., see Roth 120 (1992) 212
Benson, S.W., see Francis 112 (1991) 474
Benz, K.W., see Meyer 117 (1992) 656
Benz II, R.G., B.K. Wagner, D. Rajavel and C.J. Summers, Chemical beam epitaxy of CdTe, HgTe, and HgCdTe 111 (1991) 725
Bergmann, R., see Hansson 114 (1991) 573
Berkowski, M., see Scheel 115 (1991) 19

Berlouis, L.E.A., L.M. Peter, R. Greef and M.A. Astles, In-situ spectroscopic characterisation of passivation layers on (Cd,Hg)Te 117 (1992) 918
Bernardi, S., C. Bocchi, C. Ferrari, P. Franzosi and L. Lazzarini, Structural characterization of $Hg_{0.78}Cd_{0.22}Te/CdTe$ LPE heterostructures grown from Te solutions 113 (1991) 53
Bernklau, D., see Riechert 111 (1991) 1100
Beserman, R., see Turco-Sandroff 111 (1991) 762
Betrouni, M., see Fikri 119 (1992) 41
Bhargava, R.N., Compact blue lasers in the near future 117 (1992) 894
Bhat, H.L., see Dhanaraj 113 (1991) 456
Bhat, I.B., Recent advances in the organometallic vapor phase epitaxial growth of HgCdTe by the direct alloy growth process 117 (1992) 1
Bhat, R., see Caneau 114 (1991) 481
Bhat, R., see Caneau 118 (1992) 467
Bhat, R., see Aspnes 120 (1992) 71
Bhat, R., Current status of selective area epitaxy by OMCVD 120 (1992) 362
Bhattacharya, P.K., see Chen 111 (1991) 228
Bhattacharya, P.K., see Kim 111 (1991) 633
Bhattacharya, P.K., see Sherwin 120 (1992) 162
Bicknell-Tassius, R.N., see Kuhn 117 (1992) 660
Bicknell-Tassius, R.N., see Waag 117 (1992) 820
Bicknell-Tassius, R.N., see Yakovlev 117 (1992) 854
Bicknell-Tassius, R.N., see Kuhn 117 (1992) 871
Bicknell-Tassius, R.N., see Uraltsev 117 (1992) 877
Biderman, S., see Horowitz 119 (1992) 391
Bienfait, M., see Maruyama 118 (1992) 33
Bierlein, J.D., see Cheng 112 (1991) 309
Bilger, G., see Mauch 117 (1992) 964
Bilgram, J.H., see Steininger 112 (1991) 201
Bimberg, D., see Grundmann 115 (1991) 150
Bindal, M.M., S.K. Singhal, B.P. Singh, R.K. Nayar, R. Chopra and A. Dhar, Synthesis of cubic boron nitride using magnesium as the catalyst 112 (1991) 386
Binder, R., see Masumoto 117 (1992) 732
Binsma, J.J.M., see Kolar 116 (1992) 473
Bird, C.D., see Bordui 113 (1991) 61
Biswas, D. and H. Morkoç, A safety system for gas source molecular beam epitaxy 113 (1991) 209
Black, D., see Steiner 114 (1991) 707
Blackmore, G., see Astles 117 (1992) 213
Blaha, J., see McCrary 112 (1991) 39
Bleuse, J., see Pautrat 117 (1992) 454
Bleuse, J., N. Magnea, L. Ulmer, J.L. Pautrat and H. Mariette, Room-temperature laser emission near 2 μm from an optically pumped HgCdTe separate-confinement heterostructure 117 (1992) 1046
Blez, M., see Allovon 111 (1991) 484
Bliss, D.E., see Vanderah 118 (1992) 385
Block, T.R. and B.G. Streetman, Correlation between the dampening of RHEED oscillations and the photoluminescence of quantum wells in the presence of AsO 111 (1991) 98
Blood, P., see Foxon 111 (1991) 1047
Blunier, S., see Tiwari 111 (1991) 730
Bocchi, C., see Bernardi 113 (1991) 53
Bocchi, C., C. Ferrari, P. Franzosi, M. Scaffardi, P. Diaz, J.G. Rodriguez and T.A. Prutskij, Investigation of LPE $Ga_{1-x}Al_xAs/GaAs$ laser structures by double crystal diffractometry 113 (1991) 540
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Bochkarev, A.E., see Kazakov 116 (1992) 204
Böckenhoff, E. and H. Benisty, Evolution of 3D growth patterns on nonplanar substrates 114 (1991) 619
Boeck, T., see Rudolph 118 (1992) 204
Boek, E.S., D. Feil, W.J. Briels and P. Bennema, From wave function to crystal morphology: application to urea and alpha-glycine 114 (1991) 389
Boggess, T.F., see Hasenberg 111 (1991) 388
Bohling, D.A., see Abernathy 120 (1992) 195
Bohling, D.S., see Abernathy 111 (1991) 574
Boland, J.J., see Takamori 112 (1991) 660
Bolt, R.J., M. van der Mooren and M.T. Sebastian, Etching experiments on flux grown potassium titanyl phosphate $KTiOPO_4$ (KTP) 112 (1991) 773
Bolt, R.J., M.H. van der Mooren and H. de Haas, Growth of $KTiOPO_4$ (KTP) single crystals by means of phosphate and phosphate/sulfate fluxes out of a three-zone furnace 114 (1991) 141
Bolt, R.J. and W.J.P. van Enckevort, Observation of growth steps and growth hillocks on the {100}, {210}, {011} and {101} faces of flux grown $KTiOPO_4$ (KTP) 119 (1992) 329
Bonnafé, J., see Triboulet 117 (1992) 227
Bonner, W.A., see Caneau 114 (1991) 481
Bonnet, J.E., see Marbeuf 117 (1992) 197
Bonnevie, D., see Goldstein 120 (1992) 157
Bordui, P.F., R.G. Norwood, C.D. Bird and G.D. Calvert, Compositional uniformity in growth and poling of large-diameter lithium niobate crystals 113 (1991) 61
Borisov, A.G., O.P. Fedorov and V.V. Maslow, Growth of succinonitrile dendrites in different crystallographic directions 112 (1991) 463
Borle, W.N., see Bagai 112 (1991) 402
Borlind, J., see Nordell 114 (1991) 92

Borrego, J.M., see Venkatasubramanian 112 (1991) 7
Bothra, S., see Venkatasubramanian 112 (1991) 7
Böttner, H., see Springholz 113 (1991) 593
Bouchenaki, C., see Ullrich 117 (1992) 902
Bouchenaki, C., see Ullrich 117 (1992) 925
Boulesteix, C., see Marfaing 118 (1992) 27
Boulou, M., see Starck 120 (1992) 349
Boutellier, R., see Sun 112 (1991) 71
Bove, P., see Garcia 111 (1991) 578
Bowen, D.K., see Powell 111 (1991) 907
Bowen, D.K., see Capano 116 (1992) 260
Bowers, K.A., see Ren 111 (1991) 772
Bowers, K.A., see Ren 111 (1991) 829
Bowers, K.A., see Ren 117 (1992) 510
Boyce, P.J., see Nakano 117 (1992) 331
Bozovic, I., see Eckstein 111 (1991) 973
Brabers, V.A.M., see Emmen 118 (1992) 477
Bradley, R.R., see Kightley 112 (1991) 359
Bradley, R.R., see Woodhouse 120 (1992) 323
Brandt, G.B., see Kun 117 (1992) 987
Brandt, O., L. Tapfer, K. Ploog, M. Hohenstein and F. Phillipp, Growth processes and relaxation mechanisms in the molecular beam epitaxy of InAs/GaAs heterostructures 111 (1991) 383
Brandt, O., K. Ploog, L. Tapfer, M. Hohenstein and F. Phillipp, Synthesis and structural configuration of highly strained InAs films in GaAs 115 (1991) 99
Brantley, S.L., see Voigt 113 (1991) 527
Brasil, M.J.S.P., see Turco-Sandroff 111 (1991) 762
Bratina., G., see Vanzetti 117 (1992) 573
Braun, R.J. and S.H. Davis, Oscillatory instabilities in rapid directional solidification: bifurcation theory 112 (1991) 670
Brečević, L., see Marković 118 (1992) 93
Brennan, T.M., see Tsao 111 (1991) 125
Breuilly, L., see Muranaka 112 (1991) 808
Briels, W.J., see Boek 114 (1991) 389
Brighten, J.C., see Powell 111 (1991) 907
Brightwell, J.W., see Viney 117 (1992) 806
Brightwell, J.W., see Arterton 117 (1992) 1008
Brillouet, F., see Pagnod-Rossiaux 120 (1992) 317
Brinkman, A.W., see Sang 113 (1991) 1
Brinkman, A.W., see Loginov 117 (1992) 259
Brinkman, A.W., see Alnajjar 117 (1992) 385
Brinkman, A.W., see Simmons 117 (1992) 959
Briones, F., see González 111 (1991) 120
Briones, F. and A. Ruiz, Atomic layer molecular beam epitaxy (ALMBE): growth kinetics and applications 111 (1991) 194
Briot, O., see Pagés 117 (1992) 569
Britt, J., see Chu 117 (1992) 1073
Brock, T., see Munns 120 (1992) 184
Bronshteyn, V.L. and A.A. Chernov, Freezing potentials arising on solidification of dilute aqueous solutions of electrolytes 112 (1991) 129
Broser, I., see Hoffmann 117 (1992) 640
Broser, I., see Podlowski 117 (1992) 698
Broser, I., see Thurian 117 (1992) 727
Broser, I., see Fricke 117 (1992) 783
Broser, I., Ch. Fricke, B. Lummer, R. Heitz, H. Perls and A. Hoffmann, Optical nonlinearity and fast switching due to birefringence and mode coupling in CdS crystals 117 (1992) 788
Brown, A.S., see Metzger 111 (1991) 445
Brown, D.J. and K. Alexander, Rates of nucleation in the crystallization of sucrose 118 (1992) 464
Brown, L.M., see Pike 111 (1991) 925
Brown, P.D., see Loginov 117 (1992) 259
Brown, P.D., Y.Y. Loginov, K. Durose, J.T. Mullins, T. Taguchi, T. Burbery, S. Lawson-Jack and I. Jones, Microstructural properties of epitaxial CdS, (Cd,Zn)S and CdS ||(Cd,Zn)S superlattices 117 (1992) 536
Brown, P.D., see Loginov 117 (1992) 682
Brown, R.A., see Kim 114 (1991) 411
Brown, W.E., see Eidelman 113 (1991) 643
Brown-Goebeler, K., see Chang 111 (1991) 475
Brush, L.N., G.B. McFadden and S.R. Coriell, Laser melting of thin silicon films 114 (1991) 446
Bryskiewicz, T., see Roth 113 (1991) 379
Bublik, V.T., see Charniy 116 (1992) 369
Bublik, V.T., see Charniy 118 (1992) 163
Buchan, N.I., see De Lyon 111 (1991) 564
Buhrman, R.A., see Norton 114 (1991) 258
Bulle-Lieuwma, C.W.T., see Theunissen 118 (1992) 125
Bullough, T.J., see Armstrong 120 (1992) 84
Bullough, T.J., see Joyce 120 (1992) 206
Bullough, T.J., see Farrell 120 (1992) 395
Burbery, T., see Brown 117 (1992) 536
Burdette, H., see Steiner 114 (1991) 707
Burdin, B.V., L.L. Regel, A.M. Turchaninov and O.V. Shumaev, The peculiarities of material crystallization experiments in the CF-18 centrifuge under high gravity 119 (1992) 61
Bureyev, A.V., see Butkhuzi 117 (1992) 366
Burkert, M., see Gille 114 (1991) 77
Burkhardt, E., see Sun 112 (1991) 71
Buschert, J., see Samarth 111 (1991) 816
Buskes, H., see Hartley 117 (1992) 166
Busse, W., see Hommel 117 (1992) 721
Butkhuzi, T.V., A.V. Bureyev, A.N. Georgobiani, N.P. Kekelidze and T.G. Khulordava, Optical and electrical properties of radical beam gettering epitaxy grown n- and p-type ZnO single crystals 117 (1992) 366
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Butter, E., see Keller 118 (1992) 176

Caballero, M.A., see González-Mañas 113 (1991) 669
Cabanel, R., see Etienne 111 (1991) 1003
Cacioppo, E. and M.L. Pusey, The solubility of the tetragonal form of hen egg white lysozyme from pH 4.0 to 5.4 114 (1991) 286
Cadet, G., see Asom 112 (1991) 597
Cadoret, R., see Chaput 112 (1991) 691
Calestani, G., see Bocelli 113 (1991) 663
Callec, R., see L'Haridon 113 (1991) 39
Calvert, G.D., see Bordui 113 (1991) 61
Camel, D., see Garandet 113 (1991) 587
Cammack, D., see Olego 117 (1992) 324
Caneau, C., R. Bhat, M.R. Frei, S.A. Schwarz, W.A. Bonner and M. Koza, Selective OMVPE of GaInAs and InP using a polycrystalline InP mask 114 (1991) 481
Caneau, C., R. Bhat and M.A. Koza, Dependence of doping on substrate orientation for GaAs:C grown by OMVPE 118 (1992) 467
Caneau, C., see Aspnes 120 (1992) 71
Canright, D. and S.H. Davis, Buoyancy effects of a growing, isolated dendrite 114 (1991) 153
Cao, D.S., Z.M. Fang and G.B. Stringfellow, Organometallic vapor-phase epitaxial growth of $Al_xGa_{1-x}Sb$ and $Al_xGa_{1-x}As_ySb_{1-y}$ 113 (1991) 441
Cao, F.N., see Zhong 119 (1992) 74
Cao, X.Z. and A.F. Witt, Decorated dislocations in SI-GaAs as revealed by dark field NIR transmission microscopy 112 (1991) 838
Cao, X.Z. and A.F. Witt, Identification of dislocation etch pits in n-type GaAs by NIR transmission microscopy 114 (1991) 255
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Caram, R., M. Banan and W.R. Wilcox, Directional solidification of Pb–Sn eutectic with vibration 114 (1991) 249
Cardone, F., see De Lyon 111 (1991) 564
Carlin, J.F., see Rudra 111 (1991) 589
Carlin, J.F., A. Rudra, R. Houdré, P. Ruterana and M. Ilegems, Effect of growth interruptions on ultra-thin InAs/InP quantum wells grown by chemical beam epitaxy 120 (1992) 155
Carlin, J.F., see Rudra 120 (1992) 338
Carlson, D.J. and A.F. Witt, Quantitative analysis of the effects of vertical magnetic fields on microsegregation in Te-doped LEC GaAs 116 (1992) 461
Carlson, D.J., see Laudise 118 (1992) 277
Carlson, F., see Arnold 119 (1992) 24
Carlsson, J.-O., see Hårsta 114 (1991) 507
Caroli, B., C. Caroli, G. Faivre and J. Mergy, Lamellar eutectic growth of CBr_4–C_2Cl_6: effect of crystal anisotropy on lamellar orientations and wavelength dispersion 118 (1992) 135
Caroli, C., see Caroli 118 (1992) 135
Carr, D., see Hartley 117 (1992) 166
Carter, C.B., see Norton 113 (1991) 716
Carter, C.B., see Norton 114 (1991) 258
Castagné, J., see Harris 111 (1991) 239
Castillo, J.L., P.L. García-Ybarra and D.E. Rosner, Morphological instability of a thermophoretically growing deposit 116 (1992) 105
Cavenett, B.C., see Simpson 117 (1992) 134
Cavenett, B.C., see Wallace 117 (1992) 320
Cerullo, M., see Eaglesham 111 (1991) 833
Cesnulevicius, J., see Woggon 117 (1992) 608
Chabot, B., see Scheel 115 (1991) 19
Chait, A., see Arnold 119 (1992) 24
Chalmers, S.A., see Petroff 111 (1991) 360
Chalmers, S.A., H. Kroemer and A.C. Gossard, The growth of (Al,Ga)Sb tilted superlattices and their heteroepitaxy with InAs to form corrugated-barrier quantum wells 111 (1991) 647
Chamarro, M.A., C. Gourdon and P. Lavallard, Photoluminescence polarization properties of CdS_xSe_{1-x} nanocrystals in glasses: evidence for hexagonal structure 117 (1992) 614
Chamberlain, J.M., see Stanley 111 (1991) 14
Chand, N., T.D. Harris, S.N.G. Chu, E.E. Becker, A.M. Sergent, M. Schnoes and D.V. Lang, Variation of background impurities in $Al_xGa_{1-x}As$ $(0.3 \leq x \leq 0.4)$ with growth temperature: implications for device leakage current and surface/heterointerface roughness 111 (1991) 20
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Chang, A.M., see Chin 111 (1991) 466
Chang, H.S.W., see Schleich 112 (1991) 737
Chang, L.L., see Munekata 111 (1991) 1011
Chang, L.L., see Hong 111 (1991) 1016
Chang, R.S.F., see Shaw 112 (1991) 731
Chang, S.K., see Yao 111 (1991) 823
Chang, S.K., see Lee 117 (1992) 148
Chang, S.K., C.D. Lee, H.L. Park and C.H. Chung, Exciton transfer processes in $ZnSe_{1-x}Te_x$ 117 (1992) 793
Chang, S.S., see Ando 115 (1991) 69
Chang, T.Y., see Chin 111 (1991) 466
Chang, T.Y., N.J. Sauer, J.E. Zucker, K.L. Jones, B. Tell, K. Brown-Goebeler, M. Wegener and D.S. Chemla, High quality GaInAs/AlGaInAs/AlInAs heterostructures on Si ion implanted semi-insulating InP substrates for novel high performance optical modulators 111 (1991) 475

Chang, W.S.C., see Niki 111 (1991) 419
Chang, Y.H., see Hu 114 (1991) 191
Changkang Chen, see Chen 118 (1992) 101
Chapman, J.N., see Kean 111 (1991) 189
Chaput, L., R. Cadoret and M. Mihailovic, Experimental and theoretical study of InP homoepitaxy by chemical vapour deposition from gaseous indium chloride and hydrogen diluted phosphine 112 (1991) 691
Charniy, L.A., A.N. Morozov, K.D. Scherbachov, V.T. Bublik and I.V. Stepantsova, X-ray diffuse scattering identification of matrix As-rich microdefects in GaAs crystals 116 (1992) 369
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Chatenoud, F., see Williams 111 (1991) 1066
Chaudhry, M.I., R.J. McCluskey and R.L. Wright, The role of carrier gases in the epitaxial growth of β-SiC on Si by CVD 113 (1991) 120
Chemla, D.S., see Chang 111 (1991) 475
Chen, C.H., see Xue 113 (1991) 371
Chen Changkang, B.M. Wanklyn, E. Dieguez, A.J. Cook, J.W. Hodby, A. Schwartzbrod, A. Dabkowski and H. Dabkowska, Phase diagram and crystal growth of $Pb_2Sr_2(Y_xCa_{1-x})Cu_3O_{8+y}$ 118 (1992) 101
Chen, F.R., see Chen 118 (1992) 109
Chen, H.C., see Tao 114 (1991) 279
Chen, H.S., see Hong 111 (1991) 984
Chen, J.F. and A.Y. Cho, Tellurium doping study of GaSb grown by molecular beam epitaxy using SnTe 111 (1991) 619
Chen, J.F., L. Yang, M.C. Wu, S.N.G. Chu and A.Y. Cho, Studies of the tunneling currents in the InAs/AlSb/GaSb single-barrier interband tunneling diodes grown on GaAs substrates 111 (1991) 659
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Chen, J.X., F. Ernst, P.O. Hansson and E. Bauser, Liquid phase epitaxy of GeSi on {111} Si substrates: lattice defect structure and electronic properties 118 (1992) 452
Chen Jinfeng, see Li 118 (1992) 371
Chen Jinfeng, see Li 119 (1992) 363
Chen, L.J., see Chen 118 (1992) 109
Chen, Li, K.C. Rajkumar, A. Madhukar, Wei Chen, S. Guha and K. Kaviani, Realization of sharp excitonic features in highly strained $GaAs/In_xGa_{1-x}As$ multiple quantum wells grown on GaAs(100) substrates 111 (1991) 424
Chen, M., see Wu 111 (1991) 252
Chen, T.P., F.R. Chen, Y.C. Chuang, Y.D. Guo, J.G. Peng, T.S. Huang and L.J. Chen, Study of twins in GaAs, GaP and InAs crystals 118 (1992) 109
Chen, Wei, see Chen 111 (1991) 424
Chen, X., see O'Donnell 117 (1992) 497
Chen, X., see Trager-Cowan 117 (1992) 532
Chen, Y.C., P.K. Bhattacharya and J. Singh, Strained layer epitaxy of InGaAs by MBE and migration enhanced epitaxy – comparison of growth modes and surface quality 111 (1991) 228
Chen, Y.C., see Kim 111 (1991) 633
Chen Ying, see Li 118 (1992) 371
Chen Ying, see Li 119 (1992) 363
Chen, Yunliang, see Shen 111 (1991) 807
Cheng Gan Chao, Qian Zhi Qiang, Tang Guang Kui, Song Wen Bao and Tang Hong Gao, Top seeded growth of $KTiOPO_4$ from molten tungstate solution 112 (1991) 294
Cheng, H., see DePuydt 117 (1992) 1078
Cheng, H.C. and M.H. Juang, Growth of single-crystalline $CoSi_2$ on (111)Si at low annealing temperatures by a nonultra-high vacuum method 115 (1991) 572
Cheng, L.K., J.D. Bierlein, C.M. Foris and A.A. Ballman, Growth of epitaxial thin films in the $KTiOPO_4$ family of crystals 112 (1991) 309
Cheng, Xingyu, see Li 111 (1991) 736
Chernov, A.A., see Bronshteyn 112 (1991) 129
Chernov, A.A., see Mikheev 112 (1991) 591
Chernov, A.A., How does the flow within the boundary layer influence morphological stability of a vicinal face? 118 (1992) 333
Chi, A., see Fashe 111 (1991) 677
Chiang, C.D., see Chen 113 (1991) 520
Chibani, A., R. Gauthier, P. Pinard and P. Andonov, Etude de la texture des rubans EPR de silicium polycristallin photovoltaïque 113 (1991) 681
Chikyow, T., see Koguchi 111 (1991) 688
Chin, A., T.Y. Chang, A. Ourmazd, E.M. Monberg, A.M. Chang and C. Kurdak, Effects of substrate orientation, pseudomorphic growth and superlattice on alloy scattering in modulation doped GaInAs 111 (1991) 466
Chin, A., see Hersee 120 (1992) 218
Chiu, L.C., see Tran 113 (1991) 16
Chiu, T.H., J.E. Cunningham, J.A. Ditzenberger, W.Y. Jan and S.N.G. Chu, Characterization of the GaAs:C and AlGa

As : C doping superlattice grown by chemical beam epitaxy 111 (1991) 274
Chiu, T.H., see Cunningham 120 (1992) 306
Chiu, T.H., M.D. Williams, J.E. Zucker, F.G. Storz and S.N.G. Chu, CBE growth of InGaAsP/InP multiple quantum wells for optical modulator applications 120 (1992) 343
Cho, A.Y., Advances in molecular beam epitaxy (MBE) 111 (1991) 1
Cho, A.Y., see Chen 111 (1991) 619
Cho, A.Y., see Chen 111 (1991) 659
Cho, A.Y., see Hong 111 (1991) 1052
Cho, A.Y., see Wang 111 (1991) 1057
Cho, K.-I., see Choi 115 (1991) 579
Choi, C.-K., H.-H. Park, J.Y. Lee, K.-I. Cho, M.-C. Paek, O.-J. Kwon, K.-H. Kim and S.-J. Yang, Formation and epitaxial growth of titanium-disilicide on Si(111) 115 (1991) 579
Choi, H.K., see Eglash 111 (1991) 669
Choi, K.Y., see Droopad 114 (1991) 327
Choi, K.Y., see Shiralagi 114 (1991) 337
Choi, K.Y., see Edwards 120 (1992) 78
Choi, K.Y., see Droopad 120 (1992) 200
Chokron, S., see Schieber 115 (1991) 31
Chopra, M.A., see Tewari 118 (1992) 183
Chopra, R., see Bindal 112 (1991) 386
Chow, D.H., see Collins 111 (1991) 664
Chow, D.H., R.H. Miles, C.W. Nieh and T.C. McGill, Growth of InAs/$Ga_{1-x}In_xSb$ infrared superlattices 111 (1991) 683
Chow, P.C., see Fashe 111 (1991) 677
Christensson, F., see Lundager Madsen 114 (1991) 613
Christer, J., see Stagg 120 (1992) 98
Christoffersen, J., E. Rostrup and M.R. Christoffersen, Relation between interfacial surface tension of electrolyte crystals in aqueous suspension and their solubility; a simple derivation based on surface nucleation 113 (1991) 599
Christoffersen, M.R., see Christoffersen 113 (1991) 599
Chu, S.N.G., see Chand 111 (1991) 20
Chu, S.N.G., see Chiu 111 (1991) 274
Chu, S.N.G., see Chen 111 (1991) 659
Chu, S.N.G., see Wang 111 (1991) 1057
Chu, S.N.G., see McCrary 112 (1991) 39
Chu, S.N.G., see Chiu 120 (1992) 343
Chu, S.S., see Chu 117 (1992) 1073
Chu, T.L., S.S. Chu, C. Ferekides, C.Q. Wu, J. Britt and C. Wang, High efficiency thin film CdS/CdTe heterojunction solar cells 117 (1992) 1073
Chu, T.Y., A. Dodabalapur, A. Srinivasan, D.P. Neikirk and B.G. Streetman, Properties and applications of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) grown at low temperatures 111 (1991) 26
Chuang, Y.C., see Zhou 114 (1991) 283
Chuang, Y.C., see Chen 118 (1992) 109
Chung, C., F. Jain and G. Drake, Prospects of fabricating blue/green lasers using ZnSe based metal–insulator–semiconductor (MIS) heterostructures 117 (1992) 1062
Chung, C.H., see Lee 117 (1992) 148
Chung, C.H., see Chang 117 (1992) 793
Cibert, J., R. André, C. Deshayes, Le Si Dang, H. Okumura, S. Tatarenko, G. Feuillet, P.H. Jouneau, R. Mallard and K. Saminadayar, Piezoelectric fields in CdTe-based heterostructures 117 (1992) 424
Cingolani, R., see Crook 111 (1991) 184
Cingolani, R., see Lovergine 118 (1992) 304
Clark, R.J.H., see Chandley 116 (1992) 151
Clark, S.A., see Westwood 114 (1991) 346
Clarke, S., see Wilby 111 (1991) 864
Clausing, R.E., see Specht 114 (1991) 38
Claxton, P.A., M. Hopkinson, J. Kovac, G. Hill, M.A. Pate and J.P.R. David, Quantum-confined Stark effect in InGaAs/InP multiple quantum wells grown by solid source molecular beam epitaxy 111 (1991) 1080
Claxton, P.A., see Ravila 114 (1991) 569
Clegg, J.B., see Harris 111 (1991) 239
Clemens, H., see Springholz 113 (1991) 593
Clérot, F., see Le Corre 120 (1992) 353
Cloitre, T., see Pagés 117 (1992) 569
Cockayne, B., see Dhese 117 (1992) 91
Cockayne, B., see Parbrook 117 (1992) 492
Cockayne, B., see O'Donnell 117 (1992) 497
Cockayne, B., see Trager-Cowan 117 (1992) 532
Coddens, G., see Maruyama 118 (1992) 33
Cody, A.M. and R.D. Cody, Chiral habit modifications of gypsum from epitaxial-like adsorption of stereospecific growth inhibitors 113 (1991) 508
Cody, R.D., see Cody 113 (1991) 508
Coffey, D.W., see Bamberger 112 (1991) 47
Colas, E., see Aspnes 120 (1992) 71
Cole-Hamilton, D.J., see Bell 117 (1992) 58
Cole-Hamilton, D.J., see Armitage 117 (1992) 1082
Collins, D.A., D.Z.-Y. Ting, E.T. Yu, D.H. Chow, J.R. Söderström, Y. Rajakarunanayake and T.C. McGill, Interband tunneling in InAs/GaSb/AlSb heterostructures 111 (1991) 664
Collins, D.A., see Phillips 111 (1991) 820
Colombo, P., see Hoke 111 (1991) 269
Conflant, P., see Quintero 114 (1991) 661
Cook, A.J., see Chen 118 (1992) 101
Cook, Jr., J.W., see Lansari 111 (1991) 720
Cook, Jr., J.W., see Ren 111 (1991) 772
Cook, Jr., J.W., see Ren 111 (1991) 829
Cook, Jr., J.W., see Ren 117 (1992) 510
Cooke, D.C., see Svensson 111 (1991) 450
Cooke, D.C., see Uppal 111 (1991) 623
Coquillé, R., see L'Haridon 113 (1991) 39
Coriell, S.R., see Brush 114 (1991) 446
Coriell, S.R., see Hardy 114 (1991) 467

Coronell, D.G. and K.F. Jensen, Analysis of MOCVD of GaAs on patterned substrates 114 (1991) 581
Cot, L., see Gómez Morales 116 (1992) 427
Cotell, C.M., see Panish 112 (1991) 343
Cotte, J.M., see Kesan 111 (1991) 847
Cottineau, L.M. see Garnier 119 (1992) 66
Coudenys, G., I. Moerman and P. Demeester, Influence of the nucleation and annealing conditions on the quality of InP layers grown on GaAs by MOCVD 114 (1991) 314
Couderc, J.P., see Langlais 113 (1991) 606
Coulas, D., see Roth 113 (1991) 379
Cournil, M., see Triboulet 118 (1992) 231
Covington, B.C., see Fashe 111 (1991) 677
Cox, R.T., see Bassani 117 (1992) 391
Crary, S.B., see Sherwin 111 (1991) 594
Crawley, J., see Stagg 120 (1992) 98
Cremer, C., see Heinecke 120 (1992) 376
Crochet, M.J., see Kakimoto 114 (1991) 715
Crook, G.E., L. Tapfer, L. Däweritz, R. Cingolani and K. Ploog, Control of initial surface configuration for GaAs-on-Si MBE using a Si buffer layer? 111 (1991) 184
Crouch, M.A., see Lane 120 (1992) 245
Cui, Jie, see Shen 111 (1991) 807
Cui, Jie, Hailong Wang, Fuxi Gan and Aizhen Li, The study of phonons and lattice strains in ZnSe–ZnTe and ZnS–ZnSe strained-layer superlattices by Raman and far-infrared reflectivity spectra 111 (1991) 811
Cui, Jie, Hailong Wang and Fuxi Gan, The optical and spectroscopic properties of II–VI wide-gap ZnSe/ZnS and ZnSe/ZnTe strained-layer superlattices 117 (1992) 505
Cuisinier, F.J.G., J.C. Voegel, J. Yacaman and R.M. Frank, Structure of initial crystals formed during human amelogenesis 116 (1992) 314
Cullis, A.G., see Lane 120 (1992) 245
Cunningham, J.E., see Chiu 111 (1991) 274
Cunningham, J.E., T.Y. Kuo, A. Ourmazd, K. Goossen, W. Jan, F. Storz, F. Ren and C.G. Fonstad, Gas source molecular beam epitaxy growth of heterojunction bipolar transistors containg 1 monolayer δ-Be 111 (1991) 515
Cunningham, J.E., M. Williams, T.H. Chiu, W. Jan, F. Storz and E. Westerwick, Confinement of δ Be at the one monolayer level in GaAs 120 (1992) 306
Curreri, P.A., The effectiveness of Coriolis dampening of convection during aircraft high-g arcs 119 (1992) 141

Dabkowska, H., see Xue 113 (1991) 371
Dabkowska, H., see Chen 118 (1992) 101
Dabkowski, A., see Xue 113 (1991) 371
Dabkowski, A., see Chen, 118 (1992) 101
Dabringhaus, H., see Helmrich 112 (1991) 824
Dabringhaus, H., Comment on "Transient growth and evaporation kinetics of a singular face containing linear sinks: time dependent BCF theory", by C.R. Henry and B. Mutaftschiev 118 (1992) 473
Dalas, E., The crystallization of ferric phosphate on cellulose 113 (1991) 140
Dalderop, J.H.J., see Emmen 118 (1992) 477
Dang, Le Si, see Cibert 117 (1992) 424
Daniel, G., see Schmidt 117 (1992) 748
Darby, M.I., see Taylor 119 (1992) 221
Das, S.K., see Morris 117 (1992) 929
Dash, J.G., see Maruyama 118 (1992) 33
Dassonville, R., see Kern 116 (1992) 191
Datye, A., see Klem 111 (1991) 628
Davey, R.J., M.M. Harding and R.J. Rule, The microcrystalline nature of cubic, dendritic and granular salt 114 (1991) 7
David, J.P.R., see Claxton 111 (1991) 1080
Davies, A.G., J.E.F. Frost, D.A. Ritchie, D.C. Peacock, R. Newbury, E.H. Linfield, M. Pepper and G.A.C. Jone, The growth and physics of high mobility two-dimensional hole gases 111 (1991) 318
Davies, G.J., see Singh 120 (1992) 33
Davies, G.J., see Foord 120 (1992) 103
Davies, G.J., see Skevington 120 (1992) 328
Davies, G.J., P.J. Skevington, C.L. French and J.S. Foord, Selective area growth of III–V compound semiconductors by chemical beam epitaxy 120 (1992) 369
Davies, J.J., see Dhese 117 (1992) 91
Davies, J.J., see Nakano 117 (1992) 331
Davis, S.H., see Braun 112 (1991) 670
Davis, S.H., see Canright 114 (1991) 153
Däweritz, L., J. Griesche, R. Hey and J. Herzog, Dynamics and roughness spectrum of the GaAs(001) surface during the MBE process 111 (1991) 65
Däweritz, L., see Crook 111 (1991) 184
Däweritz, L., see Nötzel 115 (1991) 318
Dawsey, J.R., see Lane 120 (1992) 245
Dawson, M.D., see Hasenberg, 111 (1991) 388
De Croon, M.H.J.M., see Hageman 116 (1992) 169
De Haas, H., see Bolt 114 (1991) 141
De Lyon, T.J., N.I. Buchan, P.D. Kirchner, J.M. Woodall, D.T. McInturff, G.J. Scilla and F. Cardone, Use of CCl_4 and $CHCl_3$ in gas source molecular beam epitaxy for carbon doping of GaAs and $Ga_xIn_{1-x}P$ 111 (1991) 564
De Melo, O., see Bocelli 113 (1991) 663
De Orúe, M.A., see Vogel 117 (1992) 710
De Yoreo, J.J., L.J. Atherton and D.H. Roberts, Elimination of scattering centers from Cr:$LiCaAlF_6$ 113 (1991) 691

Debnath, A.K., see Muthe 118 (1992) 213
Decker, M.W., see Vanderah 118 (1992) 385
Del Alamo, J.A., see Bahl 111 (1991) 479
Deleporte, C., see Dubowski 117 (1992) 862
Delgado, M., see Quintero 114 (1991) 661
DeMattei, R.C., see Givargizov 112 (1991) 758
Demeester, P., see Coudenys 114 (1991) 314
Deparis, C. and J. Massies, Surface stoichiometry variation in alternate molecular beam epitaxy of GaAs 118 (1992) 414
Deppert, K., see Paulsson 111 (1991) 115
Deppert, K., S. Jeppesen, J. Jönsson, G. Paulsson and L. Samuelson, Effects of pressure and temperature on RD detected growth oscillations 120 (1992) 88
DePuydt, J.M., M.A. Haase, J. Qiu and H. Cheng, ZnSe-based laser diodes 117 (1992) 1078
Derby, J.J. and Q. Xiao, Some effects of crystal rotation on large-scale Czochralski oxide growth: analysis via a hydrodynamic thermal-capillary model 113 (1991) 575
Derebail, R., W.R. Wilcox and L.L. Regel, Directional solidification of InSb in a centrifuge 119 (1992) 98
Desai, Y.M., see Webb 111 (1991) 309
Deshayes, C., see Cibert 117 (1992) 424
Deutscher, C., see Schieber 115 (1991) 31
Devine, P., see Ashenford 117 (1992) 233
Deymier, P.A., see Shamsuzzoha 112 (1991) 635
Dhanaraj, G., T. Shripathi and H.L. Bhat, Growth and defect characterization of L-arginine phosphate monohydrate 113 (1991) 456
Dhar, A., see Bindal 112 (1991) 386
Dhese, K., J.E. Nicholls, J. Goodwin, W.E. Hagston, J.J. Davies, M.P. Halsall, B. Cockayne and P.J. Wright, Atmospheric pressure metalorganic chemical vapour deposition growth and optical studies of $ZnSe_{1-x}Te_x$ thin film alloys 117 (1992) 91
Diaz, P., see Bocchi 113 (1991) 540
Dieguez, E., see Chen 118 (1992) 101
Dietl, T., see Enichlmair 117 (1992) 844
Ding, J., see Ren 117 (1992) 510
Ding, J., see Xie 117 (1992) 1079
Ding Yong-qing, see Peng 115 (1991) 698
Ditzenberger, J.A., see Chiu 111 (1991) 274
Dobbyn, R.C., see Steiner 114 (1991) 707
Dodabalapur, A., see Chu 111 (1991) 26
Dodson, B.W., Stress accommodation in large-mismatch systems 111 (1991) 376
Doi, Y., see Iijima 112 (1991) 467
Dolginov, L.M., see Kazakov 116 (1992) 204
Dolzhenkova, E.F., see Babijchuk 116 (1992) 529
Domen, K., K. Sugiura, C. Anayama, M. Kondo, M. Suguwara, T. Tanahashi and K. Nakajima, Study on radiative efficiency in AlGaInP/GaInP double-heterostructures: influence of deep level in cladding layers 115 (1991) 529
Domen, K., see Sandhu 120 (1992) 296
Donegan, J.F., see Doran 117 (1992) 465
Doran, J.P., J.F. Donegan, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Thermal broadening of excitons in CdZnTe/ZnTe single quantum wells 117 (1992) 465
Dormans, G.J.M., G.J.B.M. Meekes and E.G.J. Staring, OMCVD of cobalt and cobalt silicide 114 (1991) 364
Dorn, R., see Protzmann 115 (1991) 248
Downey, S.W., see Feldman 118 (1992) 295
Dowsett, M.G., see Powell 111 (1991) 907
Doyle, S.E., A.R. Gerson, K.J. Roberts, J.N. Sherwood and T. Wroblewski, Probing the structure of solids in a liquid environment: a recent in-situ crystallisation experiment using high energy wavelength scanning X-ray diffraction 112 (1991) 302
Drake, G., see Chung 117 (1992) 1062
Dreyhsig, J., see Zeinert 117 (1992) 1016
Droopad, R., see Puechner 111 (1991) 43
Droopad, R., R.A. Puechner, K.Y. Choi, K.T. Shiralagi and G.N. Maracas, Molecular beam epitaxial growth and optical properties of strained rectangular and asymmetric triangular InGaAs quantum well structures 114 (1991) 327
Droopad, R., see Shiralagi 114 (1991) 337
Droopad, R., see Edwards 120 (1992) 78
Droopad, R., K.T. Shiralagi, R.A. Puechner, K.Y. Choi and G.N. Maracas, Low temperature GaAs grown by gas source molecular beam epitaxy 120 (1992) 200
Druilhe, R., see Marbeuf 117 (1992) 10
Drummond, T.J., see Sherwin 111 (1991) 605
Dubowski, J.J., A.P. Roth, E. Deleporte, G. Peter, Z.C. Feng and S. Perkowitz, Optical properties of $CdTe–Cd_{0.90}Mn_{0.10}Te$ multiple quantum well structures grown by pulsed laser evaporation and epitaxy 117 (1992) 862
Duffar, T., see Garandet 113 (1991) 587
Duffar, T., see Katty 118 (1992) 470
Duh, K.H.G., see Ho 111 (1991) 233
Dupret, F., see Kakimoto 114 (1991) 715
Durand, A., see Triboulet 117 (1992) 227
Durand, J., see Gómez Morales 116 (1992) 427
Durbin, S.M., see Han 111 (1991) 767
Durel, S., see Le Corre 120 (1992) 353
Durose, K., see Sang 113 (1991) 1
Durose, K., see Loginov 117 (1992) 259
Durose, K., see Alnajjar 117 (1992) 385
Durose, K., see Brown 117 (1992) 536
Durose, K., see Loginov 117 (1992) 682
Durose, K., see Simmons 117 (1992) 959
Dusserre, P., see Katty 118 (1992) 470

Dutta, P.K., see Narlikar 116 (1992) 37
Duval, W.M.B., see Batur 119 (1992) 371
Dvoretsky, S.A., see Sabinina 117 (1992) 238

Eaglesham, D.J., H.-J. Gossmann, M. Cerullo, L.N. Pfeiffer and K.W. West, Limited thickness epitaxy of semiconductors and Si MBE down to room temperature 111 (1991) 833
Eaglesham, D.J., see Headrick 111 (1991) 838
Eaves, L., see Henini 111 (1991) 1089
Ebbesen, T.W., see Tanigaki 114 (1991) 3
Ebe, H., A. Sawada, K. Maruyama, Y. Nishijima, K. Shinohara and H. Takigawa, Tilt growth of CdTe epilayers on sapphire substrates by MOCVD 115 (1991) 718
Ebe, H., see Tanaka 117 (1992) 24
Eberl, K., W. Wegscheider and G. Abstreiter, Group IV element (Si, Ge and α-Sn) superlattices – low temperature MBE 111 (1991) 882
Ebrahimpour, A., Jingwu Zhang and G.H. Nancollas, Dual constant composition method and its application to studies of phase transformation and crystallization of mixed phases 113 (1991) 83
Eckstein, J.N., see Webb 111 (1991) 309
Eckstein, J.N., I. Bozovic, D.G. Schlom and J.S. Harris, Jr., Growth of superconducting $Bi_2Sr_2Ca_{n-1}Cu_nO_x$ thin films by atomically layered epitaxy 111 (1991) 973
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Egawa, T., Y. Hayashi, T. Jimbo and M. Umeno, MOCVD-grown SQWs on Si with AlGaAs/AlGaP intermediate layers and/or thermal cycle annealing: application to room-temperature CW lasers 115 (1991) 524
Eglash, S.J., see Turner 111 (1991) 105
Eglash, S.J., H.K. Choi and G.W. Turner, MBE growth of GaInAsSb/AlGaAsSb double heterostructures for infrared diode lasers 111 (1991) 669
Eguchi, M., see Kakimoto 112 (1991) 819
Eidelman, N., W.E. Brown and J.L. Meyer, Selective inhibition of crystal growth on octacalcium phosphate and nonstoichiometric hydroxyapatite by pyrophosphate at physiological concentration 113 (1991) 643
Einav, Y., see Horowitz 119 (1992) 391
Ekawa, M., K. Yasuda, M. Okada, T. Ferid, A. Tanaka and M. Saji, Mechanism of arsenic incorporation in MOVPE growth of CdTe layers 117 (1992) 254
Elliott, R., see Yilmaz 118 (1992) 377
Elta, M.E., see Sherwin 111 (1991) 594
Elta, M.E., see Sherwin 111 (1991) 605
Eltazarov, B.T., see Butkhuzi 117 (1992) 1055
Emeis, N., see Heinecke 120 (1992) 140
Emel'chenko, G.A., see Masalov 119 (1992) 297
Emeleus, C.J., see Powell 111 (1991) 907
Emeny, M.T., L.K. Howard, K.P. Homewood, J.D. Lambkin and C.R. Whitehouse, A photoluminescence study of indium desorption from strained $Ga_{1-x}In_xAs/GaAs$ 111 (1991) 413
Emerson, A.B., see Feldman 118 (1992) 295
Emery, J.-Y., see Goldstein 120 (1992) 157
Emery, J.-Y., see Starck 120 (1992) 180
Emmen, J.H.P.M., S.K.J. Lenczowski, J.H.J. Dalderop and V.A.M. Brabers, Crystal growth and annealing experiments of the high T_c superconductor $Bi_2Sr_2CaCu_2O_{8+\delta}$ 118 (1992) 477
Endo, K., see Ishiai 115 (1991) 762
Endo, S., see Ando 117 (1992) 362
Endo, Y., see Takada 117 (1992) 44
Enichlmair, H., K. Kaltenegger, H. Krenn, G. Bauer, T. Dietl and J. Humenberger, Light-induced magnetization in $Hg_{1-x}Cd_xTe$ 117 (1992) 844
Era, K., see Minami 117 (1992) 565
Era, K., see Inoue 117 (1992) 738
Erland, J., see Pantke 117 (1992) 763
Ernst, F., see Chen 118 (1992) 452
Esin, V.O., see Tarabaev 114 (1991) 603
Etienne, P., J. Massies, S. Lequien, R. Cabanel and F. Petroff, Molecular beam epitaxial growth of Cr/Fe, Ag/Fe, Ag/Cr and Ag/Co superlattices on MgO (001) substrates 111 (1991) 1003
Etoh, H., see Miyao 111 (1991) 912
Exner, H.E., see Feijóo 113 (1991) 449
Ezaki, T., see Nishimura 117 (1992) 119

Faivre, G., see Caroli 118 (1992) 135
Fan, G.H., see Guan 117 (1992) 515
Fan, G.H., see Shen 117 (1992) 519
Fan, G.H., see Zhang 117 (1992) 523
Fan, X.W., see Guan 117 (1992) 515
Fan, X.W., see Shen 117 (1992) 519
Fan, X.W., see Zhang 117 (1992) 523
Fan, Y.D., see Tang 112 (1991) 407
Fang, Z.M., see Cao 113 (1991) 441
Farber, G.K., see Strong 119 (1992) 200
Farrell, H.H., see Tamargo 111 (1991) 741
Farrell, T., see Armstrong 120 (1992) 84
Farrell, T., J.V. Armstrong, T.B. Joyce, T.J. Bullough, P. Kightley and P.J. Goodhew, XeCl excimer laser assisted CBE growth of GaAs 120 (1992) 395
Farrow, L.A., see Turco-Sandroff 111 (1991) 762

Faschinger, W., P. Juza and H. Sitter, Observation of different reflected high-energy electron diffraction patterns during atomic layer epitaxy growth of CdTe epilayers 115 (1991) 692

Fashe, R., J.T. Zborowski, T.D. Golding, H.D. Shih, P.C. Chow, K. Matsuichi, B.C. Covington, A. Chi, J. Zheng and H.F. Schaake, MBE growth and characterization of $In_xGa_{1-x}Sb/InAs$ strained layer superlattices 111 (1991) 677

Faurie, J.P., R. Sporken, S. Sivananthan and M.D. Lange, New development on the control of homoepitaxial and heteroepitaxial growth of CdTe and HgCdTe by MBE 111 (1991) 698

Favennec, P.N., see L'Haridon 113 (1991) 39

Fawcett, P.N., B.A. Joyce, X. Zhang and D.W. Pashley, Interface structure of InAs grown on GaAs(001) surfaces by molecular beam epitaxy 116 (1992) 81

Fedorov, O.P., see Borisov 112 (1991) 463

Fedorov, V.A., V.A. Ganshin and Yu.N. Korkishko, Ion exchange in zinc selenide crystals: the role of lattice-misfit-induced stresses and dislocations 112 (1991) 781

Feeney, R.E., W.H. Fink, J. Hallett, K. Harrison, D.T. Osuga, J.P. Vesenka and Y. Yeh, Investigations of the differential affinity of antifreeze glycoprotein for single crystals of ice 113 (1991) 417

Feigelson, R.S., see Givargizov 112 (1991) 758

Feigelson, R.S., see Wilde 113 (1991) 337

Feijóo, D. and H.E. Exner, Surface curvature distributions of growing dendrite crystals 113 (1991) 449

Feil, D., see Boek 114 (1991) 389

Feldman, L.C., see Headrick 111 (1991) 838

Feldman, L.C., see Hong 111 (1991) 984

Feldman, R.D., see Doran 117 (1992) 465

Feldman, R.D., R.F. Austin, A. Sher, M.L. Schnoes, S.W. Downey, A.B. Emerson, T.D. Harris, R.C. Spitzer, G.J. Gualtieri and G.P. Schwartz, Antimony doping of ZnTe grown by molecular beam epitaxy 118 (1992) 295

Feng, Y., see Taylor 119 (1992) 221

Feng, Y.J., see Tang 112 (1991) 407

Feng, Z.C., see Dubowski 117 (1992) 862

Ferekides, C., see Chu 117 (1992) 1073

Ferid, T., see Ekawa 117 (1992) 254

Fernandez, R., RHEED oscillations of arsenic-controlled growth conditions to optimize MBE growth of III/V heterostructures 116 (1992) 98

Ferrara, M., see Lovergine 118 (1992) 304

Ferrari, C., see Bernardi 113 (1991) 53

Ferrari, C., see Bocchi 113 (1991) 540

Ferrater, C., A. Lousa, F. Badia, X. Alcobé and J.L. Morenza, Crystal structure of evaporated yttrium thin films 113 (1991) 181

Feuerbacher, B.F., see Ploog 111 (1991) 344

Feuillet, G., see Cibert 117 (1992) 424

Fewster, P.F., see Woodbridge 111 (1991) 339

Fikri, M.A., G. Labrosse and M. Betrouni, The melt phase hydrodynamics for the "stabilized" Bridgman procedure applied under centrifugation; preliminary analysis and numerical results 119 (1992) 41

Filipović-Vinceković, N., see Škrtić 114 (1991) 118

Fillard, J.P., see L'Haridon 113 (1991) 39

Fillard, J.P., see Triboulet 117 (1992) 227

Filz, Th., see Kolodziejczyk 117 (1992) 549

Fink, W.H., see Feeney 113 (1991) 417

Fiorani, D., see Leccabue 112 (1991) 644

Fischer, A., see Ploog 111 (1991) 344

Fischer, R.J., see Hong 111 (1991) 1052

Fischer, R.J., see Wang 111 (1991) 1057

Fischer, R.J., see Hong 111 (1991) 1071

Fisher, F., see Oude Hengel 114 (1991) 656

FitzGerald, E.T., C.L. French and J.S. Foord, Surface chemical studies of the influence of In and Al on the decomposition of TEG on GaAS(100) 120 (1992) 57

FitzGerald, E.T., see Foord 120 (1992) 103

Flemish, J.R., see Jones 120 (1992) 150

Fletcher, E.D., see Foxon 111 (1991) 1047

Floeder, W., see Tiwari 111 (1991) 730

Flores, M.L., see Vogel 117 (1992) 710

Florez, L.T., see Harbison 111 (1991) 978

Florez, L.T., see Aspnes 120 (1992) 71

Fluegel, B., see Koch 117 (1992) 592

Fluegel, B., see Masumoto 117 (1992) 732

Fluegel, B., see Sasaki 117 (1992) 768

Folkard, M.A., see Hartley 117 (1992) 166

Fons, P., see Kitabatake 111 (1991) 870

Fonstad, C.G., see Vlcek 111 (1991) 56

Fonstad, C.G., see Cunningham 111 (1991) 515

Fonstad, C.G., see McCann 114 (1991) 687

Foord, J.S., see Singh 120 (1992) 33

Foord, J.S., see FitzGerald 120 (1992) 57

Foord, J.S., see French 120 (1992) 63

Foord, J.S., N.K. Singh, E.T. FitzGerald, G.J. Davies and A.C. Jones, Applications of MBMS and surface spectroscopic techniques in the study of reaction mechanisms in CBE; investigations of the reactivity of tritertiarybutylgallium and triisobutylgallium as alternative precursors for epilayer growth 120 (1992) 103

Foord, J.S., see Davies 120 (1992) 369

Ford, W., see Young 118 (1992) 193

Foris, C.M., see Cheng 112 (1991) 309

Foster, D.F., see Bell 117 (1992) 58

Fox, B.A., see Jansen 112 (1991) 316

Foxon, C.T., see Zhang 111 (1991) 93
Foxon, C.T., E.M. Gibson, J. Zhang, B.A. Joyce and D.E. Lacklison, A comparison of MBE and MOMBE/CBE growth mechanisms using modulated beam mass spectrometry and RHEED 111 (1991) 539
Foxon, C.T., P. Blood, E.D. Fletcher, D. Hilton, P.J. Hulyer and M. Vening, Substrate temperature dependence of SQW alloy and superlattice lasers grown by MBE using As_2 111 (1991) 1047
Foxon, C.T., see Joyce 115 (1991) 338
Foxon, C.T., see Lacklison 120 (1992) 50
Francesio, L., see Genova 120 (1992) 333
Franciosi, A., see Vanzetti 117 (1992) 573
Francis, J.T., S.W. Benson and T.T. Tsotsis, Kinetics of the very low pressure pyrolysis of trimethylgallium and arsine 112 (1991) 474
Frank, R.M., see Cuisinier 116 (1992) 314
Franzosi, P., see Bernardi 113 (1991) 53
Franzosi, P., see Bocchi 113 (1991) 540
Fredriksz, C.W., see Gravesteijn 111 (1991) 916
Frei, M.R., see Caneau 114 (1991) 481
French, C.L., see FitzGerald 120 (1992) 57
French, C.L., and J.S. Foord, Reaction kinetics for the CBE growth of GaAs from triethylgallium; computer modelling studies incorporating recent surface spectroscopic data 120 (1992) 63
French, C.L., see Davies 120 (1992) 369
Frey, H., see Helmrich 112 (1991) 824
Fricke, Ch., see Hoffmann 117 (1992) 640
Fricke, Ch., U. Neukirch, R. Heitz, A. Hoffmann and I. Broser, Recombination kinetics of CdS : In 117 (1992) 783
Fricke, Ch., see Broser 117 (1992) 788
Frigeri, C., see Licci 112 (1991) 606
Frijlink, P.M., J.L. Nicolas, H.P.M.M. Ambrosius, R.W.M. Linders, C. Waucquez and J.M. Marchal, The radial flow planetary reactor: low pressure versus atmospheric pressure MOVPE 115 (1991) 203
Fripp, A., see Steiner 114 (1991) 707
Frost, J.E.F., see Ritchie 111 (1991) 300
Frost, J.E.F., D.A. Ritchie and G.A.C. Jones, The growth of shallow high mobility two-dimensional electron gas structures 111 (1991) 305
Frost, J.E.F., see Davies 111 (1991) 318
Frost, J.E.F., D.A. Ritchie and G.A.C. Jones, The growth of shallow high mobility two-dimensional electron gas structures (E) 113 (1991) 726
Fuchs, F., see Ralston 111 (1991) 989
Fujii, S., see Terada 117 (1992) 54
Fujii, T., see Sandhu 111 (1991) 559
Fujii, T., see Ueda 115 (1991) 375
Fujii, T., see Ando 115 (1991) 464
Fujii, T., see Nakata 115 (1991) 504
Fujii, T., see Yoshida 117 (1992) 75
Fujii, T., see Ando 120 (1992) 228
Fujii, T., see Sandhu 120 (1992) 296
Fujii, Y., see Suzuki 115 (1991) 623
Fujii, Y., see Suemune 117 (1992) 1068
Fujii, Y., see O'Donnell 117 (1992) 1077
Fujimoto, I., see Shigeta 111 (1991) 284
Fujimoto, M., see Yao 111 (1991) 823
Fujimoto, M., see Katayama 115 (1991) 289
Fujimoto, M., see Suemune 117 (1992) 1068
Fujimoto, Y., see Okuyama 114 (1991) 107
Fujimura, N., see Nagai 115 (1991) 769
Fujimura, N., see Goto 115 (1991) 816
Fujimura, N., T. Ito and M. Kakinoki, Heteroepitaxy of $LiNbO_3$ and $LiNb_3O_8$ thin films on C-cut sapphire 115 (1991) 821
Fujisaki, Y., see Ohishi 111 (1991) 792
Fujisaki, Y., see Ohishi 117 (1992) 125
Fujishiro, H., see Sakurai 112 (1991) 153
Fujita, K., see Katahama 115 (1991) 141
Fujita, Sg., see Wu 111 (1991) 757
Fujita, Sg., see Fujita 115 (1991) 269
Fujita, Sg., see Wu 115 (1991) 664
Fujita, Sg., see Fujita 117 (1992) 67
Fujita, Sg., see Ichino 117 (1992) 527
Fujita, Sg., see Funato 117 (1992) 543
Fujita, Sg., see Ichimura 117 (1992) 689
Fujita, Sz., see Wu 111 (1991) 757
Fujita, Sz., S. Hirata and Sg. Fujita, Investigation of photo-induced surface reactions by mass analysis in OMVPE of II–VI semiconductors 115 (1991) 269
Fujita, Sz., see Wu 115 (1991) 664
Fujita, Sz. and Sg. Fujita, Photo-assisted metalorganic vapor phase epitaxial growth of wide-gap II–VI semiconductors 117 (1992) 67
Fujita, Sz., see Ichino 117 (1992) 527
Fujita, Sz., see Funato 117 (1992) 543
Fujita, Sz., see Ichimura 117 (1992) 689
Fujita, Y., see Terada 117 (1992) 54
Fujiwara, H., see Gotoh 117 (1992) 85
Fujiyama, A., see Terashima 115 (1991) 745
Fujiyasu, H., see Tatsuoka 117 (1992) 554
Fujiyasu, H., see Suzuki 117 (1992) 881
Fujiyasu, H., Y. Takeuchi, K. Hikida, K. Ishino and A. Ishida, Mn doped ZnS and ZnS–CdS superlattice double insulating electroluminescent devices made by hot wall epitaxy 117 (1992) 1026
Fukada, T., see Matsumura 111 (1991) 787
Fukada, T., see Matsumura 115 (1991) 279
Fukamachi, T., see Yamada 111 (1991) 584
Fukatsu, S.J., S. Kubo, Y. Shiraki and R. Ito, Redistribution of delta-doped Sb in Si 111 (1991) 843
Fukuda, H., see Akinaga 115 (1991) 765

Fukuda, T., see Machida 112 (1991) 835
Fukuda, T., see Miyazaki 113 (1991) 227
Fukuda, T., see Kan 119 (1992) 215
Fukuda, T., see Kawasaki 119 (1992) 317
Fukui, T. and H. Saito, Step-flow growth and fractional-layer superlattices on GaAs vicinal surfaces by MOCVD 115 (1991) 61
Fukui, T., see Ando 115 (1991) 69
Fukui, T., see Kasu 115 (1991) 406
Fukuoka, M., see Ueda 112 (1991) 507
Fukuoka, M., see Ueda 113 (1991) 69
Fukushima, Y., see Matsumura 111 (1991) 787
Fullowan, T.R., see Abernathy 120 (1992) 234
Funato, K., see Nakamura 115 (1991) 474
Funato, M., M. Ishii, P.A. Murawala, O. Tsuji, Sz. Fujita and Sg. Fujita, Metalorganic vapor phase epitaxial growth and characterization of ZnSe–GaAs multilayered structures 117 (1992) 543
Furdyna, J.K., see Samarth 111 (1991) 816
Füredi-Milhofer, H., see Škrtić 114 (1991) 118
Furuhata, N. and A. Okamoto, Selective growth mechanism of GaAs in metalorganic molecular beam epitaxy 112 (1991) 1
Furukawa, A., see Koide 115 (1991) 365
Furukawa, K., see Suzuki 115 (1991) 623
Furukawa, S., see Minemura 114 (1991) 307
Furukawa, S., see Tsuda 115 (1991) 556
Furukawa, T., see Nitta 115 (1991) 515
Furukawa, Y., see Noda 115 (1991) 802
Furukawa, Y., see Oguri 117 (1992) 116
Furukawa, Y., see Isshiki 117 (1992) 410
Furumiya, M., see Itoh 117 (1992) 835
Furuno, M., see Kircher 115 (1991) 439
Futami, H., see Kasuga 115 (1991) 711
Fuwa, K., see Shigetomi 111 (1991) 110

Gaborit, F., see Lambert 111 (1991) 495
Gaborit, F., see Goldstein 120 (1992) 157
Gaborit, F., see Pagnod-Rossiaux 120 (1992) 317
Gafni, G., see Azoulay 116 (1992) 515
Gafni, G., see Azoulay 117 (1992) 276
Gagnon, R., M. Oussena and M. Aubin, Growth of large $YBa_2Cu_3O_{7-x}$ crystals in the presence of a temperature gradient 114 (1991) 186
Gailhanou, M., see Houdré 111 (1991) 456
Gailhanou, M., see Rudra 120 (1992) 338
Galambos, L., see Wilde 114 (1991) 500
Gall, P., see L'Haridon 113 (1991) 39
Gall, P., see Triboulet 117 (1992) 227
Galun, E., G. Hodes, M. Peisach, E. Muranevich and R. Tenne, Shallow donor state removal via photoelectrochemical etching in Cd(Se,Te) 117 (1992) 666
Gambino, R.J., see Munekata 111 (1991) 1011
Gamelin, J., see Hong 111 (1991) 1052
Gamelin, J., see Hong 111 (1991) 1071
Gan, Fuxi, see Cui 111 (1991) 811
Gan, Fuxi, see Cui 117 (1992) 505
Gandhi, D.P., see Muthe 118 (1992) 213
Ganeau, M., see L'Haridon 113 (1991) 39
Ganesha, R., D. Arivuoli and P. Ramasamy, Observations made during the growth of trihalides of group Vb elements 119 (1992) 303
Ganière, J.-D., see Houdré 111 (1991) 456
Ganser, P., see Köhler 111 (1991) 295
Ganshin, V.A., see Fedorov 112 (1991) 781
Gao, D., A.W. Stevenson, S.W. Wilkins and G.N. Pain, Anisotropic microstructure in $Cd_{1-x}Mn_xTe/Cd_{1-y}Mn_yTe$ superlattices studied by X-ray diffraction 112 (1991) 487
Gao, Q.Z., J. Mita, T. Tsuruoka, M. Kobayashi and K. Kawamura, High luminance white EL devices using SrS:Ce,Eu,K films deposited in a H_2 atmosphere 117 (1992) 983
Gao, Y., see Kazmierski 116 (1992) 75
Gao, Y., see Benchimol 120 (1992) 189
Gaponenko, S., see Uhrig 117 (1992) 598
Garabedian, P., see Pagnod-Rossiaux 120 (1992) 317
Garandet, J.P., A. Rouzaud, T. Duffar and D. Camel, Comparison between order of magnitude and numerical estimates of the solute boundary layer in an idealized horizontal Bridgman configuration 113 (1991) 587
Garandet, J.P., On the problem of radial segregation in an idealized horizontal Bridgman configuration: scaling and numerical approaches 114 (1991) 593
Garbato, L., A. Geddo-Lehmann and F. Ledda, Growth and structural properties of quaternary copper thiostannates 114 (1991) 299
García-Ruiz, J.M. and F. Otálora, Concentration distribution around a crystal growing under diffusional control; a computer simulation 118 (1992) 160
García-Ybarra, P.L., see Castillo 116 (1992) 105
Garcia, J.C., P. Maurel, P. Bove, J.P. Hirtz and A. Barski, Chemical beam epitaxy growth of $GaAs/Ga_{0.5}In_{0.5}P$ heterostructures: growth kinetics, electrical and optical properties 111 (1991) 578
Gardeniers, J.G.E. and L.J. Giling, Vapour growth of silicon: growth anisotropy and adsorption 115 (1991) 542
Garnier, J. and L.M. Cottineau, Questions raised about material processing in a centrifuge: lessons derived from the LCPC's experience 119 (1992) 66
Gastaldi, L., see Genova 120 (1992) 333
Gates, S.M., Kinetics and mechanisms of surface reactions in epitaxial growth of Si from SiH_4 and Si_2H_6 120 (1992) 269

Gauch, M. and G. Quentel, Morphological instability of a vapour-grown crystal: in situ study of (0001) cadmium face 118 (1992) 243
Gauthier, R., see Chibani 113 (1991) 681
Gazit, D., see Horowitz 119 (1992) 391
Ge, Peiwen, see Huo 114 (1991) 486
Ge, Y.L., see Jin 116 (1992) 524
Gebhardt, W., see Bauer 117 (1992) 297
Gebhardt, W., see Wagner 117 (1992) 303
Geddo-Lehmann, A., see Garbato 114 (1991) 299
Géminard, J.C., J. Bechhoefer and P. Oswald, On wetting an apparently asymmetric kinetics in free growth 114 (1991) 640
Gencer, F. and J.S. Abell, The growth of $YBa_2Cu_3O_{7-\delta}$ single crystals with the aid of a NaCl–KCl flux 112 (1991) 337
Genova, F., A. Antolini, L. Francesio, L. Gastaldi, C. Lamberti, C. Papuzza and C. Rigo, Influence of growth parameters on the interface abruptness in CBE-grown InGaAs/InP QWs and SLs 120 (1992) 333
Gentile, P., see Ulmer 111 (1991) 711
Georgalis, Y., A. Zouni and W. Saenger, Dynamics of protein precrystallization cluster formation 118 (1992) 360
George, T., see Soga 115 (1991) 418
Georgobiani, A.N., see Butkhuzi 117 (1992) 366
Georgobiani, A.N., see Butkhuzi 117 (1992) 1055
Gérard, J.M., see Moisson 111 (1991) 141
Gérard, J.M., J.Y. Marzin and B. Jusserand, Modulated molecular beam epitaxy: a successful route toward high quality highly strained heterostructure 111 (1991) 205
Gerber, D.S., see Puechner 111 (1991) 43
Germanenko, A.V., G.M. Min'kov and O.E. Rut, Acceptor states in the dilute magnetic semiconductor p-HgMnTe with $E_g > 0$ under uniaxial stress 117 (1992) 850
Gershoni, D., see Nagle 111 (1991) 264
Gerson, A.R., see Doyle 112 (1991) 302
Ges, A.P., see Barilo 119 (1992) 403
Geva, M., see Asom 111 (1991) 246
Geva, M., see Asom 111 (1991) 260
Ghandhi, S.K., see Ayers 113 (1991) 430
Ghiordanescu, V., see Voda 119 (1992) 339
Gibbings, C.J., see Capano 116 (1992) 260
Gibis, R., see Künzel 111 (1991) 461
Gibson, E.M., see Zhang 111 (1991) 93
Gibson, E.M., see Foxon 111 (1991) 539
Gibson, E.M., see Lacklison 120 (1992) 50
Giling, L.J., see Van Enckevort 113 (1991) 295
Giling, L.J., see Gardeniers 115 (1991) 542
Giling, L.J., see Hageman 116 (1992) 169
Gill, D.M., see Uppal 111 (1991) 623
Gill, S.S., see Lane 120 (1992) 245
Gill, W.N., see Ananth 118 (1992) 60
Gille, P., F.M. Kiessling and M. Burkert, A new approach to crystal growth of $Hg_{1-x}Cd_xTe$ by the travelling heater method (THM) 114 (1991) 77
Ginde, R.M. and A.S. Myerson, Cluster size estimation in binary supersaturated solutions 116 (1992) 41
Giriat, W., see Homyonfer 117 (1992) 1080
Giugni, S., T.L. Tansley and G.J. Griffiths, Graded compositional heterostructures in the GaAs/$Al_xGa_{1-x}As$ system 111 (1991) 50
Givargizov, E.I., M.O. Kliya, V.R. Melik-Adamyan, A.I. Grebenko, R.C. DeMattei and R.S. Feigelson, Artificial epitaxy (graphoepitaxy) of proteins 112 (1991) 758
Glicksman, M.E., see Rubinstein 112 (1991) 84
Glicksman, M.E., see Rubinstein 112 (1991) 97
Glicksman, M.E., see Singh 118 (1992) 78
Glicksman, M.E., see Sokolowski 119 (1992) 126
Göbel, E.O., see Protzmann 115 (1991) 248
Göbel, E.O., see Yakovlev 117 (1992) 854
Godlewski, M. and K. Świątek, Excitonic processes in II–VI compounds doped with transition metal and rare earth impurities 117 (1992) 634
Goede, O., see Heimbrodt 117 (1992) 859
Goede, O., W. Heimbrodt, Th. Köpp, H.-E. Gumlich and B. Lunn, Magneto-optical anisotropy of CdTe/(Cd,Mn)Te quantum-well structures due to lattice-misfit induced strain 117 (1992) 886
Golding, T.D., see Fashe 111 (1991) 677
Goldstein, L., see Lambert 111 (1991) 495
Goldstein, L., C. Starck, J.-Y. Emery, F. Gaborit, D. Bonnevie, F. Poingt and M. Lambert, Optoelectronic devices by gas source molecular beam epitaxy 120 (1992) 157
Goldstein, L., see Starck 120 (1992) 180
Gómez Morales, J., R. Rodríguez Clemente, J. Durand and L. Cot, Solubility of berlinite in H_2SO_4–HCl mixtures under hydrothermal conditions 116 (1992) 427
Gomyo, A., see Suzuki 111 (1991) 353
Gonda, S., see Takeyasu 111 (1991) 502
Gonda, S., see Kaneko 111 (1991) 638
Gonda, S., see Okuno 115 (1991) 236
Gonda, S., see Kaneko 120 (1992) 39
Gonda, S., see Asahi 120 (1992) 252
González, L., see González 111 (1991) 120
González, Y., L. González and F. Briones, In-situ monitoring of antiphase domain evolution during atomic layer MBE (ALMBE) and MBE growth of GaAs/Si(001) by reflectance difference 111 (1991) 120
González-Mañas, M. and M.A. Caballero, Morphogenetical characterization of the

Brazil twin appearing in $-X$ and Z' growth sectors of synthetic quartz crystals by X-ray topography 113 (1991) 669
Goodhew, P.J., see Kightley 112 (1991) 359
Goodhew, P.J., see Armstrong 120 (1992) 84
Goodhew, P.J., see Joyce 120 (1992) 206
Goodhew, P.J., see Farrell 120 (1992) 395
Goodnick, S.M., see Yoo 111 (1991) 1095
Goodwin, J., see Dhese 117 (1992) 91
Goodwin, J., see Jackson 117 (1992) 867
Goossen, K., see Cunningham 111 (1991) 515
Gordon-Smith, D., see Capano 116 (1992) 260
Gospodinov, M., see Sveshtarov 113 (1991) 186
Gospodinov, M., see Sveshtarov 118 (1992) 439
Gossard, A.C., see Petroff 111 (1991) 360
Gossard, A.C., see Chalmers 111 (1991) 647
Gossmann, H.-J., see Eaglesham 111 (1991) 833
Goto, S., N. Fujimura, T. Nishihara and T. Ito, Heteroepitaxy of zinc oxide thin films, considering non-epitaxial preferential orientation 115 (1991) 816
Goto, S., see Isu 120 (1992) 45
Goto, S., Y. Morishita, Y. Nomura, Y. Katayama and T. Isu, Hillock formation observed in MOMBE of InGaAs grown on a patterned GaAs substrate 120 (1992) 382
Goto, T., see Iijima 112 (1991) 467
Gotoh, H., see Nagao 111 (1991) 511
Gotoh, H., see Nagao 111 (1991) 521
Gotoh, J., H. Fujiwara, H. Shirai, J. Hanna and I. Shimizu, Low-temperature growth of ZnSe-based pseudomorphic structures by hydrogen-radical-enhanced chemical vapor deposition 117 (1992) 85
Gottlieb, M., see Singh 118 (1992) 78
Gourdon, C., see Chamarro 117 (1992) 614
Grabmaier, B.C., see Trauth 112 (1991) 451
Granger, R., see Bagot 117 (1992) 189
Granger, R. and C.M. Pelletier, Electron mobility evaluation in $Hg_{1-x}Cd_xTe$ and $Hg_{1-x}Zn_xTe$ with two-optical-mode dispersion 117 (1992) 203
Granger, R., see Rolland 117 (1992) 208
Granger, R., see Benhlal 117 (1992) 281
Grant, M., see Weeks 112 (1991) 244
Grasza, K. and U. Zuzga-Grasza, Temperature field computations in $Pb_{1-x}Sn_xTe$ crystal grown by inverted Bridgman method 116 (1992) 139
Grattepain, C., see Bassani 117 (1992) 391
Gravesteijn, D.J., T. Mishima, C.W. Fredriksz, G.F.A. van de Walle and R.A. van den Heuvel, Transport properties of p-Si/ SiGe single-modulation-doped heterostructures grown by MBE 111 (1991) 916
Gravesteijn, D.J., see Theunissen 118 (1992) 125
Gray, R.T., see Banan 113 (1991) 557
Grebenko, A.I., see Givargizov 112 (1991) 758
Greedan, J.E., see Xue 113 (1991) 371
Greef, R., see Berlouis 117 (1992) 918
Green, M.A., see Healy 112 (1991) 287
Greene, J.E., see Kitabatake 111 (1991) 870
Gregory, S., see Aspnes 120 (1992) 71
Gregory, T.J., see Heimbrodt 117 (1992) 859
Gregory, T.J., see Jackson 117 (1992) 867
Gresslehner, K.H., see Lang 117 (1992) 954
Griesche, J., see Däweritz 111 (1991) 65
Griffiths, G.J., see Giugni 111 (1991) 50
Grillo, D.C., see Xie 117 (1992) 1079
Grima, P., M. Quintero and J.C. Woolley, $T(z)$ diagrams and lattice parameter values for the $Hg_{2x}(CuIn)_yMn_{2z}Te_2$ and $Hg_{2x}(AgIn)_yMn_{2z}Te_2$ systems 119 (1992) 381
Grimes, R.T., see Stanley 111 (1991) 14
Grote, N., see Künzel 111 (1991) 461
Grundmann, M., A. Krost and D. Bimberg, Antiphase-domain-free InP on Si(001): optimization of MOCVD process 115 (1991) 150
Gruzintsev, A.N., V.T. Volkov and A.N. Pronin, Investigation of luminescence centers of unactivated CaS films 117 (1992) 975
Gryaznov, V.G., see Trusov 114 (1991) 133
Gualtieri, G.J., see Feldman 118 (1992) 295
Guan, Q.C., see Wang 116 (1992) 27
Guan, Z.P., J.H. Zhang, G.H. Fan and X.W. Fan, Excitonic transition of (ZnSe–ZnS)/CaF_2 strained-layer superlattices under lower excitation 117 (1992) 515
Gueissaz, F., see Houdré 111 (1991) 456
Gueissaz, F., R. Houdré and M. Ilegems, High electron density and mobility in single and double planar doped InGaAs/InAlAs heterojunctions on InP 111 (1991) 470
Guerrero, E., see Quintero 114 (1991) 661
Guha, S., see Chen 111 (1991) 424
Guha, S., K.C. Rajkumar and A. Madhukar, The nature and control of morphology and the formation of defects in InGaAs epilayers and InAs/GaAs superlattices grown via MBE on GaAs(100) 111 (1991) 434
Guha, S., see Kapre 111 (1991) 1110
Guimarães, F.E.G., see Heuken 117 (1992) 336
Guimarães, F.E.G., J. Söllner, K. Marquardt, M. Heuken and K. Heime, Optical investigations and optimization of ZnSe/ZnS multi-quantum wells grown by MOVPE 117 (1992) 1075
Gumlich, H.-E., see Waldmann 117 (1992) 715
Gumlich, H.-E., see Hommel 117 (1992) 721
Gumlich, H.-E., Heimbrodt 117 (1992) 859
Gumlich, H.-E., see Goede 117 (1992) 886
Gumlich, H.-E., see Zeinert 117 (1992) 1016
Gunshor, R.L., see Qiu 111 (1991) 747

Gunshor, R.L., see Han 111 (1991) 767
Gunshor, R.L., see Li 111 (1991) 1038
Gunshor, R.L., M. Kobayashi, N. Otsuka and A.V. Nurmikko, Properties of II–VI/III–V heterovalent interfaces 115 (1991) 652
Gunshor, R.L., see Nurmikko 117 (1992) 432
Gunshor, R.L., see Xie 117 (1992) 1079
Guo, D.F., see Liu 114 (1991) 700
Guo Xibin, see Li 118 (1992) 371
Guo, Y.D., see Chen 118 (1992) 109
Gupta, M.K., see Narlikar 116 (1992) 37
Gupta, M.K., see Muthe 118 (1992) 213
Gupta, S.K., see Muthe 118 (1992) 213
Gurestskii, S.A., see Barilo 119 (1992) 403
Guseva, M.B., see Shibaev 119 (1992) 399
Gutakovsky, A.K., see Sabinina 117 (1992) 238
Gutowski, J., see Kudlek 117 (1992) 290
Gutowski, J., see Kudlek 117 (1992) 309
Gutowski, J., see Schmolke 117 (1992) 650

Haase, M.A., see DePuydt 117 (1992) 1078
Haddad, G.I., see Sherwin 111 (1991) 594
Haddad, G.I., see Sherwin 111 (1991) 605
Haddad, G.I., see Munns 120 (1992) 184
Hafich, M.J., H.Y. Lee, P. Silvestre and G.Y. Robinson, GSMBE growth of GaAs at low AsH_3 cracking temperatures 111 (1991) 507
Hafich, M.J., see Lee 111 (1991) 525
Hageman, P.R., M.H.J.M. de Croon, J.N.H. Reek and L.J. Giling, Pressure and temperature dependence of silicon doping of GaAs using Si_2H_6 in metalorganic chemical vapour deposition 116 (1992) 169
Hagerott, M., see Han 111 (1991) 767
Hagihara, S., see Miyazaki 113 (1991) 227
Hagino, M., see Nomura 111 (1991) 61
Hagston, W.E., see Dhese 117 (1992) 91
Hagston, W.E., see Jackson 117 (1992) 867
Hails, J.E., see Bell 117 (1992) 58
Hakkarainen, T., see Tappura 112 (1991) 27
Hakkarainen, T., see Riesz 114 (1991) 127
Hakkarainen, T., see Tappura 120 (1992) 145
Hakkarainen, T., see Zhang 120 (1992) 172
Halden, E., see Müller 117 (1992) 948
Halfpenny, P.J., L. O'Neill, J.N. Sherwood, G.S. Simpson, A. Yokotani, A. Miyamoto, T. Sasaki and S. Nakai, X-ray topographic study of flux grown KTP crystals 113 (1991) 722
Hall, E.L., see Ho 111 (1991) 233
Hall, R.S., see Astles 117 (1992) 213
Hallett, J., see Feeney 113 (1991) 417
Halliwell, M.A.G., see Capano 116 (1992) 260
Halliwell, M.A.G., see Skevington 120 (1992) 328
Halsall, M.P., see Dhese 117 (1992) 91
Hamada, T., see Takei 115 (1991) 309
Hamakawa, Y., see Hyun 117 (1992) 587
Hamakawa, Y., see Sohn 117 (1992) 907
Hamakawa, Y., see Noma 117 (1992) 1030
Hamilton, A., see Ritchie 111 (1991) 300
Hamm, R.A., see Panish 112 (1991) 343
Hammons, B.E., see Tsao 111 (1991) 125
Hamza, S.M., Crystal growth of calcium fluoride in the presence of some metal ions 113 (1991) 637
Han, J., S.M. Durbin, R.L. Gunshor, M. Kobayashi, D.R. Menke, N. Pelekanos, M. Hagerott, A.V. Nurmikko, Y. Nakamura and N. Otsuka, Quantum wells with zincblende MnTe barriers 111 (1991) 767
Han, S.C., see Schieber 115 (1991) 31
Hanada, T., see Kawai 112 (1991) 745
Hanna, J., see Gotoh 117 (1992) 85
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Hanssen, L.M., see Snail 112 (1991) 651
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Hansson, P.O., see Chen 118 (1992) 452
Hara, K., see Kawai 115 (1991) 216
Hara, K., see Otoma 115 (1991) 807
Harada, H., see Konishi 117 (1992) 939
Harada, K., see Hashimoto 111 (1991) 393
Harada, T., M. Asano and Y. Mizutani, Epitaxial growth of Ag deposited on air-cleaved MgO(100) surface by molecular beam deposition 116 (1992) 243
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Harbison, J.P., see Aspnes 120 (1992) 71
Harding, M.M., see Davey 114 (1991) 7
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Hariu, T., see Takei 115 (1991) 309
Hariu, T., see Yamauchi 115 (1991) 660
Harmand, J.C., see Inoue 111 (1991) 313
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$Al_{0.33}Ga_{0.67}As$ with Sn, Si and Be: a comparative study 111 (1991) 239
Harris, Jr., J.S., see Lee 111 (1991) 131
Harris, Jr., J.S., see Pao 111 (1991) 489
Harris, Jr., J.S., see Eckstein 111 (1991) 973
Harris, K.A., see Yanka 111 (1991) 715
Harris, T.D., see Chand 111 (1991) 20
Harris, T.D., see Feldman 118 (1992) 295
Harrison, K., see Feeney 113 (1991) 417
Hårsta, A. and J.-O. Carlsson, Thermodynamic modeling of MOCVD of $Bi_2Sr_2CaCu_2O_{8+x}$: influence of metal and oxygen source 114 (1991) 507
Hart, L., see Capano 116 (1992) 260
Hartford, Jr., E.H., see Norton 113 (1991) 716
Hartley, R.H., M.A. Folkard, D. Carr, P.J. Orders, D. Rees, I.K. Varga, V. Kumar, G. Shen, T.A. Steele, H. Buskes and J.B. Lee, Ellipsometry: a technique for real time monitoring and analysis of MBE-grown CdHgTe and CdTe/HgTe superlattices 117 (1992) 166
Hartman, P., see Van der Voort 112 (1991) 445
Hartman, P., Equality of the structural morphologies of ammonium nitrate (III) and barite, $BaSO_4$ 114 (1991) 497
Hase, T., see Kita 115 (1991) 752
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Hasegawa, S., M. Sato, K. Maehashi, H. Asahi and H. Nakashima, Formation of quantum well wire-like structures by MBE growth of AlGaAs/GaAs superlattices on GaAs (110) surfaces 111 (1991) 371
Hasegawa, Y., see Ikeda 115 (1991) 211
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Hashimoto, M., see Tomita 115 (1991) 299
Hashimoto, M., see Koide 115 (1991) 639
Hashimoto, S., see Schowalter 111 (1991) 948
Hashimoto, Y., K. Hirakawa, K. Harada and T. Ikoma, Strain induced change in band offsets at pseudomorphically grown InAs/GaAs heterointerfaces characterized by X-ray photoelectron spectroscopy 111 (1991) 393
Hasnain, G., see Hong 111 (1991) 1052
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Hata, M., see Isu 111 (1991) 210
Hata, M., see Watanabe 111 (1991) 554
Hata, M., T. Isu, A. Watanabe, Y. Kajikawa and Y. Katayama, Surface diffusion and sticking coefficient of adatoms to atomic steps during molecular beam epitaxy growth 114 (1991) 203
Hata, M., see Watanabe 115 (1991) 371
Hata, M., see Isu 115 (1991) 423
Hata, M., see Isu 120 (1992) 45
Hatakoshi, G., see Nishikawa 112 (1991) 628
Hatakoshi, G., see Suzuki 115 (1991) 498
Hatano, A., T. Izumiya and Y. Ohba, Magnesium doping using an adduct of trimethylaluminum and dimethylmagnesium in metalorganic chemical vapor deposition 115 (1991) 455
Hatano, K., see Kumazaki 117 (1992) 285
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Haugstad, G., see Vanzetti 117 (1992) 573
Hayafuji, N., see Kadoiwa 115 (1991) 128
Hayakawa, Y., see Ozawa 115 (1991) 728
Hayashi, H., see Yoshida 115 (1991) 533
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Hayashi, T., see Kitamura 116 (1992) 327
Hayashi, T., see Misawa 117 (1992) 617
Hayashi, Y., see Egawa 115 (1991) 524
Hayes, T., see Asom 111 (1991) 260
He, Li, see Li 111 (1991) 736
He, Li, see Li 119 (1992) 322
He Youping, Su Genbo, Pan Feng, Wu Bochang and Jang Rihong, Growth of N-(4-nitrophenyl)-(L)-prolinol (NPP) crystal in organic solvents and its characterization 113 (1991) 157
He Youping, Su Genbo, Pan Feng and Jang Rihong, Growth of beryllium sulfate tetrahydrate (BST) crystal in hydrate solution 113 (1991) 161
He Youping, Su Genbo, Wu Bochang and Jang Rihong, Growth and characteristics of 5-nitrouracil crystal 119 (1992) 393
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Healy, S.A., T.L. Young and M.A. Green, Low-temperature growth of silicon on $Si_{1-x}Ga_x$ by liquid phase epitaxy 112 (1991) 287
Heatherly, L., see Specht 114 (1991) 38
Hegarty, J., see Doran 117 (1992) 465

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Heimbrodt, W., see Goede 117 (1992) 886
Heime, K., see Heuken 117 (1992) 336
Heime, K., see Guimarães 117 (1992) 1075
Heinecke, H., B. Baur, R. Höger, A. Miklis and R. Treichler, Growth of GaInAs and GaInAsP lattice matched by InP by metalorganic MBE 111 (1991) 599
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Heinecke, H., see Beer 120 (1992) 312
Heinecke, H., B. Baur, R. Schimpe, R. Matz, C. Cremer, R. Höger and A. Miklis, Selective area epitaxy of InP/GaInAsP heterostructures by MOMBE 120 (1992) 376
Heitz, R., see Hoffmann 117 (1992) 640
Heitz, R., see Thurian 117 (1992) 727
Heitz, R., see Fricke 117 (1992) 783
Heitz, R., see Broser 117 (1992) 788
Helak, Z., R. Korbutowicz, M. Panek, R. Paszkiewicz and M. Tłaczała, Ga–As–Bi phase equilibrium study by LPE for thin solutions 115 (1991) 294
Heller, C., see Ullrich 117 (1992) 902
Hellman, E.S., see Norton 113 (1991) 716
Helmrich, R., H. Dabringhaus, H. Frey and H.J. Meyer, Investigation of condensation and evaporation of alkali halide crystals by molecular beam methods. XIII. Development of two-dimensional islands on the (100) surface of KCl 112 (1991) 824
Henderson, B., see Parbrook 117 (1992) 492
Henderson, B., see O'Donnell 117 (1992) 497
Henderson, B., see Trager-Cowan 117 (1992) 532
Henderson, T.S., see Beam III 116 (1992) 436
Hendriks, H.T., see Hoke 111 (1991) 269
Henige, J.A., see Metzger 111 (1991) 445
Henini, M., C.R.H. White, P.E. Simmonds, L. Eaves, M.S. Skolnick, D.K. Maude, O.H. Hughes and J.C. Portal, Investigation of a double barrier resonant tunnelling structure which incorporates an optical window layer in the top contact 111 (1991) 1089
Henningsen, T., see Singh 118 (1992) 78
Heremans, J.P., see Partin 111 (1991) 614
Heremans, J.P., see Youngdale 111 (1991) 693
Herrmann, K.H., K.-P. Möllmann and J.W. Tomm, Broadening mechanisms near the E_0 transition in narrow-gap $Hg_{1-x}Cd_xTe$ ($0.2 < x < 0.6$) 117 (1992) 758
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Herzog, J., see Däweritz, 111 (1991) 65
Hesselink, L., see Wilde 113 (1991) 337
Hesselink, L., see Wilde 114 (1991) 500
Heuken, M., J. Söllner, F.E.G. Guimarães, K. Marquardt and K. Heime, Reduced incorporation of unintentional impurities and intrinsic defects in ZnSe and ZnS grown by MOVPE 117 (1992) 336
Heuken, M., see Guimarães 117 (1992) 1075
Hey, R., see Däweritz, 111 (1991) 65
Hibiya, T., see Kakimoto 112 (1991) 819
Hicks, R.F., see Liu 112 (1991) 192
Hieke, K., see Heimbrodt 117 (1992) 859
Hiesinger, P., see Ralston 111 (1991) 989
Higuchi, M., T. Hosokawa and S. Kimura, Growth of rutile single crystals by floating zone method 112 (1991) 354
Higuchi, M., see Wada 114 (1991) 321
Hikida, K., see Fujiyasu 117 (1992) 1026
Hill, G., see Claxton 111 (1991) 1080
Hilton, D., see Foxon 111 (1991) 1047
Hincelin, G., M. Zahzouh, R. Mellet and A.M. Pougnet, Growth of InP in chemical beam epitaxy with high purity tertiarybutylphosphine 120 (1992) 119
Hingerl, K., see Plotz 115 (1991) 186
Hingerl, K., see Kudlek 117 (1992) 290
Hingerl, K., see Kudlek 117 (1992) 309
Hingerl, K., W. Jantsch, P. Juza, M. Lang, H. Sitter, J. Lilja, M. Pessa, D.J. As and W. Rothemund, Determination of acceptor binding energies in ZnSe 117 (1992) 341
Hingerl, K., see Imai 117 (1992) 406
Hipólito, O., see Notari 116 (1992) 518
Hirahara, K., see Shigenaka 117 (1992) 37
Hirahara, K., see Shigenaka 117 (1992) 49
Hirai, T., see Suzuki 112 (1991) 621
Hirakawa, K., see Hashimoto 111 (1991) 393
Hiraki, A., see Moon 115 (1991) 589
Hiramatsu, K., see Yanagase 115 (1991) 304
Hiramatsu, K., see Kuwano 115 (1991) 381
Hiramatsu, K., S. Itoh, H. Amano, I. Akasaki, N. Kuwano, T. Shiraishi and K. Oki, Growth mechanism of GaN grown on sapphire with AlN buffer layer by MOVPE 115 (1991) 628
Hiramatsu, K., see Takeuchi 115 (1991) 634
Hiramatsu, K., see Koide 115 (1991) 639
Hiramatsu, K., see Murakami 115 (1991) 648
Hiramatsu, M., see Matsushima 117 (1992) 328
Hirata, A., see Saitou 113 (1991) 147
Hirata, A., see Saitou 118 (1992) 365

Hirata, S., see Fujita 115 (1991) 269
Hiratani, Y., Y. Ohki, Y. Sugimoto and K. Akita, In-situ selective-area epitaxy of GaAs using a GaAs oxide layer as a mask 111 (1991) 570
Hiratani, Y., Y. Ohki and M. Sasaki, In-situ selective-area epitaxy of a GaAs-based heterostructure using a GaAs oxide layer as a mask 115 (1991) 74
Hiratani, Y., see Ohki 115 (1991) 226
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Hirayama, H., see Tatsumi 111 (1991) 961
Hiroi, M., see Hirayama 111 (1991) 856
Hiroi, M., see Tatsumi 120 (1992) 275
Hiroi, M. and T. Tatsumi, Selective epitaxial growth of $Si_{1-x}Ge_x$ by cold-wall ultra-high vacuum chemical vapor deposition using disilane and germane 120 (1992) 279
Hirono, S., see Kanisawa 115 (1991) 348
Hirosawa, I., see Tatsumi 111 (1991) 961
Hirose, H., see Iizuka 111 (1991) 429
Hirota, Y., T. Isshiki, K. Okashita and M. Shiojiri, High-resolution transmission electron microscopy of growth and structures of Ag–Te and Cu–Se crystals produced by solid–solid reactions 112 (1991) 55
Hirtz, J.P., see Garcia 111 (1991) 578
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Hiyamizu, S., see Shimomura 111 (1991) 1105
Hladina, R., see Leitner 112 (1991) 437
Ho, P., S.C. Wang, T. Yu, J.M. Ballingall, P.A. Martin, K.H.G. Duh, S.M.J. Liu, G.A. Hutchins and E.L. Hall, Improved device performance by migration-enhanced epitaxy 111 (1991) 233
Hoare, R.D., see Armstrong 120 (1992) 94
Hobbs, A., see Ueda 115 (1991) 133
Hobbs, A., see Sugiyama 117 (1992) 161
Hobbs, A., see Ueda 117 (1992) 266
Hobbs, A., O. Ueda, I. Sugiyama and H. Takigawa, Dislocation interactions in CdTe/GaAs grown by hot wall epitaxy with CdTe/CdZnTe superlattices 117 (1992) 475
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Hobbs, A.K. and P. Metzener, Directional solidification: interface dynamics and weak remote flow 118 (1992) 319
Hobbs, L.W., see Capano 116 (1992) 260
Hodby, J.W., see Chen 118 (1992) 101
Hodes, G., see Galun 117 (1992) 666
Hoffman, C.A., see Youngdale 111 (1991) 693
Hoffmann, A., B. Lummer, Ch. Fricke, R. Heitz and I. Broser, Fast relaxation phenomena in Ni-doped II–VI compounds 117 (1992) 640
Hoffmann, A., see Podlowski 117 (1992) 698
Hoffmann, A., see Thurian 117 (1992) 727
Hoffmann, A., see Fricke 117 (1992) 783
Hoffmann, A., see Broser 117 (1992) 788
Hoffmann, H., see Waldmann 117 (1992) 715
Hofmann, D.M., see Meyer 117 (1992) 656
Hogan, L.M., see Shamsuzzoha 112 (1991) 635
Höger, R., see Heinecke 111 (1991) 599
Höger, R., see Heinecke 120 (1992) 376
Hogg, J.H.C., see Ashenford 117 (1992) 233
Hogg, J.H.C., see Jackson 117 (1992) 867
Hohenstein, M., see Brandt 111 (1991) 383
Hohenstein, M., see Brandt 115 (1991) 99
Hoke, W.E., P.J. Lemonias, P.S. Lyman, H.T. Hendriks, D. Weir and P. Colombo, Carbon doping of MBE GaAs and $Ga_{0.7}Al_{0.3}As$ films using a graphite filament 111 (1991) 269
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Holland, M.C., see Stanley 111 (1991) 14
Holland, M.C., see Kean 111 (1991) 189
Holzinger, A., see Springholz 113 (1991) 593
Homewood, K.P., see Emeny 111 (1991) 413
Hommel, D., W. Busse, H.-E. Gumlich, D. Suisky and J. Röseler, Energy transfer processes in rare earth doped ZnS under non-linear excitation 117 (1992) 721
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Hong, J.M., D.D. Awschalom, F. Agulló-Rueda and L.L. Chang, Growth and novel properties of magnetic heterostructures by molecular beam epitaxy 111 (1991) 1016
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Hong, M., see Wang 111 (1991) 1057

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Hongo, S., see Urano 115 (1991) 411
Hopkins, R.H., see Singh 118 (1992) 78
Hopkinson, M., see Claxton 111 (1991) 1080
Hor, P.H., see Tao 114 (1991) 279
Hori, H., see Kawakyu 114 (1991) 561
Horikoshi, Y., M. Kawashima and N. Kobayashi, Optical investigation of GaAs growth process in molecular beam epitaxy and migration-enhanced epitaxy 111 (1991) 200
Horikoshi, Y., see Ramesh 111 (1991) 752
Horikoshi, Y., see Sato 115 (1991) 221
Horikoshi, Y., see Sudersena Rao 115 (1991) 328
Horikoshi, Y., see Ramesh 115 (1991) 333
Horikoshi, Y., see Kobayashi 115 (1991) 353
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Hosaka, M., Synthesis of micro α-quartz crystals by hydrothermal hot-press method 112 (1991) 291
Hoshikawa, K., see Kan 119 (1992) 215
Hoshikawa, K., see Kawasaki 119 (1992) 317
Hoshino, A., see Isoda 115 (1991) 388
Hoshino, A., S. Isoda and T. Kobayashi, Epitaxial growth of organic crystals on organic substrates – polynuclear aromatic hydrocarbons 115 (1991) 826
Hosogai, H., see Sakai 116 (1992) 421
Hosokawa, T., see Higuchi 112 (1991) 354
Hosomi, S., see Sohn 117 (1992) 907
Hosomi, S., see Noma 117 (1992) 1030
Hou, H.Q. and C.W. Tu, InGaAsP/InP multiple quantum wells grown by gas-source molecular beam epitaxy 120 (1992) 167
Hou Li, see Qi 112 (1991) 580
Hou Li, see Qi 113 (1991) 726
Houdré, R., F. Gueissaz, M. Gailhanou, J.-D. Ganière, A. Rudra and M. Ilegems, Characterization of InGaAs and InAlAs layers on InP by four-crystal high resolution X-ray diffraction and wedge transmission electron microscopy 111 (1991) 456
Houdré, R., see Gueissaz 111 (1991) 470
Houdré, R., see Carlin 120 (1992) 155
Houlton, M., see Lane 120 (1992) 245
Houzay, F., see Moisson 111 (1991) 141
Hovinen, M., see Tappura 112 (1991) 27
Howard, L.K., see Emeny 111 (1991) 413
Hricovini, K., see Marbeuf 117 (1992) 197
Hsieh, Y.F., see Wang 111 (1991) 1057
Hsiung, L.M., see Schowalter 111 (1991) 948
Hu, L.J., Y.H. Chang, I.N. Lin and S.J. Yang, Defects of lithium niobate crystals heavily doped with MgO 114 (1991) 191
Hu, Y.Z., see Koch 117 (1992) 592
Hu, Z.Q., see Jin 116 (1992) 524
Hua, G.C., see Xie 117 (1992) 1079
Huang, Bai-Biao, see Liu 115 (1991) 83
Huang Bingrong, Su Genbo and Pan Feng, Growth of urea crystals with very large cross-sectional area 112 (1991) 729
Huang Chaoen, see Ji 112 (1991) 283
Huang, Gong-Fan, J.T. Lin, Jiang Rihong and Su Genbo, Growth of large single crystals of meta-nitroaniline 119 (1992) 309
Huang, J.G., see Zhou 114 (1991) 283
Huang, T.S., see Chen 118 (1992) 109
Huang, X.R., see Hasenberg 111 (1991) 388
Huang, Yi, see Zhou 111 (1991) 288
Huang, Z.J., see Tao 114 (1991) 279
Hughes, B.T., see Lane 120 (1992) 245
Hughes, O.H., see Henini 111 (1991) 1089
Hugill, K.J., see Myers-Beaghton 111 (1991) 328
Hulyer, P.J., see Foxon 111 (1991) 1047
Humenberger, J., see Enichlmair 117 (1992) 844
Humenberger, J., see Lang 117 (1992) 954
Hunt, J.D., see Rodway 112 (1991) 554
Hunt, J.D., see Rodway 112 (1991) 563
Hunter, J.J., see Wallace 117 (1992) 320
Huo, Chongru, Peiwen Ge, Zhengyi Xu and Zhenhe Zhu, An analysis of the characteristics of crystal growth from solution under microgravity 114 (1991) 486
Huo Yujing, see Ji 112 (1991) 283
Huppert, H.E., see Shirtcliffe 113 (1991) 566
Hurle, D.T.J., see Series 113 (1991) 305
Hutchins, G.A., see Ho 111 (1991) 233
Hvam, J.M., see Pantke 117 (1992) 763
Hvam, J.M., V.G. Lyssenko and H. Schwab, Photon echo, dephasing and recombination of bound excitons in CdSe 117 (1992) 773
Hvam, J.M., see Schwab 117 (1992) 778
Hwang, S., see Lansari 111 (1991) 720
Hwang, S., see Ren 111 (1991) 772
Hyun, D.G., S.Y. Lee, S.H. Sohn and Y. Hamakawa, Anion vacancy states in insulator/CaS and insulator/SrS interfaces 117 (1992) 587
Hyun, D.G., see Sohn 117 (1992) 907

Iba, Y., see Kasuga 115 (1991) 711
Ichihashi, T., see Tanigaki 114 (1991) 3
Ichihashi, T., see Kawano 117 (1992) 171
Ichimura, M. and T. Wada, Calculation of native defect concentrations in GaAs

grown by organometallic vapor-phase epitaxy 115 (1991) 479
Ichimura, M., T. Wada, Sz. Fujita and Sg. Fujita, Reduction of compensating defects in ZnSe and ZnS by photo-irradiation 117 (1992) 689
Ichino, K., see Wu 115 (1991) 664
Ichino, K., Y. Wu, Y. Kawakami, Sz. Fujita and Sg. Fujita, Fabrication of ZnCdSSe alloys by MOMBE and their applications for double-hetero and quantum-well structures 117 (1992) 527
Ichinose, A., see Tajima 114 (1991) 59
Ichizono, K., see Shigenaka 117 (1992) 37
Ichizono, K., see Shigenaka 117 (1992) 49
Iga, K., see Uchida 111 (1991) 1062
Iga, K., see Uchida 120 (1992) 357
Iga, R., see Yamada 120 (1992) 177
Iga, R., see Sugiura 120 (1992) 389
Igasaki, Y., H. Yamauchi and S. Okamura, Structural properties of In–Se thin films prepared by direct evaporation of InSe chunk 112 (1991) 797
Igasaki, Y., Epitaxial growth of aluminum-doped zinc oxide films on (11$\bar{2}$0) oriented sapphire substrates 116 (1992) 357
Ignatenko, A.A., see Barilo 119 (1992) 403
Ignatiev, A., see Hansen 116 (1992) 271
Igumentsev, A.N., see Barilo 119 (1992) 403
Ihara, M., see Ueda 115 (1991) 774
Iida, F., see Kumazaki 117 (1992) 285
Iida, S., see Katoh 112 (1991) 368
Iida, S., see Kinto 117 (1992) 348
Iijima, M., H. Kamemizu, N. Wakamatsu, T. Goto, Y. Doi and Y. Moriwaki, Precipitation of octacalcium phosphate at 37 °C and at pH 7.4: in relation to enamel formation 112 (1991) 467
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Iijima, S., see Kawano 117 (1992) 171
Iizuka, K., T. Yoshida, T. Suzuki and H. Hirose, Observation of dark line defects in InGaAs/GaAs strained layer superlattices by photoluminescence topography 111 (1991) 429
Ikeda, H., K. Saitoh, Y. Hasegawa, A. Koukitu and H. Seki, Thermodynamic analysis of GaAs growth by cold-wall metalorganic-chloride vapor phase epitaxy 115 (1991) 211
Ikeda, M., see Akimoto 117 (1992) 420
Ikeda, S., see Kakishita 115 (1991) 793
Ikei, T., see Takano 111 (1991) 216
Ikoma, T., see Hashimoto 111 (1991) 393
Ilegems, M., see Houdré 111 (1991) 456
Ilegems, M., see Gueissaz 111 (1991) 470
Ilegems, M., see Rudra 111 (1991) 589
Ilegems, M., see Carlin 120 (1992) 155
Ilegems, M., see Rudra 120 (1992) 338
Imai, K., see Kumazaki 117 (1992) 285
Imai, K., see Kudlek 117 (1992) 309
Imai, K., E. Kuusisto, J. Lilja, M. Pessa, D. Suzuki, H. Ozaki, K. Kumazaki and K. Hingerl, Electrical characterization of Li-doped ZnSe grown by molecular beam epitaxy 117 (1992) 406
Imaizumi, T., M. Seiwa and O. Oda, Delta-doped GaAs grown by chloride CVD 115 (1991) 443
Imamura, Y., see Ogasawara 115 (1991) 254
Inaoka, K., see Yase 118 (1992) 348
Inatomi, Y. and K. Kuribayashi, Real-time measurement of LPE growth rate in GaP 114 (1991) 380
Indro, M., see Taylor 119 (1992) 221
Ino, S., see Shigetomi 111 (1991) 110
Inoue, K., J.C. Harmand and T. Matsuno, High-quality $In_xGa_{1-x}As/InAlAs$ modulation-doped heterostructures grown lattice-mismatched on GaAs substrates 111 (1991) 313
Inoue, K., see Minami 117 (1992) 565
Inoue, K., F. Minami, Y. Kato, K. Yoshida and K. Era, Exciton resonance of hyper-Raman and hyper-Rayleigh scatterings in II–VI compounds 117 (1992) 738
Inoue, M., see Yano 111 (1991) 397
Inoue, M., see Yano 111 (1991) 609
Inoue, M., see Yoh 111 (1991) 643
Inoue, N., MBE monolayer growth control by in-situ electron microscopy 111 (1991) 75
Inoue, N., see Yokoyama 115 (1991) 89
Inoue, N., see Kanisawa 115 (1991) 348
Inoue, T., M. Kuriyama and H. Komatsu, Growth of CuCl single crystals by the top seeded solution growth method 112 (1991) 531
Inoue, Y., see Nagao 111 (1991) 511
Inoue, Y., see Nagao 111 (1991) 521
Irie, T., see Ando 117 (1992) 362
Irisawa, T., see Arima 115 (1991) 428
Irvine, D.J., see O'Donnell 117 (1992) 497
Ishiai, J., S. Yamada, S. Yoshizawa and K. Endo, Preparation of $Bi_2Sr_2Ca_{n-1}Cu_nO_{2n+4}$ ($n = 1, 2, 3$ and 4) thin films by MOCVD 115 (1991) 762
Ishida, A., see Fujiyasu 117 (1992) 1026
Ishigaki, T., see Okada 116 (1992) 307
Ishihara, E., see Matsumoto 115 (1991) 674
Ishii, M., see Funato 117 (1992) 543
Ishikawa, H., see Sandhu 111 (1991) 559
Ishikawa, H., see Kawakyu 114 (1991) 561

Ishikawa, H., see Ando 120 (1992) 228
Ishikawa, M., see Nishikawa 112 (1991) 628
Ishikawa, M., see Suzuki 113 (1991) 127
Ishikawa, M., see Suzuki 115 (1991) 498
Ishikawa, T., see Kimura 116 (1992) 22
Ishino, K., see Fujiyasu 117 (1992) 1026
Ishizawa, Y., see Otani 113 (1991) 329
Ishizawa, Y., see Otani 118 (1992) 461
Isoda, S., I. Kubo, A. Hoshino, N. Asaka, H. Kurata and T. Kobayashi, Molecular imaging of epitaxially grown organic double-layer 115 (1991) 388
Isoda, S., see Hoshino 115 (1991) 826
Isshiki, M., see Mochizuki 115 (1991) 687
Isshiki, M., see Oguri 117 (1992) 116
Isshiki, M., K.S. Park, Y. Furukawa and W. Uchida, Photoluminescence of Li-doped ZnSe single crystals 117 (1992) 410
Isshiki, T., see Hirota 112 (1991) 55
Isu, T., see Hata 111 (1991) 83
Isu, T., M. Hata and A. Watanabe, Real-time μ-RHEED observations of GaAs surfaces during growth with alternating source supply 111 (1991) 210
Isu, T., see Watanabe 111 (1991) 554
Isu, T., see Hata 114 (1991) 203
Isu, T., see Watanabe 115 (1991) 371
Isu, T., M. Hata, Y. Morishita, Y. Nomura and Y. Katayama, Surface diffusion length during MBE and MOMBE measured from distribution of growth rates 115 (1991) 423
Isu, T., M. Hata, Y. Morishita, Y. Nomura, S. Goto and Y. Katayama, Surface diffusion length during MOMBE and CBE growth measured by μ-RHEED 120 (1992) 45
Isu, T., see Goto 120 (1992) 382
Itakura, H., T. Suzuki, Z.K. Jiang, T. Soga, T. Jimbo and M. Umeno, Effect of InGaAs/InP strained layer superlattice in InP-on-Si 115 (1991) 154
Itani, Y., see Kaneko 111 (1991) 638
Itani, Y., see Okuno 115 (1991) 236
Itani, Y., see Asahi 120 (1992) 252
Itaya, K., see Suzuki 115 (1991) 498
Ito, Y., K. Kushida and H. Takeuchi, Role of chromium sublayers in the growth of highly crystalline (111)-oriented gold films on sapphire 112 (1991) 427
Ito, H., see Kawai 115 (1991) 216
Ito, K., see Kouta 114 (1991) 676
Ito, R., see Fukatsu 111 (1991) 843
Ito, T., see Moon 115 (1991) 589
Ito, T., see Nagai 115 (1991) 769
Ito, T., see Goto 115 (1991) 816
Ito, T., see Fujimura 115 (1991) 821
Itoh, K., see Kuwano 115 (1991) 381
Itoh, K., see Koide 120 (1992) 284
Itoh, M., see Kôzuki 114 (1991) 683
Itoh, S., see Hiramatsu 115 (1991) 628
Itoh, T., see Nitta 115 (1991) 515
Itoh, T., K. Shinone, N. Katagiri, M. Furumiya and T. Tezuka, Stress-induced mixing of light and heavy exciton states in thin films of CdTe and CdMnTe epitaxially grown on GaAs substrates 117 (1992) 835
Iuchi, T., see Terada 117 (1992) 54
Ivanov, S.V., P.S. Kop'ev and N.N. Ledentsov, Thermodynamic analysis of segregation effects in MBE of A^{III}–B^{V} compounds 111 (1991) 151
Iwai, Y., see Yano 111 (1991) 397
Iwai, Y., see Yano 111 (1991) 609
Iwanaga, H., see Kawaguchi 118 (1992) 309
Iwanari, S. and K. Takayanagi, Surfactant epitaxy of Si on Si(111) surface mediated by a Sn layer. I. Reflection electron microscope observation of the growth with and without a Sn layer mediate the step flow 119 (1992) 229
Iwanari, S., Y. Kimura and K. Takayanagi, Surfactant epitaxy of Si on Si(111) surface mediated by a Sn layer. II. Critical step flow of the growth with and without mediate 119 (1992) 241
Iwata, H., see Mochizuki 115 (1991) 687
Iwawaki, T., see Yano 111 (1991) 397
Iyer, S.S., see Kesan 111 (1991) 847
Iyer, S.S., see Kesan 111 (1991) 936
Iyer, S.S., see Schowalter 111 (1991) 948
Iyi, N., see Kitamura 116 (1992) 327
Izumi, H., see Hase 115 (1991) 788
Izumiya, T., see Hatano 115 (1991) 455

Jackson, S., W.E. Hagston, T.J. Gregory, J. Goodwin, J.E. Nicholls, J.H.C. Hogg, B. Lunn and D.E. Ashenford, Vertical transport in $CdTe/Cd_{1-x}Mn_xTe$ superlattices incorporating extended wells 117 (1992) 867
Jacobs, K., see Rudolph 118 (1992) 204
Jain, F., see Chung 117 (1992) 1062
Jan, W., see Cunningham 120 (1992) 306
Jan, W.Y., see Chiu 111 (1991) 274
Jan, W.Y., see Cunningham 111 (1991) 515
Janam, R. and O.N. Srivastava, Characterization of neutron irradiated $YBa_2Cu_3O_7$ single crystals 113 (1991) 403
Jang Rihong, see He 113 (1991) 157
Jang Rihong, see He 113 (1991) 161
Jang Rihong, see He 119 (1992) 393
Jansen, A.N., M.E. Orazem, B.A. Fox and W.A. Jesser, Numerical study of the influence of reactor design on MOCVD with a comparison to experimental data 112 (1991) 316
Janssen, G., see Van Enckevort 113 (1991) 295

Jantsch, W., see Hingerl 117 (1992) 341
Järvinen, R.J.O., see Podkletnov 114 (1991) 198
Jensen, K.F., see Coronell 114 (1991) 581
Jeon, H., see Ren 117 (1992) 510
Jeon, H., see Xie 117 (1992) 1079
Jeppesen, S., see Paulsson 111 (1991) 115
Jeppesen, S., see Deppert 120 (1992) 88
Jesser, W.A., see Jansen 112 (1991) 316
Ji Yangyang, Zhao Shuqing, Huo Yujing, Zhang Hongwu, Li Ming and Huang Chaoen, Growth of lithium triborate (LBO) single crystal fiber by the laser-heated pedestal growth method 112 (1991) 283
Jiang, M., see Zhou 114 (1991) 283
Jiang, Min-Hua, see Liu 115 (1991) 83
Jiang Rihong, see Huang 119 (1992) 309
Jiang, S.S., Q. Li and X.Y. Xu, Growth defects of natural beryls observed by X-ray topography 116 (1992) 93
Jiang, Xue-Lin, see Tanaka 117 (1992) 997
Jiang, Xue-Yin, see Zhang 117 (1992) 1012
Jiang, Z.K., see Itakura 115 (1991) 154
Jimbo, T., see Itakura 115 (1991) 154
Jimbo, T., see Suzuki 115 (1991) 158
Jimbo, T., see Soga 115 (1991) 418
Jimbo, T., see Egawa 115 (1991) 524
Jimenez, J.R., see Schowalter 111 (1991) 948
Jin, H., Y.L. Ge, Q.M. Liu, Z.Q. Hu and C.H. Shi, Morphologies and structures of Bi-based oxide fibrous crystals 116 (1992) 524
Jin, Weimin, see Zhou 111 (1991) 288
Jin, Y., see Kobayashi 113 (1991) 491
Jin, Ying, see Shen 117 (1992) 470
Jo, J., see Santos 111 (1991) 366
Johansen, T.H., On the inherent stability of the Czochralski crystal growth process 114 (1991) 27
Johansen, T.H., The weight gain signal in Czochralski crystal growth 118 (1992) 353
Johnson, D.A., see Puechner 111 (1991) 43
Jones, A.C., see Foord 120 (1992) 103
Jones, E.D., N.M. Stewart and J.B. Mullin, The diffusion of copper in cadmium telluride 117 (1992) 244
Jones, E.D., see Aslam 117 (1992) 249
Jones, E.D., V. Thambipillai and J.B. Mullin, The diffusion of mercury in cadmium telluride 118 (1992) 1
Jones, G.A.C., see Ritchie 111 (1991) 300
Jones, G.A.C., see Frost 111 (1991) 305
Jones, G.A.C., see Davies 111 (1991) 318
Jones, G.A.C., see Frost 113 (1991) 726
Jones, H., see Moir 113 (1991) 77
Jones, I., see Brown 117 (1992) 536
Jones, I.P., see Taylor 119 (1992) 221
Jones, K.A., J.R. Flemish, H. Shen and V.S. Ban, Incorporation of phosphorus during gas phase epitaxy 120 (1992) 150
Jones, K.L., see Chang 111 (1991) 475
Jönsson, J., see Paulsson 111 (1991) 115
Jönsson, J., see Deppert 120 (1992) 88
Jouneau, P.H., see Cibert 117 (1992) 424
Jouneau, P.H., see Pautrat 117 (1992) 454
Joyce, B.A., see Zhang 111 (1991) 93
Joyce, B.A., see Foxon 111 (1991) 539
Joyce, B.A., see Yuen 111 (1991) 943
Joyce, B.A., J. Zhang, T. Shitara, J.H. Neave, A. Taylor, S. Armstrong, M.E. Pemble and C.T. Foxon, Dynamics and kinetics of MBE growth 115 (1991) 338
Joyce, B.A., see Fawcett 116 (1992) 81
Joyce, B.A., see Lacklison 120 (1992) 50
Joyce, B.A., see Mokler 120 (1992) 290
Joyce, T.B., see Armstrong 120 (1992) 84
Joyce, T.B., T.J. Bullough, P. Kightley, C.J. Kiely, Y.R. Xing and P.J. Goodhew, CBE growth of GaAs/GaAs, GaAs/Si and AlGaAs/GaAs using TEG, AsH_3 and amine-alane precursors 120 (1992) 206
Joyce, T.B., see Farrell 120 (1992) 395
Juang, M.H., see Cheng 115 (1991) 572
Jundt, D.H., see Wilde 114 (1991) 500
Jurčová, M., see Söhnel 112 (1991) 415
Jusserand, B., see Moisson 111 (1991) 141
Jusserand, B., see Gérard 111 (1991) 205
Juza, P., see Faschinger 115 (1991) 692
Juza, P., see Hingerl 117 (1992) 341

Kadoiwa, K., see Nishimura 112 (1991) 791
Kadoiwa, K., T. Nishimura, N. Hayafuji, M. Miyashita, H. Kizuki and K. Mizuguchi, Study of initial buffer layer in GaAs-on-Si growth 115 (1991) 128
Kadota, Y., see Kajigaya 112 (1991) 123
Kadoya, Y., A. Sato, H. Kano and H. Sakaki, Electrical properties and dopant incorporation mechanisms of Si doped GaAs and (AlGa)As grown on (111)A GaAs surfaces by MBE 111 (1991) 280
Kaganer, V.M., see Charniy 118 (1992) 163
Kagawa, M., see Suzuki 112 (1991) 621
Kaiser, R., see Künzel 111 (1991) 1084
Kajigaya, T., T. Kimura and Y. Kadota, Effect of the magnetic flux direction on LEC GaAs growth under magnetic field 112 (1991) 123
Kajikawa, Y., see Hata 114 (1991) 203
Kajimoto, A., see Yoshimoto 115 (1991) 265
Kakimoto, K., M. Eguchi and T. Hibiya, In-situ monitoring of dopant concentration variation in a silicon melt during Czochralski growth 112 (1991) 819
Kakimoto, K., P. Nicodème, M. Lecomte, F. Dupret and M.J. Crochet, Numerical simulation of molten silicon flow; comparison with experiment 114 (1991) 715

Kakinoki, M., see Fujimura 115 (1991) 821
Kakishita, K., S. Ikeda and T. Suda, Zn_3P_2 epitaxial growth by MOCVD 115 (1991) 793
Kakuta, J., see Matsumura 115 (1991) 279
Kakuta, J., see Matsumura 117 (1992) 129
Kaldis, E., see Piechotka 113 (1991) 251
Kaldis, E., see Zha 115 (1991) 43
Kallel, M.A., V. Arbet-Engels, K.L. Wang and R.P.G. Karunasiri, MBE Si_mGe_n strained monolayer superlattices 111 (1991) 897
Kallis, N., see Waag 117 (1992) 820
Kaltenegger, K., see Enichlmair 117 (1992) 844
Kamada, H., see Ogasawara 115 (1991) 254
Kamata, A., see Yoshida 117 (1992) 75
Kamata, A., H. Yoshida and T. Uemoto, Homoepitaxial growth and characterization of ZnSe on different ZnSe substrates by metalorganic vapor phase epitaxy 117 (1992) 96
Kamemizu, H., see Iijima 112 (1991) 467
Kamigaki, K., see Terashima 115 (1991) 745
Kamiya, I., see Aspnes 120 (1992) 71
Kamp, M., F. König, G. Mörsch and H. Lüth, New aluminium precursors for MOMBE (CBE): a comparative study 120 (1992) 124
Kan, S., M. Sakamoto, Y. Okano, K. Hoshikawa and T. Fukuda, $LiNbO_3$ single crystal growth by the continuous charging Czochralski method with Li/Nb ratio control 119 (1992) 215
Kan, S., see Kawasaki 119 (1992) 317
Kanaji, T., see Urano 115 (1991) 411
Kanaya, Y., see Takano 111 (1991) 216
Kanehisa, O., see Shiiki 117 (1992) 1035
Kaneko, S., M. Tanaka, K. Masu, K. Tsubouchi and N. Mikoshiba, Epitaxial growth of AlN film by low-pressure MOCVD in gas-beam-flow reactor 115 (1991) 643
Kaneko, T., see Takeyasu 111 (1991) 502
Kaneko, T., H. Asahi, Y. Itani, Y. Okuno and S. Gonda, MOMBE growth of GaSb and InAsSb using triethylstibine and triethylarsine 111 (1991) 638
Kaneko, T., see Okuno 115 (1991) 236
Kaneko, T., H. Asahi and S. Gonda, Theoretical consideration of the growth kinetics for GaAs and GaSb 120 (1992) 39
Kaneko, T., see Asahi 120 (1992) 252
Känel, H. von, E. Müller, H.-U. Nissen, W. Bacsa, M. Ospelt, K.A. Mäder, R. Stalder and A. Baldereschi, Silicon heteroepitaxy: interface structure and physical properties 111 (1991) 889
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Kang, T.W., see Kuo 111 (1991) 996
Kanisawa, K., J. Osaka, S. Hirono and N. Inoue, In situ measurement method of GaAs surface coverage using secondary electron intensity 115 (1991) 348
Kanno, T., see Takami 117 (1992) 16
Kanno, T., see Shigenaka 117 (1992) 37
Kanno, T., see Shigenaka 117 (1992) 49
Kanno, T., see Kawano 117 (1992) 171
Kanno, T., see Oda 117 (1992) 193
Kanno, T., see Sasaki 117 (1992) 222
Kano, H., see Kadoya 111 (1991) 280
Kano, H., see Tomita 115 (1991) 299
Kao, M., see Hersee 120 (1992) 218
Kapitulnik, A., see Lombardo 118 (1992) 483
Kapre, R.M., A. Madhukar and S. Guha, Highly strained pseudomorphic $In_xGa_{1-x}As/AlAs$ based resonant tunneling diodes grown on patterned and nonpatterned GaAs(100) substrates 111 (1991) 1110
Kaprelov, A.M., see Trusov 114 (1991) 133
Karasawa, T., see Ohkawa 111 (1991) 797
Kargodorian, T.V., see Metzger 111 (1991) 445
Karl, N., see Möbus 116 (1992) 495
Kartenko, N.F., see Volkov 119 (1992) 122
Karunasiri, R.P.G., see Kallel 111 (1991) 897
Kasai, K., see Kikkawa 115 (1991) 448
Kasai, Y. and S. Sakai, In-situ growth of Bi–Sr–Ca–Cu oxide superconducting thin films by molecular beam epitaxy with a pure ozone source 115 (1991) 758
Kashchiev, D., see Verdoes 118 (1992) 401
Kasu, M., H. Saito and T. Fukui, Step-density dependence of growth rate on vicinal surface of MOCVD 115 (1991) 406
Kasuga, M., see Yoshioka 115 (1991) 705
Kasuga, M., H. Futami and Y. Iba, Vapor phase epitaxy of CdTe on sapphire and GaAs 115 (1991) 711
Katagiri, N., see Itoh 117 (1992) 835
Katahama, H., see Shigeta 111 (1991) 284
Katahama, H., Y. Matsuda, Y. Shiba and K. Fujita, Raman scattering study on the first step growth of GaAs on Si grown by MOCVD 115 (1991) 141
Katayama, S., see Yokota 112 (1991) 723
Katayama, T., M. Fujimoto, M. Shimizu and T. Shiosaki, Photo-MOCVD of $PbTiO_3$ thin films 115 (1991) 289
Katayama, Y., see Hata 114 (1991) 203
Katayama, Y., see Watanabe 115 (1991) 371
Katayama, Y., see Isu 115 (1991) 423
Katayama, Y., see Isu 120 (1992) 45
Katayama, Y., see Goto 120 (1992) 382
Katayama-Yoshida, H., T. Sasaki and T. Oguchi, Theory of the self-compensation in p-type ZnSe 117 (1992) 625
Kato, F., see Teraguchi 115 (1991) 798

Kato, H., see Koide 115 (1991) 639
Kato, K., T. Kusunoki, C. Takenaka, T. Tanahashi and K. Nakajima, Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth 115 (1991) 174
Kato, M., J. Murota and S. Ono, Control of composition and deposition rate in Si–Ge CVD epitaxy on Si 115 (1991) 117
Kato, T., see Matsumoto 115 (1991) 674
Kato, T., see Matsumoto 117 (1992) 578
Kato, Y., see Sasaoka 115 (1991) 94
Kato, Y., see Minami 117 (1992) 565
Kato, Y., see Inoue 117 (1992) 738
Katoh, M., see Nagao 111 (1991) 521
Katoh, M., S. Iida, Y. Sugita and K. Okamoto, X-ray characterization of tungsten single crystals grown by secondary recrystallization method 112 (1991) 368
Katsuyama, T., see Yoshida 115 (1991) 533
Katty, A., P. Dusserre, R. Triboulet and T. Duffar, Surface tension of II–VI compounds and contact angle on glassy carbon 118 (1992) 470
Kaviani, K., see Chen 111 (1991) 424
Kavokin, A.V., see Uraltsev 117 (1992) 877
Kawaguchi, M., K. Nozaki, S. Motojima and H. Iwanaga, A growth mechanism of regularly coiled carbon fibers through acetylene pyrolysis 118 (1992) 309
Kawaguchi, Y., see Ohki 117 (1992) 102
Kawai, H., see Nakamura 115 (1991) 474
Kawai, J., H. Ito and K. Hara, MOVPE growth of GaAs using metallic arsenic and trimethylgallium 115 (1991) 216
Kawai, M., S. Watanabe and T. Hanada, Molecular beam epitaxy of $Bi_2Sr_2CuO_x$ and $Bi_2Sr_2Ca_{0.85}Sr_{0.15}Cu_2O_x$ ultra thin films at 300 °C 112 (1991) 745
Kawakami, K., see Matsumoto 117 (1992) 578
Kawakami, Y., see Wu 111 (1991) 757
Kawakami, Y., see Wu 115 (1991) 664
Kawakami, Y., see Ichino 117 (1992) 527
Kawakita, T., see Sakai 116 (1992) 421
Kawakyu, Y., H. Hori, H. Ishikawa and M. Mashita, Low pressure metalorganic chemical vapor deposition of InGaP using tetiarybutylphosphine 114 (1991) 561
Kawamura, K., see Gao 117 (1992) 983
Kawanishi, E., see Nagao 111 (1991) 511
Kawano, M., N. Oda, T. Sasaki, T. Ichihashi, S. Iijima, T. Kanno and M. Saga, Twin-formation mechanisms for HgCdTe epilayers 117 (1992) 171
Kawano, M., see Sone 117 (1992) 218
Kawano, M., see Sasaki 117 (1992) 222
Kawasaki, K., Y. Okano, S. Kan, M. Sakamoto, K. Hoshikawa and T. Fukuda, Uniformity of Fe-doped $LiNbO_3$ single crystal grown by the Czochralski method 119 (1992) 317
Kawashima, M., see Horikoshi 111 (1991) 200
Kawashima, M., see Seto 117 (1992) 271
Kawashima, M., see Zhu 117 (1992) 400
Kawazu, Z., see Takami 117 (1992) 16
Kawazu, Z., see Yasumura 117 (1992) 20
Kayser, O., R. Westphalen, B. Opitz and P. Balk, Control of selective area growth of InP 112 (1991) 111
Kazakov, A.I., I.N. Kishmar, A.E. Bochkarev and L.M. Dolginov, Stability analysis of quaternary $In_xGa_{1-x}Sb_yAs_{1-y}$ alloys 116 (1992) 204
Kazmierski, C., see Allovon 111 (1991) 484
Kazmierski, C., D. Robein and Y. Gao, Universal iron behaviour in Zn-, Cd- and Be-doped p-type InP 116 (1992) 75
Kean, A.H., see Stanley 111 (1991) 14
Kean, A.H., C.R. Stanley, M.C. Holland, J.L. Martin and J.N. Chapman, Gallium desorption from (Al,Ga)As grown by molecular beam epitaxy at high temperatures 111 (1991) 189
Kekelidze, N.P., see Butkhuzi 117 (1992) 366
Keller, B.P., R. Schwabe, R. Pickenhain, W. Seifert, E. Butter and J.L. Staehli, MOVPE growth and properties of GaP using nitrogen bridged adduct 118 (1992) 176
Keller, K.W., Spontaneous and preferential two-dimensional nucleation – a quantitative analysis of growth hill observations 112 (1991) 496
Kelly, K.W., K. Koai and S. Motakef, Model-based control of thermal stresses during LEC growth of GaAs. I. Validation of thermal model 113 (1991) 254
Kelly, K.W., S. Motakef and K. Koai, Model-based control of thermal stresses during LEC growth of GaAs. II. Crystal growth experiments 113 (1991) 265
Kelly, K.W., see Motakef 113 (1991) 279
Kelly, K.W., see Motakef 116 (1992) 242
Kenny, M.J., see Wielunski 117 (1992) 460
Keramidas, V.G., see Harbison 111 (1991) 978
Keramidas, V.G., see Aspnes 120 (1992) 71
Kerkow, H., V.X. Quang and B. Selle, Post-range implantation damage in II–VI compounds due to electronically stimulated diffusion 117 (1992) 677
Kern, R. and R. Dassonville, Growth inhibitors and promoters examplified on solution growth of paraffin crystals 116 (1992) 191
Kesan, V.P., S.S. Iyer and J.M. Cotte, Dopant incorporation in epitaxial germanium grown on Ge(100) substrates by MBE 111 (1991) 847
Kesan, V.P., P.G. May, F.K. LeGoues and S.S. Iyer, Si/SiGe heterostructures grown

on SOI substrates by MBE for integrated optoelectronics 111 (1991) 936
Kheng, K., see Bassani 117 (1992) 391
Khulordava, T.G., see Butkhuzi 117 (1992) 366
Khulordava, T.G., see Butkhuzi 117 (1992) 1055
Kido, G., see Nakahara 117 (1992) 830
Kiely, C.J., see Joyce 120 (1992) 206
Kiessling, F.M., see Gille 114 (1991) 77
Kightley, P., P.J. Goodhew, R.R. Bradley and P.D. Augustus, A mechanism of misfit dislocation reaction for GaInAs strained layers grown onto off-axis GaAs substrates 112 (1991) 359
Kightley, P., see Armstrong 120 (1992) 84
Kightley, P., see Joyce 120 (1992) 206
Kightley, P., see Farrell 120 (1992) 395
Kijima, S., see Sato 115 (1991) 740
Kijima, T., see Yoshida 113 (1991) 221
Kikkawa, T., T. Ohori, H. Tanaka, K. Kasai and J. Komeno, Effective Si planar doping of GaAs by MOVPE using tertiarybutylarsine 115 (1991) 448
Kikuta, T., see Yoshida 113 (1991) 221
Kim, D.H. and R.A. Brown, Modelling of the dynamics of HgCdTe growth by the vertical Bridgman method 114 (1991) 411
Kim, J.H., D. Yang, Y.-C. Chen and P. Bhattacharya, Growth and properties of $InAs_xSb_{1-x}$, $Al_yGa_{1-y}Sb$, and $InAs_xSb_{1-x}/Al_yGa_{1-y}Sb$ heterostructures 111 (1991) 633
Kim, K.-H., see Choi 115 (1991) 579
Kim, T., see Tran 113 (1991) 16
Kimoto, T., see Yoo 115 (1991) 733
Kimura, H., T. Numazawa, M. Sato, H. Maeda and M. Sakamoto, Minimization of lattice parameter change in Czochralski grown $(Gd_{1-x}Y_x)Ga_5O_{12}$ garnet single crystal 119 (1992) 313
Kimura, R., M. Konagai and K. Takahashi, Atomic layer epitaxy of ZnSe on GaAs(100) by metalorganic molecular beam epitaxy 116 (1992) 283
Kimura, S., see Higuchi 112 (1991) 354
Kimura, S., T. Ishikawa, J. Mizuki and J. Matsui, Analysis of minute strain fields around A-swirl defects in a float zone silicon crystal by means of plane wave X-ray topography using extremely collimated X-rays 116 (1992) 22
Kimura, S., see Kitamura 116 (1992) 327
Kimura, T., see Kajigaya 112 (1991) 123
Kimura, T., see Ueda 115 (1991) 774
Kimura, Y., see Iwanari 119 (1992) 241
Kinoshita, S., Y. Suzuki and T. Nishinaga, Epitaxial lateral overgrowth of Si on non-planar substrate 115 (1991) 561
Kinto, K., M. Yagi, K. Tanigashira, T. Yamada, H. Uchiki and S. Iida, Photoluminescence studies of p- and n-type ZnS layers grown by vapor phase epitaxy 117 (1992) 348
Kircher, R., M. Furuno, J. Murota and S. Ono, Low-temperature epitaxial growth of in-situ doped silicon films 115 (1991) 439
Kirchner, P.D., see De Lyon 111 (1991) 564
Kishmar, I.N., see Kazakov 116 (1992) 204
Kita, R., T. Hase, M. Sasaki, T. Morishita and S. Tanaka, Epitaxial growth of CuO thin films by in situ oxidation of Cu thin films 115 (1991) 752
Kitabatake, M., P. Fons and J.E. Greene, Molecular dynamics and quasidynamics simulations of low-energy ion/surface interactions leading to decreased epitaxial temperatures and increased dopant incorporation probabilities during Si MBE 111 (1991) 870
Kitagawa, F., see Tomita 115 (1991) 299
Kitahara, K., see Ueda 115 (1991) 133
Kitamura, K., J.K. Yamamoto, N. Iyi, S. Kimura and T. Hayashi, Stoichiometric $LiNbO_3$ single crystal growth by double crucible Czochralski method using automatic powder supply system 116 (1992) 327
Kizuki, H., see Kadoiwa 115 (1991) 128
Klauda, M., see Markl 113 (1991) 395
Klem, J.F., S.R. Kurtz and A. Datye, Growth and properties of GaAsSb/InGaAs superlattices in InP 111 (1991) 628
Klingshirn, C., see Uhrig 117 (1992) 598
Klingshirn, C., Properties of the electron–hole plasma in II–VI semiconductors 117 (1992) 753
Klingshirn, C., see Schwab 117 (1992) 778
Kliya, M.O., see Givargizov 112 (1991) 758
Klíma, P., see Leitner 112 (1991) 437
Knoll, P., see Ullrich 117 (1992) 902
Koai, K., see Kelly 113 (1991) 254
Koai, K., see Kelly 113 (1991) 265
Koai, K., see Motakef 113 (1991) 279
Koai, K., see Motakef 116 (1992) 242
Kobayashi, H., see Tanaka 117 (1992) 997
Kobayashi, K., see Shigeta 111 (1991) 284
Kobayashi, K., see Shimomura 111 (1991) 1105
Kobayashi, K., see Shima 115 (1991) 359
Kobayashi, M., see Qiu 111 (1991) 747
Kobayashi, M., see Han 111 (1991) 767
Kobayashi, M., see Li 111 (1991) 1038
Kobayashi, M., see Gunshor 115 (1991) 652
Kobayashi, M., see Nurmikko 117 (1992) 432
Kobayashi, M., see Gao 117 (1992) 983
Kobayashi, M., see Xie 117 (1992) 1079
Kobayashi, N., see Horikoshi 111 (1991) 200
Kobayashi, N., see Ramesh 111 (1991) 752
Kobayashi, N., Oxygen transport under an axial magnetic field in Czochralski silicon growth (E) 112 (1991) 308
Kobayashi, N., see Sato 115 (1991) 221

Kobayashi, N., see Ramesh 115 (1991) 333
Kobayashi, N., Y. Yamauchi and Y. Horikoshi, In-situ optical monitoring of pyrolysis process on substrate surface in GaAs MOCVD 115 (1991) 353
Kobayashi, N., see Zhang 117 (1992) 1074
Kobayashi, R., Y. Jin, F. Hasegawa, A. Koukitu and H. Seki, Low temperature growth of GaAs and AlAs by direct reaction between $GaCl_3$, $AlCl_3$ and AsH_3 113 (1991) 491
Kobayashi, T., see Isoda 115 (1991) 388
Kobayashi, T., see Hoshino 115 (1991) 826
Kobayashi, T., see Möbus 116 (1992) 495
Kobayashi, T., see Misawa 117 (1992) 617
Koch, S.W., Y.Z. Hu, B. Fluegel and N. Peyghambarian, Coulomb effects and optical properties of semiconductor quantum dots 117 (1992) 592
Koch, S.W., see Masumoto 117 (1992) 732
Kochereshko, V.P., see Uraltsev 117 (1992) 877
Koda, T., see Kanemitsu 117 (1992) 316
Kodama, K., see Sakuma 114 (1991) 31
Kodama, K., see Sakuma 115 (1991) 324
Kodama, K., see Ohtsuka 115 (1991) 460
Koepke, J., see Tietz 118 (1992) 314
Koga, A., see Kuwano 115 (1991) 381
Koguchi, N., S. Takahashi and T. Chikyow, New MBE growth method for InSb quantum well boxes 111 (1991) 688
Köhler, K., P. Ganser, M. Maier and K.H. Bachem, Modulation doped inverted and normal GaAs/Al_xGa_{1-x}As heterostructures: influence of Si-segregation on the two-dimensional electron gas 111 (1991) 295
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Koide, Y., see Ohshima 115 (1991) 106
Koide, Y., A. Furukawa, S. Zaima and Y. Yasuda, In-situ RHEED study of growth processes in the initial stage of SiGe alloy film deposition by gas source molecular beam epitaxy 115 (1991) 365
Koide, Y., S. Zaima, K. Itoh and Y. Yasuda, In-situ RHEED study on the effect of light irradiation on Ge/Si heteroepitaxial growth by GeH_4 source MBE 120 (1992) 284
Koinuma, H., see Nagata 118 (1992) 299
Kokubo, N., see Matsumoto 117 (1992) 578
Kokubun, Y., see Nishikawa 112 (1991) 628
Kokubun, Y., see Suzuki 113 (1991) 127
Kokubun, Y., see Suzuki 115 (1991) 498
Kokubun, Y., see Nishikawa 119 (1992) 292
Kolar, Z.I., J.J.M. Binsma and B. Subotić, Kinetic study of the solution-mediated transformation of orthorhombic barium fluoride into cubic barium fluoride 116 (1992) 473
Kolenda, J., see Woggon 117 (1992) 608
Kolodziejczyk, M., Th. Filz, A. Krost, W. Richter and D.R.T. Zahn, The likelihood of III_2–VI_3 compound formation during epitaxial growth of II–VI on III–V semiconductors 117 (1992) 549
Koma, A., K. Ueno and K. Saiki, Heteroepitaxial growth by Van der Waals interaction in one-, two- and three-dimensional materials 111 (1991) 1029
Koma, A., see Ohuchi 111 (1991) 1033
Komatsu, H., see Inoue 112 (1991) 531
Komatsu, S., see Okada 116 (1992) 307
Komeno, J., see Kikkawa 115 (1991) 448
Komiyama, S., see Terashima 115 (1991) 745
Konagai, M., see Yamada 111 (1991) 584
Konagai, M., see Takemura 111 (1991) 802
Konagai, M., see Teraguchi 115 (1991) 798
Konagai, M., see Kimura 116 (1992) 283
Konagai, M., see Takemura 117 (1992) 144
Konagai, M., Wide band-gap II–VI compounds grown by MOMBE 120 (1992) 261
Konagai, M., see Tokumitsu 120 (1992) 301
Kondo, A., see Takahashi 117 (1992) 979
Kondo, K., see Saito 111 (1991) 544
Kondo, M., J. Okazaki, H. Sekiguchi, T. Tanahashi, S. Yamazaki and K. Nakajima, Highly-uniform large-area MOVPE growth of InGaAsP by controlled stagnation point flow 115 (1991) 231
Kondo, M., see Domen 115 (1991) 529
Kondow, M., see Minagawa 118 (1992) 425
König, F., see Kamp 120 (1992) 124
Konishi, R., K. Noda, H. Harada and H. Sasakura, The preparation of transparent ZnO:Al thin films 117 (1992) 939
Kop'ev, P.S., see Ivanov 111 (1991) 151
Kopf, R.F., see Asom 111 (1991) 246
Kopf, R.F., see Hong 111 (1991) 1052
Köpp, Th., see Heimbrodt 117 (1992) 859
Köpp, Th., see Goede 117 (1992) 886
Korbutowicz, R., see Helak 115 (1991) 294
Korkishko, Yu.N., see Fedorov 112 (1991) 781
Kornack, J., see Woggon 117 (1992) 608
Kortan, A.R., see Hong 111 (1991) 984
Koshizuka, N., see Tajima 114 (1991) 59
Kosmyna, M.B., see Babijchuk 116 (1992) 529
Kosyachenko, L.A., V.P. Makhniy, V.Ye. Baranyuk and V.V. Melnik, Optoelectronic properties of diode heterostructures based on ZnS and ZnSe 117 (1992) 583
Kothiyal, G.P., see Muthe 118 (1992) 213
Kotljarevsky, M.B., see Butkhuzi 117 (1992) 1055
Kou, S., see Lan 114 (1991) 517

Kou, S., see Lan 118 (1992) 151
Kou, S., see Lan 119 (1992) 281
Koukitu, A., see Kobayashi 113 (1991) 491
Koukitu, A., see Ikeda 115 (1991) 211
Kouta, H., Y. Kuwano, K. Ito and F. Marumo, β-BaB_2O_4 single crystal growth by Czochralski method. II 114 (1991) 676
Kovac, J., see Claxton 111 (1991) 1080
Koyama, F., see Uchida 111 (1991) 1062
Koyama, F., see Uchida 120 (1992) 357
Koyama, K., see Hirayama 111 (1991) 856
Koyama, T., S. Ohtsuka, H. Nagata and S. Tanaka, Fabrication of microcrystallites of II–VI compound semiconductors by laser ablation method 117 (1992) 156
Koyanagi, T., see Anno 117 (1992) 816
Koza, M., see Caneau 114 (1991) 481
Koza, M.A., see Caneau 118 (1992) 467
Koza, M.A., see Aspnes 120 (1992) 71
Kozlowsky, V.I., see Nasibov 117 (1992) 1040
Kôzuki, Y. and M. Itoh, Metastable crystal growth of the low temperature phase of barium metaborate from the melt 114 (1991) 683
Krasilnikov, A.B., see Aseev 115 (1991) 393
Krasilnikov, A.B., A.V. Latyshev, A.L. Aseev and S.I. Stenin, Monoatomic step clustering during superstructural transitions on Si(111) surface 116 (1992) 178
Kraus, M.M., see Waag 117 (1992) 820
Krawczyk, S.K., see Triboulet 117 (1992) 227
Krčmář, S., see Söhnel 112 (1991) 415
Krenn, H., see Springholz 113 (1991) 593
Krenn, H., see Enichlmair 117 (1992) 844
Křivánková, I., see Söhnel 112 (1991) 415
Kroemer, H., see Miller 111 (1991) 323
Kroemer, H., see Petroff 111 (1991) 360
Kroemer, H., see Chalmers 111 (1991) 647
Kropp, E., see Rudolph 118 (1992) 204
Krost, A., see Grundmann 115 (1991) 150
Krost, A., see Kolodziejczyk 117 (1992) 549
Krot, O.I., see Barilo 119 (1992) 403
Kubiak, R.A.A., see Powell 111 (1991) 907
Kubiak, R.A.A., see Pike 111 (1991) 925
Kubo, I., see Isoda 115 (1991) 388
Kubo, M. and T. Narusawa, A novel in-situ molecular beam epitaxy monitoring system using low energy ion scattering 111 (1991) 136
Kubo, S., see Fukatsu 111 (1991) 843
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Kudo, K., see Lee 115 (1991) 164
Kudo, Y., see Sato 115 (1991) 740
Kuech, T.F., The use of chloride based precursors in metalorganic vapor phase epitaxy 115 (1991) 52
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Kuhn, T.A., see Waag 117 (1992) 820
Kuhn, W., see Bauer 117 (1992) 297
Kuhn, W., see Wagner 117 (1992) 303
Kukimoto, H., see Otoma 115 (1991) 807
Kulakov, M.P. and I.V. Balyakina, Solid state wurtzite–sphalerite transformation and phase boundaries in ZnSe–CdSe 113 (1991) 653
Kumabe, H., see Nishimura 112 (1991) 791
Kumar, V., see Hartley 117 (1992) 166
Kumazaki, K., F. Iida, K. Ohno, K. Hatano and K. Imai, Lattice strain near interface of MBE-grown ZnTe on GaAs 117 (1992) 285
Kumazaki, K., see Imai 117 (1992) 406
Kumugawa, M., see Ozawa 115 (1991) 728
Kun, Z.K., D. Leksell and G.B. Brandt, Crystal growth aspects of the fabrication of high output thin film electroluminescent Edge Emitter^{TM} arrays 117 (1992) 987
Kuniyoshi, S., see Lee 115 (1991) 164
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Künzel, H., R. Kaiser, W. Passenberg, D. Trommer and G. Unterbörsch, Critical issues in the MBE growth of $Ga_{0.47}In_{0.53}As$ for waveguide/PIN/JFET integration 111 (1991) 1084
Kuo, J.M., see Asom 111 (1991) 246
Kuo, T.C., T.W. Kang and K.L. Wang, RHEED studies of epitaxial growth of CoGa on GaAs by MBE – determination of epitaxial phases and orientations 111 (1991) 996
Kuo, T.Y., see Cunningham 111 (1991) 515
Kurasawa, T., see Noda 115 (1991) 802
Kurata, H., see Isoda 115 (1991) 388
Kurdak, C., see Chin 111 (1991) 466
Kuribayashi, K., see Inatomi 114 (1991) 380
Kurita, T., see Uchida 114 (1991) 565
Kuriyama, K., N. Mineo and Y. Takahashi, Preparation and characterization of the

filled tetrahedral semiconductor LiZnP film on GaP(111) 113 (1991) 333
Kuriyama, M., see Inoue 112 (1991) 531
Kuriyama, M., see Steiner 114 (1991) 707
Kurlov, V.N., see Rossolenko 116 (1992) 185
Kurochkin, L.A., see Barilo 119 (1992) 403
Kuroda, T., see Maki 115 (1991) 567
Kuroda, Y., see Suemune 117 (1992) 1068
Kuroshima, S., see Tanigaki 114 (1991) 3
Kurtz, S.R., see Klem 111 (1991) 628
Kusaka, I., see Tomino 113 (1991) 633
Kushida, K., see Ito 112 (1991) 427
Kusunoki, T., C. Takenaka and K. Nakajima, LEC growth of InGaAs bulk crystal fed with a GaAs source 112 (1991) 33
Kusunoki, T., see Nakajima 113 (1991) 485
Kusunoki, T., see Takenaka 114 (1991) 293
Kusunoki, T., see Kato 115 (1991) 174
Kusunoki, T., C. Takenaka and K. Nakajima, Growth of ternary $In_{0.14}Ga_{0.86}As$ bulk crystal with uniform composition at constant temperature through GaAs supply 115 (1991) 723
Kuusisto, E., see Kudlek 117 (1992) 309
Kuusisto, E., see Imai 117 (1992) 406
Kuwabara, H., see Tatsuoka 117 (1992) 554
Kuwahara, H., see Wang 115 (1991) 261
Kuwano, N., see Matsumura 115 (1991) 194
Kuwano, N., T. Shiraishi, A. Koga, K. Oki, K. Hiramatsu, H. Amano, K. Itoh and I. Akasaki, Cross-sectional TEM study of microsctructures in MOVPE GaN films grown on α-Al_2O_3 with a buffer layer of AlN 115 (1991) 381
Kuwano, N., see Hiramatsu 115 (1991) 628
Kuwano, Y., see Kouta 114 (1991) 676
Kuwata-Gonokami, M., see Saiki 117 (1992) 802
Kuzmin, V.D., see Sabinina 117 (1992) 238
Kuznetsov, Yu.G., see Vekilov 119 (1992) 248
Kwo, J., Growth and properties of high T_c films in $Y_1Ba_2Cu_3O_{7-x}$ perovskite by molecular beam epitaxy 111 (1991) 965
Kwo, J., see Hong 111 (1991) 984
Kwo, J., see Hong 111 (1991) 1071
Kwon, O.-J., see Choi 115 (1991) 579
Kwon, Y., see Munns 120 (1992) 184

Labrosse, G., see Fikri 119 (1992) 41
Lacelle, C., see Roth 113 (1991) 379
Lacelle, C., see Roth 120 (1992) 212
Lacis, I., see Uhrig 117 (1992) 598
Lacklison, D.E., see Foxon 111 (1991) 539
Lacklison, D.E., C.T. Foxon, J. Zhang, B.A. Joyce and E.M. Gibson, RHEED studies of MOMBE growth using TMGa or TEGa with As_2 120 (1992) 50
Lagally, M.G., see Mo 111 (1991) 876
Laks, D.B., see Van de Walle 117 (1992) 704
Lambert, B., see Le Corre 120 (1992) 353
Lambert, M., L. Goldstein, A. Perales, F. Gaborit, C. Starck and J.-L. Lievin, High quality InP and $In_{1-x}Ga_xAs_yP_{1-y}$ grown by gas source MBE 111 (1991) 495
Lambert, M., see Goldstein 120 (1992) 157
Lambert, M., see Pagnod-Rossiaux 120 (1992) 317
Lamberti, C., see Genova 120 (1992) 333
Lambkin, J.D., see Emeny 111 (1991) 413
Lan, C.W. and S. Kou, Effects of rotation on heat transfer, fluid flow and interfaces in normal gravity floating-zone crystal growth 114 (1991) 517
Lan, C.W. and S. Kou, A simple method for improving the stability of float zones under normal gravity 118 (1992) 151
Lan, C.W. and S. Kou, Shortened floating zone crystal growth under normal gravity 119 (1992) 281
Landwehr, G., see Kuhn 117 (1992) 660
Landwehr, G., see Waag 117 (1992) 820
Landwehr, G., see Yakovlev 117 (1992) 854
Landwehr, G., see Kuhn 117 (1992) 871
Landwehr, G., see Uraltsev 117 (1992) 877
Lane, P.A., see Martin 120 (1992) 25
Lane, P.A., C.R. Whitehouse, T. Martin, M. Houlton, G.M. Williams, A.G. Cullis, S.S. Gill, J.R. Dawsey, G. Ball, B.T. Hughes, M.A. Crouch and M.B. Allenson, CBE growth of GaAs/GaAlAs HBTs using the new DEAlH–NMe_3 precursor and all-gaseous dopants 120 (1992) 245
Lang, A.R., see Walmsley 116 (1992) 225
Lang, D.V., see Chand 111 (1991) 20
Lang, M., see Hingerl 117 (1992) 341
Lang, M., J. Humenberger, K.H. Gresslehner and K. Lischka, Tunneling in metal–insulator–semiconductor structures on epitaxially grown p-type $Hg_{1-x}Cd_xTe$ 117 (1992) 954
Lange, M.D., see Faurie 111 (1991) 698
Langlais, F., C. Prebende and J.P. Couderc, Physical and chemical kinetic processes in the CVD of silicon from SiH_2Cl_2/H_2 gaseous mixtures in a vertical cylindrical hot-water reactor 113 (1991) 606
Lankes, S., see Wagner 117 (1992) 303
Lansari, Y., Z. Yang, S. Hwang, F.E. Reed, A.T. Sowers, J.W. Cook, Jr. and J.F. Schetzina, Very low temperature growth and doping of Hg-based epilayers and superlattices 111 (1991) 720
Lanzillotto, A.-M., see Santos 111 (1991) 366
Lao, Pudong, see Li 119 (1992) 322
Larsen, C.A., see Li 112 (1991) 515
Latyshev, A.V., see Aseev 115 (1991) 393
Latyshev, A.V., see Krasilnikov 116 (1992) 178

Laudise, R.A., W.A. Sunder, H.M. O'Bryan, D.J. Carlson and A.F. Witt, Czochralski growth of single crystals of $Ni_{3-x}Mn_xSn$ 118 (1992) 277
Lavallard, P., see Chamarro 117 (1992) 614
Lawson-Jack, S., see Brown 117 (1992) 536
Lazzarini, L., see Bernardi 113 (1991) 53
Le Corre, A., S. Durel, F. Clérot, B. Lambert, A. Poudoulec, S. Salaün and D. Lecrosnier, Critical layer thickness of $In_{0.82}Ga_{0.18}As/InP$ quantum wells 120 (1992) 353
Le Gouezigou, L., see Pagnod-Rossiaux 120 (1992) 317
Le Guillou, Y., see L'Haridon 113 (1991) 39
Le Roux, G., see Benchimol 120 (1992) 189
Leccabue, F., R. Panizzieri, B.E. Watts, D. Fiorani, E. Agostinelli, A. Testa and E. Paparazzo, Growth, thermodynamic and magneto-structural study of $FeGa_2O_4$ single crystals 112 (1991) 644
Leccabue, F., see Bocelli 113 (1991) 663
Lecomte, M., see Kakimoto 114 (1991) 715
Lecrosnier, D., see Le Corre 120 (1992) 353
Ledda, F., see Garbato 114 (1991) 299
Ledentsov, N.N., see Ivanov 111 (1991) 151
Lee, C.D., B.H. Lim, C. Lim, H.L. Park, C.H. Chung and S.K. Chang, Growth of ZnSe on (100) GaAs by atomic layer epitaxy 117 (1992) 148
Lee, C.D., see Chang 117 (1992) 793
Lee, C.Y., see Wu 112 (1991) 803
Lee, H.C., see Tran 113 (1991) 16
Lee, H.Y., see Hafich 111 (1991) 507
Lee, H.Y., M.J. Hafich, G.Y. Robinson, K. Mahalingam and N. Otsuka, Improved InGaP/GaAs heterointerfaces during gas-source MBE growth 111 (1991) 525
Lee, J., K. Kudo, S. Kuniyoshi, K. Tanaka, Y. Makita and A. Yamada, Formation of InAs microstructures on variously oriented GaAs substrates 115 (1991) 164
Lee, J.B., see Hartley 117 (1992) 166
Lee, J.S., see Kudo 111 (1991) 402
Lee, J.W., see McCrary 112 (1991) 39
Lee, J.Y., see Choi 115 (1991) 579
Lee, P., see Ren 112 (1991) 587
Lee, S.Y., see Hyun 117 (1992) 587
Lee, W.S., G.W. Yoffe, D.G. Schlom and J.S. Harris, Jr., Accurate measurement of MBE substrate temperature 111 (1991) 131
LeGoues, F.K., see Kesan 111 (1991) 936
Lei Gang, see Xu 117 (1992) 935
Leibenguth, R.E., see Asom 111 (1991) 246
Leibenguth, R.E., see Asom 111 (1991) 260
Leibenguth, R.E., see Asom 112 (1991) 597
Leising, G., see Ullrich 117 (1992) 902
Leising, G., see Ullrich 117 (1992) 925
Leitner, J., J. Mikulec, P. Voňka, J. Stejskal, R. Hladina and P. Klíma, Thermodynamic analysis of the deposition of GaAs epitaxial layers prepared by the MOCVD method 112 (1991) 437
Leksell, D., see Kun 117 (1992) 987
Lemoine, D., see Benhlal 117 (1992) 281
Lemonias, P.J., see Hoke 111 (1991) 269
Lemonias, P.J., see Hoke 111 (1991) 1024
Lenczowski, S.K.J., see Emmen 118 (1992) 477
Lequien, S., see Etienne 111 (1991) 1003
Levi, A.F.J., see Headrick 111 (1991) 838
L'Haridon, H., R. Callec, R. Coquillé, P.N. Favennec, J.P. Fillard, P. Gall, M. Ganeau and Y. Le Guillou, Inhomogeneity in a semi-insulating indium phosphide ingot 113 (1991) 39
Li, Aizhen, see Shen 111 (1991) 807
Li, Aizhen, see Cui 111 (1991) 811
Li, C.J., see Zhong 119 (1992) 74
Li, D., see Qiu 111 (1991) 747
Li, D., Y. Nakamura, N. Otsuka, J. Qiu, M. Kobayashi and R.L. Gunshor, Reconstruction structure at $Ge_2Se_3/GaAs$ epitaxial interface 111 (1991) 1038
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Li, H.D., see Tang 112 (1991) 407
Li, Hua, see Ming 115 (1991) 199
Li, Jie, Li He, Wei Shan, Xingyu Cheng and Shixin Yuan, Atomic layer epitaxy of $(CdTe)_m(ZnTe)_n$–ZnTe multiquantum wells on (001)GaAs substrate 111 (1991) 736
Li, Jie, see Shen 117 (1992) 470
Li, Jie, Li He, Nanchang Zhu, Pudong Lao and Shixin Yuang, Molecular beam epitaxial growth and characterization of ZnTe and ZnTe–CdTe superlattice 119 (1992) 322
Li, L., see Parfeniuk 119 (1992) 261
Li Ming, see Ji 112 (1991) 283
Li, Q., see Jiang 116 (1992) 93
Li Qingchun, see Liu 113 (1991) 289
Li, S.H., C.A. Larsen and G.B. Stringfellow, Radical reactions in pyrolysis of triethylarsine and diethylarsine 112 (1991) 515
Li Zhengdong, see Su 119 (1992) 368
Liang, B.W. and C.W. Tu, The roles of group-V species in metalorganic molecular-beam epitaxy and chemical-beam epitaxy of III–V compounds 111 (1991) 550
Licci, F., H.J. Scheel and P. Tissot, Determi-

nation of the eutectic composition by crystal growth and flux separation: example $BaCuO_2$–CuO_x 112 (1991) 600
Licci, F., C. Frigeri and H.J. Scheel, Effect of flux composition on crucible corrosion and aluminum distribution coefficient in YBCO single crystals 112 (1991) 606
Lievin, J.-L., see Lambert 111 (1991) 495
Lilja, J., see Kudlek 117 (1992) 309
Lilja, J., see Hingerl 117 (1992) 341
Lilja, J., see Imai 117 (1992) 406
Lim, B.H., see Lee 117 (1992) 148
Lim, C., see Lee 117 (1992) 148
Lin, C.H., see Wang 116 (1992) 483
Lin, Cheng-Hsiung, see Wang 114 (1991) 435
Lin, I.N., see Hu 114 (1991) 191
Lin, J.T., see Huang 119 (1992) 309
Lin, L.Y., see Zhong 119 (1992) 74
Linders, R.W.M., see Frijlink 115 (1991) 203
Linfield, E.H., see Ritchie 111 (1991) 300
Linfield, E.H., see Davies 111 (1991) 318
Link, P., see Wagner 117 (1992) 303
Lipsanen, H., see Ravila 114 (1991) 569
Lipton, H.L., see Luo 119 (1992) 407
Lischka, K., see Riesz 114 (1991) 127
Lischka, K., see Schmidt 117 (1992) 748
Lischka, K., see Lang 117 (1992) 954
Liu, B., A.H. McDaniel and R.F. Hicks, Modeling of the coupled kinetics and transport in the organometallic vapor-phase epitaxy of cadmium telluride 112 (1991) 192
Liu Jiming, see Yang 114 (1991) 351
Liu, Li-Qiang, Bai-Biao Huang, Hong-Wen Ren and Min-Hua Jiang, Surface adsorption and carbon incorporation in ALE GaAs growth process 115 (1991) 83
Liu, Q.M., see Jin 116 (1992) 524
Liu Qifu, see Liu 113 (1991) 289
Liu Qiyang, Li Qingchun and Liu Qifu, Epitaxial growth of silicon in a high purity Al–22 wt% Si alloy 113 (1991) 289
Liu, S.M.J., see Ho 111 (1991) 233
Liu, W.C., D.F. Guo, C.Y. Sun and W.S. Lour, Morphological defects on Be-doped AlGaAs layers grown by MBE 114 (1991) 700
Liu, W.K., see Yuen 111 (1991) 943
Liu, W.K., see Mokler 120 (1992) 290
Liu, Y.G., see Wang 116 (1992) 27
Liu, Y.X., Y. Rajakarunanayake and T.C. McGill, Excitons in II–VI heterostructures 117 (1992) 742
Liu, Y.X., M.W. Wang, J.O. McCaldin and T.C. McGill, Proposal for the formation of a minority carrier injecting contact on wide bandgap semiconductors 117 (1992) 913
Liu, Y.X., see Phillips 117 (1992) 1050
Liu Zu-Gang, see Zhang 117 (1992) 1012
Livescu, G., see Asom 111 (1991) 246
Livescu, G., see Asom 111 (1991) 260
Lo, S., see Ullrich 117 (1992) 902
Loginov, Y.Y., P.D. Brown, K. Durose, N. Thompson, A.A. Alnajjar, A.W. Brinkman and J. Woods, Transmission electron microscopic studies of n- and p-type doped CdTe 117 (1992) 259
Loginov, Y.Y., see Brown 117 (1992) 536
Loginov, Y.Y., P.D. Brown, N. Thompson and K. Durose, Transmission electron microscopic study of defect formation within II–VI compounds irradiated with 100 keV electrons 117 (1992) 682
Løken-Larsen, H., see Hardtdegen 116 (1992) 521
Lomako, I.D., see Barilo 119 (1992) 403
Lombardo, L.W. and A. Kapitulnik, Growth of $Bi_2Sr_2CaCu_2O_8$ single crystals using MgO crucibles 118 (1992) 483
Longenbach, K.F., L.F. Luo, S. Xin and W.I. Wang, Resonant tunneling in polytype InAs/AlSb/GaSb heterostructures 111 (1991) 651
Lopez, M., see Takano 111 (1991) 216
Lorberth, J., see Protzmann 115 (1991) 248
Lothian, J.R., see Abernathy 120 (1992) 234
Lour, W.S., see Liu 114 (1991) 700
Lousa, A., see Ferrater 113 (1991) 181
Lovergine, N., R. Cingolani, A.M. Mancini and M. Ferrara, Photoluminescence of CVD grown CdS epilayers on CdTe substrates 118 (1992) 304
Low, T.S., see Miller 111 (1991) 30
Lowe-Ma, C.K., see Vanderah 118 (1992) 385
Lu Jian, see Li 118 (1992) 371
Lu, K. and J.T. Wang, A micromechanism for crystallization of amorphous alloys. I. An in situ TEM observation 112 (1991) 525
Lu, K., M.L. Sui and J.T. Wang, A micromechanism for crystallization of amorphous alloys. II. Bulk crystallization process 113 (1991) 242
Lu, S.C., see Wu 112 (1991) 803
Lu Taijing, K. Toyoda, N. Nango and T. Ogawa, Detection and characterization of microdefects and microprecipitates in Si wafers by Brewster angle illumination using an optical fiber system 114 (1991) 64
Lu, Y.T., see Petroff 111 (1991) 360
Lube, E.L., see Zlatkin 118 (1992) 218
Luftman, H.S., see Panish 112 (1991) 343
Luginets, A.M., see Barilo 119 (1992) 403
Lui, M., see Metzger 111 (1991) 445
Łukasiewicz, T. and A. Majchrowski, Czochralski growth of TeO_2 single crystals under conditions of forced convection in the melt 116 (1992) 364
Lumley, J.L., see Ristorcelli 116 (1992) 447

Lummer, B., see Hoffmann 117 (1992) 640
Lummer, B., see Broser 117 (1992) 788
Lundager Madsen, H.E., On the surface energy of ionic crystals 112 (1991) 458
Lundager Madsen, H.E. and F. Christensson, Precipitation of calcium phosphate at 40 °C from neutral solution 114 (1991) 613
Lundager Madsen, H.E., Affinity and entropy production in electrolyte crystallization 118 (1992) 71
Lunn, B., see Ashenford 117 (1992) 233
Lunn, B., see Heimbrodt 117 (1992) 859
Lunn, B., see Jackson 117 (1992) 867
Lunn, B., see Goede 117 (1992) 886
Luo, H., see Samarth 111 (1991) 816
Luo, L.F., see Longenbach 111 (1991) 651
Luo, M., C.X. Zhang, D.W. Toth and H.L. Lipton, Addition of β-mercaptoethanol produced stable crystals of Theiler's virus 119 (1992) 407
Luo, Zundu, see Wang 116 (1992) 505
Lüth, H., see Tang 116 (1992) 1
Lüth, H., see Hardtdegen 116 (1992) 521
Lüth, H., see Kamp 120 (1992) 124
Luther, L.C., see Asom 111 (1991) 246
Luther, L.C., see Asom 111 (1991) 260
Lyman, P.F., S. Thevuthasan and L.E. Seiberling, Low temperature pseudomorphic growth of Ge on Si(100)-(2 × 1) 113 (1991) 45
Lyman, P.S., see Hoke 111 (1991) 269
Lyons, M.H., see Skevington 120 (1992) 328
Lyssenko, V.G., see Hvam 117 (1992) 773
Lyssenko, V.G., see Schwab 117 (1992) 778

Ma, J.S., see Moon 115 (1991) 589
Ma, W.J., see Zhong 119 (1992) 74
Mach, R., see Müller 117 (1992) 948
Mach, R., G.U. Reinsperger, G.O. Müller, B. Selle and G. Matzkeit, ZnS:Te, a blue electroluminescence emitter? 117 (1992) 1002
Machida, H. and T. Fukuda, Difficulties encountered during the Czochralski growth of TiO_2 single crystals 112 (1991) 835
MacKinnon, A., see Myers-Beaghton 111 (1991) 328
Mäder, K.A., see Von Känel 111 (1991) 889
Madhukar, A., see Chen 111 (1991) 424
Madhukar, A., see Guha 111 (1991) 434
Madhukar, A., see Kapre 111 (1991) 1110
Maeda, H., see Kimura 119 (1992) 313
Maeda, T., see Saito 111 (1991) 544
Maehashi, K., see Hasegawa 111 (1991) 371
Maejima, Y., see Oda 117 (1992) 193
Magnea, N., see Ulmer 111 (1991) 711
Magnea, N., see Bassani 117 (1992) 391
Magnea, N., see Pautrat 117 (1992) 454
Magnea, N., see Bleuse 117 (1992) 1046
Mahalingam, K., see Melloch 111 (1991) 39
Mahalingam, K., see Lee 111 (1991) 525
Maharizi, M., see Schieber 115 (1991) 31
Mahnke, H.-E., see Waldmann 117 (1992) 715
Maier, M., see Köhler 111 (1991) 295
Maier, M., see Springholz 113 (1991) 593
Maigne, P. and A.P. Roth, Structural characterization of InGaAs/GaAs superlattices grown on misoriented substrates 118 (1992) 117
Maigné, P., see Roth 120 (1992) 212
Majchrowski, A., see Łukasiewicz 116 (1992) 364
Makepeace, A.P.W., see Wierzchowski 114 (1991) 209
Makhniy, V.P., see Kosyachenko 117 (1992) 583
Maki, K., Y. Shigeta and T. Kuroda, Critical thickness for growth of epitaxial grains in silicon film deposited on superlattice surface of silicon (111) 115 (1991) 567
Makita, Y., see Kudo 111 (1991) 402
Makita, Y., see Lee 115 (1991) 164
Maksym, P.A., see McCoy 111 (1991) 178
Malik, R.J., see Nagle 111 (1991) 264
Mallard, R., see Cibert 117 (1992) 424
Mallecot, F., see Starck 120 (1992) 349
Manabe, K., see Koide 115 (1991) 639
Mancini, A.M., see Lovergine 118 (1992) 304
Mannaerts, J.P., see Hong 111 (1991) 984
Mannaerts, J.P., see Hong 111 (1991) 1052
Mannaerts, J.P., see Hong 111 (1991) 1071
Mantani, M., M. Sugiyama and T. Ogawa, Electronic measurement of concentration gradient around a crystal growing from a solution by using Mach–Zehnder interferometer 114 (1991) 71
Mäntylä, T.A., see Podkletnov 114 (1991) 198
Mao, Jianmin, see Zhou 111 (1991) 288
Maracas, G.N., see Puechner 111 (1991) 43
Maracas, G.N., see Droopad 114 (1991) 327
Maracas, G.N., see Shiralagi 114 (1991) 337
Maracas, G.N., see Edwards 120 (1992) 78
Maracas, G.N., see Droopad 120 (1992) 200
Marbeuf, A., R. Druilhe, R. Triboulet and G. Patriarche, Thermodynamic analysis of Zn–Cd–Te, Zn–Hg–Te and Cd–Hg–Te: phase separation in $Zn_xCd_{1-x}Te$ and in $Zn_xHg_{1-x}Te$ 117 (1992) 10
Marbeuf, A., D. Ballutaud, P. Martin, R. Triboulet, Y. Marfaing, J.E. Bonnet, K. Hricovini and R. Pinchaux, Angle-resolved photoemission study of $Zn_{0.15}Hg_{0.85}Te$: valence band determination 117 (1992) 197
Marchal, J.M., see Frijlink 115 (1991) 203
Marfaing, J., Y. Wang, V. Wadhawan, C. Boulesteix, J.P. Sorbier and P. Odier, Superconducting thick films from combined heat treatment of mixtures of YBaCuO and BiPbSrCaCuO 118 (1992) 27
Marfaing, Y., see Marbeuf 117 (1992) 197
Mariette, H., see Ulmer 111 (1991) 711
Mariette, H., see Pautrat 117 (1992) 454

Mariette, H., see Bleuse 117 (1992) 1046
Markl, J., J.P. Ströbel, M. Klauda and G. Saemann-Ischenko, Preparation of $Ln_{2-x}Ce_xCu_1O_{4-\delta}$ single crystals (Ln = Nd, Sm) by a modified flux flow method 113 (1991) 395
Markova, L.V., see Barilo 119 (1992) 403
Marković, M. and L. Brečević, The role of strontium in the precipitation system $CaCl_2$–$SrCl_2$–H_3PO_4–NaOH–H_2O–0.15M NaCl 118 (1992) 93
Marquardt, K., see Heuken 117 (1992) 336
Marquardt, K., see Guimarães 117 (1992) 1075
Marqueton, Y., see Benhlal 117 (1992) 281
Marschner, T., see Protzmann 115 (1991) 248
Marshall, T., see Olego 117 (1992) 324
Martel, D.C., see Svensson 111 (1991) 450
Marti Ceschin, A. and J. Massies, Strain induced 2D–3D growth mode transition in molecular beam epitaxy of $In_xGa_{1-x}As$ on GaAs(001) 114 (1991) 693
Martin, J.L., see Kean 111 (1991) 189
Martin, P., see Marbeuf 117 (1992) 197
Martin, P., see Hersee 120 (1992) 218
Martin, P.A., see Ho 111 (1991) 233
Martin, R.J., see Tamargo 111 (1991) 741
Martin, R.J., see Turco-Sandroff 111 (1991) 762
Martin, T., C.R. Whitehouse and P.A. Lane, Growth reactions and mechanisms in chemical beam epitaxy (CBE) 120 (1992) 25
Martin, T., see Lane 120 (1992) 245
Martini, L., see Tao 114 (1991) 279
Marumo, F., see Kouta 114 (1991) 676
Maruno, S., see Nakao 115 (1991) 313
Maruyama, H., K. Pak, K. Sakakibara, M. Nakamura, Y. Takano and H. Yonezu, Solid phase epitaxial growth of InP on GaAs 115 (1991) 180
Maruyama, K., see Ebe 115 (1991) 718
Maruyama, K., see Ueda 117 (1992) 266
Maruyama, M. Bienfait, J.G. Dash and G. Coddens, Interfacial melting of ice in graphite and talc powers 118 (1992) 33
Marzin, J.Y., see Gérard 111 (1991) 205
Masa, Y., see Seto 117 (1992) 271
Masalov, V.M., G.A. Emel'chenko and A.B. Mikhajlov, Hydrodynamics and oscillation of temperature in single crystal growth from high-temperature solutions with use of ACRT 119 (1992) 297
Mashikhin, A.Yu., see Tarabaev 114 (1991) 603
Mashita, M., see Kawakyu 114 (1991) 561
Maslow, V.V., see Borisov 112 (1991) 463
Mason, S., see Arterton 117 (1992) 1008
Massies, J., see Moisson 111 (1991) 141
Massies, J., see Etienne 111 (1991) 1003
Massies, J., see Marti Ceschin 114 (1991) 693
Massies, J., see Deparis 118 (1992) 414
Masu, K., see Kaneko 115 (1991) 643
Masumoto, K., see Mochizuki 115 (1991) 687
Masumoto, K., see Noda 115 (1991) 802
Masumoto, Y., see Kanemitsu 117 (1992) 316
Masumoto, Y., see Yamada 117 (1992) 484
Masumoto, Y., see Yamamoto 117 (1992) 488
Masumoto, Y., B. Fluegel, K. Meissner, S.W. Koch, R. Binder, A. Paul and N. Peyghambarian, Band-gap renormalization and optical gain formation in highly excited CdSe 117 (1992) 732
Masumoto, Y., see Sasaki 117 (1992) 768
Matabon, M., see Starck 120 (1992) 180
Matsubara, K., see Anno 117 (1992) 816
Matsuda, Y., see Katahama 115 (1991) 141
Matsuda, Y., see Terashima 115 (1991) 745
Matsue, H., see Kanemitsu 117 (1992) 316
Matsuhata, H., see Miki 111 (1991) 902
Matsui, J., see Kimura 116 (1992) 22
Matsuichi, K., see Fashe 111 (1991) 677
Matsumoto, K. and K. Uchida, Photoluminescence of deep levels induced by sub-ppm H_2O in AlGaAs grown by MOVPE 115 (1991) 484
Matsumoto, S., see Okada 116 (1992) 307
Matsumoto, T., T. Kato and E. Ishihara, Interface characterization of heteroepitaxial ZnSe layers on GaAs substrates by cathodoluminescence 115 (1991) 674
Matsumoto, T., N. Kokubo, K. Kawakami and T. Kato, Capacitance–voltage characterization of n-ZnSe/n-GaAs heterojunctions 117 (1992) 578
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Matsumura, N., K. Senga, J. Kakuta, T. Fukada and J. Saraie, Study on the behavior of surface adatoms during photoassisted MBE of ZnSe and improvement of surface morphology 115 (1991) 279
Matsumura, N., K. Senga, J. Kakuta and J. Saraie, Reflection high energy electron diffraction study on adatom desorption from ZnSe surface under electron beam irradiation and light irradiation 117 (1992) 129
Matsumura, S., K. Takano, N. Kuwano and K. Oki, Dynamical Monte Carlo simulation of $L1_1$(CuPt)-type ordering during (001) epitaxial growth of III–V semiconductor alloys 115 (1991) 194
Matsunami, H., see Yoshimoto 115 (1991) 265
Matsunami, H., see Yoo 115 (1991) 733
Matsuno, T., see Inoue 111 (1991) 313
Matsushima, Y., K. Yoshino, Y. Yamamoto, S.R. Tiong and M. Hiramatsu, The band profile of zinc sulfoselenide single crystals grown by sublimation method 117 (1992) 328
Mattera, V.D., see Asom 111 (1991) 246

Mattera, V.D., see Asom 111 (1991) 260
Mattey, N.L., see Powell 111 (1991) 907
Matuhata, H., see Yao 111 (1991) 221
Matz, R., see Heinecke 120 (1992) 376
Matzkeit, G., see Mach 117 (1992) 1002
Mauch, R.H., K.O. Velthaus, G. Bilger and H.W. Schock, High efficiency SrS,SrSe: $CeCl_3$ based thin film electroluminescent devices 117 (1992) 964
Maude, D.K., see Henini 111 (1991) 1089
Maurel, P., see Garcia 111 (1991) 578
Mavlonov, Sh., The phenomena of crystallization in centrifugal force fields and the dynamo effect 119 (1992) 167
May, P.G., see Kesan 111 (1991) 936
Mazelsky, R., see Singh 118 (1992) 78
Mazurowski, J., see Hersee 120 (1992) 218
McCaldin, J.O., see Rajakarunanayake 111 (1991) 782
McCaldin, J.O., see Phillips 111 (1991) 820
McCaldin, J.O., see Liu 117 (1992) 913
McCaldin, J.O., see Phillips 117 (1992) 1050
McCallum, D.S., see Hasenberg 111 (1991) 388
McCann, P.J. and C.G. Fonstad, Liquid phase epitaxial growth of PbSe on (111) and (100) BaF_2 114 (1991) 687
McCluskey, R.J., see Chaudhry 113 (1991) 120
McCoy, J.M. and P.A. Maksym, Monte Carlo simulation of MBE growth of the 2×4 reconstructed GaAs(001) surface 111 (1991) 178
McCrary, V.R., D.L. Van Haren, J.L. Zilko, J. Blaha, S.E.G. Slusky, J.W. Lee, S.N.G. Chu, P. Thomas and V. Swaminathan, Low pressure MOCVD in a vertical reactor: growth and characterization of In GaAsP on (100)InP for 1.3 μm lasers 112 (1991) 39
McCray, L.G.., see Metzger 111 (1991) 445
McDaniel, A.H., see Liu 112 (1991) 192
McDonald, K.A., see Young 118 (1992) 193
McFadden, G.B., see Brush 114 (1991) 446
McFadden, G.B., see Hardy 114 (1991) 467
McGill, T.C., see Collins 111 (1991) 664
McGill, T.C., see Chow 111 (1991) 683
McGill, T.C., see Rajakarunanayake 111 (1991) 782
McGill, T.C., see Phillips 111 (1991) 820
McGill, T.C., see Liu 117 (1992) 742
McGill, T.C., see Liu 117 (1992) 913
McGill, T.C., see Phillips 117 (1992) 1050
McInturff, D.T., see De Lyon 111 (1991) 564
McKee, R.A., see Walker 116 (1992) 235
McQueen, A.E.D., see Bell 117 (1992) 58
Meekes, G.J.B.M., see Dormans 114 (1991) 364
Meekes, H., see Vogels 116 (1992) 397
Meissner, K., see Masumoto 117 (1992) 732
Meissner, K., see Sasaki 117 (1992) 768
Melekh, B.T., see Volkov 119 (1992) 122
Melik-Adamyan, V.R., see Givargizov 112 (1991) 758
Mellet, R., see Hincelin 120 (1992) 119
Melloch, M.R., K. Mahalingam, N. Otsuka, J.M. Woodall and A.C. Warren, GaAs buffer layers grown at low substrate temperatures using As_2 and the formation of arsenic precipitates 111 (1991) 39
Melnik, V.V., see Kosyachenko 117 (1992) 583
Menke, D.R., see Qiu 111 (1991) 747
Menke, D.R., see Han 111 (1991) 767
Menken, M.J.V., A.J.M. Winkelman and A.A. Menovsky, Crystal growth of Bi-based (85 K) high-T_c superconducting compounds with a mirror furnace 113 (1991) 9
Menovsky, A.A., see Menken 113 (1991) 9
Mergy, J., see Caroli 118 (1992) 135
Metiu, H., see Petroff 111 (1991) 360
Metzener, P., see Hobbs 118 (1992) 319
Metzener, Ph., see Hobbs 112 (1991) 539
Metzger, R.A., A.S. Brown, W.E. Stanchina, M. Lui, R.G. Wilson, T.V. Kargodorian, L.G. McCray and J.A. Henige, Growth and characterization of low temperature AlInAs 111 (1991) 445
Meyer, B.K., W. Stadler, D.M. Hofmann, P. Omling, D. Sinerius and K.W. Benz, On the nature of the deep 1.4 eV emission bands in CdTe – a study with photoluminescence and ODMR spectroscopy 117 (1992) 656
Meyer, H.J., see Helmrich 112 (1991) 824
Meyer, J.L., see Eidelman 113 (1991) 643
Meyer, J.R., see Youngdale 111 (1991) 693
Meyer, R., see Hardtdegen 116 (1992) 521
Middleman, S., Some problems related to the performance of an evaporator as a vapor delivery system 114 (1991) 13
Migita, M., A. Taike and H. Yamamoto, n-Type and p-type conductivity control of ZnSe grown by metalorganic molecular beam epitaxy using methyliodide and ammonia 111 (1991) 776
Migita, M., see Ohsawa 116 (1992) 351
Mihailovic, see Chaput 112 (1991) 691
Mii, Y.J., see Wu 111 (1991) 252
Mikami, A., K. Terada, M. Yoshida and S. Nakajima, Chemical vapor deposition of ZnS:Tb electroluminescent films in a by-pass-HCl flow system 117 (1992) 991
Mikhajlov, A.B., see Masalov 119 (1992) 297
Mikheev, L.V. and A.A. Chernov, Mobility of a diffuse simple crystal–melt interface 112 (1991) 591
Miki, K., H. Okumura, K. Sakamoto, H. Matsuhata, T. Sakamoto and S. Yoshida, Structure dependence of photoluminescence in Ge_n/Si_m strained-layer superlattices 111 (1991) 902
Miklis, A., see Heinecke 111 (1991) 599
Miklis, A., see Heinecke 120 (1992) 376
Mikoshiba, N., see Sakuraba 115 (1991) 79

Mikoshiba, N., see Kaneko 115 (1991) 643
Mikulec, J., see Leitner 112 (1991) 437
Miles, R.H., see Chow 111 (1991) 683
Miller, J.N. and T.S. Low, Low-temperature growth of GaAs and AlGaAs by MBE and effects of post-growth thermal annealing 111 (1991) 30
Miller, M.M., see Vanderah 118 (1992) 385
Miller, M.S., C.E. Pryor, H. Weman, L.A. Samoska, H. Kroemer and P.M. Petroff, Serpentine superlattice: concept and first results 111 (1991) 323
Miller, M.S., see Petroff 111 (1991) 360
Minagawa, S., M. Kondow, H. Yanagisawa and T. Tanaka, Effect of cap layer and cooling atmosphere on the hole concentration of p(Zn)–AlGaInP grown by organometallic vapor phase epitaxy 118 (1992) 425
Minami, F., Y. Kato, K. Yoshida, K. Inoue and K. Era, Estimation of misfit strain in epitaxially grown ZnSe/GaAs with two-photon absorption spectroscopy 117 (1992) 565
Minami, F., see Inoue 117 (1992) 738
Minami, T., H. Sato, K. Ohashi, T. Tomofuji and S. Takata, Conduction mechanism of highly conductive and transparent zinc oxide thin films prepared by magnetron sputtering 117 (1992) 370
Minami, T., see Miyata 117 (1992) 1021
Minemura, T., J. Asano, K. Tsutsui and S. Furukawa, Crystallinity of heteroepitaxial GaAs layers grown on $(Ca,Sr)F_2/CaF_2/Si(100)$ structures by molecular beam epitaxy 114 (1991) 307
Minemura, T., see Yazawa 115 (1991) 519
Mineo, N., see Kuriyama 113 (1991) 333
Miner, C.J., see Wasilewski 111 (1991) 70
Ming, Nai-Ben and Hua Li, Twin lamella mechanism of fcc crystal growth: the Monte Carlo simulation approach 115 (1991) 199
Min'kov, G.M., see Germanenko 117 (1992) 850
Misawa, K., H. Yao, T. Hayashi and T. Kobayashi, Superradiative emission from CdS microcrystallites 117 (1992) 617
Misawa, S., see Okumura 120 (1992) 114
Mise, K., see Uchida 111 (1991) 1062
Mishima, T., see Gravesteijn 111 (1991) 916
Mishina, T., see Sasaki 117 (1992) 768
Missous, M., E.H. Rhoderick, K.E. Singer and W.S. Truscott, Comprehensive analysis of epitaxial $Al/Al_xGa_{1-x}As$ Schottky barriers made by MBE: barrier heights and band edge discontinuities 111 (1991) 1116
Mita, J., see Gao 117 (1992) 983
Mitrović, M.M. and R.I. Ristić, Growth rate dispersion of small $MnCl_2 \cdot 4H_2O$ crystals. I. Growth without a magnetic field 112 (1991) 160
Mitrović, M.M., Growth rate dispersion of small $MnCl_2 \cdot 4H_2O$ crystals. II. Growth in a magnetic field 112 (1991) 171
Mitsui, K., see Takami 117 (1992) 16
Mitsuyu, T., see Ohkawa 111 (1991) 797
Mitsuyu, T., see Ohkawa 117 (1992) 375
Mitsuyu, T., see Saiki 117 (1992) 802
Miura, A., see Nakayama 115 (1991) 831
Miura, N., see Takeyama 117 (1992) 1081
Miya, T., see Ando 117 (1992) 362
Miyadera, H., see Muranaka 112 (1991) 808
Miyajima, T., see Akimoto 115 (1991) 683
Miyajima, T., see Okuyama 117 (1992) 139
Miyajima, T., H. Okuyama, K. Akimoto, Y. Mori, L. Wei and S. Tanigawa, Observation of point defects in ZnSe using the positron annihilation method 117 (1992) 694
Miyajima, T., see Nakano 117 (1992) 797
Miyake, H., see Sugiyama 113 (1991) 390
Miyake, H., see Sugiyama 118 (1992) 41
Miyake, R., see Yamada 111 (1991) 584
Miyamoto, A., see Halfpenny 113 (1991) 722
Miyamoto, T., see Uchida 120 (1992) 357
Miyamoto, Y., see Tanaka 117 (1992) 24
Miyao, M., see Nomura 111 (1991) 61
Miyao, M., E. Murakami, H. Etoh, K. Nakagawa and A. Nishida, High hole mobility in strained Ge channel of modulation-doped $p\text{-}Si_{0.5}Ge_{0.5}/Ge/Si_{1-x}Ge_x$ heterostructure 111 (1991) 912
Miyao, M., K. Nakagawa, N. Nakamura and T. Ohshima, Characterization and application of fine-patterned $Si/CoSi_2/Si$ double heterostructures fabricated by self-aligned, two-step MBE 111 (1991) 957
Miyashita, M., see Nishimura 112 (1991) 791
Miyashita, M., see Kadoiwa 115 (1991) 128
Miyata, T., T. Minami and S. Takata, Influence of Mn doping conditions on electroluminescent characteristics of ZnS:Mn thin-film electroluminescent (TFEL) devices using insulating ceramic 117 (1992) 1021
Miyazaki, N., H. Uchida, S. Hagihara, T. Munakata and T. Fukuda, Thermal stress analysis of bulk single crystal during Czochralski growth (comparison between anisotropic analysis and isotropic analysis) 113 (1991) 227
Mizuguchi, K., see Kadoiwa 115 (1991) 128
Mizuguchi, K., see Takami 117 (1992) 16
Mizuki, J., see Tatsumi 111 (1991) 961
Mizuki, J., see Kimura 116 (1992) 22
Mizuo, Y., see Tajima 114 (1991) 59
Mizutani, T., see Tsuda 111 (1991) 88
Mizutani, Y., see Harada 116 (1992) 243
Mo, Y.-M. and M.G. Lagally, Scanning tunneling microscopy studies of the growth process of Ge on Si(001) 111 (1991) 876

Möbus, M., N. Karl and T. Kobayashi, Structure of perylene-tetracarboxylic-dianhydride thin films on alkali halide crystal substrates 116 (1992) 495
Mochizuki, K., H. Iwata, M. Isshiki and K. Masumoto, Hetero-epitaxial growth of $Pb_{1-x}Cd_xS_{1-y}Se_y$ thin film by the hot-wall method 115 (1991) 687
Möck, P., see Rudolph 118 (1992) 204
Moeckly, B.H., see Norton 114 (1991) 258
Moerman, I., see Coudenys 114 (1991) 314
Mogi, I., see Nakahara 117 (1992) 830
Mohnkern, L.M., see Yanka 111 (1991) 715
Moir, S.A. and H. Jones, The effect of temperature gradient and growth rate on spacing between primary silicon particles in rapidly solidified hypereutectic aluminium–silicon alloys 113 (1991) 77
Moisson, J.M., F. Houzay, F. Barthe, J.M. Gérard, B. Jusserand, J. Massies and F.S. Turco-Sandroff, Surface segregation in III–V alloys 111 (1991) 141
Mokler, S.M., W.K. Liu, N. Ohtani and B.A. Joyce, RHEED studies of the growth of Si(001) by gas source MBE from disilane 120 (1992) 290
Möllmann, K.-P., see Herrmann 117 (1992) 758
Mollot, F., see Starck 120 (1992) 349
Monberg, E.M., see Chin 111 (1991) 466
Monterrat, E., see Pautrat 117 (1992) 454
Montgomery, R.K., see Abernathy 120 (1992) 234
Moon, J., T. Ito, J.S. Mo and A. Hiraki, Formation of TiN by nitridation of magnetron sputtered Ti films using microwave plasma CVD 115 (1991) 589
Moore, K.J., see Woodbridge 111 (1991) 339
Moore, M., see Wierzchowski 114 (1991) 209
Morenza, J.L., see Ferrater 113 (1991) 181
Mori, H., see Zhu 117 (1992) 400
Mori, K., see Sugiyama 113 (1991) 390
Mori, K., see Sugiyama 118 (1992) 41
Mori, Y., see Akimoto 115 (1991) 683
Mori, Y., see Akimoto 117 (1992) 420
Mori, Y., see Miyajima 117 (1992) 694
Morimoto, K., Effects of hydrides of the group V elements on the growth of ZnSe by metalorganic chemical vapor deposition 117 (1992) 111
Morimoto, S., see Tanaka 117 (1992) 997
Morishita, T., see Kita 115 (1991) 752
Morishita, T., see Hase 115 (1991) 788
Morishita, Y., see Isu 115 (1991) 423
Morishita, Y., see Isu 120 (1992) 45
Morishita, Y., see Goto 120 (1992) 382
Morita, Y. and T. Narusawa, Growth and characterization of Cu–Al–Se system by MBE 115 (1991) 811
Morita, Y., see Aibara 116 (1992) 289
Moriuchi, T., see Yoh 111 (1991) 643
Moriwaki, Y., see Iijima 112 (1991) 467
Moriwaki, Y., see Iijima 112 (1991) 571
Moriwaki, Y., see Iijima 116 (1992) 319
Moriyoshi, Y., see Okada 116 (1992) 307
Morkoç, H., see Biswas 113 (1991) 209
Morocoima, M., see Quintero 114 (1991) 661
Morozov, A.N., see Charniy 116 (1992) 369
Morozov, A.N., see Charniy 118 (1992) 163
Morris, D., see Roth 120 (1992) 212
Morris, G.C., S.K. Das and P.G. Tanner, Some factors affecting efficiencies of n-CdS/p-CdTe thin film solar cells 117 (1992) 929
Mörsch, G., see Kamp 120 (1992) 124
Mosovsky, J., see Asom 112 (1991) 597
Motakef, S., see Kelly 113 (1991) 254
Motakef, S., see Kelly 113 (1991) 265
Motakef, S., K.W. Kelly and K. Koai, Comparison of calculated and measured dislocation density in LEC-grown GaAs crystals 113 (1991) 279
Motakef, S., Fundamental considerations in creep-based determination of dislocation density in semiconductors grown from the melt 114 (1991) 47
Motakef, S., K.W. Kelly and K. Koai, Comparison of calculated and measured dislocation density in LEC-grown GaAs crystals (E) 116 (1992) 242
Motojima, S., see Kawaguchi 118 (1992) 309
Mühlberg, M., see Rudolph 118 (1992) 204
Mühlberg, M., see Pfeiffer 118 (1992) 269
Muhr, G.T., see Abernathy 111 (1991) 574
Mukai, K., M. Sugawara and S. Yamazaki, Interdiffusion process in InGaAs/InP quantum well structures 115 (1991) 433
Müller, E., see Von Känel 111 (1991) 889
Müller, G., see Rupp 113 (1991) 131
Müller, G., G. Neumann and W. Weber, The growth of homogeneous semiconductor crystals in a centrifuge by the stabilizing influence of the Coriolis force 119 (1992) 8
Müller, G.O., R. Mach, G.U. Reinsperger, E. Halden and G. Schulz, High-field electron transport in wide-gap II–VI compounds investigated by vacuum emission 117 (1992) 948
Müller, G.O., see Mach 117 (1992) 1002
Müller, M., see Woggon 117 (1992) 608
Müller, R., see Rothfritz 120 (1992) 130
Müller, R., see Tränkle 120 (1992) 240
Mullin, J.B., see Jones 117 (1992) 244
Mullin, J.B., see Aslam 117 (1992) 249
Mullin, J.B., see Jones 118 (1992) 1
Mullins, J.T. and T. Taguchi, Non-linear optical properties of the $Cd_{1-x}Zn_xS$: $Cd_{1-y}Zn_yS$ strained-layer superlattice system 117 (1992) 501
Mullins, J.T., see Brown 117 (1992) 536

Munakata, T., see Miyazaki 113 (1991) 227
Munekata, H., H. Ohno, R.R. Ruf, R.J. Gambino and L.L. Chang, p-Type diluted magnetic III–V semiconductors 111 (1991) 1011
Munns, G.O., see Sherwin 111 (1991) 594
Munns, G.O., see Sherwin 111 (1991) 605
Munns, G.O., see Sherwin 120 (1992) 162
Munns, G.O., M.E. Sherwin, T. Brock, G.I. Haddad, Y. Kwon, G.I. Ng and D. Pavilidis, InAlAs/InGaAs/InP sub-micron HEMTs grown by CBE 120 (1992) 184
Munson, S., see Pusey 113 (1991) 385
Murakami, E., see Miyao 111 (1991) 912
Murakami, H., T. Asahi, H. Amano, K. Hiramatsu, N. Sawaki and I. Akasaki, Growth of Si-doped $Al_xGa_{1-x}N$ on (0001) sapphire substrate by metalorganic vapor phase epitaxy 115 (1991) 648
Murakami, S., see Takigawa 117 (1992) 28
Murakami, S., Y. Sakachi, H. Nishino, T. Saito, K. Shinohara and T. Takigawa, Compositional profile of HgCdTe in metalorganic chemical vapor deposition (MOCVD) system with multinozzles 117 (1992) 33
Murakami, T., see Yasumura 117 (1992) 20
Murakami, T., see Takada 117 (1992) 44
Muranaka, Y., H. Yamashita, H. Miyadera and L. Breuilly, Synthesis of polycrystalline diamond films in CO_2/H_2 and $CO/CO_2/H_2$ systems 112 (1991) 808
Muranevich, E., see Galun 117 (1992) 666
Muranoi, T., PL and SIMS of vapor phase epitaxial ZnSe films 115 (1991) 679
Muranoi, T., p–n Junction diodes prepared in vapor-phase epitaxial ZnSe films using metallic Zn and Se 117 (1992) 1059
Murata, T., see Hattori 115 (1991) 607
Murawala, P.A., see Funato 117 (1992) 543
Murota, J., see Sakuraba 115 (1991) 79
Murota, J., see Kato 115 (1991) 117
Murota, J., see Kircher 115 (1991) 439
Murotani, T., see Nishimura 112 (1991) 791
Murotani, T., see Takami 117 (1992) 16
Murray, J.J., see Wu 111 (1991) 252
Mushiage, M., see Tanaka 111 (1991) 1043
Muthe, K.P., J.C. Vyas, G.P. Kothiyal, D.P. Gandhi, A.K. Debnath, S.K. Gupta, S.C. Sabharwal and M.K. Gupta, Thin film deposition of BaO by molecular beam epitaxy 118 (1992) 213
Myers, T.H., see Yanka 111 (1991) 715
Myers-Beaghton, A.K. and D.D. Vvedensky, Nonlinear diffusion equation for epitaxial growth and recovery on vicinal surfaces 111 (1991) 162
Myers-Beaghton, A.K., J.P.G. Taylor, D.D. Vvedensky, K.J. Hugill and A. MacKinnon, Growth kinetics and electronic characteristics of quantum wires 111 (1991) 328
Myerson, A.S., see Ginde 116 (1992) 41

Nabeta, H., see Kanemitsu 117 (1992) 316
Nadarajah, A., F. Rosenberger and J.I.D. Alexander, Effects of buoyancy-driven flow and thermal boundary conditions on physical vapor transport 118 (1992) 49
Nagai, S., N. Fujimura, T. Ito and K. Shiraishi, The crystallization and growth of the high-T_c phase in the Bi–Sr–Ca–Cu–O thin films 115 (1991) 769
Nagano, K., see Urano 115 (1991) 411
Nagao, S., Y. Inoue, E. Kawanishi and H. Gotoh, Residual impurities originating from AsH_3 in GS-MBE grown GaAs 111 (1991) 511
Nagao, S., M. Takashima, Y. Inoue, M. Katoh and H. Gotoh, Abruptness of GaAs/AlInP hetero-interfaces grown by GS-MBE 111 (1991) 521
Nagao, Y., see Nishimura 117 (1992) 119
Nagasawa, H. and Y. Yamaguchi, Suppression of etch pit and hillock formation on carbonization of Si substrate and low temperature growth of SiC 115 (1991) 612
Nagata, H., see Koyama 117 (1992) 156
Nagata, H., M. Yoshimoto and H. Koinuma, Hetero-epitaxial growth of CeO_2 film on GaAs(001) substrate by laser molecular beam epitaxy 118 (1992) 299
Nagata, Y., see Kanemitsu 117 (1992) 316
Nagle, J., R.J. Malik and D. Gershoni, A comparison of atomic carbon versus beryllium acceptor doping in GaAs grown by molecular beam epitaxy 111 (1991) 264
Nahory, R.E., see Tamargo 111 (1991) 741
Nahory, R.E., see Turco-Sandroff 111 (1991) 762
Nakagawa, K., see Miyao 111 (1991) 912
Nakagawa, K., see Miyao 111 (1991) 957
Nakahara, H., see Yao 111 (1991) 221
Nakahara, J., T. Nouchi, H. Arai, I. Mogi, G. Kido and J. Watanabe, Magneto-photoluminescence in $Cd_{1-x}Mn_xTe$ 117 (1992) 830
Nakai, H., see Yokota 112 (1991) 723
Nakai, S., see Halfpenny 113 (1991) 722
Nakajima, K., see Kusunoki 112 (1991) 33
Nakajima, K., Calculation of stresses in $In_{0.12}Ga_{0.88}As$ ternary bulk crystals with compositionally graded $In_{1-x}Ga_xAs$ layers on GaAs seeds 113 (1991) 477
Nakajima, K., T. Kusunoki and C. Takenaka, Growth of ternary $In_xGa_{1-x}As$ bulk crystals with a uniform composition through supply of GaAs 113 (1991) 485
Nakajima, K., see Takenaka 114 (1991) 293

Nakajima, K., Calculation of the compositional variation-slope of $In_{1-x}Ga_xAs$ grown from In–Ga–As solution by ramp-cooling 114 (1991) 633
Nakajima, K., see Anayama 115 (1991) 65
Nakajima, K., see Kato 115 (1991) 174
Nakajima, K., see Kondo 115 (1991) 231
Nakajima, K., see Domen 115 (1991) 529
Nakajima, K., see Kusunoki 115 (1991) 723
Nakajima, S., see Suzuki 115 (1991) 623
Nakajima, S., see Mikami 117 (1992) 991
Nakamura, A., see Tokizaki 117 (1992) 603
Nakamura, F., K. Taira, K. Funato and H. Kawai, Se and Te doping in LP-MOCVD-grown GaSb using H_2Se and DETe 115 (1991) 474
Nakamura, M., see Maruyama 115 (1991) 180
Nakamura, M., see Suzuki 117 (1992) 881
Nakamura, N., see Miyao 111 (1991) 957
Nakamura, T., see Ueda 115 (1991) 375
Nakamura, T., see Sandhu 120 (1992) 296
Nakamura, Y., see Han 111 (1991) 767
Nakamura, Y., see Takemura 111 (1991) 802
Nakamura, Y., see Li 111 (1991) 1038
Nakanishi, H., see Takemura 111 (1991) 802
Nakanishi, H., see Takemura 117 (1992) 144
Nakanishi, H., see Ando 117 (1992) 362
Nakanishi, K., see Suemune 117 (1992) 1068
Nakanishi, Y., see Tatsuoka 117 (1992) 554
Nakano, K., see Okuyama 117 (1992) 139
Nakano, K., P.J. Boyce, J.J. Davies and D. Wolverson, Raman studies of phosphorus-doped ZnSe 117 (1992) 331
Nakano, K., H. Okuyama, T. Miyajima and K. Akimoto, Polarization of I_2 emission in ZnSe epitaxial layers on (100) GaAs 117 (1992) 797
Nakao, S., H. Watatani, S. Maruno and M. Noda, Effects of discharge current and substrate temperature on the microstructure of diamond films deposited by DC plasma CVD 115 (1991) 313
Nakashima, H., see Hasegawa 111 (1991) 371
Nakata, Y., see Ueda 115 (1991) 375
Nakata, Y., O. Ueda and T. Fujii, Two-dimensional electron gas mobility in InGaAs/N-InAlAs heterostructures with ordered InGaAs grown on (110)-oriented InP substrates by molecular beam epitaxy 115 (1991) 504
Nakata, Y., see Yoshida 117 (1992) 75
Nakayama, T., A. Miura and M. Azuma, Thin film growth characteristics of charge transfer complexes 115 (1991) 831
Nakazawa, E., see Okamoto 117 (1992) 943
Namba, S., see Shimomura 111 (1991) 1105
Nancollas, G.H., see Ebrahimpour 113 (1991) 83
Nancollas, G.H., see Zhang 118 (1992) 287
Nanev, Chr.N., Instability of faceted crystal shapes growing under diffusion control 112 (1991) 235
Nango, N., see Lu 114 (1991) 64
Narlikar, A.V., P.K. Dutta, S.B. Samanta, O.N. Srivastava, P. Ramasamy, S.C. Sabarwal, M.K. Gupta and B.D. Padalia, STM studies of growth spirals in bulk single crystals of superconducting Y-123 and Bi-2122 116 (1992) 37
Narusawa, T., see Kubo 111 (1991) 136
Narusawa, T., see Yokogawa 115 (1991) 670
Narusawa, T., see Morita 115 (1991) 811
Narusawa, T., see Yokogawa 117 (1992) 480
Nasibov, A.S., V.I. Kozlowsky, P.V. Reznikov, Ya.K. Skasyrsky and Yu.M. Popov, Full color TV projector based on A_2B_6 electron-beam pumped semiconductor lasers 117 (1992) 1040
Naughton, M.J., see Ren 112 (1991) 587
Nayar, R.K., see Bindal 112 (1991) 386
Naylor, T., see Powell 111 (1991) 907
Neave, J.H., see Joyce 115 (1991) 338
Negrii, V.D., Dynamic and optical properties of screw dislocations introduced by plastic deformation of CdS crystals at 77–4.2 K 117 (1992) 672
Neikirk, D.P., see Chu 111 (1991) 26
Nekrasov, V.V., see Babijchuk 116 (1992) 529
Neubert, M., see Rudolph 118 (1992) 204
Neukirch, U., see Fricke 117 (1992) 783
Neumann, G., see Müller 119 (1992) 8
Neumark, G.F., see Van de Walle 117 (1992) 704
Neuroth, N., see Uhrig 117 (1992) 598
Newbury, R., see Davies 111 (1991) 318
Newman, R.C., see Woodhouse 120 (1992) 323
Newnham, R.E., see Rossetti, Jr. 116 (1992) 251
Newstead, S.M., see Powell 111 (1991) 907
Newstead, S.M., see Pike 111 (1991) 925
Ng, G.I., see Munns 120 (1992) 184
Nicholls, J.E., see Dhese 117 (1992) 91
Nicholls, J.E., see Jackson 117 (1992) 867
Nichols, D.T., see Sherwin 120 (1992) 162
Nicklin, R., see Woodhouse 120 (1992) 323
Nicodème, P., see Kakimoto 114 (1991) 715
Nicolas, J.L., see Frijlink 115 (1991) 203
Nieh, C.W., see Chow 111 (1991) 683
Niino, T., see Tatsumi 111 (1991) 961
Niki, S., W.S.C. Chang, H.H. Wieder and T.E. Van Eck, Molecular beam epitaxial growth and properties of highly strained $In_xGa_{1-x}As/GaAs$ multiple quantum wells 111 (1991) 419
Nishida, A., see Miyao 111 (1991) 912
Nishihara, T., see Goto 115 (1991) 816
Nishijima, Y., see Ebe 115 (1991) 718
Nishikawa, Y., M. Ishikawa, H. Sugawara, G. Hatakoshi and Y. Kokubun, Anomalous dependence of In incorporation on substrate temperature into Zn-doped InGaAlP grown by low-pressure MOCVD 112 (1991) 628

Nishikawa, Y., see Suzuki 113 (1991) 127
Nishikawa, Y., see Suzuki 115 (1991) 498
Nishikawa, Y., H. Sugawara and Y. Kokubun, Anomalous Mg incorporation behavior in InGaAlP grown by metalorganic chemical vapor deposition 119 (1992) 292
Nishimura, K., K. Sakai, Y. Nagao and T. Ezaki, Low temperature metalorganic vapor phase epitaxial growth of $Cd_xZn_{1-x}S$ on GaAs 117 (1992) 119
Nishimura, T., K. Kadoiwa, M. Miyashita, H. Kumabe and T. Murotani, Crack-free and low dislocation density GaAs-on-Si grown by 2-reactor MOCVD system 112 (1991) 791
Nishimura, T., see Kadoiwa 115 (1991) 128
Nishinaga, T., see Tanaka 111 (1991) 168
Nishinaga, T., see Suzuki 111 (1991) 173
Nishinaga, T., see Uen 115 (1991) 122
Nishinaga, T., see Sakawa 115 (1991) 145
Nishinaga, T. and T. Suzuki, The role of step kinetics in MBE of compound semiconductors 115 (1991) 398
Nishinaga, T., see Kinoshita 115 (1991) 561
Nishine, S., see Shigeta 111 (1991) 284
Nishino, H., see Takigawa 117 (1992) 28
Nishino, H., see Murakami 117 (1992) 33
Nishino, S., see Takahashi 115 (1991) 617
Nishio, M., H. Ogawa and A. Yoshida, Effect of Ar laser-illumination upon ZnTe growth in atmospheric-pressure MOVPE 115 (1991) 284
Nishioka, K., see Tomino 113 (1991) 633
Nishiyama, I., see Ohshita 115 (1991) 551
Nishizawa, J., see Sakurai 112 (1991) 153
Nishizawa, J., Molecular layer epitaxy and its fundaments 115 (1991) 12
Nishizawa, J., see Suzuki 115 (1991) 498
Nissen, H.-U., see Von Känel 111 (1991) 889
Nistor, S.V., see Voda 119 (1992) 339
Nitta, S., K. Ogawa, T. Furukawa, T. Itoh and S. Nonomura, Optical reflectance spectra of amorphous random multilayers and the classical localization of light 115 (1991) 515
Nittono, O., see Sugawara 115 (1991) 596
Noad, J.P., see Roth 113 (1991) 379
Noakes, T.C.Q., see Aslam 117 (1992) 249
Noda, K., see Konishi 117 (1992) 939
Noda, M., see Nakao 115 (1991) 313
Noda, S., see Tabuchi 115 (1991) 169
Noda, S., see Wang 115 (1991) 261
Noda, T., M. Tanaka and H. Sakaki, Characterization of lateral correlation length of interface roughness in MBE grown GaAs/AlAs quantum wells by mobility measurement 111 (1991) 348
Noda, Y., T. Kurasawa, Y. Furukawa and K. Masumoto, Growth of $AgGaS_2$ single crystals by chemical transport with halogen 115 (1991) 802
Noguchi, Y., see Yamada 120 (1992) 177
Noma, H., see Suzuki 117 (1992) 881
Noma, M., see Sohn 117 (1992) 907
Noma, M., S. Hosomi, S.H. Sohn and Y. Hamakawa, An effect of oxygen content on ZnS:TbOF green color thin film electroluminescent devices prepared by electron-beam evaporation method 117 (1992) 1030
Nomura, T., H. Ogasawara, M. Miyao and M. Hagino, Composition control of GaAsP grown by molecular beam epitaxy 111 (1991) 61
Nomura, Y., see Isu 115 (1991) 423
Nomura, Y., see Isu 120 (1992) 45
Nomura, Y., see Goto 120 (1992) 382
Nonomura, S., see Nitta 115 (1991) 515
Nordell, N. and J. Borlind, MOVPE growth of InP around reactive ion etched mesas 114 (1991) 92
Normandin, R., see Williams 111 (1991) 1066
Norton, M.G., E.S. Hellman, E.H. Hartford, Jr. and C.B. Carter, Early stages of growth of epitactic barium bismuth oxide films on single-crystal MgO 113 (1991) 716
Norton, M.G., B.H. Moeckly, C.B. Carter and R.A. Buhrman, Growth mechanism of $YBa_2Cu_3O_{7-\delta}$ thin films on vicinal MgO 114 (1991) 258
Norton, P., see Springholz 113 (1991) 593
Norwood, R.G., see Bordui 113 (1991) 61
Notari, A.C., B. Schrappe, P. Basmaji and O. Hipólito, Heavily Se spike-doped GaAs grown by molecular beam epitaxy 116 (1992) 518
Nottenburg, R.N., see Abernathy 120 (1992) 234
Nötzel, R., L. Däweritz and K. Ploog, Direct synthesis of semiconductor quantum wires by molecular-beam epitaxy on (311) surfaces 115 (1991) 318
Nouchi, T., see Nakahara 117 (1992) 830
Nouruzi-Khorasani, A., see Taylor 119 (1992) 221
Nozaki, K., see Kawaguchi 118 (1992) 309
Nozaki, S., see Yamada 111 (1991) 584
Nozaki, S., see Tokumitsu 120 (1992) 301
Numazawa, T., see Kimura 119 (1992) 313
Nunoshita, M., see Yasumura 117 (1992) 20
Nunoshita, M., see Takada 117 (1992) 44
Nurmikko, A.V., see Han 111 (1991) 767
Nurmikko, A.V., see Samarth 111 (1991) 816
Nurmikko, A.V., see Gunshor 115 (1991) 652
Nurmikko, A.V., R.L. Gunshor and M. Kobayashi, Optical properties and device prospects of ZnSe-based quantum structures 117 (1992) 432
Nurmikko, A.V., see Ren 117 (1992) 510
Nurmikko, A.V., see Xie 117 (1992) 1079
Nye, J.F., The rotting of temperate ice 113 (1991) 465

Obata, H., see Tatsuyama 115 (1991) 112
O'Bryan, H.M., see Laudise 118 (1992) 277
Oda, N., see Kawano 117 (1992) 171

Oda, N., T. Kanno, M. Saga, R. Oikawa and Y. Maejima, Composition characterization methods for HgCdTe epilayers grown by molecular beam epitaxy 117 (1992) 193
Oda, N., see Sone 117 (1992) 218
Oda, N., see Sasaki 117 (1992) 222
Oda, O., see Imaizumi 115 (1991) 443
Odier, P., see Marfaing 118 (1992) 27
O'Donnell, K.P., see Parbrook 117 (1992) 492
O'Donnell, K.P., P.J. Parbrook, F. Yang, X. Chen, D.J. Irvine, C. Trager-Cowan, B. Henderson, P.J. Wright and B. Cockayne, The optical properties of wide bandgap binary II–VI superlattices 117 (1992) 497
O'Donnell, K.P., see Trager-Cowan 117 (1992) 532
O'Donnell, K.P., Y. Fujii, P.J. Parbrook and I. Suemune, Are localized excitons responsible for lasing in disordered short period II–VI strained layer superlattices? 117 (1992) 1077
Ogasawara, H., see Nomura 111 (1991) 61
Ogasawara, M., H. Kamada and Y. Imamura, Characterization of InP grown by low-pressure MOVPE using ethyldimethylindium and tertiarylbutylphosphine 115 (1991) 254
Ogawa, H., see Nishio 115 (1991) 284
Ogawa, K., see Nitta 115 (1991) 515
Ogawa, T., see Lu 114 (1991) 64
Ogawa, T., see Mantani 114 (1991) 71
Ogihara, S., see Yase 116 (1992) 333
Oguchi, T., see Katayama-Yoshida 117 (1992) 625
Oguri, H., K.S. Park, M. Isshiki and Y. Furukawa, Growth of $ZnSe_{1-x}Te_x$ thin films by metalorganic chemical vapour deposition 117 (1992) 116
Oh, E.-S., see Samarth 111 (1991) 816
Ohashi, K., see Minami 117 (1992) 370
Ohata, K., see Hase 115 (1991) 788
Ohba, Y., see Hatano 115 (1991) 455
Ohishi, M., H. Saito, H. Torihara, Y. Fujisaki and K. Ohmori, Ultraviolet irradiation effect on the MBE growth of ZnSe/GaAs observed by RHEED 111 (1991) 792
Ohishi, M., H. Saito, M. Yoneta and Y. Fujisaki, Low temperature growth of ZnSe/GaAs using hot molecular beams 117 (1992) 125
Ohkawa, K., T. Karasawa and T. Mitsuyu, Doping of nitrogen acceptors into ZnSe using radical beam during MBE growth 111 (1991) 797
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Ohkawa, K., see Saiki 117 (1992) 802
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Ohki, A., see Ando 117 (1992) 560
Ohki, Y., see Hiratani 111 (1991) 570
Ohki, Y., see Hiratani 115 (1991) 74
Ohki, Y., Y. Hiratani and M. Sasaki, Large difference in the decomposition rate of metalorganics between on As- and Ga-saturated GaAs (111)B surfaces 115 (1991) 226
Ohkoshi, H., see Uchida 114 (1991) 565
Ohmori, K., see Ohishi 111 (1991) 792
Ohnishi, T., see Oka 117 (1992) 840
Ohno, H., see Munekata 111 (1991) 1011
Ohno, K., see Kumazaki 117 (1992) 285
Ohno, T., Growth of small particles of iron–cobalt alloys prepared by gas-evaporation technique 115 (1991) 602
Ohori, T., see Kikkawa 115 (1991) 448
Ohsawa, J., A. Tomita and M. Migita, LPE growth of undoped n-type GaAs at 636°C with extremely low compensation 116 (1992) 351
Ohshima, N., Y. Koide, S. Zaima and Y. Yasuda, Atomic mixing phenomena and changes in faceted structure of Ge films grown on (100)Si by thermal annealing 115 (1991) 106
Ohshima, T., see Miyao 111 (1991) 957
Ohshita, Y., F. Uesugi and I. Nishiyama, Reaction of Si_2H_6 molecule on a silicon surface 115 (1991) 551
Ohtani, N., see Mokler 120 (1992) 290
Ohtsuka, N., see Sakuma 114 (1991) 31
Ohtsuka, N., see Ueda 115 (1991) 133
Ohtsuka, N., see Sakuma 115 (1991) 324
Ohtsuka, N., K. Kodama, M. Ozeki and Y. Sakuma, Extremely high Be doping of InGaAs by low-temperature atomic layer epitaxy 115 (1991) 460
Ohtsuka, S., see Koyama 117 (1992) 156
Ohuchi, F.S., T. Shimada, B.A. Parkinson, K. Ueno and A. Koma, Growth of $MoSe_2$ thin films with Van der Waals epitaxy 111 (1991) 1033
Oikawa, R., see Oda 117 (1992) 193
Oikawa, S., see Tsuda 115 (1991) 556
Oka, Y., T. Ohnishi, H. Sato and I. Souma, Spin correlation and dynamics of excitons in $Cd_{1-x}Mn_xTe$, $Cd_{1-x}Mn_xSe$ and $Cd_{1-x}Co_xSe$ 117 (1992) 840
Oka, Y., see Suzuki 117 (1992) 881
Okada, K., S. Komatsu, T. Ishigaki, S. Matsumoto and Y. Moriyoshi, Spontaneous growth of whiskers from an interlayer of Mo_2C beneath a diamond particle deposited in a combustion-flame 116 (1992) 307
Okada, M., see Yase 116 (1992) 333
Okada, M., see Ekawa 117 (1992) 254
Okada, M., see Yase 118 (1992) 348
Okada, T., see Ando 117 (1992) 362
Okada, Y., see Yao 111 (1991) 221

Okajima, M. and T. Tohda, Heteroepitaxial growth of MnS on GaAs substrates 117 (1992) 810
Okamoto, A., see Furuhata 112 (1991) 1
Okamoto, K., see Katoh 112 (1991) 368
Okamoto, N., see Shimomura 111 (1991) 1105
Okamoto, N., see Ando 115 (1991) 464
Okamoto, N., see Ando 120 (1992) 228
Okamoto, N., see Sandhu 120 (1992) 296
Okamoto, S., E. Nakazawa and T. Suzuki, Single insulating thin-film cold cathode using hot electrons in II–IV compounds 117 (1992) 943
Okamoto, T., see Yoshikawa 115 (1991) 274
Okamoto, T., see Yoshikawa 117 (1992) 107
Okamura, S., see Igasaki 112 (1991) 797
Okano, Y., see Shigeta 111 (1991) 284
Okano, Y., see Kan 119 (1992) 215
Okano, Y., see Kawasaki 119 (1992) 317
Okashita, K., see Hirota 112 (1991) 55
Okazaki, J., see Kondo 115 (1991) 231
Oki, K., see Matsumura 115 (1991) 194
Oki, K., see Kuwano 115 (1991) 381
Oki, K., see Hiramatsu 115 (1991) 628
Okumura, H., see Miki 111 (1991) 902
Okumura, H., see Cibert 117 (1992) 424
Okumura, H., S. Yoshida, S. Misawa and E. Sakuma, Epitaxial growth of GaAs and GaN by gas source molecular beam epitaxy using organic group V compounds 120 (1992) 114
Okuno, Y., see Kaneko 111 (1991) 638
Okuno, Y., H. Asahi, T. Kaneko, Y. Itani, K. Asami and S. Gonda, MOMBE growth of AlGaSb 115 (1991) 236
Okuno, Y., see Asahi 120 (1992) 252
Okuyama, F., S. Aoyama and Y. Fujimoto, A new approach to corona needle growth based on geometrical and structural analyses 114 (1991) 107
Okuyama, H., see Akimoto 115 (1991) 683
Okuyama, H., K. Nakano, T. Miyajima and K. Akimoto, Epitaxial growth of Zn MgSSe on GaAs substrate by molecular beam epitaxy 117 (1992) 139
Okuyama, H., see Akimoto 117 (1992) 420
Okuyama, H., see Miyajima 117 (1992) 694
Okuyama, H., see Nakano 117 (1992) 797
Olego, D.J., J. Petruzzello, T. Marshall and D. Cammack, Spectroscopy of bound and free holes in p-type ZnSe layers 117 (1992) 324
Olszyna, A., see Sokołowska 116 (1992) 507
Omino, A. and T. Suzuki, Bridgman growth of ZnSe crystals with a PBN crucible sealed in a molybdenum capsule 117 (1992) 80
Omling, P., see Meyer 117 (1992) 656
O'Neill, L., see Halfpenny 113 (1991) 722
Ono, K., see Saito 111 (1991) 544
Ono, S., see Sakuraba 115 (1991) 79
Ono, S., see Kato 115 (1991) 117
Ono, S., see Kircher 115 (1991) 439
Ono, S., see Yamauchi 115 (1991) 660
Ono, Y.A., see Ando 117 (1992) 969
Onuma, K., see Sakai 116 (1992) 421
Oosterbaan, S.J.M., see Vogels 114 (1991) 239
Opitz, B., see Kayser 112 (1991) 111
Orazem, M.E., see Jansen 112 (1991) 316
Orders, P.J., see Hartley 117 (1992) 166
Osaka, J., see Kanisawa 115 (1991) 348
Osofsky, M.S., see Vanderah 118 (1992) 385
Ospelt, M., see Von Känel 111 (1991) 889
Ossau, W., see Kuhn 117 (1992) 660
Ossau, W., see Waag 117 (1992) 820
Ossau, W., see Yakovlev 117 (1992) 854
Ossau, W., see Kuhn 117 (1992) 871
Osuga, D.T., see Feeney 113 (1991) 417
Oswald, P., see Géminard 114 (1991) 640
Otálora, F., see García-Ruiz 118 (1992) 160
Otani, S., T. Tanaka and Y. Ishizawa, Effect of PrB_6 addition to LaB_6 crystals grown by the floating zone method 113 (1991) 329
Otani, S. and Y. Ishizawa, Preparation of LaB_6 single crystals by the traveling solvent floating zone method 118 (1992) 461
Otoma, H., T. Honda, K. Hara, J. Yoshino and H. Kukimoto, Growth of $CuGaS_2$ by alternating-source-feeding MOVPE 115 (1991) 807
Otsuka, N., see Melloch 111 (1991) 39
Otsuka, N., see Lee 111 (1991) 525
Otsuka, N., see Qiu 111 (1991) 747
Otsuka, N., see Han 111 (1991) 767
Otsuka, N., see Takemura 111 (1991) 802
Otsuka, N., see Samarth 111 (1991) 816
Otsuka, N., see Li 111 (1991) 1038
Otsuka, N., see Gunshor 115 (1991) 652
Otsuka, N., see Xie 117 (1992) 1079
Ouazzani, J., see Alexander 113 (1991) 21
Oude Hengel, R. and F. Fisher, TSZM growth of β-BaB_2O_4 crystals 114 (1991) 656
Ourmazd, A., see Chin 111 (1991) 466
Ourmazd, A., see Cunningham 111 (1991) 515
Oussena, M., see Gagnon 114 (1991) 186
Ovrutsky, A.M., Numerical analysis of faceted shape stability during growth from stagnant solutions 116 (1992) 158
Oyama, Y., see Suzuki 115 (1991) 498
Ozaki, H., see Imai 117 (1992) 406
Ozaki, K., see Tanaka 117 (1992) 24
Ozasa, K., see Yoshimoto 115 (1991) 265
Ozawa, S., see Yoshida 113 (1991) 221
Ozawa, T., Y. Hayakawa and M. Kumagawa, Interface instability in the growth of $Ga_{1-x}In_xAs_ySb_{1-y}$ and thermodynamic considerations 115 (1991) 728
Ozeki, M., see Sakuma 114 (1991) 31
Ozeki, M., see Ueda 115 (1991) 133
Ozeki, M., see Sakuma 115 (1991) 324

Ozeki, M., see Ohtsuka 115 (1991) 460
Ozeki, M., see Takanohashi 115 (1991) 538

Padalia, B.D., see Narlikar 116 (1992) 37
Paek, M.-C., see Choi 115 (1991) 579
Pagés, O., M.A. Renucci, O. Briot, T. Cloitre and R.L. Aulombard, Depth profiling of carriers in ZnSe/GaAs heterostructures by Raman spectroscopy 117 (1992) 569
Pagnod-Rossiaux, Ph., M. Lambert, F. Gaborit, F. Brillouet, P. Garabedian and L. Le Gouezigou, Growth of semi-insulating InP by GSMBE 120 (1992) 317
Pain, G.N., see Gao 112 (1991) 487
Pain, G.N., see Wielunski 117 (1992) 460
Pak, K., see Takano 111 (1991) 216
Pak, K., see Maruyama 115 (1991) 180
Pakalnis, S., see Baltramiejūnas 117 (1992) 622
Palazoglu, A., see Young 118 (1992) 193
Palfrey, H.D., see Archer 117 (1992) 177
Palmer, J., see Ando 117 (1992) 560
Palosz, W., see Wiedemeier 119 (1992) 79
Pan Feng, see Huang 112 (1991) 729
Pan Feng, see He 113 (1991) 157
Pan Feng, see He 113 (1991) 161
Pan Rfen, see Su 119 (1992) 368
Panek, M., see Helak 115 (1991) 294
Panish, M.B., R.A. Hamm, D. Ritter, H.S. Luftman and C.M. Cotell, Redistribution of beryllium in InP and $Ga_{0.47}In_{0.53}As$ grown by hydride source molecular beam epitaxy and metalorganic molecular beam epitaxy 112 (1991) 343
Panizzieri, R., see Leccabue 112 (1991) 644
Pantelides, S.T., see Van de Walle 117 (1992) 704
Pantke, K.-H., J. Erland and J.M. Hvam, Picosecond spectroscopy of exciton–biexciton transitions in CdSe 117 (1992) 763
Pao, Y.C. and J.S. Harris, Jr., Molecular beam epitaxial growth and structural design of $In_{0.52}Al_{0.48}As/In_{0.53}Ga_{0.47}As/InP$ HEMTs 111 (1991) 489
Paparazzo, E., see Leccabue 112 (1991) 644
Papuzza, C., see Genova 120 (1992) 333
Paradies, C., see Singh 118 (1992) 78
Parbrook, P.J., B. Henderson, K.P. O'Donnell, P.J. Wright and B. Cockayne, Critical thickness of common-anion II–VI strained layer superlattices (SLSs) 117 (1992) 492
Parbrook, P.J., see O'Donnell 117 (1992) 497
Parbrook, P.J., see Trager-Cowan 117 (1992) 532
Parbrook, P.J., see O'Donnell 117 (1992) 1077
Parfeniev, R.V., see Volkov 119 (1992) 122
Parfeniuk, C., F. Weinberg, I.V. Samarasekera, C. Schvezov and L. Li, Measured critical resolved shear stress and calculated temperature and stress fields during growth of CdZnTe 119 (1992) 261
Park, H.-H., see Choi 115 (1991) 579
Park, H.L., see Lee 117 (1992) 148
Park, H.L., see Chang 117 (1992) 793
Park, K.S., see Oguri 117 (1992) 116
Park, K.S., see Isshiki 117 (1992) 410
Parker, E.H.C., see Powell 111 (1991) 907
Parker, E.H.C., see Pike 111 (1991) 925
Parkinson, B.A., see Ohuchi 111 (1991) 1033
Parry, C., see Powell 111 (1991) 907
Parsons, J.D., Inverted-vertical OMVPE reactor: design and characterization 116 (1992) 387
Parthier, L., see Rudolph 118 (1992) 204
Partin, D.L., J. Heremans and C.M. Thrush, Indium antimonide doped with lead telluride grown by molecular beam epitaxy 111 (1991) 614
Partin, D.L., see Youngdale 111 (1991) 693
Pashley, D.W., see Fawcett 116 (1992) 81
Passenberg, W., see Künzel 111 (1991) 1084
Paszkiewicz, R., see Helak 115 (1991) 294
Pate, M.A., see Claxton 111 (1991) 1080
Patel, H. and M.E. Pemble, External reflection IR spectroscopy from trimethylgallium adsorbed at a GaAs(100) surface at 300 K – a feasibility study 116 (1992) 511
Patriarche, G., see Marbeuf 117 (1992) 10
Patterson, I.P., see Armitage 117 (1992) 1082
Paul, A., see Masumoto 117 (1992) 732
Pauli, H., see Kudlek 117 (1992) 290
Paulsson, G., K. Deppert, S. Jeppesen, J. Jönsson, L. Samuelson and P. Schmidt, Reflectance-difference probing of surface kinetics of (001) GaAs during vacuum chemical epitaxy 111 (1991) 115
Paulsson, G., see Deppert 120 (1992) 88
Pautrat, J.L., E. Monterrat, L. Ulmer, N. Magnea, H. Mariette, J. Bleuse and P.H. Jouneau, Band gap engineering in II–VI based heterostructures 117 (1992) 454
Pautrat, J.L., see Bleuse 117 (1992) 1046
Pavilidis, D., see Munns 120 (1992) 184
Peacock, D.C., see Ritchie 111 (1991) 300
Peacock, D.C., see Davies 111 (1991) 318
Pearah, P.J., see Tower 114 (1991) 665
Pearton, S.J., see Abernathy 111 (1991) 574
Pearton, S.J., see Abernathy 113 (1991) 412
Pearton, S.J., see Abernathy 120 (1992) 234
Peisach, M., see Galun 117 (1992) 666
Pelekanos, N., see Han 111 (1991) 767
Pelletier, C.M., see Granger 117 (1992) 203
Pelosi, C., see Bocelli 113 (1991) 663
Pemble, M.E., see Joyce 115 (1991) 338
Pemble, M.E., see Patel 116 (1992) 511
Pemble, M.E., see Armstrong 120 (1992) 94
Peng, J.G., see Chen 118 (1992) 109
Peng Rui-wu, Xu Fei and Ding Yong-qing, Kinetic and interface studies for MOCVD CdTe and HgCdTe epilayers grown on GaAs substrates 115 (1991) 698

Pepper, M., see Davies 111 (1991) 318
Perales, A., see Lambert 111 (1991) 495
Perkowitz, S., see Dubowski 117 (1992) 862
Perls, H., see Broser 117 (1992) 788
Pesek, A., see Riesz 114 (1991) 127
Pesek, A., see Kudlek 117 (1992) 290
Pessa, M., see Kudlek 117 (1992) 309
Pessa, M., see Hingerl 117 (1992) 341
Pessa, M., see Imai 117 (1992) 406
Pessa, M., see Zhang 120 (1992) 172
Peter, G., see Dubowski 117 (1992) 862
Peter, L.M., see Berlouis 117 (1992) 918
Pet'kov, I.S., see Rossolenko 116 (1992) 185
Petrauskas, M., see Woggon 117 (1992) 608
Petroff, F., see Etienne 111 (1991) 1003
Petroff, P.M., see Miller 111 (1991) 323
Petroff, P.M., M.S. Miller, Y.T. Lu, S.A. Chalmers, H. Metiu, H. Kroemer and A.C. Gossard, MBE growth of tilted superlattices: advances and novel structures 111 (1991) 360
Petruzello, J., see Olego 117 (1992) 324
Petty, J.T., see Barber 112 (1991) 613
Peyghambarian, N., see Koch 117 (1992) 592
Peyghambarian, N., see Masumoto 117 (1992) 732
Peyghambarian, N., see Sasaki 117 (1992) 768
Peyre, J.-L., see Starck 120 (1992) 349
Pfeiffer, L.N., H.L. Störmer, K. West and K.W. Baldwin, Quantum wire structures by MBE overgrowth on a cleaved edge 111 (1991) 333
Pfeiffer, L.N., see Eaglesham 111 (1991) 833
Pfeiffer, M. and M. Mühlberg, Interface shape observation and calculation in crystal growth of CdTe by the vertical Bridgman method 118 (1992) 269
Philipp, F., see Brandt 115 (1991) 99
Phillipp, F., see Brandt 111 (1991) 383
Phillips, M.C., E.T. Yu, Y. Rajakarunanayake, J.O. McCaldin, D.A. Collins and T.C. McGill, Characterization of CdSe/ZnTe heterojunctions 111 (1991) 820
Phillips, M.C., J.F. Swenberg, Y.X. Liu, M.W. Wang, J.O. McCaldin and T.C. McGill, Forming of Al-doped ZnTe epilayers grown by molecular beam epitaxy 117 (1992) 1050
Piao, Z.S., see Shen 117 (1992) 519
Pickenhain, R., see Keller 118 (1992) 176
Piechotka, M., M. Zha and E. Kaldis, A novel method for nucleation control of mercuric iodide from the vapour phase 113 (1991) 251
Piechotka, M., see Zha 115 (1991) 43
Piekarczyk, W., Diamond–vapour interface and processes proceeding on it during growth of diamond crystals. I. Diamond (111) face 119 (1992) 345
Pier, Th., see Heimbrodt 117 (1992) 859
Pierrot, P.L.M., see Vogels 114 (1991) 239
Pike, W.T., L.M. Brown, R.A.A. Kubiak, S.M. Newstead, A.R. Powell, E.H.C. Parker and T.E. Whall, The determination of strain in Si–Ge superlattices by electron diffraction in a scanning transmission electron microscope 111 (1991) 925
Pinard, P., see Chibani 113 (1991) 681
Pinchaux, R., see Marbeuf 117 (1992) 197
Ploog, K., see Crook 111 (1991) 184
Ploog, K., A. Fischer, L. Tapfer and B.F. Feuerbacher, Narrow luminescence linewidth in GaAs single quantum wells by insertion of thin AlAs smoothing layers 111 (1991) 344
Ploog, K., see Brandt 111 (1991) 383
Ploog, K., see Brandt 115 (1991) 99
Ploog, K., see Nötzel 115 (1991) 318
Plotz, W.M., K. Hingerl and H. Sitter, Monte Carlo simulation of epitaxial growth in MBE and ALE mode 115 (1991) 186
Plovnick, R.H., Crystallization of brushite from EDTA-chelated calcium in agar gels 114 (1991) 22
Podkletnov, E.E., R.J.Ↄ. Järvinen, P.T. Vuorinen and T.A. Mäntylä, Morphology and microstructure of $YBa_2Cu_3O_7$ thin films on $SrTiO_3$ single crystal by RF magnetron sputtering 114 (1991) 198
Podlowski, L., A. Hoffmann and I. Broser, Calorimetric absorption spectroscopy at mK temperatures – an extremely sensitive method to determine nonradiative processes in solids 117 (1992) 698
Pohl, U.W., see Kudlek 117 (1992) 309
Pohl, U.W., see Waldmann 117 (1992) 715
Pohlmann, A., see Yakovlev 117 (1992) 854
Poingt, F., see Goldstein 120 (1992) 157
Point, J.J. and D. Villers, Nucleation-controlled growth and normal growth: a unified view 114 (1991) 228
Polychroniadis, E.K., see Assenov 112 (1991) 227
Popov, Yu.M., see Nasibov 117 (1992) 1040
Portal, J.C., see Henini 111 (1991) 1089
Posthill, J.B., see Xing 113 (1991) 113
Poudoulec, A., see Le Corre 120 (1992) 353
Pougnet, A.M., see Hincelin 120 (1992) 119
Povey, I.M., see Armstrong 120 (1992) 94
Powell, A.R., R.A.A. Kubiak, S.M. Newstead, C. Parry, N.L. Mattey, D.W. Smith, J.C. Brighten, C.J. Emeleus, T. Naylor, E. Basaran, T.E. Whall, M.G. Dowsett, R.D. Barlow, E.H.C. Parker and D.K. Bowen, Elemental boron and antimony doping of MBE Si and SiGe structures grown at temperatures below 600 °C 111 (1991) 907
Powell, A.R., see Pike 111 (1991) 925
Pozina, G.R., see Uraltsev 117 (1992) 877
Prasad, H., see Sangeeta 118 (1992) 396

Prebende, C., see Langlais 113 (1991) 606
Presser, N., see Kudlek 117 (1992) 290
Presser, N., see Kudlek 117 (1992) 309
Pressl, M., see Ullrich 117 (1992) 902
Prior, K.A., see Simpson 117 (1992) 134
Prior, K.A., see Wallace 117 (1992) 320
Proctor, M.J., see Rudra 111 (1991) 589
Proctor, M.J., see Tiwari 111 (1991) 730
Pronin, A.N., see Gruzintsev 117 (1992) 975
Protzmann, H., T. Marschner, O. Zsebök, W. Stolz, E.O. Göbel, R. Dorn and J. Lorberth, Group III hydride precursors for the metalorganic vapour phase epitaxy (MOVPE) of (AlGa)As/GaAs heterostructures 115 (1991) 248
Prutskij, T.A., see Bocchi 113 (1991) 540
Pryor, C.E., see Miller 111 (1991) 323
Pu Xin, see Qi 112 (1991) 580
Pu Xin, see Qi 113 (1991) 726
Pudensi, M.A.A., see Aspnes 120 (1992) 71
Puechner, R.A., D.A. Johnson, K.T. Shiralagi, D.S. Gerber, R. Droopad and G.N. Maracas, Electrical and optical characterization of gas source and solid source MBE low temperature buffers 111 (1991) 43
Puechner, R.A., see Droopad 114 (1991) 327
Puechner, R.A., see Shiralagi 114 (1991) 337
Puechner, R.A., see Droopad 120 (1992) 200
Pusey, M.L. and S. Munson, Micro-apparatus for rapid determinations of protein solubilities 113 (1991) 385
Pusey, M.L., see Cacioppo 114 (1991) 286
Py, M.A., see Baeta Moreira 112 (1991) 14

Qi Lichang, Xuan Zhenwu, Yang Peichun, Pu Xin and Hou Li, Presence of core particles in diamond crystals grown by electron assisted chemical vapor deposition 112 (1991) 580
Qi Lichang, Xuan Zhenwu, Yang Peichun, Pu Xin and Hou Li, Presence of core particles in diamond crystals grown by electron assisted chemical vapor deposition (E) 113 (1991) 726
Qi, M., see Tokumitsu 120 (1992) 301
Qian, Q.-D., see Qiu 111 (1991) 747
Qian Zhi Qiang, see Cheng 112 (1991) 294
Qiao, G.W., see Zhou 114 (1991) 283
Qiu, J., D.R. Menke, M. Kobayashi, R.L. Gunshor, Q.-D. Qian, D. Li and N. Otsuka, ZnSe/GaAs heterovalent interfaces: interface microstructure versus electrical properties 111 (1991) 747
Qiu, J., see Li 111 (1991) 1038
Qiu, J., see DePuydt 117 (1992) 1078
Quang, V.X., see Kerkow 117 (1992) 677
Quentel, G., see Gauch 118 (1992) 243
Quillec, M., see Allovon 111 (1991) 484
Quinn, W.E., see Aspnes 120 (1992) 71
Quintero, M., M. Morocoima, E. Guerrero, R. Tovar, M. Delgado, J.C. Woolley and P. Conflant, $T(z)$ diagram of the $Mn_{3z}In_{2(1-z)}Te_3$ system in the range $0 < z < 0.7$ 114 (1991) 661
Quintero, M., see Grima 119 (1992) 381

Racah, D., see Schieber 115 (1991) 31
Radhakrishnan, S. and J.M. Schultz, Polymer-induced crystallization of inorganic salts: PEO–$CuCl_2$ 116 (1992) 378
Raisanen, A., see Vanzetti 117 (1992) 573
Raizman, A., see Schieber 115 (1991) 31
Rajakarunanayake, Y., see Collins 111 (1991) 664
Rajakarunanayake, Y., J.O. McCaldin and T.C. McGill, Electric field assisted doping of semiconductors during epitaxial growth 111 (1991) 782
Rajakarunanayake, Y., see Phillips 111 (1991) 820
Rajakarunanayake, Y., see Liu 117 (1992) 742
Rajan, K., see Schowalter 111 (1991) 948
Rajavel, D., see Benz 111 (1991) 725
Rajkumar, K.C., see Chen 111 (1991) 424
Rajkumar, K.C., see Guha 111 (1991) 434
Rakennus, K., see Tappura 112 (1991) 27
Rakennus, K., see Riesz 114 (1991) 127
Rakennus, K., see Tappura 120 (1992) 145
Rakennus, K., see Zhang 120 (1992) 172
Ralston, J.D., J. Wagner, F. Fuchs, P. Hiesinger and J. Schmälzlin, Overgrowth and strain in MBE-grown GaAs/ErAs/GaAs structures 111 (1991) 989
Ramasamy, P., see Narlikar 116 (1992) 37
Ramasamy, P., see Ganesha 119 (1992) 303
Ramdas, A.K., see Samarth 111 (1991) 816
Ramesh, R., see Harbison 111 (1991) 978
Ramesh, S., N. Kobayashi and Y. Horikoshi, High-quality ZnSe/GaAs superlattices: MEE growth, and structural and optical characterization 111 (1991) 752
Ramesh, S., N. Kobayashi and Y. Horikoshi, Study of high-quality ZnSe/GaAs/ZnSe single quantum well and ZnSe/GaAs heterostructures 115 (1991) 333
Rappl, P.H.O., see Regel 119 (1992) 94
Rashkovich, L.N. and B.Yu. Shekunov, Study of the growth mechanism of L-arginine chloride monohydrate (LACh) crystals 112 (1991) 183
Rashkovich, L.N., see Shekunov 116 (1992) 340
Ravila, P., V.M. Airaksinen, H. Lipsanen, T. Tuomi and P.A. Claxton, X-ray diffraction analysis of superlattices grown on misoriented substrates 114 (1991) 569
Ray, B., see Viney 117 (1992) 806
Ray, B., see Arterton 117 (1992) 1008

Red'kin, B.S., see Rossolenko 116 (1992) 185
Reed, F.E., see Lansari 111 (1991) 720
Reed, F.E., see Ren 111 (1991) 829
Reedyk, M., see Xue 113 (1991) 371
Reek, J.N.H., see Hageman 116 (1992) 169
Rees, D., see Hartley 117 (1992) 166
Regel, L.L., see Arnold 119 (1992) 24
Regel, L.L., see Burdin 119 (1992) 61
Regel, L.L. and O.V. Shumaev, GaSb directional solidification under high gravity conditions 119 (1992) 70
Regel, L.L., see Wiedemeier 119 (1992) 79
Regel, L.L., A.M. Turchaninov, O.V. Shumaev, I.N. Bandeira, C.Y. An and P.H.O. Rappl, Growth of lead–tin telluride crystals under high gravity 119 (1992) 94
Regel, L.L., see Derebail 119 (1992) 98
Regel, L.L., see Volkov 119 (1992) 122
Regel, L.L., see Bárczy 119 (1992) 160
Reinsperger, G.U., see Müller 117 (1992) 948
Reinsperger, G.U., see Mach 117 (1992) 1002
Reithmaier, J.-P., H. Riechert, H. Schlötterer and G. Weimann, Indium desorption during MBE growth of strained InGaAs layers 111 (1991) 407
Reithmaier, J.-P., see Riechert 111 (1991) 1100
Rejman-Greene, M.A.Z., see Scott 111 (1991) 1076
Rejman-Greene, M.A.Z., see Skevington 120 (1992) 328
Remitz, K., see Uhrig 117 (1992) 598
Ren, F., see Cunningham 111 (1991) 515
Ren, F., see Abernathy 113 (1991) 412
Ren, F., see Abernathy 120 (1992) 234
Ren, Hong-Wen, see Liu 115 (1991) 83
Ren, J., K.A. Bowers, S. Hwang, J.W. Cook, Jr. and J.F. Schetzina, Substitutional doping of ZnSe films 111 (1991) 772
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Renucci, M.A., see Pagés 117 (1992) 569
Reznikov, P.V., see Nasibov 117 (1992) 1040
Rhoderick, E.H., see Missous 111 (1991) 1116
Richter, W., see Kolodziejczyk 117 (1992) 549
Ricketts, M.W., see Wilby 111 (1991) 864
Riechert, H., see Reithmaier 111 (1991) 407
Riechert, H., D. Bernklau, J.-P. Reithmaier and R.D. Schnell, MBE growth and post-growth annealing of GaAs-based resonant tunneling structures, viewed in relation to interface roughness 111 (1991) 1100
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Rigo, C., see Genova 120 (1992) 333
Rinaudo, C. and A. Zarka, X-ray topographic study of synthetic single and twinned gypsum crystals 116 (1992) 87
Ristić, R.I., Mitrović 112 (1991) 160
Ristorcelli, J.R. and J.L. Lumley, Instabilities, transition and turbulence in the Czochralski crystal melt 116 (1992) 447
Ritchie, D.A., J.E.F. Frost, D.C. Peacock, E.H. Linfield, A. Hamilton and G.A.C. Jones, The growth and characterisation of back-gated high mobility two-dimensional electron gas structures 111 (1991) 300
Ritchie, D.A., see Frost 111 (1991) 305
Ritchie, D.A., see Davies 111 (1991) 318
Ritchie, D.A., see Frost 113 (1991) 726
Ritter, D., see Panish 112 (1991) 343
Rivas, D., J. Sanz and C. Vázquez, Temperature field in a cylindrical crystal heated in a mono-ellipsoid mirror furnace 116 (1992) 127
Rivera-Iratchet, J., see Vogel 117 (1992) 710
Robein, D., see Kazmierski 116 (1992) 75
Roberts, C., see Harris 111 (1991) 239
Roberts, D.H., see De Yoreo 113 (1991) 691
Roberts, K.J., see Doyle 112 (1991) 302
Robinson, G.Y., see Hafich 111 (1991) 507
Robinson, G.Y., see Lee 111 (1991) 525
Rodríguez Clemente, R., see Gómez Morales 116 (1992) 427
Rodriguez, J.G., see Bocchi 113 (1991) 540
Rodriguez, V., see Sun 112 (1991) 71
Rodway, D.C., A simple system for multi-wafer large area, thick film growth of cadmium telluride on gallium arsenide 116 (1992) 55
Rodway, G.H. and J.D. Hunt, Thermoelectric investigation of solidification of lead. I. Pure lead 112 (1991) 554
Rodway, G.H. and J.D. Hunt, Thermoelectric investigation of solidification of lead. II. Lead alloys 112 (1991) 563
Rolland, S., see Bagot 117 (1992) 189
Rolland, S., R. Granger and R. Triboulet, p-to-n conversion in $Hg_{1-x}Zn_xTe$ by ion beam milling effect 117 (1992) 208
Romanov, A.E., see Trusov 114 (1991) 133
Rooney, M.-L.T., {115} Growth in boron-doped synthetic diamonds 116 (1992) 15
Röseler, J., see Hommel 117 (1992) 721
Rosenauer, A., see Bauer 117 (1992) 297
Rosenberger, F., see Alexander 113 (1991) 21

Rosenberger, F., see Xiao 114 (1991) 536
Rosenberger, F., see Xiao 114 (1991) 549
Rosenberger, F., see Nadarajah 118 (1992) 49
Rosenthal, B.N., see Batur 119 (1992) 371
Rosner, D.E., see Castillo 116 (1992) 105
Rossetti, Jr., G.A., D.J. Watson, R.E. Newnham and J.H. Adair, Kinetics of the hydrothermal crystallization of the perovskite lead titanate 116 (1992) 251
Rossolenko, S.N., I.S. Pet'kov, V.N. Kurlov and B.S. Red'kin, Servo-controlled crystal growth by the Czochralski method estimating the state vector of the controlled object 116 (1992) 185
Rostrup, E., see Christoffersen 113 (1991) 599
Roth, A.P., Z. Wasilewski, Q. Sun, C. Lacelle, T. Bryskiewicz, D. Coulas and J.P. Noad, Properties of InGaAs epitaxial layers lattice matched to InGaAs single crystal substrates 113 (1991) 379
Roth, A.P., see Dubowski 117 (1992) 862
Roth, A.P., see Maigne 118 (1992) 117
Roth, A.P., D. Morris, Q. Sun, C. Lacelle, Z. Wasilewski, P. Maigné and A. Bensaoula, Anisotropy in InGaAs/GaAs heterostructures grown by low-pressure MOVPE and CBE 120 (1992) 212
Roth, M., see Azoulay 116 (1992) 515
Roth, M., see Azoulay 117 (1992) 276
Roth, S., see Ullrich 117 (1992) 902
Roth, S., see Ullrich 117 (1992) 925
Rothemund, W., see Hingerl 117 (1992) 341
Rothfritz, H., G. Tränkle, R. Müller and G. Weimann, High-quality InP grown by chemical beam epitaxy 120 (1992) 130
Rothfritz, H., see Tränkle 120 (1992) 240
Rotter, S., see Schieber 115 (1991) 31
Rotter, S., see Azoulay 116 (1992) 515
Rotter, S., see Azoulay 117 (1992) 276
Rousseau, R.W., see Tai 116 (1992) 294
Rouzaud, A., see Garandet 113 (1991) 587
Rozenak, P., see Tsai 111 (1991) 931
Rubinstein, E.R. and M.E. Glicksman, Dendritic growth kinetics and structure. I. Pivalic acid 112 (1991) 84
Rubinstein, E.R. and M.E. Glicksman, Dendritic growth kinetics and structure. II. Camphene 112 (1991) 97
Rückmann, I., see Woggon 117 (1992) 608
Rudolph, P., M. Mühlberg, M. Neubert, T. Boeck, P. Möck, L. Parthier, K. Jacobs and E. Kropp, Origin and evolution of background impurity content of materials used in the preparation of (Hg,Cd)Te LPE layers on CdTe substrates 118 (1992) 204
Rudra, A., see Houdré 111 (1991) 456
Rudra, A., J.F. Carlin, M. Proctor and M. Ilegems, Luminescence and transport properties of high quality InP grown by CBE between 450 and 550 °C 111 (1991) 589
Rudra, A., see Carlin 120 (1992) 155
Rudra, A., J.F. Carlin, P. Ruterana, M. Gailhanou, J.L. Staehli and M. Ilegems, Growth of GaInAs(P) and GaInAsP/GaInAs MQW structures by CBE 120 (1992) 338
Ruf, R.R., see Munekata 111 (1991) 1011
Ruiz, A., see Briones 111 (1991) 194
Rule, R.J., see Davey 114 (1991) 7
Rupp, R. and G. Müller, Experimental study of the surface tension of molten GaAs and its temperature dependence under controlled As-vapor pressure 113 (1991) 131
Russell, G.J., see Taylor 119 (1992) 221
Rut, O.E., see Germanenko 117 (1992) 850
Ruterana, P., see Carlin 120 (1992) 155
Ruterana, P., see Rudra 120 (1992) 338

Sabarwal, S.C., see Narlikar 116 (1992) 37
Sabhapathy, P. and M.E. Salcudean, Numerical study of Czochralski growth of silicon in an axisymmetric magnetic field 113 (1991) 164
Sabharwal, S.C., see Muthe 118 (1992) 213
Sabharwal, S.C., see Sangeeta 118 (1992) 396
Sabinina, I.V., A.K. Gutakovsky, Yu.G. Sidorov, S.A. Dvoretsky and V.D. Kuzmin, Defect formation during growth of CdTe(111) and HgCdTe films by molecular beam epitaxy 117 (1992) 238
Saemann-Ischenko, G., see Markl 113 (1991) 395
Saenger, W., see Georgalis 118 (1992) 360
Saga, M., see Takami 117 (1992) 16
Saga, M., see Shigenaka 117 (1992) 37
Saga, M., see Shigenaka 117 (1992) 49
Saga, M., see Kawano 117 (1992) 171
Saga, M., see Oda 117 (1992) 193
Saga, M., see Sasaki 117 (1992) 222
Saiki, K., see Koma 111 (1991) 1029
Saiki, T., K. Takeuchi, M. Kuwata-Gonokami, T. Mitsuyu and K. Ohkawa, Giant excitonic optical nonlinearity in ZnSe grown by molecular beam epitaxy 117 (1992) 802
Saito, H., see Ohishi 111 (1991) 792
Saito, H., see Fukui 115 (1991) 61
Saito, H., see Kasu 115 (1991) 406
Saito, H., see Suzuki 115 (1991) 623
Saito, H., see Ohishi 117 (1992) 125
Saito, J., T. Maeda, K. Ono and K. Kondo, Background pressure dependence of GaAs and AlGaAs growth rates in gas-source molecular beam epitaxy 111 (1991) 544
Saito, K., see Uchida 114 (1991) 565
Saito, T., see Takigawa 117 (1992) 28
Saito, T., see Murakami 117 (1992) 33
Saito, T., see Sugiyama 117 (1992) 161
Saitoh, K., see Ikeda 115 (1991) 211

Saitou, M. and A. Hirata, Numerical calculation of two-dimensional unsteady solidification problem 113 (1991) 147
Saitou, M. and A. Hirata, Ratio of liquid to solid thermal conductivity calculated from the solid–liquid interface shape 118 (1992) 365
Saji, M., see Hattori 115 (1991) 607
Saji, M., see Ekawa 117 (1992) 254
Sakachi, Y., see Murakami 117 (1992) 33
Sakai, A., see Terashima 111 (1991) 920
Sakai, H., H. Hosogai, T. Kawakita, K. Onuma and K. Tsukamoto, Transformation of α-glycine to γ-glycine 116 (1992) 421
Sakai, J., see Aketagawa 111 (1991) 860
Sakai, J., see Tatsumi 120 (1992) 275
Sakai, K., see Nishimura 117 (1992) 119
Sakai, S., see Kasai 115 (1991) 758
Sakaki, H., see Kadoya 111 (1991) 280
Sakaki, H., see Noda 111 (1991) 348
Sakakibara, K., see Wada 114 (1991) 321
Sakakibara, K., see Maruyama 115 (1991) 180
Sakamoto, K., see Miki 111 (1991) 902
Sakamoto, M., see Kan 119 (1992) 215
Sakamoto, M., see Kimura 119 (1992) 313
Sakamoto, M., see Kawasaki 119 (1992) 317
Sakamoto, T., see Miki 111 (1991) 902
Sakaue, K., see Urano 115 (1991) 411
Sakawa, S. and T. Nishinaga, Faceting of LPE GaAs grown on a misoriented Si-(100) substrate 115 (1991) 145
Sakawa, S., see Uen 115 (1991) 122
Sakuma, E., see Okumura 120 (1992) 114
Sakuma, Y., M. Ozeki, K. Kodama and N. Ohtsuka, Role of interface strain in atomic layer epitaxy growth kinetics of $In_xGa_{1-x}As$ 114 (1991) 31
Sakuma, Y., M. Ozeki, K. Kodama and N. Ohtsuka, InAs/InP short-period strained-layer superlattices grown by atomic layer epitaxy 115 (1991) 324
Sakuma, Y., see Ohtsuka 115 (1991) 460
Sakuraba, M., J. Murota, N. Mikoshiba and S. Ono, Atomic layer epitaxy of germanium on silicon using flash heating chemical vapor deposition 115 (1991) 79
Sakurai, F., H. Fujishiro, K. Suto and J. Nishizawa, ZnSe epitaxial growth by the temperature difference method under controlled vapor pressure (TDM–CVP) using Se solvent 112 (1991) 153
Salaün, S., see Le Corre 120 (1992) 353
Salcudean, M.E., see Sabhapathy 113 (1991) 164
Samanta, L.K., see Sato 115 (1991) 740
Samanta, S.B., see Narlikar 116 (1992) 37
Samarasekera, I.V., see Parfeniuk 119 (1992) 261
Samarth, N., H. Luo, J. Buschert, J.K. Furdyna, W.J. Walecki, A.V. Nurmikko, R.G. Alonso, E.-S. Oh, A.K. Ramdas and N. Otsuka, Growth and properties of new wide-gap quantum well structures: Zn_{1-x}-$Mn_xSe/Zn_{1-y}Cd_ySe$ 111 (1991) 816
Saminadayar, K., see Bassani 117 (1992) 391
Saminadayar, K., see Cibert 117 (1992) 424
Samoska, L.A., see Miller 111 (1991) 323
Samuelson, L., see Paulsson 111 (1991) 115
Samuelson, L., see Deppert 120 (1992) 88
Sandhu, A., T. Fujii, H. Ando, T. Takahashi, H. Ishikawa and N. Yokoyama, P^+/N GaAs–AlGaAs heterostructures grown by gas source MBE using gaseous p- and n-type dopant sources 111 (1991) 559
Sandhu, A., see Ando 115 (1991) 464
Sandhu, A., see Ando 120 (1992) 228
Sandhu, A., T. Nakamura, H. Ando, K. Domen, N. Okamoto and T. Fujii, The electrical, optical and crystalline properties of GaAs:C grown by GSMBE using TMG and AsH_3 for application to HBTs 120 (1992) 296
Sandlin, A.C., see Andrews 119 (1992) 152
Sands, T., see Harbison 111 (1991) 978
Sang Wen-bin, K. Durose, A.W. Brinkman and J. Woods, In-situ mass spectrometric investigation of tricarbonyl (methylcyclopentadienyl) manganese (TCMn) pyrolysis mechanism during MOVPE 113 (1991) 1
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Sangster, M.J.L., see Woodhouse 120 (1992) 323
Sano, M., see Yase 116 (1992) 333
Santos, M., J. Jo, M. Shayegan and A.-M. Lanzillotto, Fabrication of quasi-three-dimensional electron systems and superlattices in wide parabolic wells 111 (1991) 366
Sanz, J., see Rivas 116 (1992) 127
Saraie, J., see Matsumura 111 (1991) 787
Saraie, J., see Matsumura 115 (1991) 279
Saraie, J., see Takahashi 115 (1991) 617
Saraie, J., see Matsumura 117 (1992) 129
Sasaki, A., see Tabuchi 115 (1991) 169
Sasaki, A., see Wang 115 (1991) 261
Sasaki, A., Optical and luminescence properties of disordered superlattices 115 (1991) 490
Sasaki, F., T. Mishina, Y. Masumoto, B. Fluegel, K. Meissner and N. Peyghambarian, Femtosecond optical nonlinearities under resonant excitation of excitons in CdSe 117 (1992) 768
Sasaki, M., see Hiratani 115 (1991) 74
Sasaki, M., see Ohki 115 (1991) 226
Sasaki, M., see Kita 115 (1991) 752
Sasaki, T., see Halfpenny 113 (1991) 722
Sasaki, T., see Kawano 117 (1992) 171
Sasaki, T., see Sone 117 (1992) 218

Sasaki, T., N. Oda, M. Kawano, S. Sone, T. Kanno and M. Saga, Mercury annealing effect on the electrical properties of HgCdTe grown by molecular beam epitaxy 117 (1992) 222
Sasaki, T., see Katayama-Yoshida 117 (1992) 625
Sasaki, T., see Yase 118 (1992) 348
Sasakura, H., see Konishi 117 (1992) 939
Sasaoka, C., Y. Kato and A. Usui, Temperature programmed desorption study of gallium chloride adsorbed on GaAs surfaces 115 (1991) 94
Sassa, M., see Koide 115 (1991) 639
Sato, A., see Kadoya 111 (1991) 280
Sato, H., T. Yamada and H. Sugiura, New Organometallic sources for MOMBE/laser-assisted MOMBE 115 (1991) 241
Sato, H., see Minami 117 (1992) 370
Sato, H., see Oka 117 (1992) 840
Sato, K., Y. Kudo, S. Kijima and L.K. Samanta, Characterization of I–III–VI_2 bulk crystals grown by chemical vapor deposition: application of phase-shift-difference spectroscopy 115 (1991) 740
Sato, K., see Sawada 117 (1992) 826
Sato, M., see Hasegawa 111 (1991) 371
Sato, M., N. Kobayashi and Y. Horikoshi, Effect of precracking of organometallics and arsine on growth of GaAs 115 (1991) 221
Sato, M., see Weyers 115 (1991) 469
Sato, M., see Kimura 119 (1992) 313
Satoh, K., see Yokota 112 (1991) 723
Satoh, T., see Terashima 115 (1991) 745
Sauer, N.J., see Chang 111 (1991) 475
Savage, J.A., Preparation and properties of hard crystalline materials for optical applications – a review 113 (1991) 698
Sawada, A., see Ebe 115 (1991) 718
Sawada, T., Y. Takada and K. Sato, Growth technique and optical characterization of (Cd,Mn)Te for fiber-optic magnetic field sensors 117 (1992) 826
Sawaki, N., see Takeuchi 115 (1991) 634
Sawaki, N., see Murakami 115 (1991) 648
Scaffardi, M., see Bocchi 113 (1991) 540
Schaake, H.F., see Fashe 111 (1991) 677
Schäpers, Th., see Hardtdegen 116 (1992) 521
Schaus, C.F., see Sun 113 (1991) 103
Scheel, H.J., see Licci 112 (1991) 600
Scheel, H.J., see Licci 112 (1991) 606
Scheel, H.J., M. Berkowski and B. Chabot, Problems in epitaxial growth of high-T_c superconductors 115 (1991) 19
Scherbachev, K.D., see Charniy 118 (1992) 163
Scherbachov, K.D., see Charniy 116 (1992) 369
Schetzina, J.F., see Lansari 111 (1991) 720
Schetzina, J.F., see Ren 111 (1991) 772
Schetzina, J.F., see Ren 111 (1991) 829
Schetzina, J.F., see Ren 117 (1992) 510
Schieber, M., S.C. Han, Y. Ariel, S. Chokron, T. Tsach, M. Maharizi, C. Deutscher, D. Racah, A. Raizman and S. Rotter, Comparison of thin films of $YBa_2Cu_3O_{7-x}$ deposited by physical (laser ablation) and chemical (OMCVD) methods for device applications 115 (1991) 31
Schier, M., see Heinecke 120 (1992) 140
Schimpe, R., see Heinecke 120 (1992) 376
Schlaak, W., see Künzel 111 (1991) 461
Schleich, D.M. and H.S.W. Chang, Iron pyrite and iron marcasite thin films prepared by low pressure chemical vapor deposition 112 (1991) 737
Schlom, D.G., see Lee 111 (1991) 131
Schlom, D.G., see Eckstein 111 (1991) 973
Schlötterer, H., see Reithmaier 111 (1991) 407
Schmale, A.L., see Andrews 119 (1992) 152
Schmälzlin, J., see Ralston 111 (1991) 989
Schmeusser, S., see Waag 117 (1992) 820
Schmeusser, S., see Yakovlev 117 (1992) 854
Schmid, H., see Sun 112 (1991) 71
Schmidt, P., see Paulsson 111 (1991) 115
Schmidt, T., G. Daniel and K. Lischka, The excitation power dependence of the near band edge photoluminescence of II–VI semiconductors 117 (1992) 748
Schmied, B., see Waag 117 (1992) 820
Schmolke, R., E. Schöll and J. Gutowski, A model for impurity-related optical bistability in II–VI semiconductors 117 (1992) 650
Schnell, R.D., see Riechert 111 (1991) 1100
Schnoes, M., see Chand 111 (1991) 20
Schnoes, M.L., see Feldman 118 (1992) 295
Schock, H.W., see Mauch 117 (1992) 964
Schöll, E., see Schmolke 117 (1992) 650
Schowalter, L.J., J.R. Jimenez, L.M. Hsiung, K. Rajan, S. Hashimoto, R.D. Thompson and S.S. Iyer, Control of misoriented grains and pinholes in $CoSi_2$ grown on Si(001) 111 (1991) 948
Schowalter, L.J., see Ayers 113 (1991) 430
Schrappe, B., see Notari 116 (1992) 518
Schubert, E.F., see Asom 111 (1991) 246
Schubert, E.F., see Hong 111 (1991) 1052
Schultz, J.M., see Radhakrishnan 116 (1992) 378
Schulz, G., see Müller 117 (1992) 948
Schvezov, C., see Parfeniuk 119 (1992) 261
Schwab, H., see Hvam 117 (1992) 773
Schwab, H., V.G. Lyssenko, J.M. Hvam, M. Urban and C. Klingshirn, Dephasing and energy relaxation of localized excitons in $CdS_{1-x}Se_x$ mixed crystals 117 (1992) 778
Schwabe, R., see Keller 118 (1992) 176
Schwartz, G.P., see Feldman 118 (1992) 295

Schwartzbrod, A., see Chen 118 (1992) 101
Schwarz, S.A., see Caneau 114 (1991) 481
Schwarz, S.A., see Aspnes 120 (1992) 71
Sciau, Ph., see Sun 112 (1991) 71
Scilla, G.J., see De Lyon 111 (1991) 564
Scott, C.G.; see Ashenford 117 (1992) 233
Scott, E.G. and M.A.Z. Rejman-Greene, MBE growth of InP/InGaAs MQW modulators 111 (1991) 1076
Seabaugh, A.C., see Beam III 116 (1992) 436
Sebastian, M.T., see Bolt 112 (1991) 773
Sebastian, P.J. and V. Sivaramakrishnan, The growth and characterization of $CdSe_xTe_{1-x}$ thin films 112 (1991) 421
Seiberling, L.E., see Lyman 113 (1991) 45
Seifert, W., see Keller 118 (1992) 176
Seiwa, M., see Imaizumi 115 (1991) 443
Sekerka, R.F., see Hardy 114 (1991) 467
Seki, H., see Kobayashi 113 (1991) 491
Seki, H., see Ikeda 115 (1991) 211
Sekiguchi, H., see Kondo 115 (1991) 231
Sekiguchi, Y., see Wada 114 (1991) 321
Selle, B., see Kerkow 117 (1992) 677
Selle, B., see Mach 117 (1992) 1002
Senga, K., see Matsumura 111 (1991) 787
Senga, K., see Matsumura 115 (1991) 279
Senga, K., see Matsumura 117 (1992) 129
Sergent, A.M., see Chand 111 (1991) 20
Series, R.W. and D.T.J. Hurle, The use of magnetic fields in semiconductor crystal growth 113 (1991) 305
Seth, J. and W.R. Wilcox, Effect of convection on the microstructure of a lamellar eutectic growing with a stepped interface 114 (1991) 357
Seto, H., see Shigeta 111 (1991) 284
Seto, S., A. Tanaka, Y. Masa and M. Kawashima, Chlorine-related photoluminescence lines in high-resistivity Cl-doped CdTe 117 (1992) 271
Shamsuzzoha, M., L.M. Hogan, D.J. Smith and P.A. Deymier, A transmission and high-resolution electron microscope study of cozonally twinned growth of eutectic silicon in unmodified Al–Si alloys 112 (1991) 635
Shan, Wei, see Li 111 (1991) 736
Shank, S.M. and G.W. Wicks, Electrooptic effects of piezo-electrically strained AlGaAs/GaAs(111) quantum wells 111 (1991) 440
Sharma, K., see Bagai 112 (1991) 402
Sharpless, R.B., see Batur 119 (1992) 371
Shaw, L.B. and R.S.F. Chang, Rare earth doped YLF grown by laser-heated pedestal growth technique 112 (1991) 731
Shaw, N., see Astles 117 (1992) 213
Shayegan, M., see Santos 111 (1991) 366
Shekunov, B.Yu., see Rashkovich 112 (1991) 183
Shekunov, B.Yu., L.N. Rashkovich and L.L. Smol'skii, Nonstationary growth of the cubic faces of a barium nitrate crystal 116 (1992) 340
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Shen, D.Z., see Zhang 117 (1992) 523
Shen, G., see Hartley 117 (1992) 166
Shen, H., see Jones 120 (1992) 150
Shen, Meng-Yan, Xiao-Jie Zhang, Ying Jin, Jing-Jing Wang, Shu-Lin Zhang, Jie Li and Shi-Xin Yuan, Spectroscopy in the ZnTe/CdTe multiple quantum wells 117 (1992) 470
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Sher, A., see Feldman 118 (1992) 295
Sherwin, M.E., G.O. Munns, M.E. Elta, E.G. Woelk, S.B. Crary, F.L. Terry and G.I. Haddad, The optimization of In_xGa_{1-x}As and InP growth conditions by CBE 111 (1991) 594
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Sherwin, M.E., see Munns 120 (1992) 184
Sherwood, J.N., see Doyle 112 (1991) 302
Sherwood, J.N., see Shepherd 113 (1991) 360
Sherwood, J.N., see Halfpenny 113 (1991) 722
Shi, C.H., see Jin 116 (1992) 524
Shi Zhengzhu, see Li 118 (1992) 371
Shi Zhenzhu, see Li 119 (1992) 363
Shiba, Y., see Katahama 115 (1991) 141
Shibaev, P.V. and M.B. Guseva, Molecular orientation in propyl- and hexyloxy-cyanobiphenyl vacuum deposited thin films 119 (1992) 399
Shibli, S.M., see Tamargo 111 (1991) 741
Shibuya, K., see Takahashi 117 (1992) 979
Shigenaka, K., T. Uemoto, L. Sugiura, K. Ichizono, K. Hirahara, T. Kanno and M. Saga, $Hg_{1-x}Cd_xTe$ epitaxial layers grown

by low mercury partial pressure metalorganic chemical vapor deposition and extended defect characterization 117 (1992) 37
Shigenaka, K., T. Kanno, M. Saga, T. Uemoto, L. Sugiura, K. Ichizono and K. Hirahara, Effects of mercury partial pressure on defects in HgTe epitaxial layers grown by metalorganic chemical vapor deposition 117 (1992) 49
Shigeta, M., Y. Okano, H. Seto, H. Katahama, S. Nishine, K. Kobayashi and I. Fujimoto, Si doping and MBE growth of GaAs on tilted (111)A substrates 111 (1991) 284
Shigeta, M., see Shimomura 111 (1991) 1105
Shigeta, Y., see Maki 115 (1991) 567
Shigetomi, J., K. Fuwa, S. Shimizu, H. Yamakawa and S. Ino, Initial growth stage of InAs/GaAs studied by RHEED–TRAXS method 111 (1991) 110
Shih, H.D., see Fashe 111 (1991) 677
Shih, Z.W., see Wang 116 (1992) 483
Shih, Zong-Whie, see Wang 114 (1991) 435
Shiiki, M. and O. Kanehisa, Electroluminescence of zinc sulfide thin films activated with donors and acceptors 117 (1992) 1035
Shima, M., Y. Tanishiro, K. Kobayashi and K. Yagi, UHV-REM study of hemoepitaxial growth of Si 115 (1991) 359
Shimada, T., see Ohuchi 111 (1991) 1033
Shimizu, I., see Gotoh 117 (1992) 85
Shimizu, M., see Katayama 115 (1991) 289
Shimizu, S., see Shigetomi 111 (1991) 110
Shimomura, S., N. Okamoto, M. Takeuchi, E. Tamaoka, Y. Yuba, S. Namba, S. Hiyamizu, M. Shigeta, T. Yamamoto and K. Kobayashi, MBE growth of GaAs/AlAs double-barrier structures on GaAs channeled substrates 111 (1991) 1105
Shimura, K., see Terashima 115 (1991) 745
Shinohara, K., see Ebe 115 (1991) 718
Shinohara, K., see Takigawa 117 (1992) 28
Shinohara, K., see Murakami 117 (1992) 33
Shinohara, K., see Sugiyama 117 (1992) 161
Shinohara, K., see Ueda 117 (1992) 266
Shinohara, M., see Yokoyama 115 (1991) 89
Shinone, K., see Itoh 117 (1992) 835
Shiohara, Y., see Hayashi 115 (1991) 782
Shiojiri, M., see Hirota 112 (1991) 55
Shiosaki, T., see Katayama 115 (1991) 289
Shirai, H., see Gotoh 117 (1992) 85
Shiraishi, K., see Nagai 115 (1991) 769
Shiraishi, T., see Kuwano 115 (1991) 381
Shiraishi, T., see Hiramatsu 115 (1991) 628
Shirakashi, J., see Yamada 111 (1991) 584
Shirakashi, J., see Tokumitsu 120 (1992) 301
Shiraki, Y., see Fukatsu 111 (1991) 843
Shiralagi, K.T., see Puechner 111 (1991) 43
Shiralagi, K.T., see Droopad 114 (1991) 327
Shiralagi, K.T., R.A. Puechner, K.Y. Choi, R. Droopad and G.N. Maracas, Narrow photoluminescence linewidth of quantum wells grown by gas source molecular beam epitaxy 114 (1991) 337
Shiralagi, K.T., see Edwards 120 (1992) 78
Shiralagi, K.T., see Droopad 120 (1992) 200
Shitara, T., see Joyce 115 (1991) 338
Shirtcliffe, T.G.L., H.E. Huppert and M.G. Worster, Measurement of the solid fraction in the crystallization of a binary melt 113 (1991) 566
Shlichta, P.J., Crystal growth and materials processing above 1000 *g* 119 (1992) 1
Shripathi, T., see Dhanaraj 113 (1991) 456
Shumaev, O.V., see Burdin 119 (1992) 61
Shumaev, O.V., see Regel 119 (1992) 70
Shumaev, O.V., see Regel 119 (1992) 94
Shumaev, O.V., see Vorobiov 119 (1992) 111
Sidorov, Yu.G., see Sabinina 117 (1992) 238
Silvestre, P., see Hafich 111 (1991) 507
Simchick, R., see Steiner 114 (1991) 707
Simes, R.J., see Starck 120 (1992) 180
Simmonds, P.E., see Henini 111 (1991) 1089
Simmons, M.Y., H.M. Al Allak, A.W. Brinkman and K. Durose, Electrical and optical characterisation of epitaxial ZnTe/CdTe/CdS and ZnTe/CdTe/GaAs p–i–n solar cell structures grown by metalorganic vapour phase epitaxy 117 (1992) 959
Simpson, G.S., see Shepherd 113 (1991) 360
Simpson, G.S., see Halfpenny 113 (1991) 722
Simpson, J., S.J.A. Adams, S.Y. Wang, J.M. Wallace, K.A. Prior and B.C. Cavenett, UV laser assisted growth of molecular beam epitaxial ZnSe 117 (1992) 134
Simpson, J., see Wallace 117 (1992) 320
Sinerius, D., see Meyer 117 (1992) 656
Singer, K.E., see Missous 111 (1991) 1116
Singh, B.P., see Bindal 112 (1991) 386
Singh, J., see Chen 111 (1991) 228
Singh, M., see Singh 118 (1992) 78
Singh, N.B., Gottlieb, M. T. Henningsen, R.H. Hopkins, R. Mazelsky, M. Singh, M.E. Glicksman and C. Paradies, Thermodynamic reactivity, growth and characterization of mercurous halide crystals 118 (1992) 78
Singh, N.B., see Batur 119 (1992) 371
Singh, N.K., J.S. Foord, P.J. Skevington and G.J. Davies, Growth and MBMS studies of reaction mechanisms for $In_xGa_{1-x}As$ CBE 120 (1992) 33
Singh, N.K., see Foord 120 (1992) 103
Singhal, S.K., see Bindal 112 (1991) 386
Sitter, H., see Plotz 115 (1991) 186
Sitter, H., see Faschinger 115 (1991) 692
Sitter, H., see Kudlek 117 (1992) 290

Sitter, H., see Kudlek 117 (1992) 309
Sitter, H., see Hingerl 117 (1992) 341
Sivananthan, S., see Faurie 111 (1991) 698
Sivaramakrishnan, V., see Sebastian 112 (1991) 421
Skasyrsky, Ya.K., see Nasibov 117 (1992) 1040
Skelton, E.F., see Vanderah 118 (1992) 385
Skevington, P.J., and S.J. Amin, Control of growth temperature at the onset of $In_{0.53}Ga_{0.47}As$ growth by chemical beam epitaxy 120 (1992) 135
Skevington, P.J., see Singh 120 (1992) 33
Skevington, P.J., M.A.G. Halliwell, M.H. Lyons, S.J. Amin, M.A.Z. Rejman-Greene and G.J. Davies, Growth of InP/InGaAs multiple quantum well structures by chemical beam epitaxy 120 (1992) 328
Skevington, P.J., see Davies 120 (1992) 369
Skolnick, M.S., see Henini 111 (1991) 1089
Skorsetz, J., see Bauer 117 (1992) 297
Skromme, B.J., see Tamargo 111 (1991) 741
Škrtić, D., N. Filipović-Vinceković and H. Füredi-Milhofer, Crystallization of calcium oxalate in the presence of dodecylammonium chloride 114 (1991) 118
Slusky, S.E.G., see McCrary 112 (1991) 39
Smallman, R.E., see Taylor 119 (1992) 221
Smirl, A.L., see Hasenberg 111 (1991) 388
Smith, D.J., see Shamsuzzoha 112 (1991) 635
Smith, D.W., see Powell 111 (1991) 907
Smith, F.W., see Wang 119 (1992) 271
Smith, P.R., see Abernathy 120 (1992) 234
Smol'skii, L.L., see Shekunov 116 (1992) 340
Snail, K.A. and L.M. Hanssen, High temperature, high rate homoepitaxial growth of diamond in an atmospheric pressure flame 112 (1991) 651
Sneed, B., see Ren 111 (1991) 829
Söderström, J.R., see Collins 111 (1991) 664
Soga, T., see Itakura 115 (1991) 154
Soga, T., see Suzuki 115 (1991) 158
Soga, T., T. George, T. Jimbo and M. Umeno, Nucleation mechanisms for compound semiconductors grown on Si by MOCVD 115 (1991) 418
Sohn, S.H., see Hyun 117 (1992) 587
Sohn, S.H., D.G. Hyun, M. Noma, S. Hosomi and Y. Hamakawa, Effective charges in II–VI semiconductors 117 (1992) 907
Sohn, S.H., see Noma 117 (1992) 1030
Söhnel, O., I. Křivánková, S. Krčmář and M. Jurčová, Gypsum crystals formed on decomposing calcium citrate 112 (1991) 415
Sokołowska, A. and A. Olszyna, Electron assisted chemical synthesis of E-BN 116 (1992) 507
Sokolowski, R.S. and M.E. Glicksman, Gravitational influence on eutectic solidification 119 (1992) 126
Söllner, J., see Heuken 117 (1992) 336
Söllner, J., see Guimarães 117 (1992) 1075
Sólyom, J., see Bárczy 119 (1992) 160
Sommer, M., see Wang 119 (1992) 271
Sone, S., N. Oda, T. Sasaki and M. Kawano, Electron mobility in HgCdTe near the zero-band-gap grown by molecular beam epitaxy 117 (1992) 218
Sone, S., see Sasaki 117 (1992) 222
Song, J., see Abernathy 113 (1991) 412
Song Wen Bao, See Cheng 112 (1991) 294
Sorba, L., see Vanzetti 117 (1992) 573
Sorbier, J.P., see Marfaing 118 (1992) 27
Souma, I., see Oka 117 (1992) 840
Souma, I., see Suzuki 117 (1992) 881
Sowers, A.T., see Lansari 111 (1991) 720
Spal, R., see Steiner 114 (1991) 707
Specht, E.D., R.E. Clausing and L. Heatherly, X-ray and optical characterization of three growth morphologies of CVD diamond films 114 (1991) 38
Speckman, D.M., Ultraviolet and infrared absorption spectra of promising organoarsine photochemical vapor deposition reagents 116 (1992) 48
Speit, B., see Uhrig 117 (1992) 598
Spellmeyer, B., see Waldmann 117 (1992) 715
Spitzer, R.C., see Feldman 118 (1992) 295
Sporken, R., see Faurie 111 (1991) 698
Springholz, G., A. Holzinger, H. Krenn, H. Clemens, G. Bauer, H. Böttner, P. Norton and M. Maier, Interdiffusion in $Pb_{1-x}Eu_xSe/PbSe$ multi-quantum-well structures 113 (1991) 593
SpringThorpe, A.J., see Wasilewski 111 (1991) 70
Srinivasan, A., see Chu 111 (1991) 26
Srivastava, M., see Bagai 112 (1991) 402
Srivastava, O.N., see Janam 113 (1991) 403
Srivastava, O.N., see Narlikar 116 (1992) 37
Stadler, W., see Meyer 117 (1992) 656
Staehli, J.L., see Keller 118 (1992) 176
Staehli, J.L., see Rudra 120 (1992) 338
Stafford, A., see Armstrong 120 (1992) 94
Stagg, J.P., J. Christer, E.J. Thrush and J. Crawley, Measurement and control of reagent concentrations in MOCVD reactor using ultrasonics 120 (1992) 98
Stalder, R., see Von Känel 111 (1991) 889
Stanaway, M.B., see Stanley 111 (1991) 14
Stanchina, W.E., see Metzger 111 (1991) 445
Stanley, C.R., M.C. Holland, A.H. Kean, J.M. Chamberlain, R.T. Grimes and M.B. Stanaway, 4×10^{15} cm^2 V^{-1} s^{-1} peak electron mobilities in GaAs grown by solid source MBE with As_2 111 (1991) 14
Stanley, C.R., see Kean 111 (1991) 189
Stanley, R.P., see Doran 117 (1992) 465

Starck, C., see Lambert 111 (1991) 495
Starck, C., see Goldstein 120 (1992) 157
Starck, C., J.-Y. Emery, R.J. Simes, M. Matabon, L. Goldstein and J. Barrau, Strained quaternary GaInAsP quantum well laser emitting at 1.5 μm grown by gas source molecular beam epitaxy 120 (1992) 180
Starck, C., F. Mollot, F. Mallecot, J.-L. Peyre and M. Boulou, Well-size dependence of electro-optic effects in GaInAsP/InP quantum wells grown by GSMBE 120 (1992) 349
Staring, E.G.J., see Dormans 114 (1991) 364
Steele, T.A., see Hartley 117 (1992) 166
Steiner, B., R.C. Dobbyn, D. Black, H. Burdette, M. Kuriyama, R. Spal, R. Simchick and A. Fripp, High resolution X-ray diffraction imaging of lead tin telluride 114 (1991) 707
Steininger, R. and J.H. Bilgram, A light scattering study of the solid–liquid interface layer of cyclohexane crystals 112 (1991) 201
Stejskal, J., see Leitner 112 (1991) 437
Stenin, S.I., see Krasilnikov 116 (1992) 178
Stepantsova, I.V., see Charniy 116 (1992) 369
Stepantsova, I.V., see Charniy 118 (1992) 163
Stern, A., see Horowitz 119 (1992) 391
Stevens, R.L., see Barber 112 (1991) 613
Stevenson, A.W., see Gao 112 (1991) 487
Stewart, H., see Wallace 117 (1992) 320
Stewart, N.M., see Jones 117 (1992) 244
Stobbs, W.M., see Baxter 112 (1991) 373
Stoddard, B.L., see Strong 119 (1992) 200
Stolz, W., see Protzmann 115 (1991) 248
Störmer, H.L., see Pfeiffer 111 (1991) 333
Storz, F., see Cunningham 111 (1991) 515
Storz, F.G., see Cunningham 120 (1992) 306
Storz, F.G., see Chiu 120 (1992) 343
Stradling, R.A., see Yuen 111 (1991) 943
Streetman, B.G., see Chu 111 (1991) 26
Streetman, B.G., see Block 111 (1991) 98
Strehblow, H.-H., see Homyonfer 117 (1992) 1080
Stringfellow, G.B., see Li 112 (1991) 515
Stringfellow, G.B., see Cao 113 (1991) 441
Stringfellow, G.B., Fundamental aspects of vapor growth and epitaxy 115 (1991) 1
Ströbel, J.P., see Markl 113 (1991) 395
Strong, R.K., B.L. Stoddard, A. Arrott and G.K. Farber, Long duration growth of protein crystals in microgravity aboard the MIR space station 119 (1992) 200
Su Genbo, see Huang 112 (1991) 729
Su Genbo, see He 113 (1991) 157
Su Genbo, see He 113 (1991) 161
Su Genbo, see Huang 119 (1992) 309
Su Genbo, Li Zhengdong, Pan Rfen, Wu Dexiang and Yang Tongqin, Growth of large crystals of pentaerythritol and tris-hydroxymethylaminomethone 119 (1992) 368
Su Genbo, see He 119 (1992) 393
Su, L.M., see Künzel 111 (1991) 461
Subotić, B., see Kolar 116 (1992) 473
Suda, T., see Kakishita 115 (1991) 793
Suddath, F.L., see Wilson 116 (1992) 414
Sudersena Rao, T. and Y. Horikoshi, Growth of $(GaAs)_{1-x}(Si_2)_x$ metastable alloys using migration-enhanced epitaxy 115 (1991) 328
Suemune, I., K. Nakanishi, Y. Fujii, Y. Kuroda, M. Fujimoto and M. Yamanishi, Photopumped ZnSe/ZnSSe blue semiconductor lasers and a theoretical calculation of the optical gain 117 (1992) 1068
Suemune, I., see O'Donnell 117 (1992) 1077
Suemune, I., Are common-anion and common-cation heterostructures applicable as excellent II–VI laser materials? 117 (1992) 1083
Sugawara, A. and O. Nittono, Interface structures of Pt/Au(001) epitaxial bilayer films prepared by means of ion beam sputtering 115 (1991) 596
Sugawara, H., see Nishikawa 112 (1991) 628
Sugawara, H., see Nishikawa 119 (1992) 292
Sugawara, K., see Hayashi 115 (1991) 782
Sugawara, M., see Mukai 115 (1991) 433
Sugimoto, T., see Hayashi 115 (1991) 782
Sugimoto, Y., see Hiratani 111 (1991) 570
Sugita, Y., see Katoh 112 (1991) 368
Sugiura, H., see Sato 115 (1991) 241
Sugiura, H., see Yamada 120 (1992) 177
Sugiura, H., R. Iga and T. Yamada, Laser-assisted chemical beam epitaxy for selective growth 120 (1992) 389
Sugiura, K., see Domen 115 (1991) 529
Sugiura, L., see Shigenaka 117 (1992) 37
Sugiura, L., see Shigenaka 117 (1992) 49
Sugiyama, I., A. Hobbs, T. Saito, O. Ueda, K. Shinohara and H. Takigawa, Dislocation reduction in HgCdTe epilayers on GaAs by using CdTe/CdZnTe strained-layer superlattices in CdTe layers 117 (1992) 161
Sugiyama, I., see Hobbs 117 (1992) 475
Sugiyama, K., K. Mori and H. Miyake, Epitaxial growth of $CuAlSe_2$ on $CuGaSe_2$ substrates 113 (1991) 390
Sugiyama, K., K. Mori, M. Tajima and H. Miyake, Thermodynamic study of equilibrium in the $CuGa_xIn_{1-x}Se_2$–I_2 system 118 (1992) 41
Sugiyama, M., see Mantani 114 (1991) 71
Sugiyama, Y., Y. Takeuchi and M. Tacano, High electron mobility pseudomorphic $In_{0.52}Al_{0.48}As/In_{0.8}Ga_{0.2}As$ heterostructure on InP grown by flux-stabilized MBE 115 (1991) 509
Suguwara, M., see Domen 115 (1991) 529

Suh, E.-K., Spin-flip Raman scattering and photoluminescence in modulation doped $CdTe/Cd_{1-x}Mn_xTe$: In superlattices 117 (1992) 890
Sui, M.L., see Lu 113 (1991) 242
Suisky, D., see Hommel 117 (1992) 721
Suita, M., see Yasumura 117 (1992) 20
Suita, M., see Takada 117 (1992) 44
Sulzer, G., see Waldmann 117 (1992) 715
Summers, C.J., see Benz 111 (1991) 725
Sun, B.N., R. Boutellier, Ph. Sciau, E. Burkhardt, V. Rodriguez and H. Schmid, High temperature solution growth of perovskite Pb_2CoWO_6 single crystals 112 (1991) 71
Sun, C.Y., see Liu 114 (1991) 700
Sun, Q, see Roth 113 (1991) 379
Sun, Q., see Roth 120 (1992) 212
Sun, S.Z., E.A. Armour, K. Zheng and C.F. Schaus, Zinc and tellurium doping in GaAs and $Al_xGa_{1-x}As$ grown by MOCVD 113 (1991) 103
Sun Weiguo and Wang Bin, The characterization of HgCdTe passivated with native fluoride-oxide and Sb_2S_3 coating 117 (1992) 183
Sunder, W.A., see Laudise 118 (1992) 277
Susuki, M., M. Ishikawa, K. Itaya, Y. Nishikawa, G. Hatakoshi, Y. Kokubun, J. Nishizawa and Y. Oyama, Electrical characterization of Si-donor-related shallow and deep states in InGaAlP alloys grown by metalorganic chemical vapor deposition 115 (1991) 498
Suto, K., see Sakurai 112 (1991) 153
Suzuki, A., Y. Fujii, H. Saito, Y. Tajima, K. Furukawa and S. Nakajima, Effect of the junction interface properties on blue emission of SiC blue LEDs grown by step-controlled CVD 115 (1991) 623
Suzuki, D., see Imai 117 (1992) 406
Suzuki, J., see Yoshida 113 (1991) 221
Suzuki, K., see Hase 115 (1991) 788
Suzuki, K., M. Nakamura, I. Souma, K. Yanata, Y. Oka, H. Fujiyasu and H. Noma, Magneto-optical properties of low-dimensional excitons in microcrystals and superlattices of $Cd_{1-x}Mn_xTe$ 117 (1992) 881
Suzuki, M., M. Kagawa, Y. Syono and T. Hirai, Thin films of rare-earth (Y, La, Ce, Pr, Nd, Sm) oxides formed by the spray-ICP technique 112 (1991) 621
Suzuki, M., Y. Nishikawa, M. Ishikawa and Y. Kokubun, Effects of substrate misorientation on doping characteristics and band gap energy for InGaAlP crystals grown by metalorganic chemical vapor deposition 113 (1991) 127
Suzuki, T., see Tanaka 111 (1991) 168
Suzuki, T. and T. Nishinaga, Surface diffusion and atom incorporation kinetics in MBE of InGaAs and AlGaAs 111 (1991) 173
Suzuki, T. and A. Gomyo, Re-examination of the formation mechanism of CuPt-type natural superlattices in alloy semiconductors 111 (1991) 353
Suzuki, T., see Iizuka 111 (1991) 429
Suzuki, T., see Itakura 115 (1991) 154
Suzuki, T., T. Soga, T. Jimbo and M. Umeno, Growth mechanism of GaP on Si substrate by MOVPE 115 (1991) 158
Suzuki, T., see Nishinaga 115 (1991) 398
Suzuki, T., see Hattori 115 (1991) 607
Suzuki, T., see Omino 117 (1992) 80
Suzuki, T., see Okamoto 117 (1992) 943
Suzuki, Y., see Kinoshita 115 (1991) 561
Svensson, S.P., W.A. Beck, D.C. Martel, P.N. Uppal and D.C. Cooke, Influence of nonuniform charge distribution in $In_{0.53}Ga_{0.47}As$ on the interpretation of dopant incorporation 111 (1991) 450
Svensson, S.P., see Uppal 111 (1991) 623
Sveshtarov, P. and M. Gospodinov, The effect of the interface shape on automatic Czochralski weight diameter control system performance 113 (1991) 186
Sveshtarov, P. and M. Gospodinov, The melt level technique of automatic Czochralski crystal growth; basic theory and comparison with the weighing method 118 (1992) 439
Swaminathan, V., see Asom 111 (1991) 246
Swaminathan, V., see Asom 111 (1991) 260
Swaminathan, V., see McCrary 112 (1991) 39
Sweck, J., see Bauer 117 (1992) 297
Swenberg, J.F., see Phillips 117 (1992) 1050
Świątek, K., see Godlewski 117 (1992) 634
Syono, Y., see Suzuki 112 (1991) 621

Tabuchi, M., S. Noda and A. Sasaki, Strain energy and critical thickness of heteroepitaxial InGaAs layers on GaAs substrate 115 (1991) 169
Tacano, M., see Sugiyama 115 (1991) 509
Tłaczała, M., see Helak 115 (1991) 294
Taguchi, T., see Yamada 117 (1992) 484
Taguchi, T., see Mullins 117 (1992) 501
Taguchi, T., see Brown 117 (1992) 536
Tai, C.Y., J.F. Wu and R.W. Rousseau, Interfacial supersaturation, secondary nucleation, and crystal growth 116 (1992) 294
Tai, K., see Hong 111 (1991) 1052
Tai, K., see Wang 111 (1991) 1057
Tai, K., see Hong 111 (1991) 1071
Taike, A., see Migita 111 (1991) 776
Taira, K., see Nakamura 115 (1991) 474

Tajima, M., see Terashima 111 (1991) 920
Tajima, M., see Sugiyama 118 (1992) 41
Tajima, S., Y. Mizuo, T. Wada, Y. Yaegashi, A. Ichinose, T. Takata, N. Koshizuka and H. Yamauchi, Crystal growth of superconducting $(Eu,Ce)_2(Ba,Eu)_2Cu_3O_{8+z}$ 114 (1991) 59
Tajima, Y., see Suzuki 115 (1991) 623
Takada, H., see Yasumura 117 (1992) 20
Takada, H., T. Murakami, M. Suita, K. Yasumura, Y. Endo, K. Takahashi and M. Nunoshita, The growth rate of $Cd_xHg_{1-x}Te$ grown by metalorganic chemical vapor deposition 117 (1992) 44
Takada, Y., see Sawada 117 (1992) 826
Takagi, Y., see Takeyama 117 (1992) 1081
Takahashi, H., see Hase 115 (1991) 788
Takahashi, K., see Yamada 111 (1991) 584
Takahashi, K., see Takemura 111 (1991) 802
Takahashi, K., S. Nishino and J. Saraie, Effect of acceptor impurity addition in low temperature growth of 3C-SiC 115 (1991) 617
Takahashi, K., see Teraguchi 115 (1991) 798
Takahashi, K., see Kimura 116 (1992) 283
Takahashi, K., see Yasumura 117 (1992) 20
Takahashi, K., see Takada 117 (1992) 44
Takahashi, K., see Takemura 117 (1992) 144
Takahashi, K., K. Shibuya and A. Kondo, Degradation induced by the Sr^{2+} vacancies in SrS:Ce electroluminescent devices 117 (1992) 979
Takahashi, K., see Tokumitsu 120 (1992) 301
Takahashi, S., see Koguchi 111 (1991) 688
Takahashi, T., see Sandhu 111 (1991) 559
Takahashi, T., see Ando 120 (1992) 228
Takahashi, Y., see Kuriyama 113 (1991) 333
Takai, T., see Tomino 113 (1991) 633
Takami, A., Z. Kawazu, T. Takiguchi, K. Mitsui, K. Mizuguchi, T. Murotani, K. Yasumura, T. Kanno and M. Saga, High quality p-$Cd_{0.22}Hg_{0.78}Te$ grown by liquid-phase epitaxy 117 (1992) 16
Takamori, T. and J.J. Boland, On pyrochlore-type bismuth platinum oxide 112 (1991) 660
Takano, K., see Matsumura 115 (1991) 194
Takano, Y., M. Lopez, T. Torihata, T. Ikei, Y. Kanaya, K. Pak and H. Yonezu, Realization of mirror surface in (111)- and (110)-oriented GaAs by migration-enhanced epitaxy 111 (1991) 216
Takano, Y., see Maruyama 115 (1991) 180
Takanohashi, T. and M. Ozeki, Exciton-absorption transitions in $(GaP)_n(GaAs)_n$/GaAs atomic/layer superlattices 115 (1991) 538
Takashima, M., see Nagao 111 (1991) 521
Takata, S., see Minami 117 (1992) 370
Takata, S., see Miyata 117 (1992) 1021
Takata, T., see Tajima 114 (1991) 59
Takaya, M., see Tokizaki 117 (1992) 603
Takayanagi, K., see Iwanari 119 (1992) 229
Takayanagi, K., see Iwanari 119 (1992) 241
Takei, H., T. Hamada and T. Hariu, Plasma-assisted epitaxy on InAs layers on GaAs 115 (1991) 309
Takemura, Y., H. Nakanishi, M. Konagai, K. Takahashi, Y. Nakamura and N. Otsuka, $(ZnSe)_m$–$(ZnTe)_n$ short-period strained layer superlattices prepared by atomic layer epitaxy 111 (1991) 802
Takemura, Y., M. Konagai, H. Nakanishi and K. Takahashi, Self-limiting growth with 0.5 monolayer per cycle in atomic layer epitaxy of ZnTe 117 (1992) 144
Takenaka, C., see Kusunoki 112 (1991) 33
Takenaka, C., see Nakajima 113 (1991) 485
Takenaka, C., and T. Kusunoki and K. Nakajima, Solute transport mechanism during liquid phase epitaxial (LPE) growth with an applied current 114 (1991) 293
Takenaka, C., see Kato 115 (1991) 174
Takenaka, C., see Kusunoki 115 (1991) 723
Takeuchi, H., see Ito 112 (1991) 427
Takeuchi, K., see Saiki 117 (1992) 802
Takeuchi, M., see Shimomura 111 (1991) 1105
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Takeuchi, Y., see Sugiyama 115 (1991) 509
Takeuchi, Y., see Fujiyasu 117 (1992) 1026
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Takigawa, H., see Ebe 115 (1991) 718
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Takigawa, H., see Sugiyama 117 (1992) 161
Takigawa, H., see Hobbs 117 (1992) 475
Takigawa, T., see Murakami 117 (1992) 33
Takiguchi, T., see Takami 117 (1992) 16
Tamaoka, E., see Shimomura 111 (1991) 1105
Tamargo, M.C., R.E. Nahory, B.J. Skromme, S.M. Shibli, A.L. Weaver, R.J. Martin and H.H. Farrell, Surface stoichiometry effects on ZnSe/GaAs heteroepitaxy 111 (1991) 741
Tamargo, M.C., see Aspnes 120 (1992) 71
Tamulaitis, G., see Baltramiejũnas 117 (1992) 622

Tamura, S., see Yokota 119 (1992) 195
Tan, Hao-Ran, see Zhou 114 (1991) 87
Tanahashi, T., see Anayama 115 (1991) 65
Tanahashi, T., see Kato 115 (1991) 174
Tanahashi, T., see Kondo 115 (1991) 231
Tanahashi, T., see Domen 115 (1991) 529
Tanaka, A., see Ekawa 117 (1992) 254
Tanaka, A., see Seto 117 (1992) 271
Tanaka, H. and M. Mushiage, MBE as a production technology for AlGaAs lasers 111 (1991) 1043
Tanaka, H., see Kikkawa 115 (1991) 448
Tanaka, H., see Aspnes 120 (1992) 71
Tanaka, K., see Kudo 111 (1991) 402
Tanaka, K., see Lee 115 (1991) 164
Tanaka, M., T. Suzuki and T. Nishinaga, Surface diffusion of Al and Ga atoms on GaAs (001) and (111)B vicinal surfaces in molecular beam epitaxy 111 (1991) 168
Tanaka, M., see Noda 111 (1991) 348
Tanaka, M., see Kaneko 115 (1991) 643
Tanaka, M., K. Ozaki, K. Yamamoto, H. Ebe and Y. Miyamoto, Epitaxial growth of HgCdTe on sapphire for photoconductive detectors 117 (1992) 24
Tanaka, S., see Yanagase 115 (1991) 304
Tanaka, S., see Kita 115 (1991) 752
Tanaka, S., see Hayashi 115 (1991) 782
Tanaka, S., see Hase 115 (1991) 788
Tanaka, S., see Koyama 117 (1992) 156
Tanaka, S., see Yodo 117 (1992) 415
Tanaka, S., S. Morimoto, K. Yamada, H. Kobayashi, Zhi-Lin Zhang and Xue-Yin Jiang, Excitation mechanism of Tm^{3+} centers in ZnS electroluminescent thin films 117 (1992) 997
Tanaka, T., see Otani 113 (1991) 329
Tanaka, T., see Minagawa 118 (1992) 425
Tanakov, M.Yu., see Trusov 114 (1991) 133
Tanbo, T., see Tatsuyama 115 (1991) 112
Tang Dingyuan, see Yang 114 (1991) 351
Tang Guang Kui, see Cheng 112 (1991) 294
Tang, H.P., J.Y. Feng, Y.D. Fan and H.D. Li, Growth of CdTe films on GaAs by ionized cluster beam epitaxy 112 (1991) 407
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Tang Hong Gao, see Cheng 112 (1991) 294
Tang, Lian-An, see Zhou 114 (1991) 87
Tanigaki, K., S. Kuroshima, T.W. Ebbesen and T. Ichihashi, Growth of thin film crystals of monochloro(meso-tetraphenylporphyrinato) gallium by organic MBE 114 (1991) 3
Tanigashira, K., see Kinto 117 (1992) 348
Tanigawa, S., see Miyajima 117 (1992) 694
Tanino, H., see Yao 111 (1991) 823
Tanishiro, Y., see Shima 115 (1991) 359
Tanner, P.G., see Morris 117 (1992) 929
Tansley, T.L., see Giugni 111 (1991) 50
Tao, F., see Zhong 119 (1992) 74
Tao, Y.K., H.C. Chen, L. Martini, J. Bechtold, Z.J. Huang and P.H. Hor, Crystal growth of $YBa_2Cu_3O_{7-x}$ and reaction of gold crucible with Ba–Cu-rich flux 114 (1991) 279
Tapfer, L., see Crook 111 (1991) 184
Tapfer, L., see Ploog 111 (1991) 344
Tapfer, L., see Brandt 111 (1991) 383
Tapfer, L., see Brandt 115 (1991) 99
Tappura, K., T. Hakkarainen, K. Rakennus, M. Hovinen and H. Asonen, The influence of growth conditions on the composition of GaInAsP grown by gas-source molecular beam epitaxy 112 (1991) 27
Tappura, K., T. Hakkarainen, K. Rakennus and H. Asonen, Temperature dependency of the composition of GaInAsP grown by GSMBE 120 (1992) 145
Tappura, K., see Zhang 120 (1992) 172
Tarabaev, L.P., A.Yu. Mashikhin and V.O. Esin, Dendritic crystal growth in supercooled melt 114 (1991) 603
Tareen, J.A.K., see Basavalingu 113 (1991) 659
Tatarenko, S., see Bassani 117 (1992) 391
Tatarenko, S., see Cibert 117 (1992) 424
Tatsumi, T., see Hirayama 111 (1991) 856
Tatsumi, T., see Aketagawa 111 (1991) 860
Tatsumi, T., see Terashima 111 (1991) 920
Tatsumi, T., I. Hirosawa, T. Niino, H. Hirayama and J. Mizuki, $\sqrt{3} \times \sqrt{3}$-B structure on a 5×5 Ge_xSi_{1-x}/Si(111) surface and its electrical conduction 111 (1991) 961
Tatsumi, T., K. Aketagawa, M. Hiroi and J. Sakai, Selective epitaxial growth by UHV-CVD using Si_2H_6 and Cl_2 120 (1992) 275
Tatsumi, T., see Hiroi 120 (1992) 279
Tatsuoka, H., H. Kuwabara, Y. Nakanishi and H. Fujiyasu, New approach to the mechanism of strain release in lattice-mismatched epitaxial films 117 (1992) 554
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Taylor, A., see Joyce 115 (1991) 338
Taylor, A.G., see Armstrong 120 (1992) 94
Taylor, J.P.G., see Myers-Beaghton 111 (1991) 328
Taylor, K.N.R., A. Nouruzi-Khorasani, M. Indro, G.J. Russell, M.I. Darby, Y. Feng, I.P. Jones and R.E. Smallman, Intersections of twins and of optical domains in crystalline $YBa_2Cu_3O_{7-\delta}$ 119 (1992) 221
Tell, B., see Chang 111 (1991) 475
Tenne, R., see Azoulay 117 (1992) 276

Tenne, R., see Galun 117 (1992) 666
Tenne, R., see Homyonfer 117 (1992) 1080
Terada, K., see Mikami 117 (1992) 991
Terada, T., Y. Fujita, S. Fujii and T. Iuchi, Composition control in $Hg_{1-x}Cd_xTe$ growth by photoassisted MOCVD using an excimer laser 117 (1992) 54
Teraguchi, N., M. Konagai, F. Kato and K. Takahashi, Growth and characterization of Ga_2Se_3 by molecular beam epitaxy 115 (1991) 798
Terasaki, T., see Tatsuyama 115 (1991) 112
Terashima, K., M. Tajima, A. Sakai and T. Tatsumi, Dislocation-related photoluminescence in $Si_{1-x}Ge_x$/Si(100) grown by molecular beam epitaxy 111 (1991) 920
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Terauchi, H., see Terashima 115 (1991) 745
Terry, F.L., see Sherwin 111 (1991) 594
Terry, F.L., see Sherwin 111 (1991) 605
Terry, Jr., F.L., see Sherwin 120 (1992) 162
Testa, A., see Leccabue 112 (1991) 644
Tewari, S.N. and M.A. Chopra, Break-down of a planar liquid–solid interface during directional solidification; influence of convection 118 (1992) 183
Tezuka, T., see Itoh 117 (1992) 835
Thambipillai, V., see Jones 118 (1992) 1
Theunissen, M.J.J., J.M.L. van Rooij-Mulder, C.W.T. Bulle-Lieuwma, D.E.W. Vandenhoudt, D.J. Gravesteijn and G.F.A. van de Walle, TEM analysis of voids in UHV-deposited amorphous Si layers used for lateral solid phase epitaxial growth 118 (1992) 125
Thevuthasan, S., see Lyman 113 (1991) 45
Thibierge, H., see Benchimol 120 (1992) 189
Thomas, C.R., see Capano 116 (1992) 260
Thomas, P., see McCrary 112 (1991) 39
Thompson, N., see Loginov 117 (1992) 259
Thompson, N., see Loginov 117 (1992) 682
Thompson, R.D., see Schowalter 111 (1991) 948
Thrush, C.M., see Partin 111 (1991) 614
Thrush, C.M., see Youngdale 111 (1991) 693
Thrush, E.J., see Stagg 120 (1992) 98
Thurian, P., R. Heitz, A. Hoffmann and I. Broser, Nonlinear Zeeman effect of the Ni^{3+} centre in ZnO 117 (1992) 727
Tietz, F., J. Koepke and W. Urland, Analytical investigations of β-Al_2O_3 and β''-Al_2O_3 crystals 118 (1992) 314
Tiller, W.A., see Yen 113 (1991) 549
Tiller, W.A., see Yen 118 (1992) 85
Tiller, W.A., see Yen 118 (1992) 259
Timmons, M.L., see Venkatasubramanian 112 (1991) 7
Timmons, M.L., see Xing 113 (1991) 113
Ting, D.Z.-Y., see Collins 111 (1991) 664
Tiong, S.R., see Matsushima 117 (1992) 328
Tissot, P., see Licci 112 (1991) 600
Tiwari, A.N., W. Floeder, S. Blunier, H. Zogg and M.J. Proctor, Heteroepitaxy of CdTe(100) on Si(100) using BaF_2–CaF_2 (100) buffer layers 111 (1991) 730
Tobin, R., see Tower 114 (1991) 665
Toda, T., see Hishida 117 (1992) 396
Tohda, H., see Iijima 116 (1992) 319
Tohda, T., see Okajima 117 (1992) 810
Tohno, S., see Ando 117 (1992) 560
Tokizaki, T., H. Akiyama, M. Takaya and A. Nakamura, Linear and nonlinear optical properties of CdS microcrystallites in glasses 117 (1992) 603
Tokuda, H., see Yokota 119 (1992) 195
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Tomino, H., I. Kusaka, K. Nishioka and T. Takai, Interfacial tension for small nuclei in binary nucleation 113 (1991) 633
Tomita, A., see Ohsawa 116 (1992) 351
Tomita, K., F. Kitagawa, H. Kano and M. Hashimoto, Uniform growth of Te-doped $Al_xGa_{1-x}As$ ($x = 0$–0.65) on (111)B GaP substrates by liquid phase epitaxy 115 (1991) 299
Tomm, J.W., see Herrmann 117 (1992) 758
Tomofuji, T., see Minami 117 (1992) 370
Torihara, H., see Ohishi 111 (1991) 792
Torihata, T., see Takano 111 (1991) 216
Toth, D.W., see Luo 119 (1992) 407
Tougaard, S., see Hansen 116 (1992) 271
Tovar, R., see Quintero 114 (1991) 661
Tower, J.P., R. Tobin, P.J. Pearah and R.M. Ware, Interface shape and crystallinity in LEC GaAs 114 (1991) 665
Toyoda, K., see Lu 114 (1991) 64
Trager-Cowan, C., see O'Donnell 117 (1992) 497
Trager-Cowan, C., P.J. Parbrook, F. Yang, X. Chen, B. Henderson, K.P. O'Donnell, B. Cockayne and P.J. Wright, Electron beam excitation and profiling of strained CdS epilayers grown by metalorganic vapour phase epitaxy on GaAs(111)A, GaAs(100), ZnSe(100) and ZnS(100) substrates 117 (1992) 532
Tran, D., H.C. Lee, C. Tu, T. Kim and L.C. Chiu, Novel surface preservation technique for large area growth of (100) InP substrate by LPE 113 (1991) 16
Tränkle, G., see Rothfritz 120 (1992) 130

Tränkle, G., H. Rothfritz, R. Müller and G. Weimann, CBE growth of high-quality AlGaAs/GaAs heterostructures for HEMT applications 120 (1992) 240
Trauth, J. and B.C. Grabmaier, The shape of the crystal/melt interface during the growth of lithium niobate crystals by the Czochralski technique 112 (1991) 451
Treichler, R., see Heinecke 111 (1991) 599
Treichler, R., see Beer 120 (1992) 312
Triboulet, P. and M. Cournil, Growth of potassium dihydrogen phosphate crystals nucleated in the presence of aluminium(III) 118 (1992) 231
Triboulet, R., see Marbeuf 117 (1992) 10
Triboulet, R., see Bagot 117 (1992) 189
Triboulet, R., see Marbeuf 117 (1992) 197
Triboulet, R., see Rolland 117 (1992) 208
Triboulet, R., A. Durand, P. Gall, J. Bonnafé, J.P. Fillard and S.K. Krawczyk, Qualification by optical means of CdTe substrates 117 (1992) 227
Triboulet, R., see Benhlal 117 (1992) 281
Triboulet, R., see Katty 118 (1992) 470
Trommer, D., see Künzel 111 (1991) 1084
Tronin, A.Yu., Ellipsometric study of growing crystal face: $(10\bar{1}0)$ $LiIO_3$ 116 (1992) 63
Truscott, W.S., see Missous 111 (1991) 1116
Trusov, L.I., M.Yu. Tanakov, V.G. Gryaznov, A.M. Kaprelov and A.E. Romanov, Relaxation of elastic stresses in overlayed microcrystals 114 (1991) 133
Tsach, T., see Schieber 115 (1991) 31
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Tsao, J.Y., T.M. Brennan and B.E. Hammons, Oscillatory As_4 surface reaction rates during molecular beam epitaxy of AlAs, GaAs and InAs 111 (1991) 125
Tsotsis, T.T., see Francis 112 (1991) 474
Tsubouchi, K., see Kaneko 115 (1991) 643
Tsuda, H. and T. Mizutani, A reflection high-energy electron diffraction study of growth processes at step edges during molecular beam epitaxy of GaAs and AlAs 111 (1991) 88
Tsuda, M., S. Oikawa and S. Furukawa, Epitaxial growth mechanism at S_B steps of Si(001) surfaces by photo-induced $Si(^1D)$ atoms 115 (1991) 556
Tsuji, O., see Funato 117 (1992) 543
Tsuji, T., see Yoshimoto 115 (1991) 265
Tsukamoto, K., see Sakai 116 (1992) 421
Tsuruoka, T., see Gao 117 (1992) 983
Tsutsui, K., see Minemura 114 (1991) 307
Tu, C., see Tran 113 (1991) 16
Tu, C.W., see Liang 111 (1991) 550
Tu, C.W., see Hou 120 (1992) 167
Tu, L.W., see Hong 111 (1991) 1052
Tuncel, E., see Baeta Moreira 112 (1991) 14
Tuomi, T., see Ravila 114 (1991) 569
Turchaninov, A.M., see Burdin 119 (1992) 61
Turchaninov, A.M., see Regel 119 (1992) 94
Turchaninov, A.M., see Volkov 119 (1992) 122
Turco-Sandroff, F.S., see Moisson 111 (1991) 141
Turco-Sandroff, F.S., R.E. Nahory, M.J.S.P. Brasil, R.J. Martin, R. Beserman, L.A. Farrow, J.M. Worlock and A.L. Weaver, Molecular beam epitaxy of Zn(Se,Te) alloys and superlattices 111 (1991) 762
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Turner, G.W., see Eglash 111 (1991) 669

Uchida, H., see Miyazaki 113 (1991) 227
Uchida, K., see Matsumoto 115 (1991) 484
Uchida, N., T. Kurita, H. Ohkoshi, K. Uematsu and K. Saito, Thermochemical etching effect of H_2O vapor on CVD diamond film 114 (1991) 565
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Uchida, T., see Uchida 111 (1991) 1062
Uchida, T.K., T. Uchida, K. Mise, N. Yokouchi, F. Koyama and K. Iga, GaInAs/InP MQW and DBR growth for surface emitting lasers by CBE 111 (1991) 1062
Uchida, T.K., see Uchida 120 (1992) 357
Uchida, W., see Isshiki 117 (1992) 410
Uchiki, H., see Kinto 117 (1992) 348
Ueba, H., see Tatsuyama 115 (1991) 112
Ueda, O., K. Kitahara, N. Ohtsuka, A. Hobbs and M. Ozeki, Transmission electron microscopic study of AlAs/Si heterostructures grown by atomic layer epitaxy 115 (1991) 113
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Ueda, O., see Nakata 115 (1991) 504
Ueda, O., T. Kimura, H. Yamawaki and M. Ihara, Study of the microstructure of CVD-grown Bi–Sr–Ca–Cu–O thin films on (001) MgO substrates by high-resolution transmission electron microscopy 115 (1991) 774
Ueda, O., see Sugiyama 117 (1992) 161
Ueda, O., K. Maruyama, A. Hobbs and K. Shinohara, Transmission electron microscopic evaluation of metalorganic chemical vapor deposition-grown CdTe crystals on sapphire substrates 117 (1992) 266
Ueda, O., see Hobbs 117 (1992) 475
Ueda, T., see Ueda 112 (1991) 507
Ueda, T., see Ueda 113 (1991) 69
Ueda, Y., T. Ueda, M. Fukuoka and M. Ashida, Epitaxial growth of 2,5-distyrylpyrazine from the vapor phase 112 (1991) 507
Ueda, Y., M. Fukuoka, T. Ueda and M. Ashida, Photopolymerization of vapor-deposited 2,5-distyrylpyrazine films 113 (1991) 69
Uematsu, K., see Uchida 114 (1991) 565
Uemoto, T., see Shigenaka 117 (1992) 37
Uemoto, T., see Shigenaka 117 (1992) 49
Uemoto, T., see Kamata 117 (1992) 96
Uen, W.Y., S. Sakawa and T. Nishinaga, Comparative study of amorphous and crystalline buffer layers in MBE growth of GaAs on Si 115 (1991) 122
Ueno, A., see Ohkawa 117 (1992) 375
Ueno, K., see Koma 111 (1991) 1029
Ueno, K., see Ohuchi 111 (1991) 1033
Uesugi, F., see Ohshita 115 (1991) 551
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Ulmer, L., see Pautrat 117 (1992) 454
Ulmer, L., see Bleuse 117 (1992) 1046
Umeno, M., see Itakura 115 (1991) 154
Umeno, M., see Suzuki 115 (1991) 158
Umeno, M., see Soga 115 (1991) 418
Umeno, M., see Egawa 115 (1991) 524
Unno, T., see Yazawa 115 (1991) 519
Unterbörsch, G., see Künzel 111 (1991) 1084
Uppal, P.N., see Svensson 111 (1991) 450
Uppal, P.N., D.M. Gill, S.P. Svensson and D.C. Cooke, Transport properties of heterostructures based on GaSb, InAs and InSb on GaAs substrates 111 (1991) 623
Uraltsev, I.N., see Yakovlev 117 (1992) 854
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Urban, M., see Schwab 117 (1992) 778
Urland, O., see Tietz 118 (1992) 314
Usui, A., see Sasaoka 115 (1991) 94
Uwai, K., Sequential self-limiting growth of CuO on MgO(100) by chemical vapor deposition 112 (1991) 298

Van de Walle, C.G., D.B. Laks, G.F. Neumark and S.T. Pantelides, Solubilities, defect reactions and doping limits in ZnSe 117 (1992) 704
Van de Walle, G.F.A., see Gravesteijn 111 (1991) 916
Van de Walle, G.F.A., see Theunissen 118 (1992) 125
Van den Heuvel, R.A., see Gravesteijn 111 (1991) 916
Van der Eerden, J.P., see Vogels 114 (1991) 239
Van der Eerden, see Van der Heijden 118 (1992) 14
Van der Heijden, A.E.D.M. and J.P. van der Eerden, Growth rate dispersion: the role of lattice strain 118 (1992) 14
Van der Mooren, M., see Bolt 112 (1991) 773
Van der Mooren, M.H., see Bolt 114 (1991) 141
Van der Voort, E. and P. Hartman, The habit of gypsum and solvent interaction 112 (1991) 445
Van Eck, T.E., see Niki 111 (1991) 419
Van Enckevort, W.J.P., G. Janssen and L.J. Giling, Anisotropy in monocrystalline CVD diamond growth. I. A sphere growth experiment 113 (1991) 295
Van Enckevort, W.J.P., Phase shifting interferometry of growth patterns on the octahedral faces of natural diamonds 119 (1992) 177
Van Enckevort, W.J.P., see Bolt 119 (1992) 329
Van Haren, D.L., see McCrary 112 (1991) 39
Van Koeven, P.A., see Vogels 114 (1991) 239
Van Rooij-Mulder, J.M.L., see Theunissen 118 (1992) 125
Van Rosmalen, G.M., see Verdoes 118 (1992) 401
Van Saarloos, W., see Weeks 112 (1991) 244
Vandenberg, J.M., see Hong 111 (1991) 1071
Vandenhoudth, D.E.W., see Theunissen 118 (1992) 125

Vanderah, T.A., C.K. Lowe-Ma, D.E. Bliss, M.W. Decker, M.S. Osofsky, E.F. Skelton and M.M. Miller, Growth of near-free-standing $YBa_2Cu_3O_7$-type crystals using a self-decanting flux method 118 (1992) 385
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Varga, I.K., see Hartley 117 (1992) 166
Vaudo, R.P., see Ren 117 (1992) 510
Vázquez, C., see Rivas 116 (1992) 127
Vekilov, P.G. and Yu.G. Kuznetsov, Growth kinetics irregularities due to changed dislocation source activity; (101) ADP face 119 (1992) 248
Velthaus, K.O., see Mauch 117 (1992) 964
Vening, M., see Foxon 111 (1991) 1047
Venkatasubramanian, R., M.L. Timmons, S. Bothra and J.M. Borrego, Optimization of the heteroepitaxy of Ge on GaAs for minority-carrier lifetime 112 (1991) 7
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Verma, M., see Ashenford 117 (1992) 233
Vescan, L., see Tang 116 (1992) 1
Vesenka, J.P., see Feeney 113 (1991) 417
Vignoles, G.L., Atomic relaxation and dynamical generation of ordered and disordered chemical vapour infiltration (CVI) SiC polytypes 118 (1992) 430
Villers, D., see Point 114 (1991) 228
Viney, I.V.F., B. Ray, J.W. Brightwell and B. Arterton, Excitation and fluorescence spectra in $Ca_{1-x}Cd_xS$ solid solutions 117 (1992) 806
Viney, I.V.F., see Arterton 117 (1992) 1008
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Voegel, J.C., see Cuisinier 116 (1992) 314
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Volkov, V.T., see Gruzintsev 117 (1992) 975
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Voorhees, P.W., see Hardy 114 (1991) 467
Vorobiov, P.A., N.A. Baturin and O.V. Shumaev, Laminar convection in the melt during crystal growth in a centrifuge 119 (1992) 111
Vreeland, T., see Tsai 111 (1991) 931
Vuorinen, P.T., see Podkletnov 114 (1991) 198
Vvedensky, D.D., see Myers-Beaghton 111 (1991) 162
Vvedensky, D.D., see Myers-Beaghton 111 (1991) 328
Vvedensky, D.D., see Wilby 111 (1991) 864
Vyas, J.C., see Muthe 118 (1992) 213

Waag, A., see Kuhn 117 (1992) 660
Waag, A., T.A. Kuhn, S. Schmeusser, B. Schmied, M.M. Kraus, N. Kallis, W. Ossau, R.N. Bicknell-Tassius and G. Landwehr, Photoassisted MBE growth of doped CdTe and CdMnTe thin films and their characterization 117 (1992) 820
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Wada, T., see Tajima 114 (1991) 59
Wada, T., see Ichimura 115 (1991) 479
Wada, T., see Ichimura 117 (1992) 689
Wadhawan, V., see Marfaing 118 (1992) 27
Wagner, B.K., see Benz 111 (1991) 725
Wagner, H.P., see Bauer 117 (1992) 297
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Wagner, J., see Ralston 111 (1991) 989

Wakahara, A., see Wang 115 (1991) 261
Wakamatsu, N., see Iijima 112 (1991) 467
Walck, S.D., see Allerman 112 (1991) 583
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Wallace, J.M., see Simpson 117 (1992) 134
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Walton, J.C., see Bell 117 (1992) 58
Wang Bin, see Sun 117 (1992) 183
Wang, C., see Chu 117 (1992) 1073
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Wang, Hailong, see Shen 111 (1991) 807
Wang, Hailong, see Cui 111 (1991) 811
Wang, Hailong, see Cui 117 (1992) 505
Wang, J.H., see Ren 112 (1991) 587
Wang, J.T., see Lu 112 (1991) 525
Wang, J.T., see Lu 113 (1991) 242
Wang, J.Y., Q.C. Guan, J.Q. Wei, M. Wang and Y.G. Liu, Growth and characterization of cubic $KTa_{1-x}Nb_xO_3$ crystals 116 (1992) 27
Wang, Jing-Chang, see Zhou 114 (1991) 87
Wang, Jing-Jing, see Shen 117 (1992) 470
Wang, K.L., see Wu 111 (1991) 252
Wang, K.L., see Kallel 111 (1991) 897
Wang, K.L., see Kuo 111 (1991) 996
Wang, M., see Wang 116 (1992) 27
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Wang, M.W., see Liu 117 (1992) 913
Wang, M.W., see Phillips 117 (1992) 1050
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Wang, Pei-Ling, see Zhou 114 (1991) 87
Wang, R.B., M. Sommer and F.W. Smith, The deposition of diamond films via the oxyacetylene torch: experimental results and thermodynamic predictions 119 (1992) 271
Wang, S.C., see Ho 111 (1991) 233
Wang, S.Y., see Simpson 117 (1992) 134
Wang, S.Y., see Wallace 117 (1992) 320
Wang, S.Y., see Zhang 117 (1992) 523
Wang, W.I., see Longenbach 111 (1991) 651
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Wang, Y., see Marfaing 118 (1992) 27
Wang, Y.H., see Hong 111 (1991) 1052
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Wang, Y.H., see Hong 111 (1991) 1071
Wang, Y.Z., see Zhou 114 (1991) 283
Wanklyn, B.M., see Chen 118 (1992) 101
Ware, R.M., see Tower 114 (1991) 665
Wargo, M.J. and A.F. Witt, Real time thermal imaging for analysis and control of crystal growth by the Czochralski technique 116 (1992) 213
Warren, A.C., see Melloch 111 (1991) 39
Wasilewski, Z., see Roth 113 (1991) 379
Wasilewski, Z., see Roth 120 (1992) 212
Wasilewski, Z.R., G.C. Aers, A.J. SpringThorpe and C.J. Miner, Growth uniformity studies in molecular beam epitaxy 111 (1991) 70
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Watanabe, A., see Hata 111 (1991) 83
Watanabe, A., see Isu 111 (1991) 210
Watanabe, A., M. Hata and T. Isu, Metalorganic molecular beam epitaxy of GaAs using hydrogen radical beam 111 (1991) 554
Watanabe, A., see Hata 114 (1991) 203
Watanabe, J., see Nakahara 117 (1992) 830
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Watanabe, S., see Kawai 112 (1991) 745
Watatani, H., see Nakao 115 (1991) 313
Watson, C.C.R., see Alnajjar 117 (1992) 385
Watson, D.J., see Rossetti, Jr. 116 (1992) 251
Watts, B.E., see Leccabue 112 (1991) 644

Watts, B.E., see Bocelli 113 (1991) 663
Waucquez, C., see Frijlink 115 (1991) 203
Weaver, A.L., see Tamargo 111 (1991) 741
Weaver, A.L., see Turco-Sandroff 111 (1991) 762
Webb, C., J.N. Eckstein and Y.M. Desai, Anisotropy in electronic transport of modulation doped structures having strained InGaAs wells 111 (1991) 309
Weber, W., see Müller 119 (1992) 8
Weeks, J.D., W. van Saarloos and M. Grant, Stability and shapes of cellular profiles in directional solidification: expansion and matching methods 112 (1991) 244
Wegener, M., see Chang 111 (1991) 475
Wegscheider, W., see Eberl 111 (1991) 882
Wei, J.Q., see Wang 116 (1992) 27
Wei, L., see Miyajima 117 (1992) 694
Weimann, G., see Reithmaier 111 (1991) 407
Weimann, G., see Rothfritz 120 (1992) 130
Weimann, G., see Tränkle 120 (1992) 240
Weinberg, F., see Parfeniuk 119 (1992) 261
Weir, B.E., see Headrick 111 (1991) 838
Weir, B.E., see Hong 111 (1991) 984
Weir, B.E., see Hong 111 (1991) 1052
Weir, D.G., see Hoke 111 (1991) 269
Weir, D.G., see Hoke 111 (1991) 1024
Weiss, M., see Horowitz 119 (1992) 391
Weman, H., see Miller 111 (1991) 323
West, K.W., see Pfeiffer 111 (1991) 333
West, K.W., see Eaglesham 111 (1991) 833
Westerwick, E., see Cunningham 120 (1992) 306
Westphalen, R., see Kayser 112 (1991) 111
Westwood, D.I., D.A. Woolf and S.A. Clark, Growth by molecular beam epitaxy of thick films on $In_xGa_{1-x}As$ ($x \sim 0.53$) on Si(100) substrates 114 (1991) 346
Weyers, M. and M. Sato, Growth of GaP by MOVPE at very low pressure: kinetics and carbon incorporation 115 (1991) 469
Whall, T.E., see Powell 111 (1991) 907
Whall, T.E., see Pike 111 (1991) 925
White, C.R.H., see Henini 111 (1991) 1089
Whitehouse, C.R., see Emeny 111 (1991) 413
Whitehouse, C.R., see Martin 120 (1992) 25
Whitehouse, C.R., see Lane 120 (1992) 245
Wicks, G.W., see Shank 111 (1991) 440
Wiedemeier, H., L.L. Regel and W. Palosz, Vapor transport and crystal growth of GaSe under normal and high acceleration 119 (1992) 79
Wieder, H.H., see Niki 111 (1991) 419
Wielunski, L.S., M.J. Kenny and G.N. Pain, Analysis of HgTe/CdTe MOCVD grown superlattice epitaxial structures on GaAs by ion beam techniques 117 (1992) 460
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Wilcox, W.R., see Banan 113 (1991) 557
Wilcox, W.R., see Caram 114 (1991) 249
Wilcox, W.R., see Seth 114 (1991) 357
Wilcox, W.R., see Arnold 119 (1992) 24
Wilcox, W.R., see Derebail 119 (1992) 98
Wilde, J.P., L. Hesselink and R.S. Feigelson, Diameter stabilization of Czochralski-grown $Sr_{0.61}Ba_{0.39}Nb_2O_6$ (SBN) crystals using real-time computer control 113 (1991) 337
Wilde, J.P., D.H. Jundt, L. Galambos and L. Hesselink, Growth of $Sr_{0.61}Ba_{0.39}Nb_2O_6$ fibers: new results regarding orientation 114 (1991) 500
Wilkens, B.J., see Harbison 111 (1991) 978
Wilkie, J.H., see Baxter 112 (1991) 373
Wilkins, S.W., see Gao 112 (1991) 487
Williams, G.M., see Lane 120 (1992) 245
Williams, J.O., see Wright 114 (1991) 99
Williams, J.O., see Zheng 117 (1992) 358
Williams, J.O., A.C. Wright and H.M. Yates, High resolution and conventional transmission electron microscopy in the characterisation of thin films and interfaces involving II–VI materials 117 (1992) 441
Williams, J.O., see Armitage 117 (1992) 1082
Williams, M.D., see Cunningham 120 (1992) 306
Williams, M.D., see Chiu 120 (1992) 343
Williams, R.L., F. Chatenoud and R. Normandin, MBE grown, visible, surface emitting harmonic generation lasers 111 (1991) 1066
Willoughby, A.F.W., see Archer 117 (1992) 177
Willoughby, A.F.W., see Aslam 117 (1992) 249
Wilson, L.J. and F.L. Suddath, Control of solvent evaporation in hen egg white lysozyme crystallization 116 (1992) 414
Wilson, R.G., see Metzger 111 (1991) 445
Winkelman, A.J.M., see Menken 113 (1991) 9
Wisk, P.W., see Abernathy 120 (1992) 234
Witt, A.F., see Cao 112 (1991) 838
Witt, A.F., see Cao 114 (1991) 255
Witt, A.F., see Wargo 116 (1992) 213
Witt, A.F., see Carlson 116 (1992) 461
Witt, A.F., see Laudise 118 (1992) 277
Woelk, E.G., see Sherwin 111 (1991) 594
Woelk, E.G., see Sherwin 111 (1991) 605
Woggon, U., Rückmann, J. Kornack, M. Müller, J. Cesnulevicius, M. Petrauskas and J. Kolenda, Interface transfer processes and spectral hole burning in CdSe quantum confined clusters 117 (1992) 608

Wolf, K., see Wagner 117 (1992) 303
Wolverson, D., see Nakano 117 (1992) 331
Woodall, J.M., see Melloch 111 (1991) 39
Woodall, J.M., see De Lyon 111 (1991) 564
Woodbridge, K., see Harris 111 (1991) 239
Woodbridge, K., K.J. Moore, N.L. Andrew and P.F. Fewster, Indium incorporation in GaInAs/GaAs quantum wells grown on GaAs 111 (1991) 339
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Woods, J., see Sang 113 (1991) 1
Woods, J., see Loginov 117 (1992) 259
Woolf, D.A., see Westwood 114 (1991) 346
Woolley, J.C., see Quintero 114 (1991) 661
Woolley, J.C., see Grima 119 (1992) 381
Worlock, J.M., see Turco-Sandroff 111 (1991) 762
Wörner, A., see Uhrig 117 (1992) 598
Worster, M.G., see Shirtcliffe 113 (1991) 566
Wright, A.C. and J.O. Williams, Detection of compound formation at the ZnSe/GaAs interface using high resolution transmission electron microscopy (HRTEM) 114 (1991) 99
Wright, A.C., see Williams 117 (1992) 441
Wright, P.J., see Dhese 117 (1992) 91
Wright, P.J., see Parbrook 117 (1992) 492
Wright, P.J., see O'Donnell 117 (1992) 497
Wright, P.J., see Trager-Cowan 117 (1992) 532
Wright, R.L., see Chaudhry 113 (1991) 120
Wroblewski, T., see Doyle 112 (1991) 302
Wu, B.J., Y.J. Mii, M. Chen, K.L. Wang and J.J. Murray, Reduced silicon donor incorporation in MBE grown GaAs layers using cracker-generated dimer arsenic 111 (1991) 252
Wu Bochang, see He 113 (1991) 157
Wu Bochang, see He 119 (1992) 393
Wu, C.Q., see Chu 117 (1992) 1073
Wu Dexiang, see Su 119 (1992) 368
Wu, J.F., see Tai 116 (1992) 294
Wu Jinhua, see Li 118 (1992) 371
Wu Jinhua, see Li 119 (1992) 363
Wu, M.C., see Chen 111 (1991) 659
Wu, M.C., S.C. Lu, C.Y. Lee and Y.C. Yang, Interface abruptness and LED performance of the AlGaAs/InGaP single heterostructure grown by liquid-phase epitaxy 112 (1991) 803
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Wu, Y.L., see Chen 113 (1991) 520
Wu, Yao-An, see Zhou 114 (1991) 87
Wynn, J.D., see Hong 111 (1991) 1052
Wynn, J.D., see Wang 111 (1991) 1057

Xiao, Q., see Derby 113 (1991) 575
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Xing, Y.R., see Joyce 120 (1992) 206
Xu Fei, see Peng 115 (1991) 698
Xu Shao-Hong, see Zhang 117 (1992) 1012
Xu, Wu, Xinyi Zhang and Xurong Xu, Energy transfer from Mn to Tm ions in ZnS at high pressure 117 (1992) 718
Xu, X.Y., see Jiang 116 (1992) 93
Xu, Xurong, see Xu 117 (1992) 718
Xu Xurong, Lei Gang and Xu Zheng, Multiplication of carriers by impact ionization 117 (1992) 935
Xu Zheng, see Xu 117 (1992) 935
Xu, Zhengyi, see Huo 114 (1991) 486
Xuan Zhenwu, see Qi 112 (1991) 580
Xuan Zhenwu, see Qi 113 (1991) 726
Xue, J.S., M. Reedyk, A. Dabkowski, H. Dabkowska, J.E. Greedan and C.H. Chen, Crystal growth and characterization of superconducting lead cuprates 113 (1991) 371
Xue, M.L., see Zhong 119 (1992) 74

Yabumi, T., see Hattori 115 (1991) 607
Yacaman, J., see Cuisinier 116 (1992) 314
Yacoot, A., see Wierzchowski 114 (1991) 209
Yaegashi, Y., see Tajima 114 (1991) 59
Yagi, K., see Shima 115 (1991) 359
Yagi, M., see Kinto 117 (1992) 348
Yakomovich, V.N., see Barilo 119 (1992) 403
Yakovlev, D.R., W. Ossau, G. Landwehr, R.N. Bicknell-Tassius, A. Waag, S.

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Yakovlev, D.R., see Uraltsev 117 (1992) 877
Yamada, A., see Kudo 111 (1991) 402
Yamada, A., see Lee 115 (1991) 164
Yamada, K., see Tanaka 117 (1992) 997
Yamada, S., see Ishiai 115 (1991) 762
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Yamada, T., see Sato 115 (1991) 241
Yamada, T., see Kinto 117 (1992) 348
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Yamada, T., see Tokumitsu 120 (1992) 301
Yamada, T., see Sugiura 120 (1992) 389
Yamada, Y., see Hayashi 115 (1991) 782
Yamada, Y., Y. Masumoto and T. Taguchi, Hydrostatic-pressure-induced type-I → type-II conversion in ZnSe-ZnS strained-layer superlattices 117 (1992) 484
Yamada, Y., see Yamamoto 117 (1992) 488
Yamaga, S. and A. Yoshikawa, Atomic layer epitaxy of ZnS by a new gas supplying system in low-pressure metalorganic vapor phase epitaxy 117 (1992) 152
Yamaga, S., see Kanemitsu 117 (1992) 316
Yamaga, S. and A. Yoshikawa, Dependence of electrical and optical properties of iodine-doped cubic ZnCdS films on solid composition 117 (1992) 353
Yamaguchi, T., see Hishida 117 (1992) 396
Yamaguchi, Y., see Nagasawa 115 (1991) 612
Yamakawa, H., see Shigetomi 111 (1991) 110
Yamamoto, A., see Kanemitsu 117 (1992) 316
Yamamoto, A., Y. Yamada and Y. Masumoto, New characterization method of biaxial stress by Raman scattering: demonstration in ZnSe–ZnS strained-layer superlattices 117 (1992) 488
Yamamoto, H., see Migita 111 (1991) 776
Yamamoto, J.K., see Kitamura 116 (1992) 327
Yamamoto, K., see Tanaka 117 (1992) 24
Yamamoto, T., see Shimomura 111 (1991) 1105
Yamamoto, Y., see Matsushima 177 (1992) 328
Yamanaka, K., see Kanemitsu 117 (1992) 316
Yamanaka, M., see Yase 118 (1992) 348
Yamanishi, M., see Suemune 117 (1992) 1068
Yamasaki, S., see Koide 115 (1991) 639
Yamashita, A., see Yoo 115 (1991) 733
Yamashita, H., see Muranaka 112 (1991) 808
Yamauchi, H., see Igasaki 112 (1991) 797
Yamauchi, H., see Tajima 114 (1991) 59
Yamauchi, S., T. Hariu and S. Ono, Effect of enhanced reactivity in plasma-assisted epitaxial growth of ZnSe 115 (1991) 660
Yamauchi, Y., see Kobayashi 115 (1991) 353
Yamaura, K., see Yokota 119 (1992) 195
Yamawaki, H., see Ueda 115 (1991) 774
Yamazaki, S., see Kondo 115 (1991) 231
Yamazaki, S., see Mukai 115 (1991) 433
Yan, Q.M., see Zhong 119 (1992) 74
Yanagase, M., S. Tanaka, K. Hiramatsu and I. Akasaki, Growth of InGaP epitaxial layers by liquid phase electro-epitaxy 115 (1991) 304
Yanagisawa, H., see Minagawa 118 (1992) 425
Yanata, K., see Suzuki 117 (1992) 881
Yang, D., see Kim 111 (1991) 633
Yang, F., see O'Donnell 117 (1992) 497
Yang, F., see Trager-Cowan 117 (1992) 532
Yang Hua, see Li 119 (1992) 363
Yang, J.Y., see Beam 116 (1992) 436
Yang Jianrong, Yu Zhenzhong, Liu Jiming and Tang Dingyuan, Composition interdiffusion in $Hg_{1-x}Cd_xTe$ annealed with Cd–Hg source 114 (1991) 351
Yang, L., see Chen 111 (1991) 659
Yang, L., see Hersee 120 (1992) 218
Yang Peichun, see Qi 112 (1991) 580
Yang Peichun, see Qi 113 (1991) 726
Yang, S.J., see Hu 114 (1991) 191
Yang, S.-J., see Choi 115 (1991) 579
Yang Tongqin, see Su 119 (1992) 368
Yang, Y.C., see Wu 112 (1991) 803
Yang, Z., see Lansari 111 (1991) 720
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Yano, M., see Yoh 111 (1991) 643
Yao, H., see Misawa 117 (1992) 617
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Yao, T., see Zhu 117 (1992) 400
Yase, K., S. Ogihara, M. Sano and M. Okada, Thin film formation of polymorph-con-

trolled triglycerides by physical vapor deposition 116 (1992) 333
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Yasuda, K., see Hattori 115 (1991) 607
Yasuda, K., see Ekawa 117 (1992) 254
Yasuda, Y., see Ohshima 115 (1991) 106
Yasuda, Y., see Koide 115 (1991) 365
Yasuda, Y., see Koide 120 (1992) 284
Yasumura, K., see Takami 117 (1992) 16
Yasumura, K., T. Murakami, M. Suita, H. Takada, K. Takahashi, M. Nunoshita and Z. Kawazu, $Cd_xHg_{1-x}Te$ double-layers grown by liquid phase epitaxy 117 (1992) 20
Yasumura, K., see Takada 117 (1992) 44
Yates, H.M., see Zheng 117 (1992) 358
Yates, H.M., see Williams 117 (1992) 441
Yates, H.M., see Armitage 117 (1992) 1082
Yazawa, Y., T. Minemura and T. Unno, Photoluminescence of GaAs layers hybrid-grown on Si by MBE and LPE 115 (1991) 519
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Yilmaz, F., O.A. Atasoy and R. Elliott, Growth structures in aluminium–silicon alloys. II. The influence of strontium 118 (1992) 377
Yoda, H., see Yoshioka 115 (1991) 705
Yodo, T. and S. Tanaka, Li^+ ion implantation into ZnS epitaxial layers grown by metalorganic vapor phase epitaxy 117 (1992) 415
Yoffe, G.W., see Lee 111 (1991) 131
Yoh, K., see Yano 111 (1991) 397
Yoh, K., T. Moriuchi, M. Yano and M. Inoue, Electrical characteristics dependence on aluminum mole fraction in $(Al_{0.5}Ga_{0.5})Sb/InAs/(Al_xGa_{1-x})Sb$ heterostructure 111 (1991) 643
Yokogawa, T. and T. Narusawa, ZnSe/ZnS strained layer superlattices grown on CaF_2 substrates by MOVPE 115 (1991) 670
Yokogawa, T. and T. Narusawa, ZnTe/ZnSTe doping superlattices grown on InP substrates by metalorganic vapor phase epitaxy 117 (1992) 480
Yokose, H., see Yano 111 (1991) 609
Yokota, K., H. Nakai, K. Satoh and S. Katayama, Segregation coefficients and activation of indium in cadmium telluride grown from tellurium-rich melt by the Bridgman technique 112 (1991) 723
Yokota, K., K. Yamaura, H. Tokuda and S. Tamura, Metalorganic beam epitaxial growth of GaAs on Si substrates treated by a partially ionized mixture of H_2 and AsH_3 119 (1992) 195
Yokotani, A., see Halfpenny 113 (1991) 722
Yokouchi, N., see Uchida 111 (1991) 1062
Yokouchi, N., see Uchida 120 (1992) 357
Yokoyama, H., M. Shinohara and N. Inoue, Atomic layer epitaxy of GaAs using N_2 carrier gas 115 (1991) 89
Yokoyama, N., see Sandhu 111 (1991) 559
Yokoyama, N., see Ando 120 (1992) 228
Yoneta, M., see Ohishi 117 (1992) 125
Yonezu, H., see Takano 111 (1991) 216
Yonezu, H., see Maruyama 115 (1991) 180
Yoo, H., S.M. Goodnick and J.R. Arthur, Transport in $Al_xGa_{1-x}As/In_yGa_{1-y}As$ resonant tunneling diodes with asymmetric layers 111 (1991) 1095
Yoo, W.S., A. Yamashita, T. Kimoto and H. Matsunami, Bulk crystal growth of 6H-SiC on polytype-controlled substrates through vapor phase and characterization 115 (1991) 733
Yoon, C.S., see Shepherd 113 (1991) 360
Yoshida, A., see Nishio 115 (1991) 284
Yoshida, H., T. Fujii, A. Kamata and Y. Nakata, Undoped ZnSe single crystal growth by the vertical Bridgman method 117 (1992) 75
Yoshida, H., see Kamata 117 (1992) 96
Yoshida, I., T. Katsuyama and H. Hayashi, Improvement of photoluminescence characteristics of AlGaInP double hetero-structures grown by OMVPE 115 (1991) 533
Yoshida, K., see Minami 117 (1992) 565
Yoshida, K., see Inoue 117 (1992) 738
Yoshida, M., see Mikami 117 (1992) 991
Yoshida, S., see Miki 111 (1991) 902
Yoshida, S., S. Ozawa, T. Kijima, J. Suzuki and T. Kikuta, InP single crystal growth with controlled supercooling during the early stage by a modified LEC method 113 (1991) 221
Yoshida, S., see Okumura 120 (1992) 114
Yoshida, T., see Iizuka 111 (1991) 429
Yoshikawa, A. and T. Okamoto, Ar ion laser irradiation effects on the MOVPE growth of ZnSe using dimethyl zinc and hydrogen selenide as reactants 115 (1991) 274
Yoshikawa, A. and T. Okamoto, On the mechanism of growth-rate enhancement

by photocatalysis in metalorganic vapor phase epitaxy of ZnSe 117 (1992) 107
Yoshikawa, A., see Yamaga 117 (1992) 152
Yoshikawa, A., see Kanemitsu 117 (1992) 316
Yoshikawa, A., see Yamaga 117 (1992) 353
Yoshimoto, M., K. Ozasa, T. Tsuji, A. Kajimoto and H. Matsunami, MOMBE growth of P-based III–V semiconductors and its photo-enhancement at low temperatures 115 (1991) 265
Yoshimoto, M., see Nagata 118 (1992) 299
Yoshino, J., see Otoma 115 (1991) 807
Yoshino, K., see Matsushima 117 (1992) 328
Yoshioka, Y., H. Yoda and M. Kasuga, Homo-epitaxial growth of CdTe by sublimation under low pressure 115 (1991) 705
Yoshizawa, S., see Ishiai 115 (1991) 762
Young, G.L., K.A. McDonald, A. Palazoglu and W. Ford, Thermal modeling of Bridgman crystal growth using a boundary element approach 118 (1992) 193
Young, T.L., see Healy 112 (1991) 287
Youngdale, E.R., J.R. Meyer, C.A. Hoffman, F.J. Bartoli, D.L. Partin, C.M. Thrush and J.P. Heremans, Strong nonlinear optical enhancement in MBE-grown $Bi_{1-x}Sb_x$ 111 (1991) 693
Yu, E.T., see Collins 111 (1991) 664
Yu, E.T., see Phillips 111 (1991) 820
Yu, S.J., see Takeyasu 111 (1991) 502
Yu, T., see Ho 111 (1991) 233
Yu, X., see Vanzetti 117 (1992) 573
Yu Zhenzhong, see Yang 114 (1991) 351
Yuan, Shixin, see Li 111 (1991) 736
Yuan, Shixin, see Li 119 (1992) 322
Yuan, Shi-Xin, see Shen 117 (1992) 470
Yuba, Y., see Shimomura 111 (1991) 1105
Yuen, W.T., W.K. Liu, R.A. Stradling and B.A. Joyce, The growth and electronic properties of α-Sn thin films grown on InSb(100) and $(\bar{1}\bar{1}\bar{1})$ substrates by molecular beam epitaxy (MBE) 111 (1991) 943

Zahn, D.R.T., see Kolodziejczyk 117 (1992) 549
Zahzouh, M., see Hincelin 120 (1992) 119
Zaima, S., see Ohshima 115 (1991) 106
Zaima, S., see Koide 115 (1991) 365
Zaima, S., see Koide 120 (1992) 284
Zarka, A., see Rinaudo 116 (1992) 87
Zborowski, J., see Hansen 116 (1992) 271
Zborowski, J.T., see Fashe 111 (1991) 677
Zeinert, A., P. Benalloul, C. Barthou, J. Benoit, J. Dreyhsig and H.-E. Gumlich, Excitation efficiency of electrons in alternating driven ZnS:Mn electroluminescent devices 117 (1992) 1016
Zeitz, W.-D., see Waldmann 117 (1992) 715
Zembutsu, S., see Ohki 117 (1992) 102
Zembutsu, S., see Ando 117 (1992) 560
Zha, M., see Piechotka 113 (1991) 251
Zha, M., M. Piechotka and E. Kaldis, Vapour growth of bulk anisotropic crystals; case study of α-HgI_2 115 (1991) 43
Zhang, Bu-Xin, see Zhang 117 (1992) 1012
Zhang, C.X., see Luo 119 (1992) 407
Zhang, G., T. Hakkarainen, K. Rakennus, K. Tappura, H. Asonen and M. Pessa, Low dark current $In_{0.53}Ga_{0.47}As/InP$ SAM avalanche photodiodes grown by gas-source MBE 120 (1992) 172
Zhang Hongwu, see Ji 112 (1991) 283
Zhang, J., E.M. Gibson, C.T. Foxon and B.A. Joyce, Modulated molecular beam study of group III desorption during growth by MBE 111 (1991) 93
Zhang, J., see Foxon 111 (1991) 539
Zhang, J., see Joyce 115 (1991) 338
Zhang, J., see Lacklison 120 (1992) 50
Zhang, J.H., see Guan 117 (1992) 515
Zhang, J.Y., X.W. Fan, S.Y. Wang, D.Z. Shen and G.H. Fan, Optical bistability in ZnSe–ZnS superlattices with a Fabry–Pérot cavity 117 (1992) 523
Zhang, Jingwu, see Ebrahimpour 113 (1991) 83
Zhang, Jingwu and G.H. Nancollas, Influence of calcium/sulfate molar ratio on the growth rate of calcium sulfate dihydrate at constant supersaturation 118 (1992) 287
Zhang, S. and N. Kobayashi, Photoluminescence from narrow ZnSe/GaAs/ZnSe quantum wells 117 (1992) 1074
Zhang, Shu-Lin, see Shen 117 (1992) 470
Zhang, X., see Fawcett 116 (1992) 81
Zhang, X.Q., see Benchimol 120 (1992) 189
Zhang, Xiao-Jie, see Shen 117 (1992) 470
Zhang, Xinyi, see Xu 117 (1992) 718
Zhang, Zhi-Lin, see Tanaka 117 (1992) 997
Zhang Zhi-Lin, Zhang Bu-Xin, Zhao Wei-Ming, Jiang Xue-Yin, Liu Zu-Gang and Xu Shao-Hong, Computer simulation of the transient process of ZnS:Mn thin film electroluminescence 117 (1992) 1012
Zhao Shuging, see Ji 112 (1991) 283
Zhao Wei-Ming, see Zhang 117 (1992) 1012
Zheng, J., see Fashe 111 (1991) 677
Zheng, Jia-zhen, J.W. Allen, H.M. Yates and J.O. Williams, The M-centre in zinc selenide grown by metalorganic chemical vapour deposition 117 (1992) 358
Zheng, K., see Sun 113 (1991) 103
Zheng, Y., see Zhong 119 (1992) 74
Zhigunov, D.I., see Barilo 119 (1992) 403
Zhong, X.R., B.J. Zhou, Q.M. Yan, F.N. Cao, C.J. Li, L.Y. Lin, W.J. Ma, Y.

Zheng, F. Tao and M.L. Xue, Preliminary results of GaAs single crystal growth under high gravity conditions 119 (1992) 74
Zhou, B.J., see Zhong 119 (1992) 74
Zhou, G.F., G.W. Qiao, J.G. Huang, M. Jiang, Y.Z. Wang and Y.C. Chuang, Synthesis of bulk $YBa_2Cu_3O_{7-x}$ by melt-spun texture growth (MSTG) 114 (1991) 283
Zhou, Junming, Weimin Jin, Jianmin Mao and Yi Huang, Effect of neutron irradiation on transport in heterostructures 111 (1991) 288
Zhou, Yan-Fei, Jing-Chang Wang, Pei-Ling Wang, Lian-An Tang, Quan-Bao Zhu, Yao-An Wu and Hao-Ran Tan, MgO-doping effects on the congruent composition of $LiNbO_3$ 114 (1991) 87
Zhu, Nanchang, see Li 119 (1992) 322
Zhu, Quan-Bao, see Zhou 114 (1991) 87
Zhu, Z., H. Mori, M. Kawashima and T. Yao, Planar doping of p-type ZnSe layers with lithium grown by molecular beam epitaxy 117 (1992) 400
Zhu, Zhenhe, see Huo 114 (1991) 486
Zilko, J.L., see McCrary 112 (1991) 39
Zilko, J.L., see Asom 112 (1991) 597
Zlatkin, A.T. and E.L. Lube, Estimation of fracture toughness and residual stress in brittle crystals from indentation-induced acoustic emission 118 (1992) 218
Zogg, H., see Tiwari 111 (1991) 730
Zouni, A., see Georgalis 118 (1992) 360
Zsebök, O., see Protzmann 115 (1991) 248
Zubets, A.V., see Barilo 119 (1992) 403
Zucker, J.E., see Chang 111 (1991) 475
Zucker, J.E., see Chiu 120 (1992) 343
Zuzga-Grasza, U., see Grasza 116 (1992) 139
Zydzik, G.J., see Hong 111 (1991) 1052

Journal of Crystal Growth 120 (1992) 475–492
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index to volumes 111–120

Adducts **117** (1992) 44, 91; **118** (1992) 176
Adsorption **111** (1991) 93, 110, 125, 162, 407, 423, 456, 502, 787, 792, 847, 856; **112** (1992) 1, 146, 192, 298, 421, 445; **113** (1991) 289, 417, 508, 606, 637; **114** (1991) 203; **115** (1991) 12, 79, 83, 94, 117, 279, 338, 348, 353, 406, 443, 542, 612; **116** (1992) 511; **117** (1992) 44, 91; **118** (1992) 60
Alkali
– halides **118** (1992) 473
Alloys **111** (1991) 978; **112** (1991) 525, 539, 563, 635; **113** (1991) 77, 242, 449; **118** (1992) 183, 277, 319, 377; **119** (1992) 126, 141, 152, 160
Alumina **118** (1992) 314; **119** (1992) 391
Aluminum **119** (1992) 167
– antimonide **111** (1991) 360, 651, 659, 664; **120** (1992) 25
– arsenide **111** (1991) 88, 125, 168, 221, 305, 978, 1071, 1105, 1110; **113** (1991) 491; **115** (1991) 61, 69, 133, 248, 318, 406, 418
– copper **113** (1991) 449
– gallium antimonide **111** (1991) 631, 643, 647; **113** (1991) 441; **115** (1991) 236
– gallium arsenide **111** (1991) 20, 26, 30, 50, 75, 98, 105, 173, 189, 239, 269, 274, 280, 295, 318, 323, 328, 360, 366, 371, 440, 544, 559, 574, 1043, 1047, 1052, 1057, 1066, 1089, 1095, 1116; **112** (1991) 803; **113** (1991) 103, 412;**114** (1991) 700; **115** (1991) 52, 248, 299, 338, 484, 490; **116** (1992) 98; **118** (1992) 414; **120** (1992) 84, 124, 189, 195, 206, 218, 228, 234, 240, 323, 362
– gallium arsenide antimonide **111** (1991) 669; **113** (1991) 441
– gallium indium arsenide **111** (1991) 475, 484
– gallium indium phosphide **115** (1991) 529, 533; **118** (1992) 425
– gallium nitride **115** (1991) 648
– gallium phosphide **115** (1991) 265
– indium **119** (1992) 152
– indium arsenide **111** (1991) 445, 456, 461, 470, 475, 479, 489
– indium phosphide **111** (1991) 521
– nickel alloys **119** (1992) 160
– nitride **115** (1991) 643
– organic **111** (1991) 274, 574; **112** (1991) 628; **113** (1991) 103, 441; **115** (1991) 52, 61, 69, 236, 265, 406, 455, 617, 648
– orthophosphate **116** (1992) 427
– silicon alloys **112** (1991) 635; **113** (1991) 77, 289; **118** (1992) 377
Ammonium
– dihydrogen phosphate **119** (1992) 248
– nitrate **114** (1992) 497
Antimonides
– of group III elements **120** (1992) 252
Antimony
– organic **111** (1991) 638; **113** (1991) 441; **115** (1991) 474
– tribromide **119** (1992) 303
– triiodide **119** (1992) 303
Apparatus
– for melt growth
– – by Bridgman–Stockbarger method
– – – in centrifuge
– – – – of lead telluride **119** (1992) 24
– – – of cadmium fluoride **119** (1992) 339
– – by Czochralski method
– – – of yttrium orthoaluminate, neodymium dopes **118** (1992) 371
– – – through automatic diameter control
– – – – of bismuth germanate **118** (1992) 439
– – – – of bismuth silicate **118** (1992) 439
– – by uniaxial solidification
– – – of alloys **118** (1992) 183
– for solution growth
– – solvent evaporation
– – – of lysozyme **116** (1992) 414
– for thin film growth
– – by chemical beam epitaxy
– – – of II–VI compounds **111** (1991) 725
– – – laser assisted
– – – – of gallium arsenide **120** (1992) 395
– – – – of III–V compounds **120** (1991) 389
– – by gas source molecular beam epitaxy
– – – of silicon **111** (1991) 860
– – by hot wall epitaxy
– – – of lead cadmium sulphoselenide **115** (1991) 687
– – – of II–VI compounds **117** (1992) 1026
– – by ion beam sputtering
– – – of platinum **115** (1991) 596
– – by liquid phase epitaxy
– – – by temperature difference method, under controlled vapor pressure
– – – – of Zinc selenide **112** (1991) 153
– – – using two-arm cover
– – – – of mercury cadmium telluride **113** (1991) 520
– – by metalorganic molecular beam epitaxy
– – – of gallium arsenide **119** (1992) 195
– – – of zinc selenide **116** (1992) 283
– – by molecular beam epitaxy
– – – of indium phosphide **115** (1991) 371
– – – safety system for **113** (1991) 209
– – – using light irradiation
– – – – of germanium **120** (1992) 284

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– – by sputtering
– – – of zinc oxide **117** (1992) 939
– – by uniform radial flow epitaxy
– – – of III–V compounds **112** (1991) 583
– – by vapor phase epitaxy
– – – through chemical vapor deposition
– – – – of silicon **113** (1991) 606
– – – – using flash heating
– – – – – of germanium **115** (1991) 79
– – – through evaporation and condensation
– – – – plasma-assisted
– – – – – of indium arsenide **115** (1991) 309
– – – – – of zinc selenide **115** (1991) 660
– – – through metalorganic chemical vapor deposition
– – – – of gallium arsenide **115** (1991) 221
– – – – of silicon carbide **113** (1991) 120
– – – – of III–V compounds **115** (1991) 203
– – – – photo-assisted
– – – – – of lead titanate **115** (1991) 289
– for vapor diffusion crystallization
– – under microgravity
– – – of proteins **119** (1992) 200
– for miscellaneous purposes
– – automatic powder supply system **116** (1992) 327
– – control of solid–liquid interface **119** (1992) 371
– – crystal growth under microgravity **116** (1992) 289
– – determination of protein solubilities **113** (1991) 385
– – dynamic optical reflectivity **120** (1992) 84
– – ECR plasma injector for chemical beam epitaxial growth **111** (1991) 605
– – epitaxial growth (MOVPE) reactor **116** (1992) 387
– – in situ measurement of surface coverage **115** (1991) 348
– – kinetic studies of simultaneous processes **113** (1991) 83
– – measurement of concentration gradient **114** (1991) 71
– – measurement of optical bistability **117** (1992) 519
– – measurement of second harmonic generation **120** (1992) 94
– – measurement of solid fraction in binary melt **113** (1991) 566
– – measurement of step velocity **114** (1991) 239
– – metalorganic molecular beam epitaxy of zinc chalcogenides **120** (1992) 261
– – monitoring concentration of gas mixtures **120** (1992) 98
– – nucleation control **113** (1991) 251
– – obtaining high gravity **119** (1992) 66
– – reaction kinetics **112** (1991) 474
– – real-time measuring of LPE growth **114** (1991) 380
– – sealing crucibles by electron beam welder **117** (1992) 80
– – thermal imaging **116** (1992) 213
– – thermochemical etching **114** (1991) 565
– – ultrahigh vacuum **115** (1991) 579
– – ultrahigh vacuum chemical vapor deposition **120** (1992) 279
– – ultrahigh vacuum evaporation **116** (1992) 55
– – undercooling **112** (1991) 554
Arginine
– (L) chloride monohydrate **112** (1991) 183
– phosphate **113** (1991) 456
Arsenic
– organic **111** (1991) 638; **112** (1991) 575; **115** (1991) 248, 353, 448; **116** (1992) 48
– triiodide **119** (1992) 303
Arsine **112** (1991) 597

Barite **114** (1991) 497
Barium
– bismuth oxide system **113** (1991) 716
– borate, β **114** (1991) 656, 676, 683
– fluoride **116** (1992) 473
– hexaferrite **114** (1991) 435; **116** (1992) 483
– nitrate **116** (1992) 340; **119** (1992) 1
– oxide **118** (1992) 213
– oxide/copper oxide eutectic **112** (1991) 600, 606
– sulphate **114** (1991) 497
– titanate **115** (1991) 745
Beryl **116** (1992) 93
Beryllium
– organic **115** (1991) 460
– sulphate tetrahydrate **113** (1991) 161
Bismuth
– antimonide **111** (1991) 693
– germanate **113** (1991) 186; **118** (1992) 396, 439
– organic **115** (1991) 762
– platinum oxide **112** (1991) 660
– silicate **113** (1991) 186; **118** (1992) 439
– strontium calcium cuprate **111** (1991) 973; **112** (1991) 745; **113** (1991) 9; 114 (1991) 507; **115** (1991) 758, 762, 765, 769, 774; **116** (1992) 37, 524, 529; **118** (1992) 27, 477, 483; **119** (1992) 122
– strontium cuprate **112** (1991) 745
– triiodide **119** (1992) 303
Boron **111** (1991) 838
– nitride **112** (1991) 386; **116** (1992) 507
Boundary element method **118** (1992) 193
Boundary layer control **113** (1991) 587; **114** (1991) 198, 486, 593; **115** (1991) 231; **116** (1991) 63; **118** (1992) 259, 333
Brushite **114** (1991) 22
Burton–Cabrera–Frank theory **118** (1992) 473; **119** (1992) 241
Burton–Prim–Slichter theory **118** (1992) 259

Cadmium **112** (1991) 235; **118** (1992) 243
– arachidate **118** (1992) 348
– cobalt selenide **117** (1992) 840
– fluoride **119** (1992) 339
– manganese selenide **117** (1992) 840
– manganese telluride **111** (1991] 1016; **112** (1991) 487; **113** (1991) 663; **117** (1992) 424, 820, 826, 830, 835, 840, 881, 1081
– mercury telluride **111** (1991) 698, 711, 715, 720, 725; **112** (1991) 402; **113** (1991) 53, 92, 520; **114** (1991) 77, 351, 411; **115** (1991) 698; **117** (1992) 1; 16, 20, 24, 28, 33, 37, 44, 54, 161, 166, 171, 177, 183, 193, 203, 213, 218, 222, 238, 454, 460, 758, 844, 954, 1046; **118** (1992) 264, 365
– organic **111** (1991) 725; **112** (1991) 192

- selenide **111** (1991) 820; **113** (1991) 653; **117** (1992) 492, 497, 603, 608, 732, 763, 768, 773, 1077, 1080
- selenide telluride **112** (1991) 421; **117** (1992) 666
- selenide/zinc selenide **113** (1991) 653
- sulphide **117** (1992) 156, 362, 420, 492, 497, 532, 536, 617, 622, 650, 672, 698, 738, 753, 788, 902, 918, 925, 1026; **118** (1992) 304
- sulphoselenide **117** (1992) 598, 614, 778, 1040
- telluride **111** (1991) 698, 725, 730, 736, 1016; **112** (1991) 192, 407, 723; **113** (1991) 147; **115** (1991) 692, 698, 705, 711, 718; **116** (1992) 55; **117** (1992) 156, 161, 227, 233, 238, 244, 249, 254, 259, 266, 271, 385, 391, 420, 424, 475, 554, 656, 660, 748, 820, 835, 854, 859, 862, 867, 871, 877, 886, 890, 929, 959, 1073; **118** (1992) 1, 269, 470; **119** (1992) 322
- zinc selenide **117** (1992) 1078
- zinc sulphide **117** (1992) 119, 501, 536
- zinc telluride **116** (1992) 515; **117** (1992) 161, 276, 281, 424, 465, 475, 656, 682; **118** (1992) 269, 470; **119** (1992) 261

Calcium
- apatites **114** (1991) 613; **118** (1992) 93
- cadmium sulphide **117** (1992) 806
- carbonate **118** (1992) 401
- fluoride **113** (1991) 637
- hydrogen phosphate dihydrate **114** (1991) 22
- hydroxyapatite **112** (1991) 467, 571; **116** (1992) 314, 319
- organic **115** (1991) 762
- phosphates **112** (1991) 467, 571; **113** (1991) 83, 643; **114** (1991) 22, 613
- sulphate **113** (1991) 508
- sulphate dihydrate **112** (1991) 415; **116** (1992) 87; **118** (1992) 287
- sulphide **117** (1992) 587, 969, 975

Camphene **112** (1991) 97

Carbon
- fibers **118** (1992) 309
- tetrabromide **114** (1991) 536, 549

Cellular growth **112** (1991) 463, 670; **113** (1991) 77; **116** (1992) 364; **118** (1992) 183

Cerium
- dioxide **118** (1992) 299

Characterization methods
- by absorption spectroscopy **111** (1991) 388, 419, 424, 720, 807, 1076; **112** (1991) 7; **113** (1991) 333; **114** (1991) 141; **115** (1991) 241, 490, 670, 793; **116** (1992) 48, 327; **117** (1992) 156, 341, 432, 497, 501, 515, 523, 532, 565, 583, 592, 598, 603, 608, 614, 622, 640, 732, 758, 763, 768, 806, 816, 859, 902; **118** (1992) 396; **119** (1992) 317, 322, 339
- by acoustic emission **118** (1992) 218
- by atomic absorption spectroscopy **118** (1992) 204
- by attenuation of light **117** (1992) 987
- by Auger electron spectroscopy **111** (1991) 669, 677, 882, 1003, 1024; **112** (1991) 39, 644, 745, 803; **114** (1991) 364; **115** (1991) 180, 411, 455, 607, 683; **116** (1992) 213; **117** (1992) 183, 634; **120** (1992) 57, 103
- by calorimetric absorption spectroscopy **117** (1992) 698
- by cathodoluminescence **111** (1991) 698, 1105; **112** (1991) 153; **113** (1991) 295; **114** (1991) 209; **115** (1991) 634, 658, 674; **117** (1992) 341, 385, 532, 560, 943, 975; **119** (1992) 74, 177
- by chemical analysis **118** (1992) 93
- by cross-sectional transmission electron microscopy **118** (1992) 245
- by deep level transient spectroscopy **111** (1991) 698, 1105; **117** (1992) 578; **118** (1992) 176
- by differential thermal analysis **112** (1991) 600; **113** (1991) 653, 659; **114** (1991) 87, 299, 373, 661, 676; **116** (1992) 505; **118** (1992) 101, 277; **119** (1992) 381
- by digital image processing **114** (1991) 239
- by direct recoil experiments **120** (1992) 269
- by electrical methods **111** (1991) 14, 20, 26, 30, 43, 50, 228, 233, 246, 252, 260, 264, 269, 280, 288, 295, 300, 305, 309, 313, 318, 333, 348, 366, 440, 445, 450, 461, 466, 470, 479, 484, 489, 495, 507, 511, 515, 559, 578, 584, 589, 594, 605, 614, 619, 623, 633, 643, 647, 651, 659, 664, 669, 683, 698, 720, 741, 747, 762, 767, 772, 776, 820, 829, 838, 847, 856, 902, 912, 916, 936, 957, 961, 965, 973, 978, 989, 1011, 1071, 1076, 1080, 1084, 1089, 1095, 1100, 1105, 1110, 1116; **112** (1991) 7, 111, 153, 227, 343, 402, 554, 563, 587, 606, 723, 803; **113** (1991) 61, 103, 113, 127, 140, 371, 403, 566; **114** (1991) 118, 186, 283, 346, 364; **115** (1991) 31, 89, 216, 236, 248, 254, 261, 289, 309, 411, 448, 455, 460, 464, 474, 498, 504, 509, 572, 623, 639, 648, 652, 679, 683, 687, 733, 765, 788, 793, 811; **116** (1992) 27, 169, 351, 387, 518, 521, 524; **117** (1992) 16, 20, 37, 49, 54, 102, 111, 119, 134, 183, 203, 208, 213, 218, 222, 227, 233, 254, 259, 271, 281, 320, 341, 353, 358, 366, 370, 385, 391, 396, 400, 406, 432, 480, 560, 569, 578, 583, 625, 666, 677, 689, 694, 850, 918, 925, 929, 935, 939, 943, 948, 954, 959, 969, 979, 983, 1002, 1012, 1021, 1026, 1030, 1035, 1040, 1050, 1055, 1059; **118** (1992) 27, 176, 295, 385, 425, 452; **119** (1992) 98; **120** (1992) 119, 124, 130, 140, 172, 180, 184, 200, 218, 228, 234, 240, 245, 261, 296, 301, 312, 317, 343, 349
- by electroluminescence **111** (1991) 829; **112** (1991) 803; **117** (1992) 432, 510, 583, 587, 964, 969, 979, 983, 987, 991, 997, 1002, 1012, 1016, 1021, 1026, 1030, 1035, 1055, 1059, 1062, 1073, 1078, 1079, 1080
- by electron beam induced current **117** (1992) 560, 1059
- by electron diffraction **111** (1991) 1038; **112** (1991) 507, 525, 635; **113** (1991) 120; **115** (1991) 79, 388, 596, 612, 788, 811; **116** (1992) 495, 524; **118** (1992) 309; **119** (1992) 221
- by electron energy loss spectroscopy **115** (1991) 313
- by electron microscopy **111** (1991) 20, 39, 50, 75, 83, 189, 210, 221, 233, 305, 353, 371, 383, 402, 407, 419, 434, 456, 489, 495, 521, 584, 628, 647, 683, 688, 698, 720, 747, 752, 767, 802, 833, 847, 860, 882, 889, 897, 920, 925, 936, 948, 957, 973, 1038, 1043, 1057, 1105; **112** (1991) 1, 47, 55, 84, 111, 227, 235, 287, 291, 337, 359, 373, 386, 415, 421, 427, 474, 496, 507, 525, 583, 621, 635, 651, 660, 731, 758, 803, 808; **113** (1991) 9, 53, 61, 69, 113, 120, 140, 242, 289, 295, 333, 395, 403, 441, 449, 485, 491, 520, 527, 540, 659, 681, 716; **114** (1991) 3, 7, 22, 38, 59, 99, 107, 191, 198, 258, 269, 279, 283, 299, 307, 364, 380, 435, 500, 565, 573, 613, 619, 687; **115** (1991) 31, 61, 69, 99, 112, 128, 133, 145, 150, 154, 164, 304, 313, 328, 333, 359, 365, 375, 381, 388, 393, 406,

418, 455, 474, 524, 538, 542, 561, 572, 579, 596, 602, 607, 612, 628, 634, 643, 698, 705, 733, 765, 774, 782, 788, 798, 811, 816, 821, 826, 831; **116** (1992) 15, 81, 225, 243, 251, 307, 314, 319, 333, 436, 495, 507, 524, 529; **117** (1992) 10, 37, 49, 156, 161, 171, 238, 259, 266, 297, 441, 475, 536, 543, 554, 560, 666, 682, 826, 862, 881, 929, 1008, 1079; **118** (1992) 27, 93, 109, 125, 135, 231, 287, 299, 309, 348, 360, 377, 452; **119** (1992) 195, 221, 229, 271; **120** (1992) 155, 157, 245, 279, 338, 343, 353, 376, 382
- by electron paramagnetic resonance **117** (1992) 656, 727
- by electron probe microanalysis **111** (1991) 371; **113** (1991) 9, 520; **114** (1991) 59, 77, 351; **115** (1991) 533, 607; **116** (1992) 151, 524; **117** (1992) 276, 826; **118** (1992) 309, 314, 483
- by electro-optical methods **111** (1991) 440
- by electron spectroscopy for chemical analysis **118** (1992) 213
- by ellipsometry **112** (1991) 146; **116** (1992) 63, 387; **117** (1992) 166, 918
- by emission **111** (1991) 1024; **112** (1991) 808; **115** (1991) 623, 639, 648, 660; **117** (1992) 309, 432, 454, 480, 527, 640, 718, 721, 732, 753, 758, 783, 806, 835, 840, 859, 881, 943, 964, 1062
- by Fourier transform infrared **111** (1991) 677, 989, 1076; **113** (1991) 520, 643; **116** (1992) 511; **118** (1992) 85; **120** (1992) 328
- by infrared microscopy **112** (1991) 838
- by infrared reflectivity **117** (1992) 281
- by infrared spectroscopy **111** (1991) 811; **112** (1991) 402; **113** (1991) 69; **114** (1991) 141; **115** (1991) 831; **116** (1992) 15, 48, 461; **118** (1992) 323; **119** (1992) 309, 339, 393, 399; **120** (1992) 323
- by infrared thermography **112** (1991) 699
- by infrared tomography **117** (1992) 227
- by infrared transmission **117** (1992) 37, 166, 193, 213, 227
- by interference spectra **117** (1992) 788
- by interferometry **112** (1991) 183, 235; **116** (1992) 64, 340; **118** (1992) 78; **119** (1992) 177, 248
- by ion beam techniques **117** (1992) 460
- by ion scattering **111** (1991) 136
- by laser scattering **118** (1992) 78
- by laser tomography **113** (1991) 39
- by light scattering **112** (1991) 201; **113** (1991) 417; **114** (1991) 64; **115** (1991) 43; **117** (1992) 227; **118** (1992) 360
- by low energy electron diffraction **111** (1991) 882; **115** (1991) 411, 567; **116** (1992) 243
- by magnetic circularly polarized emission **117** (1992) 656
- by magnetic properties **111** (1991) 318, 366, 816, 943, 978, 1011, 1016; **112** (1991) 337, 587, 644; **113** (1991) 9, 371, 395; **114** (1991) 59, 279; **117** (1992) 715; **118** (1992) 101, 385, 477, 483; **119** (1992) 122, 403
- by magneto-optical properties **117** (1992) 816, 881, 886
- by magnetophotoluminescence **117** (1992) 830
- by magnetoreflection **117** (1992) 835
- by mass spectrometry **111** (1991) 93, 507, 539, 570; **112** (1991) 474, 515; **113** (1991) 1; **115** (1991) 74, 94, 216, 226, 241, 269, 551; **117** (1992) 80; **118** (1992) 204; **120** (1992) 25, 33, 39, 103, 119, 284
- by medium energy electron diffraction **111** (1991) 787
- by microwave lifetime **112** (1991) 7
- by neutron activation analysis **114** (1991) 141
- by neutron diffraction **113** (1991) 161
- by neutron irradiation **111** (1991) 288
- by neutron scattering **118** (1992) 33
- by nuclear magnetic resonance **114** (1991) 191; **117** (1992) 58; **118** (1992) 33, 430
- by optical bistability **117** (1992) 519, 523, 650
- by optical microscopy **111** (1991) 131, 570, 762, 767, 807, 936, 957; **112** (1991) 1, 14, 33, 71, 153, 294, 337, 354, 402, 463, 487, 531, 651, 737, 753, 758; **113** (1991) 61, 77, 103, 157, 221, 295, 329, 390, 417, 456, 485, 527, 653, 669, 691; **114** (1991) 7, 38, 64, 87, 118, 141, 239, 249, 255, 269, 536, 549, 561, 573, 656, 665, 676, 683, 687; **115** (1991) 145, 158, 174, 261, 299, 418, 504, 524, 529, 639, 723; **116** (1992) 15, 27, 93, 158, 213, 283, 289, 378, 461, 473, 524, 529; **117** (1992) 20, 148, 171, 238, 672, 826, 844; **118** (1992) 109, 218, 243, 269, 371, 377, 483; **119** (1992) 70, 79, 94, 98, 160, 177, 221, 248, 281, 309, 313, 329; **120** (1992) 130, 212, 376, 382, 389
- by optical properties **112** (1991) 283, 294; **113** (1991) 698; **114** (1991) 22, 71, 141; **117** (1992) 91, 290, 505, 1068; **119** (1992) 215; **120** (1992) 84, 88, 395
- by particle size distribution analysis **112** (1991) 415; **114** (1991) 118; **116** (1992) 41, 473; **117** (1992) 156, 1008; **118** (1992) 464
- by phase-shift-difference spectroscopy **115** (1991) 740
- by photoemission spectroscopy **117** (1992) 197
- by photoionization **117** (1992) 358
- by photoluminescence **111** (1991) 20, 30, 43, 98, 184, 205, 233, 246, 260, 264, 284, 323, 344, 360, 388, 397, 402, 407, 413, 424, 429, 445, 495, 502, 507, 511, 578, 589, 599, 605, 628, 698, 730, 736, 741, 752, 767, 772, 776, 787, 797, 816, 823, 829, 897, 920, 1016, 1043, 1062, 1089; **112** (1991) 14, 39, 723, 791; **113** (1991) 39, 333, 379, 390, 441; **114** (1991) 314, 327, 337, 561; **115** (1991) 74, 89, 154, 164, 236, 248, 254, 265, 274, 294, 333, 433, 464, 484, 490, 504, 519, 524, 529, 533, 538, 652, 660, 664, 679, 733, 802, 811; **116** (1992) 169, 283, 351, 387; **117** (1992) 85, 102, 111, 125, 156, 227, 271, 285, 303, 328, 341, 348, 353, 362, 366, 375, 391, 396, 400, 410, 415, 420, 424, 441, 465, 470, 480, 484, 492, 497, 501, 510, 515, 519, 583, 614, 617, 634, 656, 660, 666, 672, 727, 748, 788, 793, 810, 820, 840, 854, 862, 867, 871, 890, 969, 991, 997, 1002, 1008, 1035, 1046, 1074, 1075, 1077, 1081 **118** (1992) 176, 295, 304, 414; **119** (1992) 195, 322; **120** (1992) 124, 130, 140, 155, 162, 167, 180, 184, 189, 195, 200, 212, 218, 240, 252, 261, 296, 312, 333, 338, 343, 349, 353, 357
- by photomagnetization **117** (1992) 844
- by photorefraction **116** (1992) 27
- by photon echo **117** (1992) 773, 778
- by radiotracer diffusion **117** (1993) 177
- by Raman spectroscopy **111** (1991) 205, 383, 609, 802, 811, 816, 889, 897, 912, 989; **112** (1991) 651, 808; **114** (1991) 565; **115** (1991) 141; **117** (1992) 285, 309, 316, 324, 331, 488, 505, 549, 569, 738, 862, 890; **119** (1992) 322; **120** (1992) 296
- by reflectance **111** (1991) 70, 209, 693, 931, 1062, 1071; **112** (1991) 368; **115** (1991) 12, 338, 353, 515, 538, 793; **117** (1992) 328, 523, 835

- by reflectance difference **117** (1992) 115, 120, 194
- by reflection electron microscopy **116** (1992) 178
- by reflection high energy electron diffraction **111** (1991) 65, 83, 88, 98, 105, 110, 125, 162, 168, 173, 184, 189, 194, 210, 221, 228, 284, 339, 388, 397, 424, 434, 461, 489, 502, 521, 539, 609; 688, 711, 730, 736, 741, 752, 757, 792, 823, 856, 897, 902, 965, 973, 978, 984, 996, 1003, 1033; **112** (1991) 14, 146, 407, 427, 745, 781; **113** (1991) 716; **114** (1991) 327, 337, 346, 693; **115** (1991) 74, 94, 99, 106, 112, 122, 180, 226, 265, 289, 318, 338, 359, 365, 371, 398, 423, 509, 579, 634, 643, 664, 692, 745, 752, 758, 793, 798, 816, 821; **116** (1992) 98, 271; **117** (1992) 129, 166, 400, 810; **118** (1992) 213, 299, 414; **119** (1992) 195, 229; **120** (1992) 50, 114, 200, 284, 290, 306, 382
- by reflection spectroscopy **117** (1992) 877, 886
- by reflection type polarization spectroscopy **117** (1992) 802
- by refractive index **111** (1991) 807
- by Rutherford back scattering **111** (1991) 948, 989; **113** (1991) 716; **114** (1991) 307; **115** (1991) 589; **117** (1992) 460; **118** (1992) 125; **120** (1992) 195
- by scanning tunneling microscopy **111** (1991) 876, 889, 1033; **115** (1991) 31, 94; **116** (1992) 37
- by second harmonic generation **112** (1991) 283, 294; **113** (1991) 61, 161; **114** (1991) 656; **117** (1992) 501, 738, 894; **120** (1992) 94
- by secondary electron emission **115** (1991) 348
- by secondary ion mass spectrometry **111** (1991) 50, 239, 246, 252, 260, 295, 366, 445, 484, 495, 511, 544, 559, 564, 599, 843, 847, 907, 916, 1084; **112** (1991) 343; **113** (1991) 593; **114** (1991) 141, 481; **115** (1991) 261, 455, 460, 469, 474, 519, 679, 821; **116** (1992) 55, 75; **117** (1992) 54, 102, 213, 353, 391, 400, 862, 1046; **118** (1992) 204, 231, 425; **120** (1992) 189, 195, 206, 228, 234, 245, 301, 306, 312, 317, 343
- by solubility **114** (1991) 286, 293
- by spectroscopic methods **120** (1992) 57, 63, 71, 78, 103, 130, 200, 240
- by thermal analysis **112** (1991) 525, 600
- by thermal expansion coefficient **117** (1992) 189
- by thermal imaging **116** (1992) 213
- by thermally indiced bistability **117** (1992) 925
- by thermochemical properties **111** (1991) 609
- by thermogravimetry **114** (1991) 118; **118** (1992) 101; **119** (1992) 393
- by thermoluminescence **118** (1992) 396
- by transmission ion channeling spectroscopy **113** (1991) 45
- by transmission microscopy **114** (1991) 255
- by transmission spectroscopy **111** (1991) 131, 683, 711, 715; **113** (1991) 257; **114** (1991) 676
- by weight loss **118** (1992) 41
- by X-ray methods **111** (1991) 56, 110, 184, 269, 274, 344, 383, 402, 445, 456, 461, 470, 515, 525, 578, 584, 599, 623, 628, 669, 677, 683, 698, 736, 752, 762, 772, 802, 838, 897, 902, 907, 931, 961, 973, 984, 996, 1003, 1016, 1024, 1062, 1071, 1076; **112** (1991) 7, 39, 55, 71, 123, 153, 287, 291, 298, 302, 309, 337, 368, 386, 421, 487, 525, 587, 606, 621, 628, 644, 651, 660, 723, 737, 745, 773, 781, 797, 808, 819; **113** (1991) 9, 53, 61, 113, 120, 161, 181, 242, 333, 360, 371, 379, 390, 395, 403, 430, 441, 456, 520, 527, 540, 593, 643, 653, 663, 669, 681, 722; **114** (1991) 3, 7, 22, 38, 59, 118, 127, 186, 191, 209, 258, 279, 283, 299, 314, 346, 364, 373, 389, 435, 481, 565, 569, 619, 647, 656, 661, 683, 687, 707; **115** (1991) 31, 99, 122, 150, 158, 164, 216, 248, 289, 304, 318, 324, 328, 371, 406, 490, 579, 589, 602, 698, 705, 711, 718, 723, 752, 758, 762, 765, 769, 788, 807, 811, 816, 821; **116** (1992) 22, 55, 87, 93, 251, 260, 271, 333, 357, 369, 378, 495, 505, 507, 515, 524, 529; **117** (1992) 28, 37, 44, 85, 96, 102, 148, 156, 166, 233, 276, 290, 309, 328, 363, 370, 375, 543, 549, 565, 573, 666, 797, 806, 810, 816, 859, 964, 983, 991, 1008, 1030, 1079, 1082; **118** (1992) 41, 93, 101, 117, 125, 163, 277, 299, 371, 385, 396, 477, 483; **119** (1992) 79, 122, 195, 248, 313, 322, 363, 381, 393, 403, 407; **120** (1992) 98, 114, 124, 135, 167, 184, 212, 296, 328, 333, 338, 343
- by X-ray photoelectron spectroscopy **111** (1991) 393, 521, 747, 820, 957; **112** (1991) 407, 421, 745, 808; **115** (1991) 589, 652; **116** (1992) 271; **117** (1992) 573, 816, 964, 1080; **120** (1992) 369
- by Zeeman effect **117** (1992) 727, 871, 881

Charge transfer complexes **115** (1991) 831

Chirality **113** (1991) 508

Chromium **114** (1991) 107
- (III) oxide **112** (1991) 427

Clusters **116** (1992) 41, 204; **118** (1992) 360

Cobalt **114** (1991) 364
- gallium **111** (1991) 996
- organic **114** (1991) 364
- silicides **111** (1991) 948, 957; **114** (1991) 364; **115** (1991) 572

Computer simulation **111** (1991) 870; **112** (1991) 699, 824; **113** (1991) 147, 508, 575; **114** (1991) 267, 517, 603, 715; **115** (1991) 65, 169, 203; **116** (1992) 139; **117** (1992) 732, 1012, 1083; **118** (1992) 160, 365; **119** (1992) 261; **120** (1992) 57, 63

Constitutional supercooling **112** (1991) 244; **116** (1992) 105, 364; **117** (1992) 276; **118** (1992) 269, 277

Convection **112** (1991) 84, 97, 451, 539, 835; **113** (1991) 21, 92, 164, 549, 575, 587; **114** (1991) 153, 249, 357, 380, 411, 486, 517, 593, 715; **116** (1992) 139, 364, 447; **118** (1992) 49, 85, 151, 183, 193, 259, 319; **119** (1992) 1, 8, 24, 41, 66, 79, 94, 98, 111, 126, 141, 152, 160, 281, 297

Copper
- aluminum selenide **113** (1991) 390; **115** (1991) 811
- aluminum sulphide **115** (1991) 740
- chloride **112** (1991) 531; **116** (1992) 378
- gallium indium selenide **118** (1992) 41
- gallium ditelluride **113** (1991) 663
- gallium sulphide **115** (1991) 740, 807
- indium ditelluride **113** (1991) 663
- lead aluminum **119** (1992) 152
- organic **115** (1991) 762, 807
- oxide **112** (1991) 298, 600, 613; **115** (1991) 752
- selenide **112** (1991) 55
- thiostannates **114** (1991) 299

Crystal growth under high gravity conditions **119** (1992) 1, 8, 24, 41, 61, 66, 70, 74, 79, 94, 98, 111, 122, 126, 141, 152, 160, 167

Crystals, hard **113** (1991) 698
Cyclohexane **112** (1991) 201

Dendritic growth **112** (1991) 84, 97, 129, 463; **113** (1991) 77, 449, 566; **114** (1991) 7, 153, 549, 603; **116** (1992) 158, 191; **118** (1992) 160, 277; **119** (1992) 141, 303
Devices **111** (1991) 1, 20, 26, 59, 136, 228, 233, 305, 419, 440, 461, 470, 475, 479, 484, 489, 515, 559, 633, 664, 669, 776, 847, 912, 916, 957, 965, 1043, 1047, 1052, 1057, 1062, 1066, 1071, 1076, 1080, 1084, 1089, 1095, 1100, 1105, 1110, 1116; **112** (1991) 287, 309, 803; **113** (1991) 16, 61, 113, 681; **114** (1991) 700; **115** (1991) 203, 524, 623, 639; **116** (1992) 387, 436; **117** (1992) 1, 16, 24, 139, 183, 193, 375, 432, 510, 523, 527, 578, 583, 587, 894, 913, 925, 929, 935, 943, 964, 969, 979, 983, 987, 997, 1008, 1012, 1016, 1021, 1026, 1030, 1035, 1040, 1050, 1055, 1059, 1062, 1068, 1073, 1078, 1079; **118** (1992) 467; **120** (1992) 140, 157, 162, 167, 172, 177, 180, 184, 218, 234, 240, 245, 296, 317, 338, 343, 349, 369
Diamond **112** (1991) 580, 651, 808; **113** (1991) 295, 698; **114** (1991) 38, 209, 565; **115** (1991) 323; **116** (1992) 15, 225; **119** (1992) **177**, 271, 345
Diamond-like **113** (1991) 698
Diffusional control **111** (1991) 83, 151, 239, 348, 515, 782, 843, 870, 876, 1076; **112** (1991) 183, 201, 235, 781, 824; **113** (1991) 77, 549, 593, 606, 691; **114** (1991) 71, 203, 321, 351, 486, 581, 593; **115** (1991) 294, 375, 423; **116** (1992) 41, 55, 158, 251, 294, 518; **117** (1992) 244, 249, 259, 385, 400, 460, 492, 677, 682, 806, 867; **118** (1992) 33, 49, 60, 85, 135, 160, 259; **119** (1992) 24, 79, 94; **120** (1992) 45
Dislocations **111** (1991) 233, 309, 376, 383, 434, 683, 698, 715, 897, 902, 920, 948; **112** (1991) 33, 39, 227, 354, 359, 402, 496, 773, 781, 791; **113** (1991) 53, 221, 227, 254, 265, 279, 379, 430, 456, 499, 527, 681, 722; **114** (1991) 47, 127, 141, 239, 255, 573, 693; **115** (1991) 154, 169, 174, 199, 596, 698, 718, 774; **116** (1992) 37, 87, 260, 307, 340, 364, 515; **118** (1992) 14, 163, 452, 461; **119** (1992) 248, 322, 329
Dissolution **113** (1991) 549, 637; **116** (1992) 421, 473
Distribution coefficient **111** (1991) 141; **112** (1991) 129, 160, 171, 244, 563, 606, 723; **113** (1991) 549, 637; **114** (1991) 77, 87; **116** (1992) 191, 461, 515; **117** (1992) 213, 276, 913; **118** (1992) 85, 259; **119** (1992) 317
Dopants **111** (1991) 1, 30, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 309, 313, 318, 450, 515, 559, 564, 584, 614, 623, 651, 669, 720, 730, 772, 776, 782, 797, 829, 833, 843, 847, 856, 870, 907, 916, 1076, 1095; **112** (1991) 153, 343, 628, 731, 819; **113** (1991) 9, 21, 103, 127, 395, 412, 520, 587; **114** (1991) 13, 87, 191, 321, 561, 700; **115** (1991) 299, 439, 443, 455, 460, 464, 469, 474, 484, 498, 617, 623, 639; **116** (1992) 15, 75, 151, 169, 191, 369, 436, 461, 518, 521; **117** (1992) 1, 102, 111, 119, 134, 213, 244, 249, 254, 259, 271, 290, 303, 320, 324, 331, 341, 385, 391, 406, 415, 420, 480, 510, 640, 660, 666, 694, 704, 718, 721, 727, 783, 788, 806, 820, 890, 913, 935, 964, 969, 979, 987, 997, 1021, 1026, 1035, 1050, 1073, 1078, 1079; **118** (1992) 85, 218, 259, 295, 371, 401, 425, 467; **119** (1992) 98, 292, 317

Electrolytes **113** (1991) 599; **118** (1992) 71
Erbium
– arsenide **111** (1991) 989
Etching
– chemical **111** (1991) 936; **112** (1991) 227, 294, 354, 402, 773, 791, 838; **113** (1991) 39, 103, 113, 221, 329, 485, 491, 681; **114** (1991) 255; **115** (1991) 154, 174, 180, 261, 299, 612, 674, 723, 728, 733; **116** (1992) 364, 369, 515; **117** (1992) 271, 549, 666; **118** (1992) 41, 109, 125, 163, 176, 218, 269; **119** (1992) 70, 98, 303;
– dry BCl_3 plasma **117** (1992) 375
– photochemical **117** (1992) 666, 1080
– thermal **114** (1991) 565; **115** (1991) 679
Eutectic growth **112** (1991) 386, 635; **113** (1991) 77, 242, 289; **114** (1991) 249, 267, 357; **118** (1992) 135, 377, 385; **119** (1992) 126, 141, 160

Fiber optics **117** (1992) 826
Finite element method **112** (1991) 699; **113** (1991) 227, 499; **114** (1991) 267, 411; **119** (1992) 261

Gadolinium
– gallium garnet **113** (1991) 575
– molybdate **116** (1992) 185
Gallium
– aluminum arsenide **111** (1991) 269; **113** (1991) 540; **115** (1991) 203, 455; **120** (1992) 25, 57, 245
– antimonide **111** (1991) 360, 550, 619, 623, 638, 651, 659, 664; **113** (1991) 557; **115** (1991) 474; **119** (1992) 8, 270;
– arsenide **111** (1991) 14, 30, 39, 43, 50, 65, 70, 83, 88, 93, 98, 115, 120, 125, 131, 136, 168, 178, 184, 189, 200, 210, 216, 233, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 318, 333, 339, 344, 348, 371, 393, 424, 507, 511, 515, 521, 539, 544, 550, 554, 559, 564, 570, 574, 578, 584, 683, 741, 747, 833, 978, 989, 1052, 1057, 1066, 1071, 1089, 1100, 1105; **112** (1991) 1, 14, 123, 316, 437, 474, 791, 838; **113** (1991) 103, 131, 227, 254, 265, 279, 412, 491; **114** (1991) 99, 203, 255, 337, 581, 665; **115** (1991) 52, 61, 65, 69, 74, 83, 89, 94, 99, 122, 128, 141, 145, 203, 211, 221, 226, 241, 248, 294, 318, 333, 338, 348, 353, 398, 406, 418, 423, 443, 448, 479, 519, 524, 538; **116** (1992) 48, 98, 169, 213, 240, 351, 369, 387, 461, 511, 518; **118** (1992) 117, 163, 414, 467; **119** (1992) 74, 195; **120** (1992) 25, 33, 39, 45, 50, 57, 63, 71, 78, 88, 94, 103, 114, 124, 200, 206, 218, 228, 234, 240, 245, 296, 306, 323, 362, 369, 389, 395
– arsenide antimonide **111** (1991) 628
– arsenide phosphide **111** (1991) 61; **120** (1992) 389
– arsenide silicide **115** (1991) 328
– indium antimonide **111** (1991) 683
– indium arsenide **111** (1991) 339, 413, 461, 466, 475, 599, 1062, 1084; **112** (1991) 343, 359; **115** (1991) 74, 203, 398; **116** (1992) 521; **120** (1992) 25, 33, 57, 140, 312, 338, 357
– indium arsenide antimonide **111** (1991) 413, 669; **115** (1991) 728
– indium arsenide phosphide **111** (1991) 599; **112** (1991) 27; **120** (1992) 140, 145, 157, 180, 338, 349, 376

– indium phosphide **111** (1991) 353, 564, 578; **112** (1991) 373; **115** (1991) 529
– nitride **111** (1991) 1024; **115** (1991) 381, 628, 634, 639; **120** (1992) 114
– organic **111** (1991) 115, 274, 539, 544, 550, 554, 570, 574, 578, 599; 638; **112** (1991) 1, 359, 474, 628; **113** (1991) 103, 441; **114** (1991) 3, 31, 481, 581; **115** (1991) 52, 61, 69, 83, 89, 154, 158, 211, 216, 221, 226, 236, 241, 248, 265, 353, 406, 423, 448, 460, 469, 474, 617, 807; **118** (1992) 117
– phosphide **111** (1991) 564; **114** (1991) 380; **115** (1991) 158, 261, 265, 418, 469, 538; **118** (1992) 176; **120** (1992) 389
– selenide **111** (1991) 1038; **114** (1991) 99; **115** (1991) 798
Garnets **113** (1991) 575; **118** (1992) 218, 396; **119** (1992) 297, 313
Germanium **111** (1991) 833, 847, 876, 882; **112** (1991) 7; **113** (1991) 21, 45, 186; **115** (1991) 79, 106, 112; **116** (1992) 158; **120** (1992) 284
– selenide **119** (1992) 79
– silicide **114** (1991) 573
– silicon **118** (1992) 452
Glycine **114** (1991) 389; **116** (1992) 421
Gold **112** (1991) 427
– telluride **116** (1992) 397
Grain boundary **111** (1991) 715; **112** (1991) 227, 354; **113** (1991) 465; **114** (1991) 198, 249, 467, 549, 665; **115** (1991) 774; **117** (1992) 96, 1098; **118** (1992) 14, 109, 135, 461; **119** (1992) 70, 98
Gypsum **112** (1991) 415, 445; **113** (1991) 508; **116** (1992) 87; **118** (1992) 287

Hafnium
– germanate **116** (1992) 151
– silicate **116** (1992) 151
Hard crystals **113** (1991) 698
Heat flow control **112** (1991) 699, 835; **113** (1991) 186, 254, 265, 279, 557, 575; **114** (1991) 27, 267, 411, 517, 603; **116** (1992) 127, 139; **118** (1992) 60, 151, 269, 439
Heterojunction **111** (1991) 20, 50, 194, 205, 221, 233, 280, 288, 295, 300, 305, 309, 313, 318, 323, 376, 383, 388, 393, 397, 419, 470, 479, 489, 515, 521, 525, 559, 578, 599, 609, 623, 628, 643, 647, 651, 659, 664, 669, 698, 747, 767, 820, 823, 829, 912, 916, 120, 136, 173, 978, 989, 996, 1016, 1033, 1076, 1089, 1095, 1116; **112** (1991) 583, 803; **113** (1991) 113, 477, 520; **114** (1991) 127, 258, 337, 700; **115** (1991) 99, 318, 365, 509, 529, 533, 612, 628, 652, 674, 687, 718, 816; **116** (1992) 436, 521; **117** (1992) 20, 85, 316, 362, 454, 488, 497, 527, 543, 549, 560, 569, 573, 578, 583, 742, 844, 894, 954, 959, 1062, 1073, 1078, 1079, 1083; **118** (1992) 299; **119** (1992) 322
High gravity crystal growth **119** (1992) 1, 8, 24, 41, 61, 66, 70, 74, 79, 94, 98, 111, 122, 126, 141, 152, 160, 167
Hydrodynamics **113** (1991) 92, 164, 575

Ice **112** (1991) 129; **113** (1991) 417, 465; **118** (1992) 33
Impurity **111** (1991) 274, 284, 450, 511, 559, 574, 776, 847; **112** (1991) 129, 227, 244, 308, 663, 723; **113** (1991) 289, 465, 508, 527, 549, 637, 691; **114** (1991) 321, 373; **115** (1991) 83, 89, 221, 241, 261, 455, 484, 519, 617, 679, 733; **116** (1992) 225, 240, 351; **117** (1992) 49, 75, 80, 213, 249, 254, 290, 303, 309, 328, 336, 348, 353, 358, 410, 415, 420, 460, 625, 634, 640, 650, 660, 666, 694, 704, 710, 715, 727, 763, 773, 783, 788, 820, 850, 894, 902, 913, 918, 948, 1080; **118** (1992) 1, 85, 176, 204, 231, 259, 304, 309, 377
Inclusions **111** (1991) 39; **113** (1991) 566; **116** (1992) 63
Indium
– aluminum arsenide **111** (1991) 313, 456, 470; **115** (1991) 509; **120** (1992) 184
– aluminum phosphide **115** (1991) 265
– antimonide **111** (1991) 614, 623, 633, 688; **119** (1992) 8, 98
– arsenide **111** (1991) 93, 110, 125, 205, 383, 388, 393, 397, 402, 434, 550, 623, 633, 651, 659, 664, 677, 683; **115** (1991) 99, 164, 309, 324; **116** (1992) 81; **120** (1992) 155
– arsenide antimonide **111** (1991) 633, 638
– arsenide phosphide **111** (1991) 61
– gallium aluminum arsenide **111** (1991) 56, 313
– gallium aluminum phosphide **112** (1991) 628; **113** (1991) 127; **115** (1991) 498; **119** (1992) 292
– gallium antinonide **111** (1991) 677, 683
– gallium antimonide arsenide **116** (1992) 204
– gallium arsenide **111** (1991) 173, 228, 233, 309, 313, 339, 407, 413, 419, 429, 434, 456, 461, 466, 470, 475, 479, 489, 584, 594, 599, 628, 1062, 1076, 1080, 1095, 1110; **112** (1991) 33, 583; **113** (1991) 379, 477, 485; **114** (1991) 31, 327, 346, 481, 569, 633, 693; **115** (1991) 154, 169, 174, 375, 433, 460, 504, 509, 723; **116** (1992) 98, 271, 436; **118** (1992) 117; **120** (1992) 33, 98, 135, 177, 184, 212, 301, 328, 333, 382, 389
– gallium arsenide phosphide **111** (1991) 495, 599; **112** (1991) 39; **115** (1991) 231; **120** (1992) 150, 162, 157, 177, 343, 353
– gallium phosphide **111** (1991) 525; **112** (1991) 39; **114** (1991) 561; **115** (1991) 265, 304; **116** (1992) 436
– manganese arsenide **111** (1991) 1011
– nitride **111** (1991) 1024
– organic **111** (1991) 578, 599, 638; **112** (1991) 359, 628; **113** (1991) 441; **114** (1991) 31, 481; **115** (1991) 74, 154, 254, 265, 324, 460, 464; **116** (1992) 511; **118** (1992) 117
– phosphide **111** (1991) 495, 502, 564, 589, 594, 599, 605, 1076, 1080; **112** (1991) 111, 343, 583, 691; **113** (1991) 16, 39, 221; **114** (1991) 92, 127, 293, 314, 321, 481; **115** (1991) 150, 154, 180, 254, 324, 371, 464; **116** (1992) 75; **120** (1992) 98, 119, 130, 140, 150, 157, 162, 167, 180, 184, 312, 317, 328, 333, 349, 353, 357, 362, 376, 389
– selenide **112** (1991) 797
Interface **111** (1991) 98, 141, 189, 221, 274, 328, 348, 383, 397, 407, 461, 521, 525, 559, 599, 609, 643, 647, 677, 698, 741, 747, 757, 767, 823, 889, 902, 920, 936, 961, 989, 1029, 1057, 1076, 1095, 1100, 1116; **112** (1991) 39, 129, 201, 359, 445, 451, 458, 463, 539, 554, 670, 699, 803, 819, 835; **113** (1991) 53, 147, 186, 289, 337, 417, 575, 633, 637; **114** (1991) 31, 99, 127, 133, 258, 267, 307, 337, 357, 389, 517, 536, 549, 640, 665; **115** (1991) 99, 133, 150, 318, 324, 381, 388, 433, 529, 579, 596, 612, 623, 652, 674, 683, 698, 774, 788; **116** (1992) 63, 81, 98, 139, 158, 235, 271, 294, 364, 397, 511, 515, 518; **117** (1992) 20, 166, 183, 276, 285, 316, 441, 460, 484, 488, 549, 560, 569, 578, 583, 587, 608, 742, 890, 918, 954, 1012,

1016, 1050, 1075; **118** (1992) 33, 85, 151, 183, 259, 269, 299, 319, 353, 365, 414, 439; **119** (1992) 70, 281, 322
Ionic crystals **112** (1991) 458
Iron
– aluminum silicide **111** (1991) 984
– carbon alloy **119** (1992) 141
– cobalt alloy **115** (1991) 602
– disulphide **112** (1991) 737
– gallate **112** (1991) 644
– pentacarbonyl **112** (1991) 737
– (III) phosphate **113** (1991) 140

Kinetics
– of adsorption **115** (1991) 12
– of anneal **111** (1991) 65
– of antiphase domain annihilation **111** (1991) 120
– of atom incorporation **111** (1991) 173
– of decomposition **112** (1991) 415, 474
– of defect creation **111** (1991) 870
– of doping **111** (1991) 239; **120** (1992) 312
– of freezing hydrolysis **112** (1991) 129
– of growth **111** (1991) 1, 43, 61, 65, 75, 83, 93, 105, 115, 136, 162, 178, 189, 194, 210, 216, 233, 252, 280, 328, 339, 353, 360, 371, 407, 434, 539, 544, 550, 554, 578, 594, 599, 638, 647, 711, 730, 757, 762, 833, 847, 856, 860, 876, 907, 948, 973, 978, 989, 1003, 1057, 1062; **112** (1991) 7, 27, 84, 97, 111, 129, 146, 160, 171, 192, 201, 294, 302, 309, 316, 407, 445, 467, 496, 515, 531, 554, 571, 591, 628, 651, 670, 691, 737, 753, 824; **113** (1991) 83, 103, 120, 127, 140, 295, 337, 417, 491, 606, 637, 643; **114** (1991) 27, 31, 71, 92, 118, 228, 239, 314, 337, 357, 364, 380, 411, 481, 486, 536, 549, 603, 613, 640; **115** (1991) 1, 43, 79, 83, 89, 112, 117, 158, 194, 199, 211, 216, 226, 236, 241, 265, 274, 279, 284, 294, 304, 333, 338, 353, 398, 406, 423, 428, 509, 602, 607, 612, 643, 687, 692, 698, 733, 752, 793, 807, 831; **116** (1992) 63, 158, 169, 251, 283, 294, 319, 340, 414, 473, 483; **117** (1992) 1, 37, 44, 67, 75, 107, 116, 125, 134, 144, 152, 166, 254, 820, 991, 1088; **118** (1992) 14, 49, 60, 71, 183, 231, 243, 287, 348, 360, 401, 430, 439, 473; **119** (1992) 248, 292, 322, 403; **120** (1992) 25, 33, 39, 45, 50, 57, 63, 78, 84, 88, 103, 140, 145, 150, 162, 167, 206, 252, 261, 269, 275, 279, 284, 312, 338, 343, 369, 376, 389, 395
– of interface control **111** (1991) 20, 30, 141, 189, 194, 344, 376, 388, 515, 578, 599, 864, 973, 1003; **112** (1991) 407, 451, 670; **114** (1991) 603; **115** (1991) 99, 324, 607, 628, 821; **116** (1992) 158, 294, 414; **117** (1992) 560;**118** (1992) 287, 333, 365; **119** (1992) 371; **120** (1992) 155, 333, 338
– of internal melting **113** (1991) 465
– of ledge diffusion **112** (1991) 824
– of luminescence decay **117** (1992) 721
– of nucleation **111** (1991) 110, 194, 402, 948, 1003; **112** (1991) 146, 407; **113** (1991) 83, 140, 599; **115** (1991) 69, 122, 150, 158, 164, 338, 567, 612; **116** (1992) 158, 191, 294, 414, 483, 495; **117** (1992) 127; **118** (1992) 231, 401, 464; **119** (1992) 141; **120** (1992) 140
– of precrystallization clusters **118** (1992) 360
– of self-compensation **117** (1992) 913
– of simultaneous processes **113** (1991) 83
– of step formation **112** (1991) 183
– of transfer processes **117** (1992) 608
– of transformation **116** (1992) 421, 473

Lanthanide
– cuprates **113** (1991) 395
Lanthanum
– cuprate **115** (1991) 745
– hexaboride **118** (1992) 461
– praseodymium hexaboride **113** (1991) 329
Lasers **111** (1991) 1043, 1047, 1052, 1057, 1062, 1066; **112** (1991) 39, 283, 731; **113** (1991) 540, 593, 691; **116** (1992) 505; **117** (1992) 139, 432, 527, 894, 1040, 1046, 1062, 1068, 1077, 1078, 1083; **118** (1992) 371; **119** (1992) 363
Lattice mismatch **111** (1991) 56,120, 221, 313, 376, 445, 479, 489, 584, 594, 599, 628, 688, 984, 1029, 1033; **112** (1991) 33, 39, 309, 628, 781, 803; **113** (1991) 379, 430, 441, 477; **114** (1991) 31, 258, 307, 561, 633, 647; **115** (1991) 169, 304, 324, 365, 529, 711, 788; **117** (1992) 10, 24, 139, 309, 316, 515, 527, 554, 560, 565, 578, 886; **118** (1992) 117, 299; **120** (1992) 33, 135, 150, 167, 184, 189, 328, 338
Lead
– alloys **112** (1991) 563
– cadmium sulphoselenide **115** (1991) 687
– cobalt tungstate **112** (1991) 71
– cuprates **113** (1991) 371
– europium selenide **113** (1991) 593
– nitrate **119** (1992) 1
– organic **115** (1991) 289
– selenide **114** (1991) 687
– strontium yttrium calcium cuprate **118** (1992) 101
– telluride **112** (1991) 227; **119** (1992) 24
– tin alloy **118** (1992) 183
– tin eutectic **114** (1991) 249
– tin telluride **114** (1991) 707; **116** (1992) 139; **119** (1992) 94
– titanate **115** (1991) 289; **116** (1992) 251
Light emitting diode **111** (1991) 829; **115** (1991) 623, 639
Lithium
– iodate **116** (1992) 63
– niobate **112** (1991) 451; **113** (1991) 61; **114** (1991) 87, 191; **115** (1991) 821; **116** (1992) 185, 327; **119** (1992) 215, 317
– triborate **112** (1991) 283
– zinc phosphide **113** (1991) 333
Lysozyme **116** (1992) 289, 414; **118** (1992) 360; **119** (1992) 200

Magnesium
– organic **115** (1991) 455
Manganese
– aluminum **111** (1991) 978
– bismuth eutectic **114** (1991) 357
– chloride **112** (1991) 160, 171
– indium telluride **114** (1991) 661
– organic **113** (1991) 1; **115** (1991) 455
– sulphide **117** (1992) 810
– telluride **111** (1991) 767; **117** (1992) 816

Mathematical model **112** (1991) 192, 244, 515; **113** (1991) 21, 164, 254, 265, 430, 477; **114** (1991) 593; **116** (1992) 139; **118** (1992) 33, 49, 231, 259
Melt growth technique
– by Bridgman–Stockbarger method
– – of cadmium cobalt selenide **117** (1992) 840
– – of cadmium fluoride **119** (1992) 339
– – of cadmium manganese selenide **117** (1992) 840
– – of cadmium manganese telluride **117** (1992) 826, 840
– – of cadmium selenide telluride **117** (1992) 666
– – of cadmium selenide/zinc selenide **113** (1991) 653
– – of cadmium telluride **112** (1991) 723; **113** (1991) 147; **117** (1992) 660; **118** (1992) 269
– – of cadmium zinc telluride **116** (1992) 515; **118** (1992) 269; **119** (1992) 261
– – of gallium antimonide **113** (1991) 557
– – of gallium indium arsenide antimonide **115** (1991) 728
– – of germanium **113** (1991) 21
– – of lead telluride **112** (1991) 227
– – of lead tin eutectic **114** (1991) 249
– – of lead tin telluride **114** (1991) 707; **116** (1992) 139
– – of mercury cadmium telluride **113** (1991) 92; **114** (1991) 411; **118** (1992) 365
– – of organic crystals **113** (1991) 360
– – of III–V compounds **118** (1992) 109
– – of zinc chalcogenides **117** (1992) 715
– – of zinc selenide **117** (1992) 75, 80
– – computer simulation of **113** (1991) 147
– – control of **119** (1992) 371
– – numerical approach of **114** (1991) 593
– – numerical simulation of **113** (1991) 21, 587
– – theory of **116** (1992) 139
– – thermal modeling of **118** (1992) 193, 365
– – using centrifuge
– – – of gallium antimonide **118** (1992) 8
– – – of immiscible alloys **118** (1992) 152
– – – of indium antimonide **118** (1992) 8
– – – of iron carbon alloys **119** (1992) 141
– – – of lead tin telluride **119** (1992) 94
– – – of lead telluride **119** (1992) 24
– – – of semiconductors **119** (1992) 66
– – – analytical study of **119** (1992) 111
– – – theory of **119** (1992) 41
– by Czochralski method
– – of β-barium borate **114** (1991) 676, 683
– – of bismuth germanide **118** (1992) 396, 439
– – of bismuth silicate **118** (1992) 439
– – of bismuth strontium calcium cuprate **113** (1991) 9
– – of gadolinium gallium garnet **113** (1991) 575
– – of gadolinium molybdate **116** (1992) 185
– – of gallium arsenide **112** (1991) 123; **113** (1991) 114; **114** (1991) 665; **116** (1992) 213, 369, 461
– – of indium gallium arsenide **112** (1991) 33; **113** (1991) 485; **115** (1991) 723
– – of indium phosphide **113** (1991) 39, 221; **114** (1991) 321
– – of lithium niobate **112** (1991) 451; **113** (1991) 61; **114** (1991) 87, 191; **116** (1992) 185, 327; **119** (1992) 215, 317
– – of nickel manganese tin alloy **118** (1992) 277
– – of semiconductors **114** (1991) 47
– – of rare earth garnets **119** (1992) 313
– – of silicon **112** (1991) 308, 699, 819; **113** (1991) 164, 549; **114** (1991) 267, 715; **118** (1992) 85
– – of strontium barium niobate **113** (1991) 337
– – of tellurium dioxide **116** (1992) 364
– – of III–V compounds **118** (1992) 109
– – of titanium dioxide **112** (1991) 835
– – of yttrium aluminate **119** (1992) 363
– – of yttrium aluminum garnet **118** (1992) 396
– – of yttrium orthoaluminate, neodymium doped **118** (1992) 371
– – model of **113** (1991) 186, 227
– – numerical study of **113** (1991) 164
– – stability of process **114** (1991) 27
– – theory of **116** (1992) 447; **118** (1992) 259, 353
– using real-time computer control **113** (1991) 337
– by floating zone method
– – of β-barium borate **114** (1991) 656
– – of bismuth strontium calcium cuprate **118** (1992) 477
– – of cadmium telluride **117** (1992) 656
– – of cadmium zinc telluride **117** (1992) 656
– – of gallium arsenide **113** (1991) 131; **118** (1992) 163
– – of lanthanum hexaboride **118** (1992) 461
– – of lanthanum praseodymium hexaboride **113** (1991) 329
– – of lead telluride **112** (1991) 227
– – of mercury cadmium telluride **117** (1992) 758
– – of mercury zinc telluride **117** (1992) 208
– – of sodium nitrate **114** (1991) 517; **118** (1992) 151; **119** (1992) 281
– – of titanium dioxide **112** (1991) 354
– – computer simulation of **114** (1991) 517
– – theory of **116** (1992) 22
– by gradient solidification method
– – of sapphire **119** (1992) 391
– by high gravity
– – of eutectic alloys **119** (1992) 126
– – of gallium arsenide **119** (1992) 74
– by ion-exchange technique
– – of zinc selenide **112** (1991) 781
– by laser-heated pedestal growth
– – of lithium triborate **112** (1991) 283
– – of strontium barium niobate fibers **114** (1991) 500
– – of yttrium lithium fluoride **112** (1991) 731
– by melt spinning
– – of nickel phosphide **112** (1991) 525
– by traveling heater method
– – of copper gallium indium selenide **118** (1992) 41
– – of mercury cadmium telluride **114** (1991) 77
– by traveling heater method in centrifuge
– – of gallium antimonide **119** (1992) 8
– – of indium antimonide **119** (1992) 8
– by uniaxial solidifation
– – of alloys **112** (1991) 539
– – of aluminum silicon alloys **118** (1992) 377
– – of binary alloys **118** (1992) 319

– – of bismuth strontium calcium cuprate **116** (1992) 529; **118** (1992) 483
– – of cadmium zinc telluride **117** (1992) 276
– – of lead tin alloy **118** (1992) 183
– – of lithium calcium aluminum fluoride **113** (1991) 691
– – of organic crystals **118** (1992) 135, 183
– – of succinonitrile **112** (1991) 463
– – of yttrium aluminum garnet **118** (1992) 218
– – of yttrium barium cuprate **114** (1991) 283
– – thermal modeling of **118** (1992) 193
– by uniaxial solidification in centrifuge
– – of alloys **119** (1992) 160
– – of gallium antimonide **119** (1992) 70
– – of indium antimonide **119** (1992) 98
– by various methods
– – of aluminum silicon alloys **113** (1991) 77
– by zone melting
– – of cyclohexane **112** (1991) 201
– – of gallium arsenide **116** (1992) 369
– – of lead **112** (1991) 554
– – of lead alloys **112** (1991) 563
– – of lead telluride **112** (1991) 227
– by zone melting in centrifuge
– – of aluminum **119** (1992) 167
– – of gallium antimonide **119** (1992) 8
– – of indium antimonide **119** (1992) 8
– theory of **112** (1991) 591, 670
– under magnetic field
– – of semiconductors **113** (1991) 305
Mercury
– cadmium telluride **111** (1991) 698, 711, 715, 720, 725; **112** (1991) 402; **113** (1991) 53, 92, 520; **114** (1991) 77, 351, 411; **115** (1991) 698; **117** (1992) 1, 16, 20, 24, 28, 33, 37, 44, 54, 161, 166, 171, 177, 183, 189, 193, 203, 213, 218, 238, 454, 460, 758, 844, 954, 1046; **118** (1992) 204, 365
– copper indium manganese telluride **119** (1992) 381
– (I) halides **118** (1992) 78
– (II) iodide **113** (1991) 251; **115** (1991) 43
– manganese telluride **113** (1991) 1; **117** (1992) 850
– silver indium manganese telluride **119** (1992) 381
– telluride **111** (1991) 720, 725; **117** (1992) 49
– zinc telluride **117** (1992) 189, 203, 208
Metals **111** (1991) 1003
Microgravity **113** (1991) 21, 131; **114** (1991) 153, 357, 486, 707; **116** (1992) 105, 127, 289; **118** (1992) 49; **119** (1992) 200
Molecular dynamics **115** (1991) 186
Molybdenum **114** (1991) 107
– carbide **116** (1992) 307
– diselenide **111** (1991) 1033
Monte Carlo method **111** (1991) 178, 328, 864; **115** (1991) 186, 194, 199, 338, 406, 428; **117** (1992) 732
Morphological stability **111** (1991) 189, 376; **112** (1991) 129, 235, 244, 539, 670; **113** (1991) 16, 465; **114** (1991) 446, 549, 603; **115** (1991) 106; **116** (1992) 105, 158, 235, 397; **117** (1992) 1008; **118** (1992) 160, 183, 243, 319, 333; **119** (1992) 152
Morphology of growth **111** (1991) 1, 65, 216, 233, 434, 489, 589, 605, 647, 720, 833, 864, 876, 882, 936, 948, 1003; **112** (1991) 7, 14, 39, 47, 71, 84, 97, 123, 153, 291, 294, 337, 373, 386, 445, 463, 487, 496, 507, 571, 613, 635, 651, 660, 670, 773, 824, 835; **113** (1991) 69, 103, 157, 161, 242, 289, 295, 360, 395, 417, 441, 449, 456, 491, 508, 566, 691, 716; **114** (1991) 7, 38, 59, 107, 118, 141, 228, 258, 269, 346, 380, 389, 481, 497, 536, 549, 569, 573, 603, 619, 687; **115** (1991) 43, 52, 128, 145, 158, 174, 186, 261, 279, 299, 304, 313, 359, 365, 418, 455, 460, 542, 561, 572, 579, 602, 612, 648, 788; **116** (1992) 15, 27, 87, 158, 191, 225, 243, 283, 314, 319, 333, 340, 378, 397, 421, 473, 495, 524; **117** (1992) 96, 148, 415, 543, 1008, 1082; **118** (1992) 109, 135, 243, 309, 348, 377, 430; **119** (1992) 79, 221, 303, 329, 403

Neodymium
– cerium cuprate **118** (1992) 385
Nickel **113** (1991) 242
– manganese tin **118** (1992) 277
– phosphide **112** (1991) 525; **113** (1991) 242
m-Nitroaniline **119** (1992) 309
Nonlinear optics **111** (1991) 693; **112** (1991) 183; **113** (1991) 157, 161, 360, 456; **117** (1992) 501, 519, 523, 598, 603, 622, 650, 738, 768, 773, 778, 788, 802, 894; **120** (1992) 94
Nucleation **111** (1991) 162, 168, 194, 210, 383, 402, 864, 876, 948, 1003; **112** (1991) 291, 407, 496, 580, 758, 808; **113** (1991) 140, 251, 289, 371, 599, 633, 637, 716; **114** (1991) 118, 198, 258, 314, 613; **115** (1991) 61, 99, 158, 164, 359, 388, 418, 542, 612, 705, 774; **116** (1992) 41, 294, 307, 314, 473, 495; **117** (1992) 598; **118** (1992) 401, 464; **119** (1992) 141, 229, 241
Numbers
– Arnold **119** (1992) 24, 66
– Biot **113** (1991) 557; **118** (1992) 193
– Grashof **112** (1991) 192, 451; **113** (1991) 21, 120, 575, 587; **114** (1991) 593, 715; **116** (1992) 447; **118** (1992) 193; **119** (1992) 24, 297
– Lewis **113** (1991) 92
– Marangoni **113** (1991) 131
– Nusselt **116** (1992) 139
– Peclet **112** (1991) 84, 97, 244; **113** (1991) 21, 164, 587, 606; **114** (1991) 357, 411, 593; **116** (1992) 139; **118** (1992) 193
– Prandtl **112** (1991) 192; **113** (1991) 92, 164; **118** (1992) 49, 193
– Rayleigh **112** (1991) 201; **113** (1991) 92, 164; **114** (1991) 411; **118** (1992) 193; **119** (1992) 8
– Reynolds **112** (1991) 192; **113** (1991) 164, 575, 606
– Schmidt **112** (1991) 539; **113** (1991) 587; **114** (1991) 411, 593
– Seeger **116** (1992) 158
– Sherwood **116** (1992) 158
– Stefan **114** (1991) 411
– Taylor **119** (1992) 8
Numerical analysis **116** (1992) 158

Optoelectronic crystals **117** (1992) 583, 732; **119** (1992) 391
Organic crystals **112** (1991) 84, 97, 201, 302, 463, 507, 729, 758;

113 (1991) 69, 157, 360, 385, 456; **114** (1991) 228, 239, 286, 389; **115** (1991) 388, 826, 831; **116** (1992) 191, 289, 314, 333, 421, 495; **118** (1992) 135, 183, 348, 360, 464; **119** (1992) 200, 309, 368, 393, 399, 407
Oxides **113** (1991) 698
Oxynitrides **113** (1991) 698

Perfection of crystals **111** (1991) 1, 56, 98, 136, 228, 288, 383, 407, 429, 434, 450, 698, 715, 720, 736, 762, 772, 870, 931, 948, 989, 1076; **112** (1991) 71, 123, 153, 227, 354, 368, 402, 407, 421, 487, 531, 587, 635, 791, 808, 838; **113** (1991) 16, 39, 45, 53, 265, 279, 295, 329, 333, 337, 360, 379, 403, 456, 527, 669, 691, 722; **114** (1991) 7, 64, 141, 191, 209, 258, 307, 314, 373, 500, 573, 656, 661, 665, 700, 707; **115** (1991) 43, 122, 128, 133, 150, 186, 248, 375, 479, 572, 612, 718, 774, 788, 811; **116** (1992) 22, 55, 63, 75, 81, 87, 93, 158, 225, 260, 369, 515; **117** (1992) 16, 20, 28, 37, 49, 67, 75, 96, 119, 125, 171, 208, 227, 233, 238, 259, 266, 276, 290, 336, 366, 385, 396, 460, 492, 536, 560, 578, 656, 660, 666, 672, 677, 682, 689, 694, 704, 758, 820, 902, 929, 979, 1055; **118** (1992) 1, 14, 163, 243, 269, 385, 430, 452, 477; **119** (1992) 1, 70, 79, 98, 221, 261, 322, 371
Periodic bond chain theory **112** (1991) 613; **114** (1991) 389, 497; **119** (1992) 329
Phase diagrams **112** (1991) 129, 244, 531, 600, 663; **113** (1991) 371, 385, 441, 485, 653, 659; **114** (1991) 269, 286, 373, 411, 435, 573, 633, 661; **115** (1991) 150, 294, 348, 602; **116** (1992) 178, 204, 427, 505; **117** (1992) 10, 991; **118** (1992) 1, 101, 135, 314, 461; **119** (1992) 271, 313, 381; **120** (1992) 71
Phenomenological theory **111** (1991) 61, 376; **112** (1991) 7, 235; **113** (1991) 7, 235; **114** (1991) 13, 497, 640; **116** (1992) 294, 397, 473; **117** (1992) 710, 830, 907; **118** (1992) 85, 231, 259, 353, 430, 439; **119** (1992) 271
Phosphorus
– organic **114** (1991) 561; **115** (1991) 254, 261
Pivalic acid **112** (1991) 84
Platinum **115** (1991) 596
Polyethylene **114** (1991) 228
Polymerization **113** (1991) 69
Polymorphism/polytypism **111** (1991) 651; **115** (1991) 733; **116** (1992) 333, 421; **117** (1992) 85, 536; **118** (1992) 430
Potassium **115** (1991) 411
– bromide **112** (1991) 235
– chloride **112** (1991) 824
– dihydrogen phosphate **112** (1991) 235; **114** (1991) 71; **118** (1992) 231
– hydrogen phthalate **114** (1991) 239
– tantalate niobate **116** (1992) 27
– titanyl phosphate **112** (1991) 294, 309, 773; **113** (1991) 722; **114** (1991) 141; **119** (1992) 329
– yttrium tungstate **116** (1992) 505
Precursor **113** (1991) 1; **114** (1991) 364, 507; **115** (1991) 52, 241, 353; **116** (1992) 48, 436; **117** (1992) 58, 119; **120** (1992) 103, 124, 150
Proteins **112** (1991) 758; **113** (1991) 385; **114** (1991) 286; **118** (1992) 360; **119** (1992) 200, 407

Purification of materials **112** (1991) 84, 97, 227, 531, 808; **113** (1991) 360; **116** (1992) 240, 414; **117** (1992) 826, 1080; **118** (1992) 78

Quantum wells/size effects **111** (1991) 1, 20, 50, 98, 189, 264, 309, 323, 328, 333, 339, 344, 348, 366, 371, 388, 397, 402, 407, 413, 419, 424, 440, 475, 484, 578, 643, 647, 651, 664, 688, 720, 736, 767, 807, 816, 823, 829, 936, 989, 1016, 1047, 1066, 1076, 1080, 1089, 1095, 1100, 1110; **113** (1991) 593; **114** (1991) 327, 337, 619, 693; **115** (1991) 52, 69, 164, 236, 333, 433, 490, 515, 524, 652, 664, 670; **117** (1992) 85, 391, 424, 432, 454, 465, 470, 480, 484, 492, 501, 510, 519, 523, 527, 543, 592, 598, 603, 608, 617, 622, 742, 753, 854, 859, 862, 867, 871, 877, 881, 886, 890, 894, 954, 1026, 1046, 1062, 1068, 1074, 1075, 1077, 1078, 1079, 1083; **118** (1992) 414; **119** (1992) 322; **120** (1992) 78, 155, 157, 162, 167, 177, 180, 328, 333, 338, 343, 349, 353, 357
Quartz **112** (1991) 291, 753; **113** (1991) 527, 669

Rare earth
– barium cuprates **114** (1991) 59; **118** (1992) 385
– oxides **112** (1991) 621
Rutile **112** (1991) 354

Safety instrumentation **113** (1991) 209
Sapphire **119** (1992) 391
Segregation **111** (1991) 141, 151, 239, 295; **112** (1991) 723; **114** (1991) 373, 411, 593; **116** (1992) 461; **117** (1992) 276
Selenium
– organic **115** (1991) 269
Self-diffusion
– of mercury **117** (1992) 177
Semiconductors **113** (1991) 305
Silicon **111** (1991) 833, 838, 843, 856, 860, 864, 870, 882, 889, 907, 916, 936, 957; **112** (1991) 287, 308, 635, 699; **113** (1991) 164, 186, 289, 606, 681; **114** (1991) 64, 446; **115** (1991) 359, 393, 439, 452, 551, 556, 567; **116** (1992) 22, 178; **118** (1992) 85, 125; **119** (1992) 229, 241
– carbide **113** (1991) 120; **115** (1991) 607, 617, 623, 733; **118** (1992) 430
– dioxide **112** (1991) 291; **113** (1991) 527, 669
– germanium **111** (1991) 889, 897, 902, 907, 912, 916, 920, 925, 931, 936, 961; **112** (1991) 287; **115** (1991) 117, 365; **116** (1992) 1, 260
– nitride **115** (1991) 515
– organic **113** (1991) 120
Silver **112** (1991) 235; **116** (1992) 243
– gallium ditelluride **113** (1991) 663
– gallium sulphide **115** (1991) 802
– telluride **112** (1991) 55
Sodium
– chloride **112** (1991) 496; **114** (1991) 7
– nitrate **113** (1991) 566; **118** (1992) 151; **119** (1992) 281
Solar cells **112** (1991) 421; **117** (1992) 929, 959, 1073
Solid growth technique
– by photopolymerization

– – of organic crystals **113** (1991) 69
– by polymorphic transformation
– – of barium fluoride **116** (1992) 473
– – of boron nitride **112** (1991) 386
– – of cadmium selenide/zinc selenide **113** (1991) 653
– – of triglycerides **116** (1992) 333
– by recrystallization
– – of cobalt disilicide **115** (1991) 572
– – of copper chloride **116** (1992) 378
– – of copper thiostannates **114** (1991) 299
– – of diamond **114** (1991) 209
– – of silicon **113** (1991) 681
– – of titanium disilicide **115** (1991) 579
– – of tungsten **112** (1991) 368
– – of zinc sulphide **117** (1992) 1008
– by strain anneal
– – of mercury cadmium telluride **114** (1991) 351
– – of nickel phosphide **113** (1991) 242
– by topochemical reaction
– – of titanium nitride **112** (1991) 47
Solubility **113** (1991) 456; **114** (1991) 141, 613; **116** (1992) 427; **117** (1992) 704; **118** (1992) 71
Solution growth technique
– by anodic oxidation
– – of cadmium sulphide **117** (1992) 918
– by centrifugation over $1000g$
– – of inclusion-free crystals **119** (1992) 1
– by dual constant composition
– – of calcium phosphates **113** (1991) 83
– by electrocrystallization
– – of silver **112** (1991) 235
– by flux method
– – of β-alumina **118** (1992) 314
– – of boron nitride **116** (1992) 507
– – of cadmium telluride **117** (1992) 271
– – of cadmium zinc telluride **117** (1992) 281
– – of copper(I) chloride **112** (1991) 531
– – of diamond **116** (1992) 15
– – of ferrogarnet **119** (1992) 297
– – of hafnium germanate **116** (1992) 151
– – of hafnium silicate **116** (1992) 151
– – of lead cobalt tungstate **112** (1991) 71
– – of lead cuprates **113** (1991) 371
– – of lead strontium yttrium calcium cuprate **118** (1992) 101
– – of potassium hydrogen phthalate **114** (1991) 239
– – of potassium tantalate niobate **116** (1992) 27
– – of potassium titanyl phosphate **112** (1991) 294, 773; **113** (1991) 722; **114** (1991) 141; **119** (1992) 329
– – of potassium yttrium tungstate **116** (1992) 505
– – of rare earth barium cuprates **114** (1991) 59; **118** (1992) 385
– – of yttrium barium cuprate **112** (1991) 337, 606; **113** (1991) 403; **114** (1991) 186, 269, 279; **119** (1992) 221, 403
– – of zinc selenide telluride **117** (1992) 793
– – of zinc silicate **114** (1991) 373
– – of zirconium germanate **116** (1992) 151
– – of zirconium silicate **116** (1992) 151
– by gel method
– – of calcium hydrogen phosphate dihydrate **114** (1991) 22
– – of gypsum **113** (1991) 508
– by hanging drop vapor diffusion
– – of virus **119** (1992) 407
– by hydrothermal growth
– – of aluminum orthophosphate **116** (1992) 427
– – of barium hexaferrite **114** (1991) 435; **116** (1992) 483
– – of lead titanate **116** (1992) 251
– – of quartz **112** (1991) 291, 753; **113** (1991) 527
– – of vanadium oxides **113** (1991) 659
– by low temperature method
– – of L-arginine chloride monohydrate **112** (1991) 183
– – of arginine phosphate **113** (1991) 456
– – of ammonium dihydrogen phosphate **119** (1992) 248
– – of barium nitrate **116** (1992) 340
– – of calcium apatites **118** (1992) 93
– – of calcium carbonate **118** (1992) 401
– – of calcium fluoride **113** (1991) 637
– – of calcium hydroxyapatite **112** (1991) 467, 571
– – of calcium phosphates **112** (1991) 467, 571; **113** (1991) 643; **114** (1991) 613
– – of calcium sulphate dihydrate **118** (1992) 287
– – of gypsum **112** (1991) 415; **116** (1992) 87
– – of ice **113** (1991) 417
– – of iron(III) phosphate **113** (1991) 140
– – of lithium iodate **116** (1992) 63
– – of lysozyme **116** (1992) 289
– – of manganese chloride **112** (1991) 160, 171
– – of m-nitroaniline **119** (1992) 309
– – of organic crystals **113** (1991) 157, 360; **119** (1992) 368, 393
– – of potassium bromide **112** (1991) 235
– – of potassium dihydrogen phosphate **112** (1991) 235; **114** (1992) 71; **118** (1992) 231
– – of sodium nitrate **113** (1991) 566
– – of sucrose **118** (1992) 464
– – of urea **112** (1991) 729
– by modified flux flow method
– – of lanthanide cuprates **113** (1991) 395
– by solvent evaporation
– – of beryllium sulphate tetrahydrate **113** (1991) 161
– – of lysozyme **116** (1992) 414
– theory of **112** (1991) 613; **118** (1992) 71, 333
Spinel **112** (1991) 644
Statistical mechanics, molecular theory **111** (1991) 864; **112** (1991) 591; **115** (1991) 194; **116** (1992) 397
Stefan problem or moving boundary problem **111** (1991) 162; **112** (1991) 539, 699; **113** (1991) 147, 575; **114** (1991) 153, 267, 411, 446, 467, 517, 603, 715; **116** (1992) 158; **118** (1992) 135, 193
Step **111** (1991) 65, 88, 125, 168, 173, 184, 328, 353, 847, 864; **112** (1991) 183, 496, 651; **113** (1991) 295; **114** (1991) 239, 258; **115** (1991) 61, 133, 145, 199, 375, 393, 398, 406, 428, 542, 556, 612, 774; **116** (1992) 158, 178; **118** (1992) 243; **119** (1992) 229, 241, 248, 329
Strain **111** (1991) 1, 205, 221, 339, 376, 383, 388, 393, 397, 402,

407, 413, 419, 424, 429, 434, 440, 445, 466, 623, 677, 715, 736, 807, 811, 882, 897, 902, 912, 916, 925, 931, 936, 1095; **112** (1991) 359; **113** (1991) 227, 265, 379, 430, 477, 499; **114** (1991) 31, 47, 133, 647, 693; **115** (1991) 19, 99, 150, 154, 164, 169, 324, 365, 718; **116** (1992) 81, 260, 271; **117** (1992) 49, 96, 161, 233, 249, 281, 285, 290, 297, 309, 316, 336, 424, 470, 484, 488, 492, 497, 505, 515, 532, 554, 560, 565, 738, 742, 797, 835, 850, 871, 886, 1075; **118** (1992) 14, 117, 218, 243; **119** (1992) 261, 322

Strontium
– barium niobate **113** (1991) 337; **114** (1991) 500
– organic **115** (1991) 762
– selenide **117** (1992) 964
– sulphide **117** (1992) 587, 943, 964, 979, 983

Succinonitrile **112** (1991) 463

Sucrose **118** (1992) 464

Sulphur
– organic **112** (1991) 737

Superconductivity **111** (1991) 965, 973; **112** (1991) 337, 587, 606, 613; **113** (1991) 9, 371, 395, 403; **114** (1991) 59, 186, 198, 258, 269, 279, 283, 507; **115** (1991) 19, 31, 745, 758, 762, 765, 769, 774, 782, 788; **116** (1992) 37, 529; **118** (1992) 27, 101, 385, 477; **119** (1992) 122, 221, 403
– bulk **112** (1991) 337, 587, 606, 613; **113** (1991) 9, 371, 395, 403; **114** (1991) 59, 186, 269, 279, 283; **116** (1992) 27, 529; **118** (1992) 27, 101, 385, 477; **119** (1992) 403
– ceramics **118** (1992) 27, 385; **119** (1992) 122
– characterization **111** (1991) 965, 973; **112** (1991) 587, 606; **113** (1991) 9, 371, 395, 403; **114** (1991) 59, 186, 198, 258, 269, 279, 283; **115** (1991) 31, 745, 758, 762, 765, 774, 782, 788; **116** (1992) 37, 529; **118** (1992) 27, 101, 385, 477; **119** (1992) 122, 221, 403
– crystal chemistry **111** (1991) 965, 973; **112** (1991) 337, 587; **114** (1991) 59, 186, 198, 258, 269, 279, 283; **115** (1991) 31, 758, 762, 765, 769; **116** (1992) 529; **118** (1992) 529; **119** (1992) 403
– high T_c **111** (1991) 965, 973; **112** (1991) 337, 587, 606, 613; **113** (1991) 9, 371, 395, 403; **114** (1991) 59, 186, 198, 258, 269, 279, 283; **115** (1991) 19, 31, 745, 758, 762, 765, 769, 774, 782, 788; **116** (1992) 37, 529; **118** (1992) 27, 385, 477; **119** (1992) 122, 221, 403
– phase relationships **113** (1991) 371, 395; **114** (1991) 269; **118** (1992) 101; **119** (1992) 122
– stoichiometry **112** (1991) 337, 587, 606; **113** (1991) 9, 371; **114** (1991) 59; **116** (1992) 529; **118** (1992) 27; **119** (1992) 122
– thin films **111** (1991) 965, 973; **114** (1991) 198, 258, 507; **115** (1991) 19, 31, 745, 758, 762, 765, 769, 774, 782, 788

Supercooling, supersaturation **112** (1991) 84, 97, 160, 171, 183, 287, 487, 497, 663, 729, 803; **113** (1991) 417; **114** (1991) 239, 573, 603, 613, 683; **115** (1991) 43; **116** (1992) 41, 158, 294, 427, 515; **118** (1992) 71, 231, 269, 287, 360, 401; **119** (1992) 248, 303, 393, 403

Superlattices **111** (1991) 1, 194, 205, 274, 323, 333, 353, 360, 366, 371, 376, 383, 388, 402, 429, 466, 628, 647, 677, 683, 720, 736, 752, 762, 802, 807, 811, 816, 829, 838, 882, 889, 897, 902, 912, 925, 936, 957, 989, 1003, 1016, 1033, 1047, 1076; **112** (1991) 359, 791; **114** (1991) 569, 657; **115** (1991) 61, 99, 154, 164, 194, 248, 324, 328, 375, 406, 433, 490, 515, 538, 670, 745; **116** (1992) 235, 397; **117** (1992) 85, 161, 166, 454, 460, 470, 475, 480, 484, 488, 492, 497, 501, 505, 510, 515, 523, 536, 742, 753, 867, 877, 881, 890, 1026, 1074, 1075, 1077, 1079; **118** (1992) 117; **119** (1992) 322

Surface energy, determination of **111** (1991) 847; **112** (1991) 84, 97, 458; **113** (1991) 131, 140, 599; **114** (1991) 467; **116** (1991) 397; **118** (1992) 401, 470

Surface processes **111** (1991) 61, 353, 847, 864, 870; **112** (1991) 129, 474; **113** (1991) 599, 606; **114** (1991) 133; **115** (1991) 199, 226, 428, 542, 556, 612, 692; **116** (1992) 158, 283, 397; **117** (1992) 134, 183, 666; **118** (1992) 33, 71, 231, 333, 473

Surface structure **111** (1991) 20, 65, 75, 88, 115, 136, 184, 194, 221, 353, 429, 489, 570, 594, 609, 792, 876, 943, 961, 1033; **112** (1991) 146, 183, 445, 487, 591, 644, 663, 781; **113** (1991) 16, 45, 295; **114** (1991) 198, 203, 389, 700; **115** (1991) 19, 94, 112, 150, 169, 186, 199, 226, 318, 348, 393, 428, 542, 612; **116** (1992) 178, 235, 340, 397; **117** (1992) 96; **119** (1992) 229, 241, 329

Surfactant **114** (1991) 118

Tellurides
– ternary **113** (1991) 663

Tellurium
– dioxide **116** (1992) 364
– organic **111** (1991) 725; **112** (1991) 192; **113** (1991) 1, 103; **115** (1991) 284, 454; **117** (1992) 58

Thallium
– barium calcium cuprate **112** (1991) 587

Thermodynamics **111** (1991) 151, 173; **112** (1991) 437, 458, 467, 644, 663, 691, 781; **113** (1991) 491, 599, 633; **114** (1991) 486, 507; **115** (1991) 83, 99, 211, 448, 479, 542, 728; **116** (1992) 1, 41, 204; **117** (1992) 10, 689, 704, 913; **118** (1992) 71, 78, 287, 401; **119** (1992) 271

Thin film growth
– by atomic layer epitaxy
– – of aluminum arsenide **115** (1991) 133
– – of cadmium telluride **115** (1991) 692
– – of gallium arsenide **115** (1991) 83, 89, 94
– – of germanium **115** (1991) 79
– – of indium arsenide **115** (1991) 324
– – of indium gallium arsenide **114** (1991) 31; **115** (1991) 460
– – of indium phosphide **115** (1991) 324
– – of II–V compounds **111** (1991) 736
– – of zinc chalcogenides **120** (1992) 261
– – of zinc selenide **117** (1992) 85, 148
– – of zinc sulphide **117** (1992) 152
– – of zinc telluride **117** (1992) 144
– – simulation of **115** (1991) 186
– – theory of **115** (1991) 83
– by atomic layer molecular beam epitaxy
– – of gallium arsenide **111** (1991) 120
– – theory of **111** (1991) 194
– by chemical beam epitaxy
– – of aluminum gallium arsenide **111** (1991) 274; **120** (1992) 84, 189, 206, 240, 245
– – of aluminum indium arsenide **120** (1992) 189

– – of gallium arsenide **111** (1991) 274, 578; **120** (1992) 33, 45, 63, 88, 103, 206, 240, 245, 369, 395
– – of gallium indium phosphide **111** (1991) 578
– – of indium aluminum arsenide **120** (1992) 184
– – of indium arsenide **120** (1992) 155
– of indium gallium arsenide **111** (1991) 594, 1062; **116** (1992) 271; **120** (1992) 33, 135, 177, 184, 212, 328, 333, 338, 357
– – of indium gallium arsenide phosphide **120** (1992) 150, 162, 177, 338, 343
– – of indium phosphide **111** (1991) 589, 594, 605; **120** (1992) 119, 130, 150, 162, 184, 328, 333, 343, 357
– – of silicon **120** (1992) 269
– – of III–V compounds **111** (1991) 550; **120** (1992) 25, 389
– – of II–VI compounds **111** (1991) 550, 725
– – advances in **120** (1992) 1
– – review of **111** (1991) 529
– by electrodeposition
– – of cadmium telluride **117** (1992) 929
– by gas source molecular beam epitaxy
– – of aluminum gallium arsenide **111** (1991) 544
– – of gallium arsenide **111** (1991) 246, 507, 511, 515, 521, 544, 559, 564, 570
– – of gallium indium phosphide **111** (1991) 564
– – of indium gallium arsenide phosphide **111** (1991) 495
– – of indium gallium phosphide **111** (1991) 525
– – of indium phosphide **111** (1991) 495, 502
– – of low temperature buffers **111** (1991) 43
– – of silicon **111** (1991) 860
– – of silicon germanium **115** (1991) 365
– – review of **111** (1991) 529
– by graphoepitaxy
– – of proteins **112** (1991) 758
– by hot wall epitaxy
– – of cadmium manganese telluride **117** (1992) 835, 881
– – of cadmium selenide **117** (1992) 768
– – of cadmium sulphide **117** (1992) 753, 1026
– – of cadmium telluride **117** (1992) 161, 475, 554, 835
– – of cadmium zinc telluride **117** (1992) 161, 475
– – of lead cadmium sulphoselenide **115** (1991) 687
– – of mercury cadmium telluride **117** (1992) 844
– – of zinc telluride **117** (1992) 290, 303
– by ion beam sputtering
– – of lithium niobate **115** (1991) 821
– – of platinum **115** (1991) 596
– – of zinc oxide **115** (1991) 816
– by ionized cluster beam
– – of manganese telluride **117** (1992) 816
– by laser ablation
– – of cadmium sulphide **117** (1992) 156
– – of cadmium telluride **117** (1992) 156, 862
– – of yttrium barium cuprate **114** (1991) 258
– by liquid phase electroepitaxy
– – of indium gallium phosphide **115** (1991) 304
– by liquid phase epitaxy
– – of aluminum gallium arsenide **112** (1991) 803; **115** (1991) 299
– – of cadmium sulphide **117** (1992) 902, 925
– – of gallium aluminum arsenide **113** (1991) 540
– – of gallium arsenide **115** (1991) 145, 294, 519; **116** (1992) 240, 351
– – of gallium phosphide **114** (1991) 380
– – of germanium silicide **114** (1991) 573; **118** (1992) 452
– – of indium gallium antimonide arsenide **116** (1992) 204
– – of indium gallium arsenide **114** (1991) 633; **115** (1991) 174
– – of indium phosphide **113** (1991) 16; **114** (1991) 293
– – of lead selenide **114** (1991) 687
– – of mercury cadmium telluride **113** (1991) 53, 520; **117** (1992) 16, 20, 24, 213; **118** (1992) 204
– – of potassium titanyl phosphate **112** (1991) 309
– – of silicon **112** (1991) 287; **115** (1991) 561
– – of silicon germanium **112** (1991) 287
– – of yttrium barium cuprate **115** (1991) 19
– – of zinc selenide **112** (1991) 153
– – theory of **114** (1991) 633
– by magnetron sputtering
– – of zinc oxide **117** (1992) 370
– by metalorganic molecular beam epitaxy
– – of aluminum gallium antimonide **115** (1991) 236
– – of aluminum gallium arsenide **111** (1991) 574, 1043; **113** (1991) 412; **120** (1992) 124, 195, 218, 234
– – of gallium antimonide **111** (1991) 638; **120** (1992) 39
– – of gallium arsenide **111** (1991) 539, 554, 570, 574, 584; **112** (1991) 1; **113** (1991) 412; **115** (1991) 74, 226, 423; **116** (1992) 511; **119** (1992) 195; **120** (1992) 39, 45, 50, 114, 124, 218, 234
– – of gallium indium arsenide **112** (1991) 343; **115** (1991) 74
– – of gallium indium arsenide phosphide **120** (1992) 140, 301, 312, 376
– – of gallium nitride **120** (1992) 114
– – of gallium selenide **115** (1991) 798
– – of group III antimonides **120** (1992) 252
– – of indium arsenide antimonide **111** (1991) 638
– – of indium gallium arsenide **111** (1991) 584, 599; **120** (1992) 382
– – of indium gallium arsenide phosphide **111** (1991) 599
– – of indium phosphide **112** (1991) 343; **115** (1991) 464; **120** (1992) 312, 376
– – of III–V compounds **115** (1991) 664
– – of II–VI compounds **115** (1991) 664
– – of zinc cadmium sulphoselenide **117** (1992) 527
– – of zinc chalcogenides **120** (1992) 261
– – of zinc selenide **116** (1992) 283
– – review of **111** (1991) 529
– by metalorganic molecular beam epitaxy, laser-assisted
– – of gallium arsenide **115** (1991) 241
– by metalorganic molecular beam epitaxy, photo-assisted
– – of III–V compounds **115** (1991) 265
– – of zinc selenide **115** (1991) 279
– by migration enhanced epitaxy
– – of aluminum arsenide **111** (1991) 221
– – of gallium arsenide **111** (1991) 200, 210, 216
– – of indium arsenide **111** (1991) 397
– – of indium gallium arsenide **111** (1991) 228

– – of indium phosphide **111** (1991) 502
– – of zinc selenide **111** (1991) 752
– – improved device performance **111** (1991) 233
– by modulated molecular beam epitaxy
– – theory of **111** (1991) 205
– by molecular beam epitaxy
– – of aluminum antimonide **111** (1991) 651, 659, 664
– – of aluminum arsenide **111** (1991) 88, 125, 168, 221, 1071, 1105, 1110; **115** (1991) 318
– – of aluminum gallium antimonide **111** (1991) 647
– – of aluminum gallium arsenide **111** (1991) 20, 26, 30, 50, 75, 98, 105, 189, 239, 269, 280, 295, 318, 366, 371, 440, 544, 559, 1043, 1047, 1052, 1057, 1066, 1089, 1095, 1116; **114** (1991) 700; **115** (1991) 338, 490; **118** (1992) 414; **120** (1992) 228
– – of aluminum gallium arsenide antimonide **111** (1991) 669
– – of aluminum gallium indium arsenide **111** (1991) 484
– – of aluminum indium arsenide **111** (1991) 445, 456, 461, 470, 479, 489
– – of aluminum indium phosphide **111** (1991) 521
– – of barium bismuth oxygen system **113** (1991) 716
– – of barium oxide **118** (1992) 213
– – of bismuth antimonide **111** (1991) 693
– – of bismuth strontium calcium cuprate **112** (1991) 745; **115** (1991) 758
– – of bismuth strontium cuprate **112** (1991) 745
– – of boron **111** (1991) 838
– – of cadmium manganese telluride **111** (1991) 1016; **117** (1992) 424, 820
– – of cadmium selenide **111** (1991) 820
– – of cadmium telluride **111** (1991) 698, 730, 1016; **117** (1992) 238, 391, 424, 660, 820, 854, 859, 871, 877, 886, 890
– – of cadmium zinc selenide **117** (1992) 1078, 1079
– – of cadmium zinc telluride **117** (1992) 424, 465
– – of cerium dioxide **118** (1992) 299
– – of cobalt disilicide **111** (1991) 948, 957
– – of cobalt gallium **111** (1991) 996
– – of copper aluminum selenide **115** (1991) 811
– – of copper oxide **115** (1991) 752
– – of erbium arsenide **111** (1991) 989
– – of gallium **112** (1991) 146
– – of gallium aluminum arsenide **111** (1991) 269
– – of gallium antimonide **111** (1991) 559, 619, 623, 651, 659, 664
– – of gallium arsenide **111** (1991) 14, 30, 39, 43, 50, 65, 70, 75, 83, 88, 93, 120, 125, 131, 136, 168, 184, 189, 200, 210, 216, 233, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 318, 333, 339, 344, 371, 393, 424, 507, 511, 515, 521, 539, 544, 550, 559, 741, 747, 833, 989, 1052, 1057, 1066, 1071, 1089, 1100, 1105; **112** (1991) 14, 597; **114** (1991) 307, 337, 619; **115** (1991) 99, 122, 318, 333, 338, 348, 398, 423, 579; **116** (1992) 518; **118** (1992) 414; **120** (1992) 71, 78, 200, 228, 296, 306
– – of gallium arsenide antimonide **111** (1991) 628
– – of gallium arsenide phosphide **111** (1991) 61
– – of gallium arsenide silicide **115** (1991) 328
– – of gallium indium arsenide **112** (1991) 343
– – of gallium indium arsenide antimonide **111** (1991) 413, 669
– – of gallium indium arsenide phosphide **112** (1991) 27; **120** (1992) 145, 157, 167, 180, 349, 353
– – of gallium nitride **111** (1991) 1024
– – of gallium selenide **111** (1991) 1038
– – of germanium **111** (1991) 833, 847, 876, 882; **113** (1991) 45; **115** (1991) 106, 112; **120** (1992) 284
– – of indium aluminum arsenide **115** (1991) 509
– – of indium antimonide **111** (1991) 614, 623, 688
– – of indium arsenide **111** (1991) 93, 110, 125, 205, 383, 388, 393, 397, 402, 434, 550, 623, 651, 659, 664, 677, 683; **115** (1991) 99, 164; **116** (1992) 81
– – of indium gallium aluminum arsenide **111** (1991) 56
– – of indium gallium antimonide **111** (1991) 677, 683
– – of indium gallium arsenide **111** (1991) 228, 233, 309, 339, 407, 413, 419, 429, 434, 450, 456, 461, 466, 470, 475, 479, 489, 628, 1076, 1080, 1084, 1095, 1100; **114** (1991) 327, 346, 569, 693; **115** (1991) 375, 398, 504, 509; **120** (1992) 33, 172
– – of indium gallium arsenide phosphide **111** (1991) 495
– – of indium gallium phosphide **111** (1991) 525
– – of indium manganese arsenide **111** (1991) 1011
– – of indium nitride **111** (1991) 1024
– – of indium phosphide **111** (1991) 495, 502, 1076, 1080; **112** (1991) 343; **114** (1991) 127; **115** (1991) 180; **120** (1992) 157, 167, 172, 180, 317, 349, 353
– – of iron aluminum silicide **111** (1991) 984
– – of lead europium selenide **113** (1991) 593
– – of manganese aluminum **111** (1991) 978
– – of manganese sulphide **117** (1992) 810
– – of manganese telluride **111** (1991) 767
– – of mercury cadmium telluride **111** (1911) 698, 711, 715, 720; **117** (1992) 166, 171, 193, 218, 222, 238, 454, 1046
– – of mercury telluride **111** (1991) 720
– – of metals **111** (1991) 1003
– – of molybdenum diselenide **111** (1991) 1033
– – of organic crystals **116** (1992) 495
– – of silicon **111** (1991) 833, 838, 843, 856, 870, 882; **115** (1991) 393, 551, 556; **120** (1992) 290
– – of silicon germanide **116** (1992) 260
– – of silicon germanium **111** (1991) 889, 897, 902, 907, 912, 916, 920, 925, 931, 936, 961
– – of silver **116** (1992) 243
– – of III–V compounds **111** (1991) 1, 125, 141, 151, 173, 194, 313, 360, 475, 550, 564, 609, 623, 643; **115** (1991) 652; **116** (1992) 98, 436
– – of tin **111** (1991) 882, 943
– – of titanium oxides **116** (1992) 235
– – of II–VI compounds **111** (1991) 811, 816; **115** (1991) 652
– – of Van der Waals crystals **111** (1991) 1029, 1033
– – of yttrium barium cuprate **111** (1991) 965
– – of zinc chalcogenides **117** (1992) 505, 510
– – of zinc magnesium sulphoselenide **117** (1991) 139
– – of zinc selenide **111** (1991) 741,757, 772, 776, 787, 792, 797, 802, 823, 829; **115** (1991) 333, 683; **117** (1992) 125, 129, 134, 233, 309, 320, 324, 341, 375, 400, 406, 573, 694, 797, 802, 1078, 1079

– – of zinc selenide telluride **111** (1991) 762, 829
– – of zinc sulphide **111** (1991) 823
– – of zinc sulphoselenide **117** (1992) 1078
– – of zinc telluride **111** (1991) 782, 802; **117** (1992) 285, 396, 1050; **118** (1992) 295
– – of zinc telluride/cadmium telluride superlattices **119** (1992) 322
– – advances in **120** (1992) 1
– – growth uniformity study of **111** (1991) 70
– – review of **111** (1991) 529
– – simulation of **115** (1991) 186
– – simulation with animation of **111** (1991) 864
– – theory of **111** (1991) 1, 61, 162, 178, 323, 328, 539; **114** (1991) 203; **115** (1991) 338, 398, 556
– by molecular layer epitaxy
– – fundamental aspects of **115** (1991) 12
– by plasma
– – of titanium nitride **115** (1991) 589
– – of zinc selenide **115** (1991) 660
– by radical beam gettering epitaxy
– – of zinc oxide **117** (1992) 366
– by radio frequency magnetron sputtering
– – of yttrium barium cuprate **114** (1991) 198
– by sintering
– – of cadmium sulphide **117** (1992) 362
– by solid source molecular beam epitaxy
– – of gallium arsenide **111** (1991) 14
– – of low temperature buffers **111** (1991) 43
– by sputtering
– – of strontium sulphide **117** (1992) 983
– – of zinc oxide **117** (1992) 939
– by vacuum chemical epitaxy
– – of gallium arsenide **111** (1991) 115
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of aluminum arsenide **113** (1991) 491
– – – of aluminum gallium arsenide **115** (1991) 52
– – – of bismuth strontium calcium cuprate **115** (1991) 774
– – – of cadmium sulphide **117** (1992) 902; **118** (1992) 304
– – – of cadmium telluride **115** (1991) 711
– – – of copper aluminum diselenide **113** (1991) 390
– – – of copper oxide **112** (1991) 298
– – – of diamond **112** (1991) 580, 808; **113** (1991) 295
– – – of gallium arsenide **113** (1991) 491; **115** (1991) 52, 443, 538; **116** (1992) 387
– – – of gallium indium phosphide **112** (1991) 373
– – – of gallium phosphide **115** (1991) 538
– – – of indium phosphide **112** (1991) 691; **116** (1992) 75
– – – of mercury cadmium telluride **117** (1992) 954
– – – of silicon **113** (1991) 606; **115** (1991) 439, 542; **120** (1992) 269, 275
– – – of silicon carbide **115** (1991) 607, 612, 617, 623; **118** (1992) 430
– – – of silicon germanide **116** (1992) 1
– – – of silicon germanium **115** (1991) 117; **120** (1992) 279
– – – of silicon nitride **115** (1991) 515, 567
– – – of III–V compounds **112** (1991) 583
– – – of triglycerides **116** (1992) 333
– – – of II–VI compounds **117** (1992) 10
– – – of yttrium barium cuprate **115** (1991) 19, 745
– – – of zinc selenide **115** (1991) 674, 679; **117** (1992) 1059, 1062, 1068
– – – of zinc sulphide **117** (1992) 348, 991
– – – performance of **114** (1991) 13
– – – theory of **118** (1992) 60, 430
– – through chemical vapor deposition, plasma assisted
– – – of zinc selenide **117** (1992) 85
– – through combustion flame
– – – of diamond **112** (1991) 651
– – through evaporation and condensation
– – – of bismuth strontium calcium cuprate **115** (1991) 765
– – – of cadmium arachidate **118** (1992) 348
– – – of cadmium selenide telluride **112** (1991) 421
– – – of cadmium telluride **112** (1991) 407; **115** (1991) 705; **116** (1992) 55
– – – of calcium sulphide **117** (1992) 587, 975
– – – of chromium(III) oxide **112** (1991) 427
– – – of copper selenide **112** (1991) 55
– – – of gold **112** (1991) 427
– – – of indium selenide **112** (1991) 797
– – – of lithium zinc phosphide **113** (1991) 333
– – – of mercury cadmium telluride **112** (1991) 402
– – – of mercury(II) iodide **115** (1991) 43
– – – of organic crystals **112** (1991) 507; **115** (1991) 388, 826, 831; **119** (1992) 399
– – – of potassium **115** (1991) 411
– – – of rare earth oxides **112** (1991) 621
– – – of silicon **118** (1992) 125
– – – of silicon carbide **115** (1991) 733
– – – of silver telluride **112** (1991) 55
– – – of strontium selenide **117** (1992) 964
– – – of strontium sulphide **117** (1992) 587, 964, 979, 983
– – – of yttrium **113** (1991) 181
– – – of zinc selenide **117** (1992) 948, 987, 1002, 1030
– – through evaporation and condensation, plasma-assisted
– – – of indium arsenide **115** (1991) 309
– – through laser ablation
– – – of yttrium barium cuprate **115** (1991) 19, 31, 788
– – through metalorganic chemical vapor deposition
– – – of aluminum arsenide **115** (1991) 61, 69, 406
– – – of aluminum gallium antimonide **113** (1991) 441
– – – of aluminum gallium arsenide **113** (1991) 103; **115** (1991) 248, 455, 484; **120** (1992) 323, 362
– – – of aluminum gallium arsenide antimonide **113** (1991) 441
– – – of aluminum gallium indium phosphide **115** (1991) 529, 533; **118** (1992) 425
– – – of aluminum gallium nitride **115** (1991) 648
– – – of aluminum nitride **115** (1991) 643
– – – of bismuth strontium calcium cuprate **114** (1991) 507; **115** (1991) 762
– – – of cadmium manganese telluride **112** (1991) 487
– – – of cadmium selenide **117** (1992) 492, 497, 1077
– – – of cadmium sulphide **117** (1992) 492, 497, 532, 536

– – – of cadmium telluride **112** (1991) 192; **115** (1991) 698, 718; **117** (1992) 254, 266, 959, 1073
– – – of cadmium zinc sulphide **117** (1992) 119, 501, 536
– – – of cobalt **114** (1991) 364
– – – of cobalt disilicide **114** (1991) 364
– – – of copper gallium disulphide **115** (1991) 807
– – – of diamond **114** (1991) 38, 565; **119** (1992) 271, 345
– – – of gallium antimonide **115** (1991) 474
– – – of gallium arsenide **112** (1991) 316, 437, 474, 791; **113** (1991) 103; **114** (1991) 581; **115** (1991) 61, 65, 69, 128, 141, 211, 216, 221, 353, 406, 448, 479, 524; **116** (1992) 169, 511; **118** (1992) 467; **120** (1992) 71, 323, 362
– – – of gallium indium arsenide **112** (1991) 359; **116** (1992) 521
– – – of gallium indium phosphide **111** (1991) 353; **115** (1991) 529
– – – of gallium nitride **115** (1991) 381, 628, 634, 639
– – – of gallium phosphide **115** (1991) 158, 261, 469; **118** (1992) 176
– – – of gallium selenide **114** (1991) 99
– – – of indium gallium aluminum phosphide **112** (1991) 628; **113** (1991) 127; **115** (1991) 498
– – – of indium gallium arsenide **113** (1991) 379; **114** (1991) 481; **115** (1991) 154; **120** (1992) 98, 212
– – – of indium gallium arsenide phosphide **112** (1991) 39; **115** (1991) 231; **119** (1992) 292; **120** (1992) 150
– – – of indium phosphide **112** (1991) 111; **114** (1991) 561; **115** (1991) 150, 154, 254; **120** (1992) 98, 150, 362
– – of iron disulphide **112** (1991) 737
– – – of mercury cadmium telluride **115** (1991) 698; **117** (1992) 1, 24, 28, 33, 37, 44, 54, 161, 460
– – – of mercury manganese telluride **113** (1991) 1
– – – of mercury telluride **117** (1992) 49
– – – of silicon carbide **113** (1991) 120
– – – of III–V compounds **115** (1991) 203, 418
– – – of yttrium barium cuprates **115** (1991) 31, 782
– – – of zinc cadmium sulphide **117** (1992) 353
– – – of zinc chalcogenides **117** (1992) 67, 91, 560
– – – of zinc phosphide **115** (1991) 793
– – – of zinc selenide **114** (1991) 99; **115** (1991) 670; **117** (1992) 96, 102, 107, 111, 336, 358, 441, 484, 488, 515, 519, 523, 543, 565, 569, 625, 738, 1075, 1077
– – – of zinc selenide telluride **117** (1992) 116
– – – of zinc silicon germanium phosphide **113** (1991) 113
– – – of zinc sulphide **115** (1991) 670; **117** (1992) 336, 415, 484, 488, 515, 523, 1021, 1035, 1075, 1082
– – – of zinc sulphoselenide **117** (1992) 44
– – – of zinc telluride **117** (1992) 303, 480, 519, 959
– – – advances in **120** (1992) 1
– – – theory of **112** (1991) 192, 316, 437; **115** (1991) 479
– – through metalorganic chemical vapor deposition, laser-assisted
– – – of zinc selenide **115** (1991) 274
– – – of zinc telluride **115** (1991) 284
– – through metalorganic chemical vapor deposition, photo-assisted
– – – of lead titanate **115** (1991) 289
– – – of II–VI compounds **115** (1991) 269
– – through photochemical stimulation
– – – of gallium arsenide **116** (1992) 48
– – – theory of **116** (1992) 48
– – through sputtering
– – – of bismuth strontium calcium cuprate **115** (1991) 769
– – – of yttrium barium cuprate **115** (1991) 19
– – – of zinc oxide **116** (1992) 357
– – through use of DC plasma
– – – of diamond **115** (1991) 313
– – fundamental aspects of **115** (1991) 1
– theory of **113** (1991) 430; **119** (1992) 229, 241
Three–five (III–V) compounds **111** (1991) 1, 125, 141, 151, 173, 194, 313, 360, 475, 550, 564, 599, 609, 623, 633, 643, 1011; **112** (1991) 373, 583; **113** (1991) 209; **115** (1991) 194, 203, 248, 265, 652; **116** (1992) 98, 436; **118** (1992) 109
Three–six (III_2–VI_3) compounds **117** (1992) 549
Tin **111** (1991) 882, 943; **114** (1991) 467
Titanium
– dioxide **112** (1991) 354, 835
– disilicide **115** (1991) 579
– nitride **112** (1991) 47; **115** (1991) 589
– organic **115** (1991) 289
– oxides **116** (1992) 235
Tungsten **112** (1991) 368
Twinning **111** (1991) 698, 715, 736; **112** (1991) 337, 635; **113** (1991) 221, 669; **114** (1991) 186, 307; **116** (1992) 87; **117** (1992) 171, 238; **118** (1992) 109, 377
Two–six (II–VI) compounds **111** (1991) 550, 711, 725, 736, 807, 811, 816; **115** (1991) 269, 652, 664; **117** (1992) 10, 67, 156, 420, 492, 549, 592, 634, 640, 682, 715, 738, 742, 907, 1026, 1079, 1083

Uniformity of growth **111** (1991) 70, 269, 599; **113** (1991) 61; **115** (1991) 203; **117** (1992) 1082; **118** (1992) 60
Urea **112** (1991) 729; **114** (1991) 389

Van der Waals crystals **111** (1991) 1029, 1033
Vanadium
– oxides **113** (1991) 659
Vapor diffusion crystallization, under microgravity
– of proteins **119** (1992) 200
Vapor growth technique
– by chemical transport
– – of cadmium telluride **117** (1992) 259
– – of calcium cadmium sulphide **117** (1992) 806
– – of copper aluminum disulphide **115** (1991) 740
– – of copper gallium disulphide **115** (1991) 740
– – of iron gallate **112** (1991) 644
– – of mercury(I) halides **118** (1992) 78
– – of silver gallium disulphide **115** (1991) 802
– – of ternary ditellurides **113** (1991) 663
– – of ternary tellurides **113** (1991) 663
– – of trihalides of group V_B elements **119** (1992) 303
– – of zinc sulphide **117** (1992) 721
– by combustion flame method
– – of molybdenum carbide **116** (1992) 307

– by evaporation and condensation
– – of cadmium **112** (1991) 235; **118** (1992) 243
– – of carbon tetrabromide **114** (1991) 536, 549
– – of iron cobalt alloy **115** (1991) 602
– – of mercury(II) iodide **113** (1991) 251
– – of zinc **112** (1991) 235
– – of zinc sulphoselenide **117** (1992) 328
– – numerical model of **118** (1992) 49
– by evaporation and condensation, in centrifuge
– – of germanium selenide **119** (1992) 79
– theory of **116** (1992) 105; **117** (1992) 689; **119** (1992) 229, 241
Vapor–liquid–solid growth
– of carbon fibers **118** (1992) 309
– of lysozyme **116** (1992) 414
Virus **119** (1992) 407

Whisker growth
– of bismuth strontium calcium cuprate **116** (1992) 524
– of carbon fibers **118** (1992) 309
– of molybdenum carbide **116** (1992) 307
– of titanium nitride **112** (1991) 47
Willemite **114** (1991) 373

Ytterbium
– barium cuprates **115** (1991) 19, 31, 745, 782, 788
Yttrium
– aluminum garnet **118** (1992) 218, 396
– barium cuprate **111** (1991) 965; **112** (1991) 337, 613; **113** (1991) 403; **116** (1992) 37; **118** (1992) 27, 385; **119** (1992) 221, 403
– lithium fluoride **112** (1991) 731
– orthoaluminate, aluminum doped **118** (1992) 371

Zinc **112** (1991) 235
– cadmium selenide **111** (1991) 816; **115** (1991) 664; **117** (1992) 1040, 1079
– cadmium sulphide **117** (1992) 353
– cadmium sulphoselenide **117** (1992) 527
– chalcogenides **117** (1992) 510, 715; **120** (1992) 261
– halides **116** (1992) 397
– magnesium sulphoselenide **117** (1992) 139
– manganese selenide **111** (1991) 816
– mercury telluride **117** (1992) 197
– organic **113** (1991) 103; **115** (1991) 269, 274, 284, 793, 816
– oxide **115** (1991) 816; **116** (1992) 357; **117** (1992) 366, 370, 727, 939
– phosphide **115** (1991) 793
– selenide **111** (1991) 741, 747, 752, 757, 772, 776, 787, 792, 797, 802, 807, 811, 823, 829; **112** (1991) 153, 781; **113** (1991) 653; **114** (1991) 99; **115** (1991) 269, 274, 279, 333, 660, 664, 674, 679, 683; **116** (1992) 283; **117** (1992) 67, 75, 80, 85, 102, 107, 111, 125, 129, 134, 148, 320, 324, 331, 336, 341, 358, 375, 400, 406, 410, 432, 441, 484, 488, 497, 505, 515, 543, 565, 569, 573, 578, 583, 625, 677, 689, 694, 704, 710, 738, 797, 894, 1055, 1059, 1062, 1068, 1074, 1077, 1078
– selenide telluride **111** (1991) 741, 762, 829; **117** (1992) 91, 116, 793
– silicate **114** (1991) 373
– silicon germanium phosphide **113** (1991) 113
– sulphide **111** (1991) 807, 811, 823; **117** (1992) 152, 336, 420, 484, 497, 505, 515, 583, 689, 718, 721, 935, 943, 948, 987, 991, 997, 1002, 1008, 1012, 1016, 1021, 1026, 1030, 1035
– sulphoselenide **115** (1991) 664; **117** (1992) 67, 316, 441, 1078
– telluride **111** (1991) 736, 782, 802, 807, 811; **115** (1991) 284; **117** (1992) 144, 297, 396, 470, 480, 505, 519, 913, 1050; **118** (1992) 295; **119** (1992) 322
Zirconium
– germanate **116** (1992) 151
– silicate **116** (1992) 151

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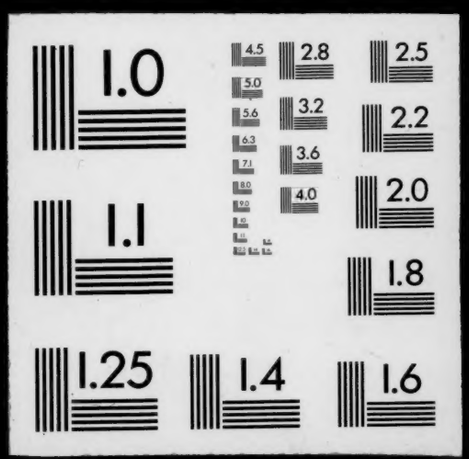
CONTENTS

Author index to volumes 111–120 407

Subject index to volumes 111–120 475


1.0
1.1
1.25
1.4
1.6
1.8
2.0
2.2
2.5
2.8
3.2
3.6
4.0
4.5
5.0
5.6
6.3
7.1
8.0
9.0